

-: HAND WRITTEN NOTES:-

OF

ELECTRICAL ENGINEERING



-: SUBJECT:-

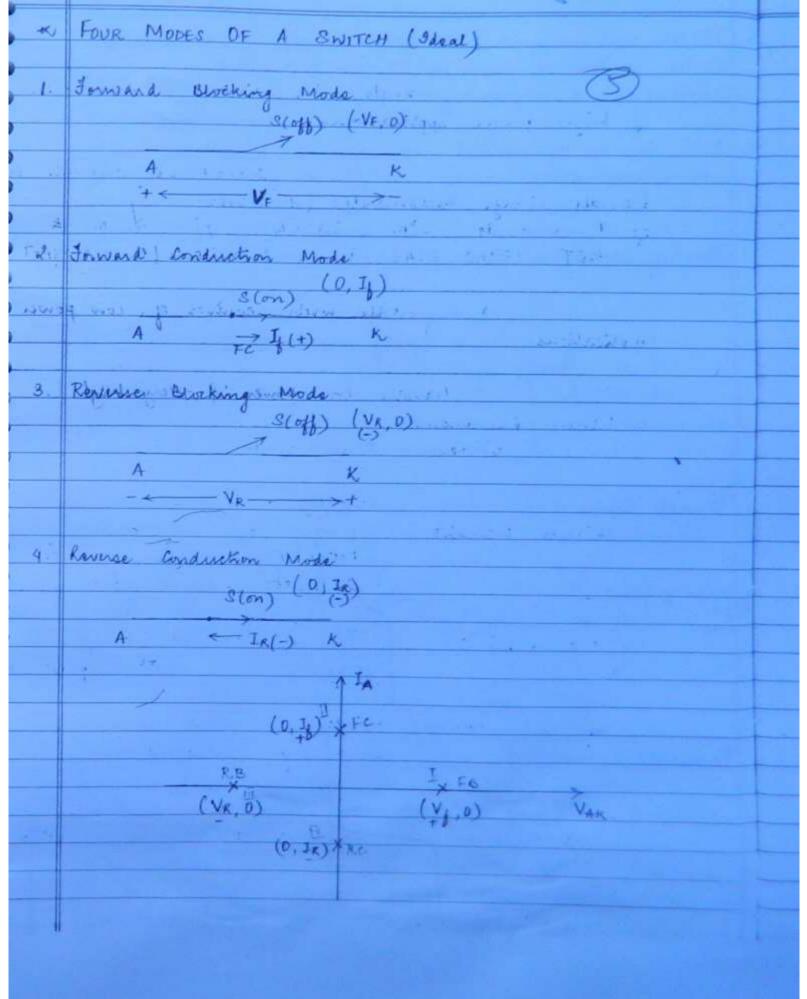
POWER ELECTRONICS

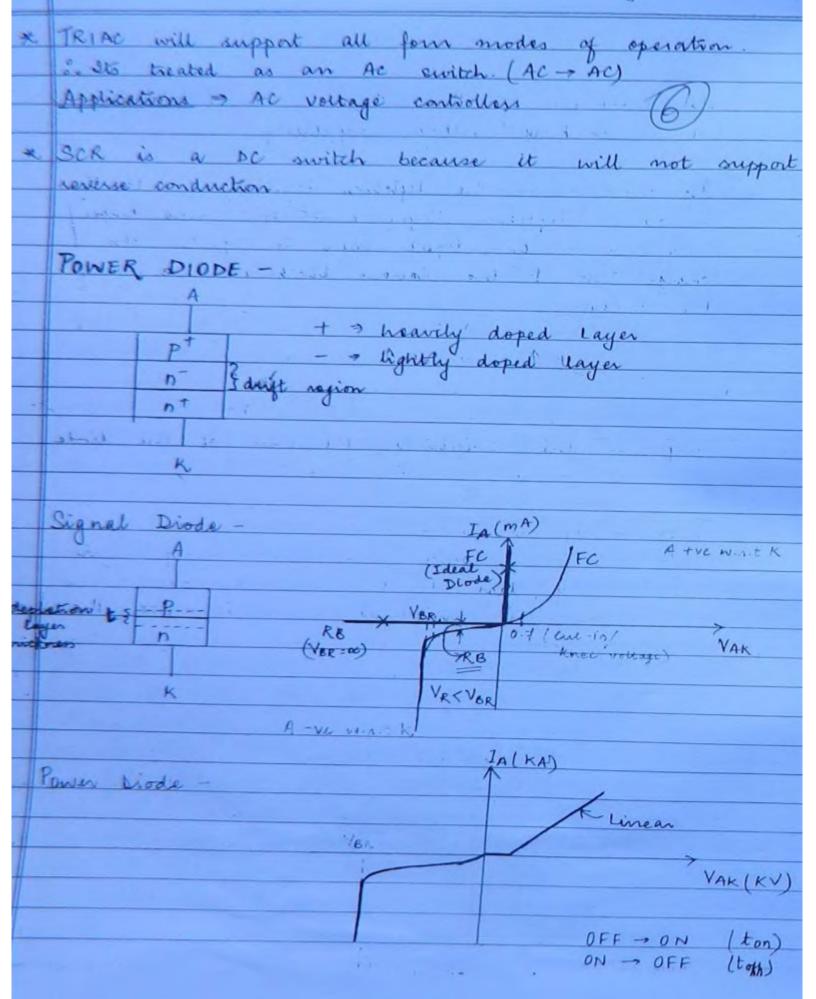
3

	TOPICS	
1.	Power semiconductor devices - 25%	
	Phase controlled rectifiers -35%	
	Application - DC drives	
	-> Charging batteries	
	- Solar batteries	
2	I unaban 1 -12°/	
	Inverters -12%	
٦.	Choppers - 12-15%	
9.	AC Voltage controllers of cycloconverters - 3 to 4%. Other applications - 7-10%.	
6.	other apprications 7 - 10%	
	- Ac Drives	
	→ HVDC	
	-> SMPS	
-		

© Wiki Engineering www.raghul.org

1-12-11	POWER SEMICONDUCTOR DEVICES (4)
	Power Electronics - deals with control of conversion of high power applications.
	Power Semiconductor devices - Should be capable to handle large magnitudes of power :
	Signal Electronics - deals with control of low power applications.
1 ->	Signal Devices - handle low power of very high switching frequencies: eg Signal diodes - Ferrer diode
	→ LEDS → Varacter diode Signal transistors → BJT → MDSFET
	→ UJT etc.
	In the fabrication of semiconductor devices we must sacrifice one quality in order to improve the other quality. eg of the device operates at very high civitching frequency the power rating is reduced.
×	A Switch can be utilized in 4 different modes out all the desrices need not operate in all the modes

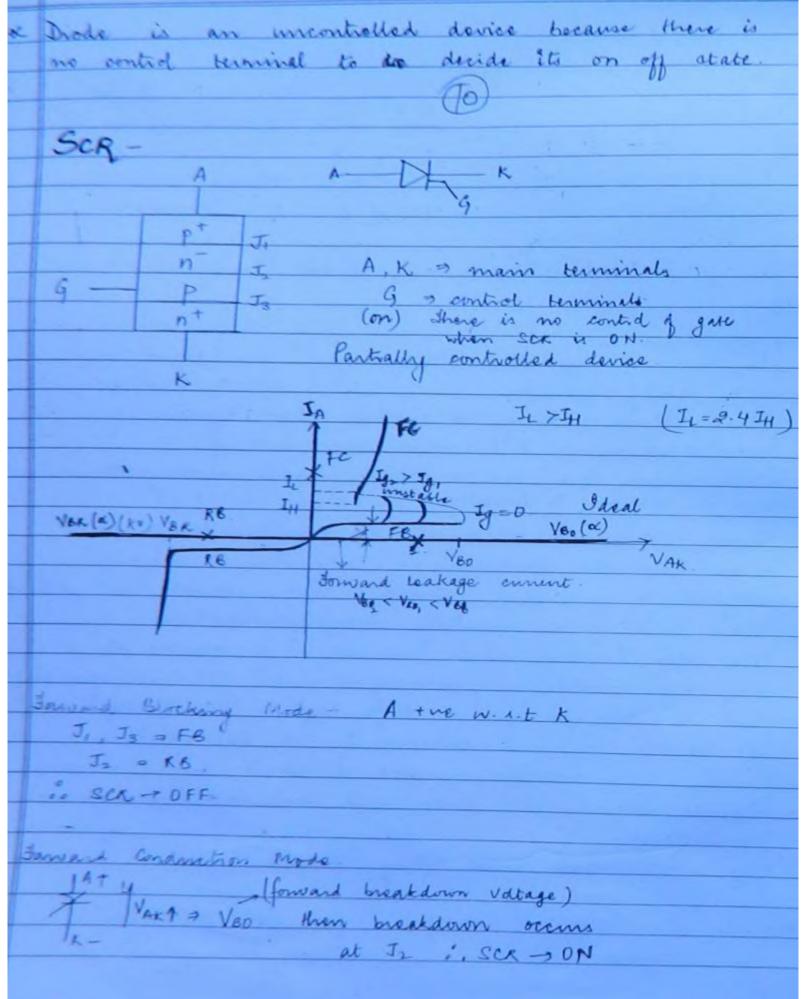




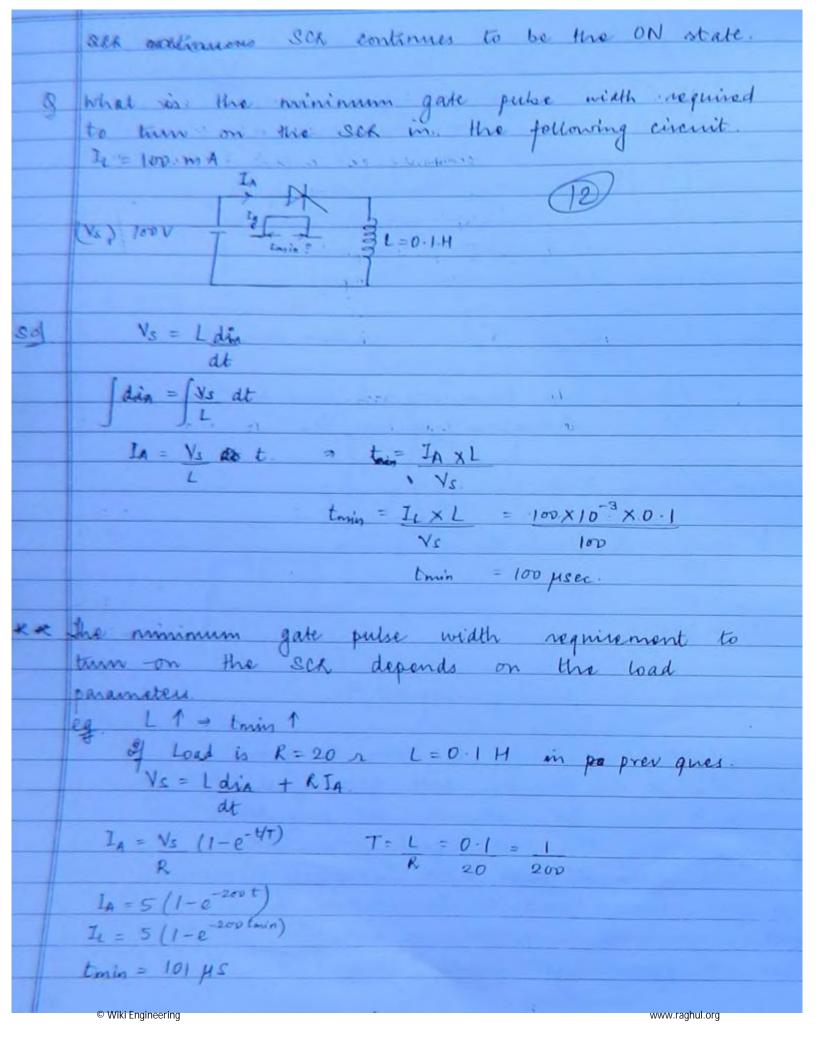
	Significance of doith resim
	Significance of drift region -
K	
	The thickness of the depletion layer decides the reverse blocking voltage capability.
	y vortage capability.
	The thickness of the depletion layer 1 due to the
	tayer penetrates more deeper
	change) This I the severse blocking capability of
	change) Ins I the reverse blocking capability of
Ħ	the diods.
	- Victoria de la companya della companya della companya de la companya della comp
-	reposit Broger WRIT
-	
	REVERSE RECOVERY CHARACTERISTICS -
K	ton ON time to DE time
	from ON time to OFF time
×	when diode is conducting some excess is
	stored in the device These encour chains again
	stored in the device. These encess charge carriers
	when divide in withhird him only carriers.
	when diode is switching from ON - OFF the
	excess charge carriers are still present in the
	device after anode coment becomes D.
~	In order to remove these excess charge
	carriers and ag acquire equilibrium state.
	recombination process takes place of homes reverse
	current flows in the device until all the
	excess charge carriers are removed from the device
- 11	
K.	This process is known as Reverse Recovery Process
	of the transition time during this process is be
	Revuse Lewy Time (ty) Wiki Engineering www.raghul.org
- 11	© Wiki Engineering www.raghul.org

recovery change) ON -> OFF tra + (IA = 0) - to: (In = 25% IKM) * The ton decides the switching frequency of the dio Classification of Power brokes based on Kenense Fast Lecovery Dioda © Wiki Engineering www.raghul.org

	(Slow) — (high speed) General Purpose Fast Recovery Schrottky bioda Diodes Diode @				
	(Stow)	- (high of	eed)		
_	General Purpose Diodes	Fast Recovery	Schottky bioda		
	Diodes	Diode	(9)		
2.1					
1.	tn - 25 Ms	tn -> 5 ps (Len)	tra - namo secs		
d.	Inating 7 11 to several	Insting -> 1A to	Isating - limited .		
	Inating 7 11 to several	several 100 of A.	I rating - limited . to 300 A		
	Vrating = 50 V to 5kV	Vrating - 50 V to 3 kV.	Vanting = 100 V.		
		,			
		1 1 21	14 1		
K	In fast recovery	diodos, the layers	are doped		
	with gold / platinu	n. 2025			
K	Gold platinum dopi	increases the spectimenters	lifetime of		
	change carriers f	increases the spec	ed of		
	recombination This	reduces the severs	e rocovery time		
K	Used in chappiers of	invertes	*		
K	Schottky dide is a metal to semiconductor junction				
	dioda. Hore the conduction is only due to majority				
	caniers.				
R	Since there is no minority change corniers the				
		much reduced			
	very high switching				
K	Due to the absence of drift region, the thickness				
	of dopletion layer is reduced io it can block a				
	small reverse volta	and the second second			
K		or power brigh swit	ching frequency		
	applications	,	U		
	eg Snitch Mode Power Supply (SMPS)				
	~	1.0			
x	Used in uncontrolled	rectifiers, free wh	seling dioder		
	for rectifiers.				
ejasa -a	© Wiki Engineering		www.raghul.org		



Significance of gate signal -· teles (1) When gate toignal is applied, change gets accumulated in depletion region p, IA 1 and 1 the thereis accumulation as it gets a conduction path. This lands to I of charge of this broatdom of depletion region tunning on the sca of ig 1 or dig 1 United conduction Area 1 and lesser vig is need for breakdown ie een voo. Reverse Blocking Mode -A mundo -ve w.n.t K J2 => FB J, J3 > RB SCA - OFF Significance of Latching Cornent -Latching current is related to turn on process when scr is in the ON state, gate signal is removed to avoid the continuous gate power ton If we remove the gate signal when IA < I then SCA fails to turn on is We must maintain the gate pulse width until IA reaches & just above costain minimum value (Latching current) When we remove gate signal, when Is > It then



Significance of Holding current -Holding current is related to turn OFF process Gate has no control to turn OFF SCR In some cases we require commutation circuit to turn OFF SCK A TM K

- VR TIO

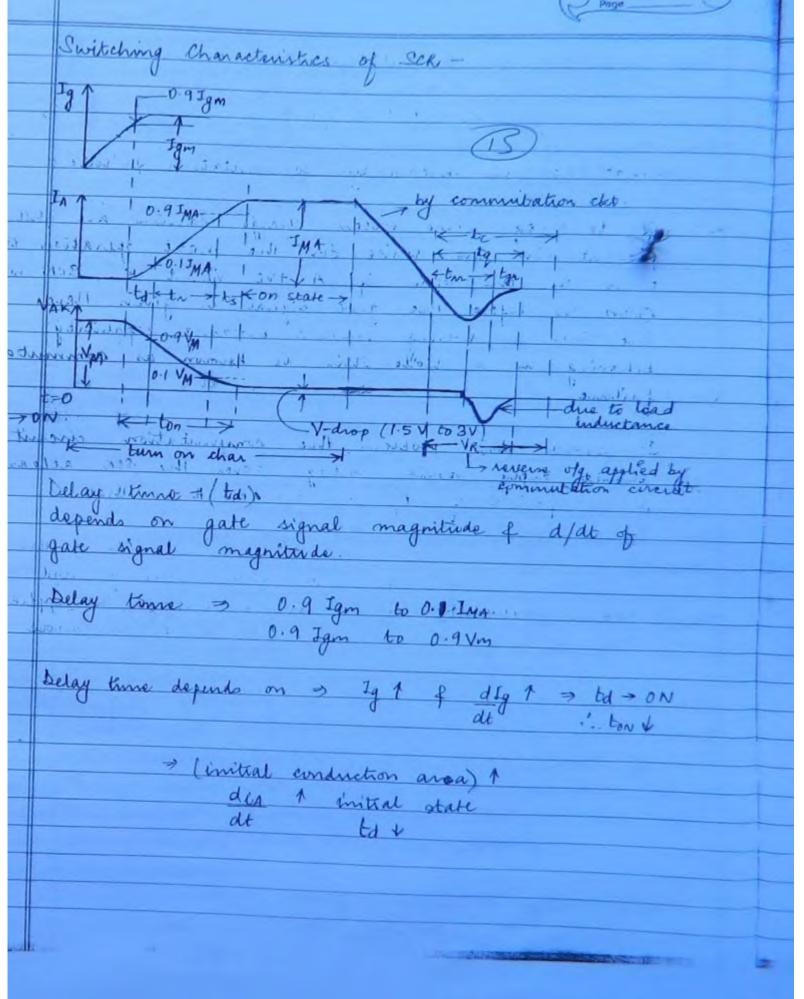
Comma circuit

A Vo

A Vo

D Comm akt forces amode orment to insdice below IH
After that it applies reverse voltage to or remove all
change carriers forces the device. * Procedure to turn OFF SCA using a commutation ckt -Commutation circuit forces anode ciment to roduce below a certain minimum value of their applies a reverse voltage across the SCA attraction for a period of device turn off time or granted Cincuit torre of there to It is the time for which the com circuit applies a reverse voltage acros after the anode current becomes O. I It is the time taken to remove change carriers present in the device provides the ty.

will turn on before applying gate (behaves asdide) For successful commutation to 7 tg always. of texty commutation fails what do you mean by commutation failure? of te to some oxcess change carriers are still piesent in the device. For the next operation to turn on the SCR if A tre Wint K, 3CR will turn on before the gate signal is given. Here the sca is loosing forward blocking capability behaving as a diode. This is known as commutation To avoid this problem, the commutation circuit should apply reverse voltage across the SCR ratleast for a period of to or greater than that Holding current is the minimum Ia below which the SCK becomes off and regains the forward blocking capability if a reverse voltage is applied across Ser atteast for a period of to or more than that © Wiki Engineering www.raghul.org

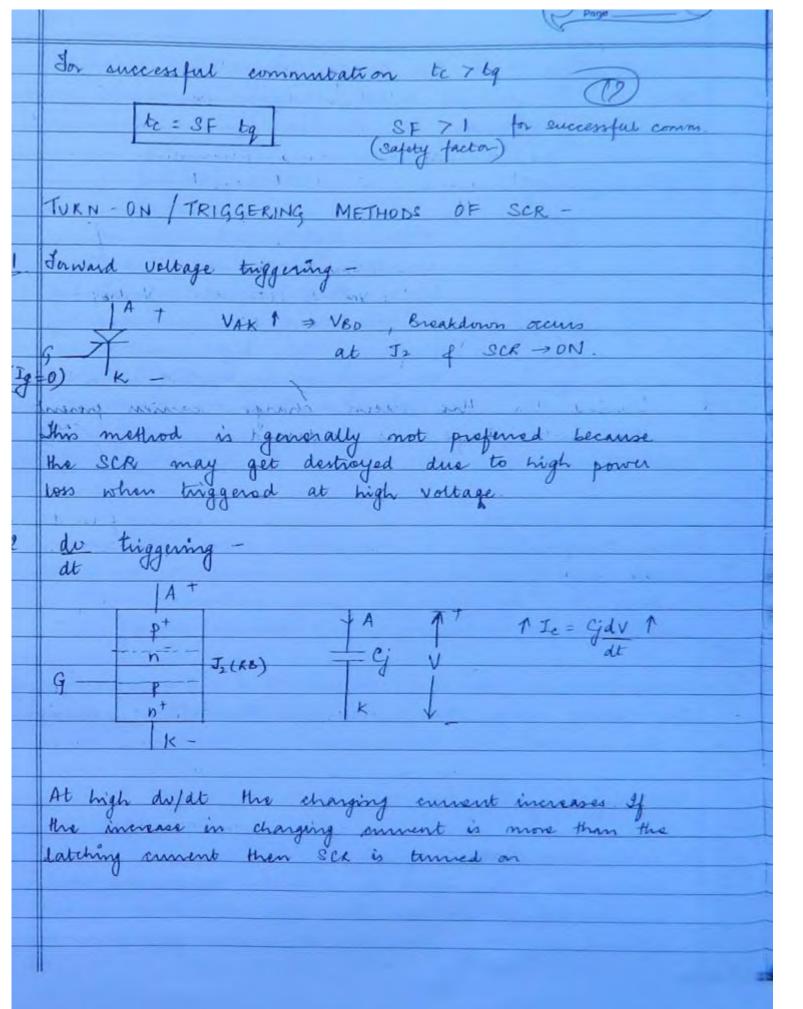


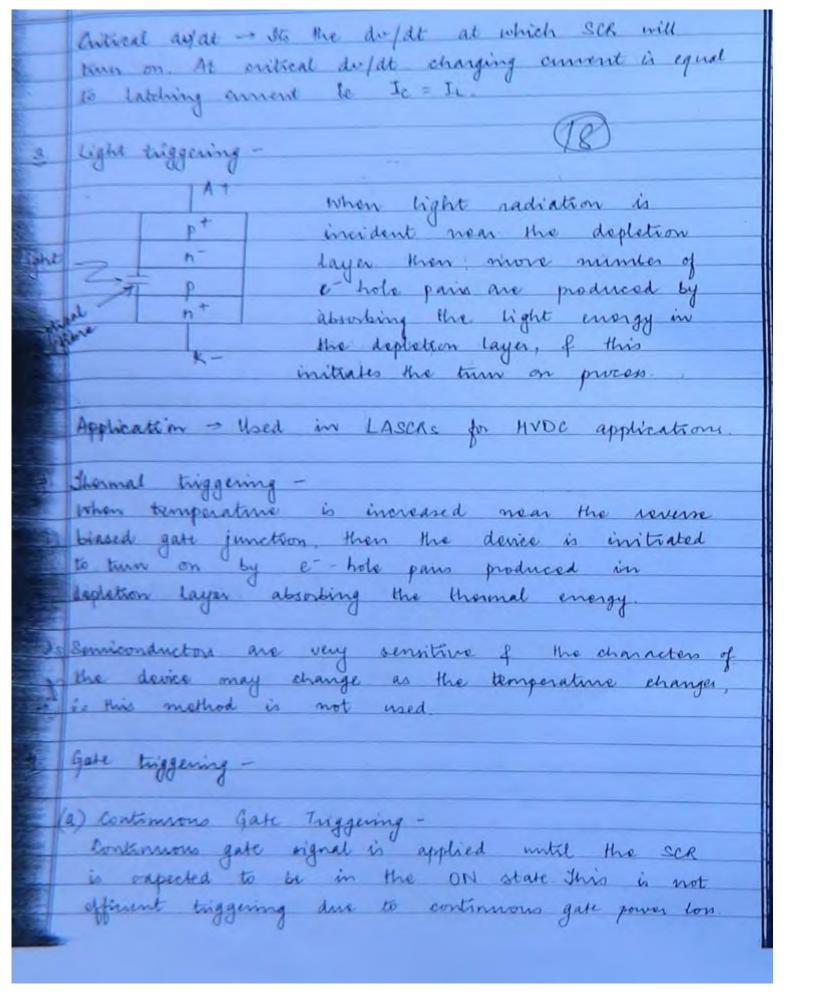
© Wiki Engineering

www.raghul.org

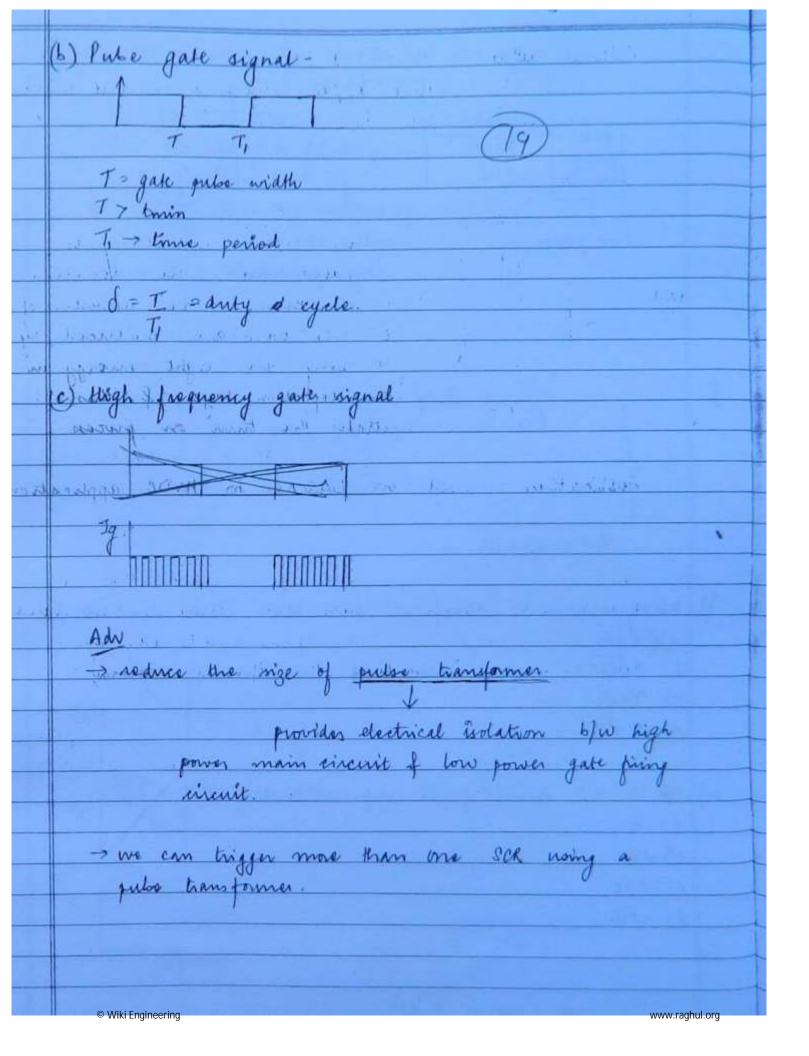
hise time (tr) 0.1 IMA 60 0.9 IMA. 0.9 Vm to 0.1 Vm Rise time depends on Load parameters Spread time (ts) D.9 Ima to IMA. 0.1 Vm to (ON state V-drop) (1.5.-3V) Leverse recovery time (tr) During ton the excen charge carriers present in Gate bocovery time (tgr)

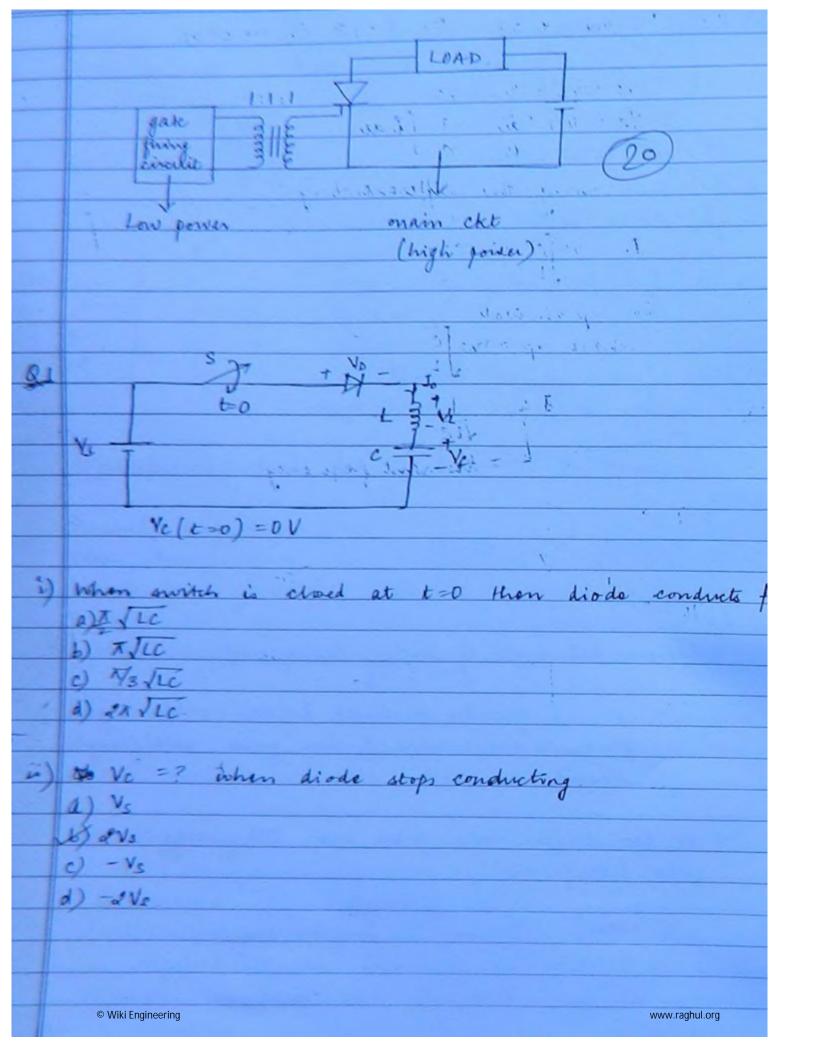
During to the excess charge carriers present in the inner layers near the gate junction is Device turn off time (tq) The device turn off time is generally very much greater than turn on time. Therefore the device turn off time decides the switching characteristics of the SCR to slow thyristons (convertes grade trysistons) - Fast thyristors (inverter grade thyristors)
ty - 3 ps to 50 ps

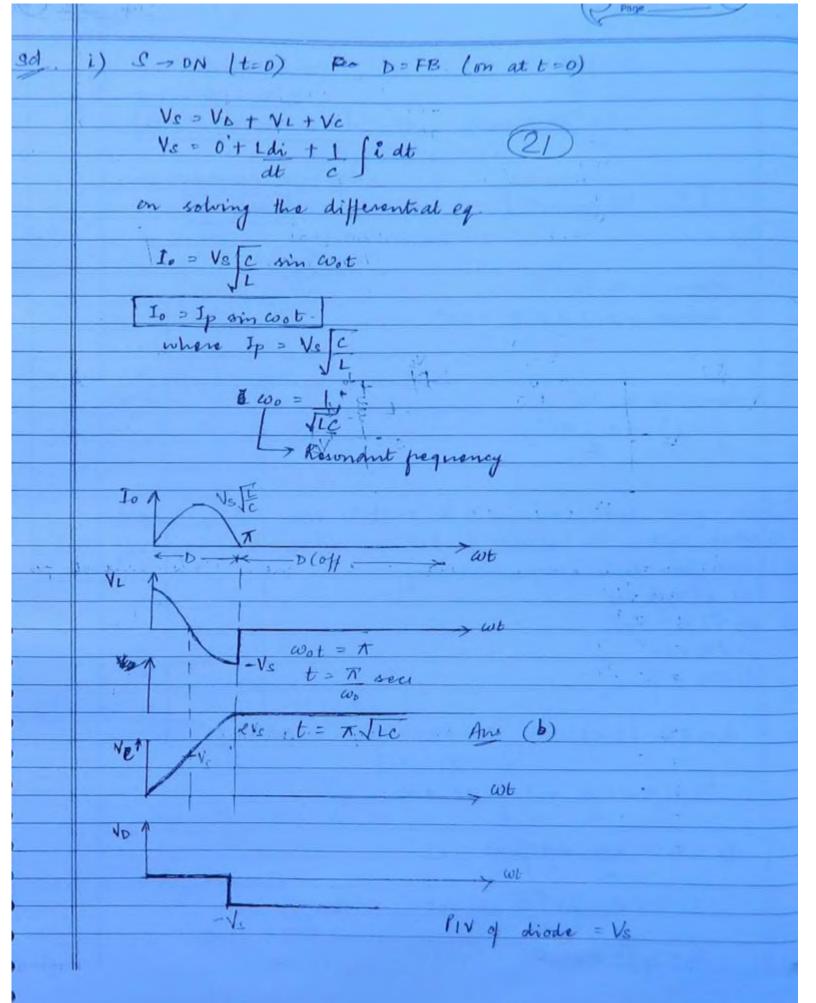


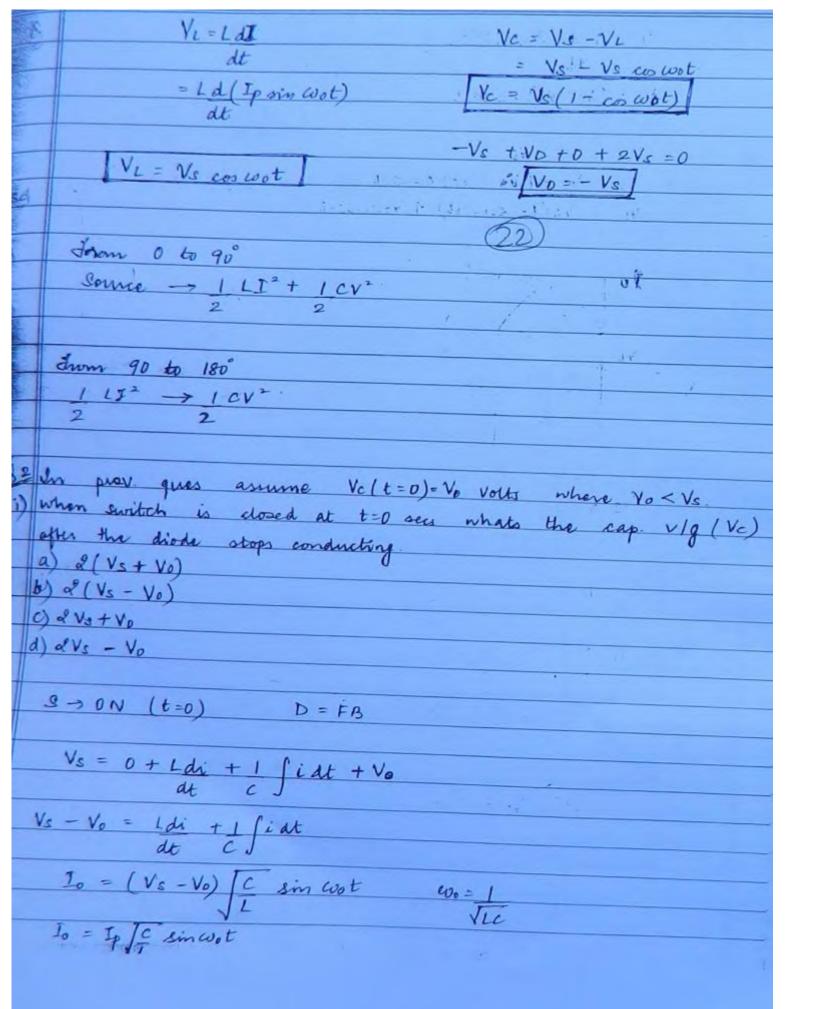


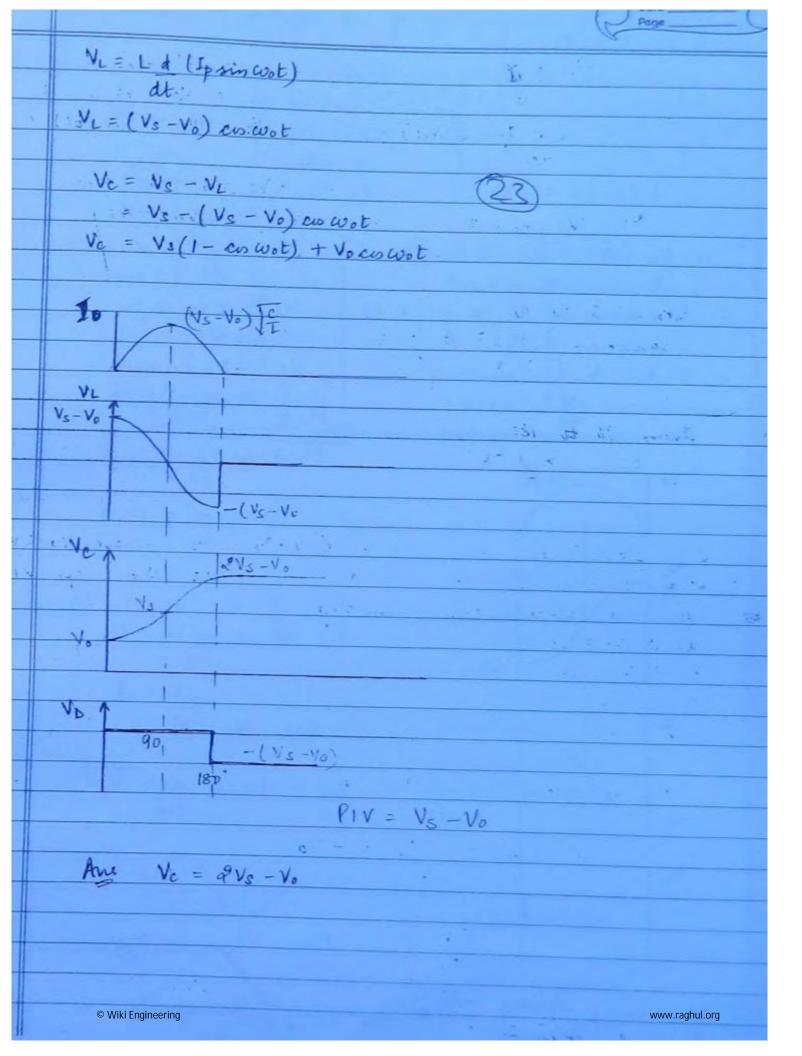
© Wiki Engineering www.raghul.org

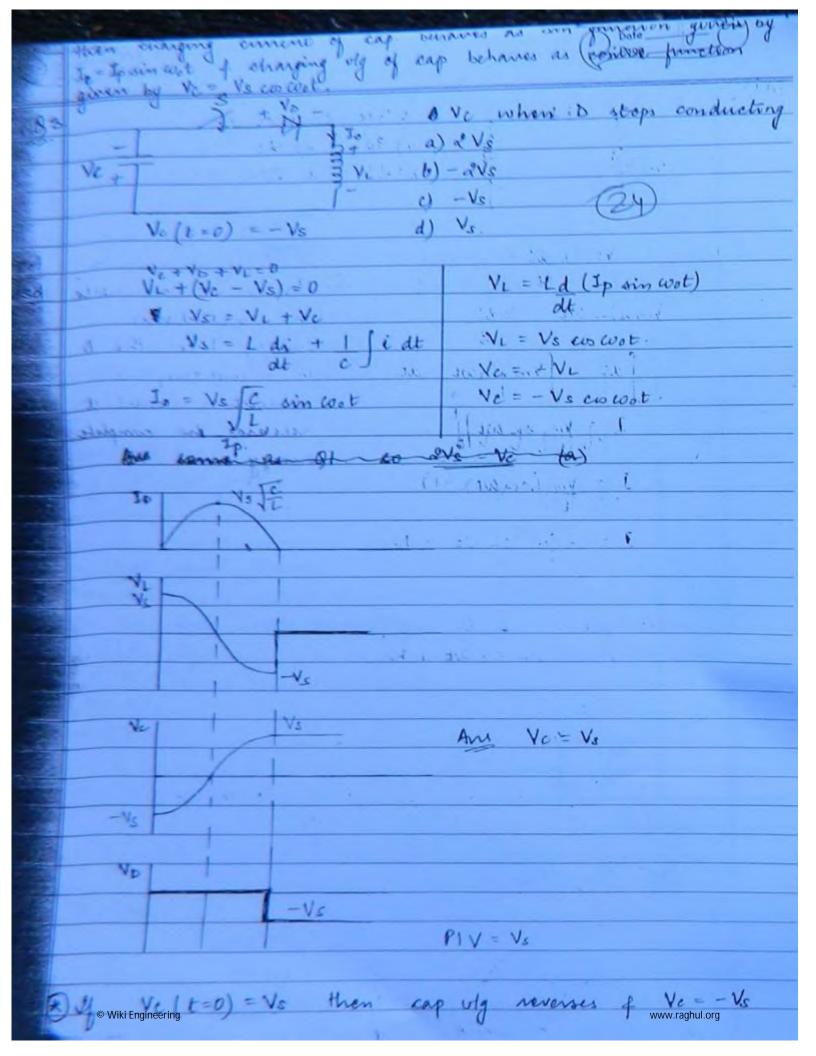


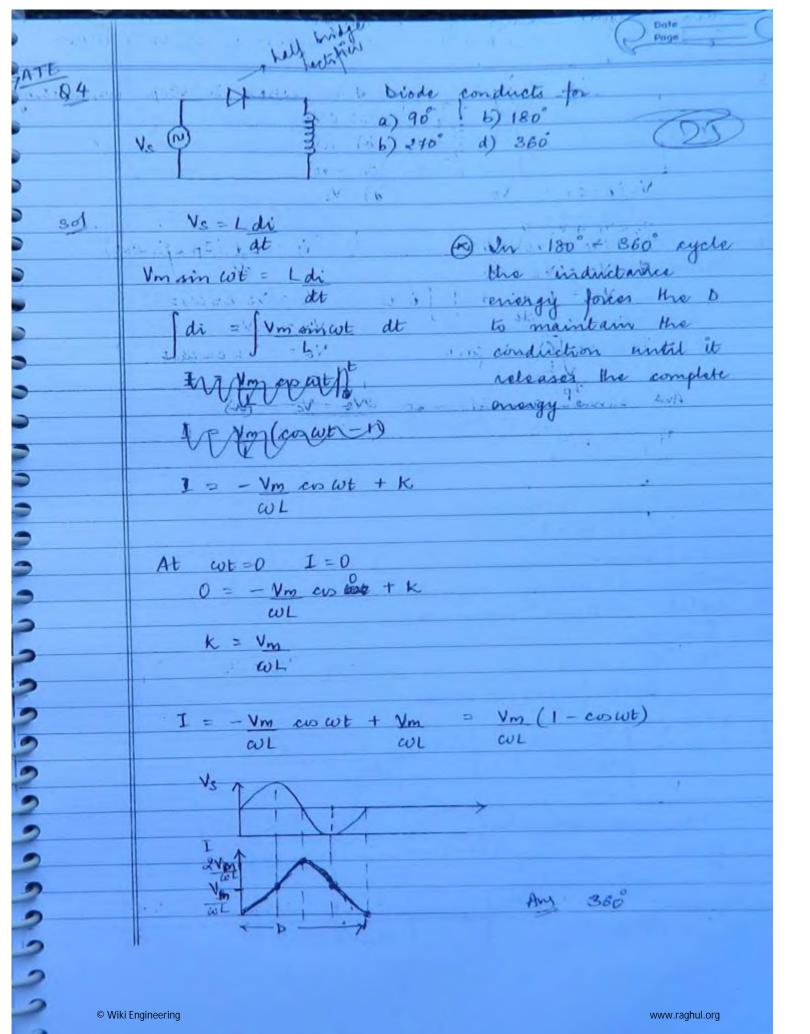


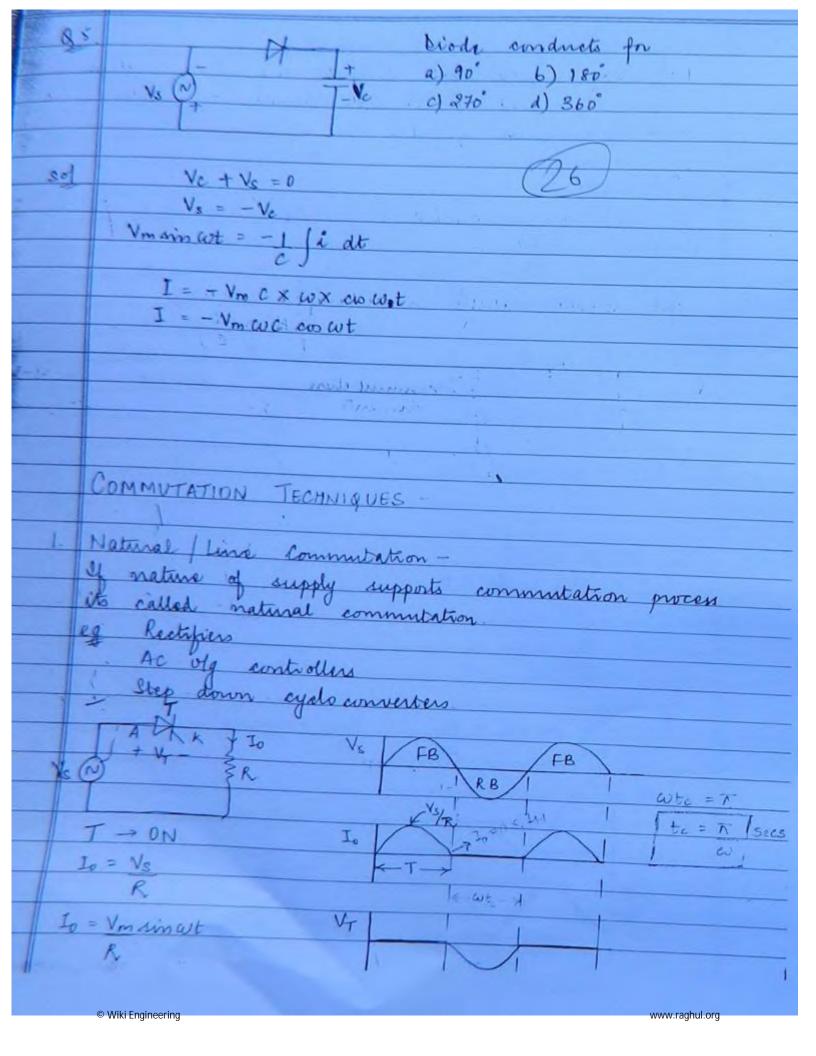


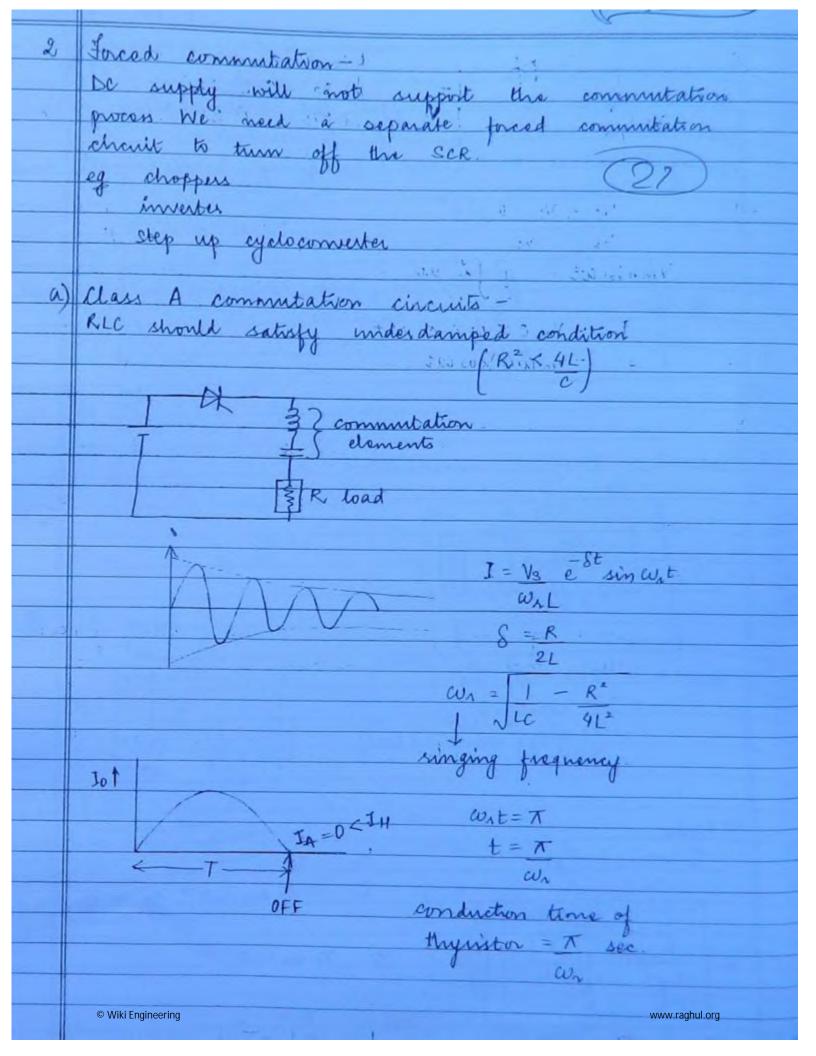


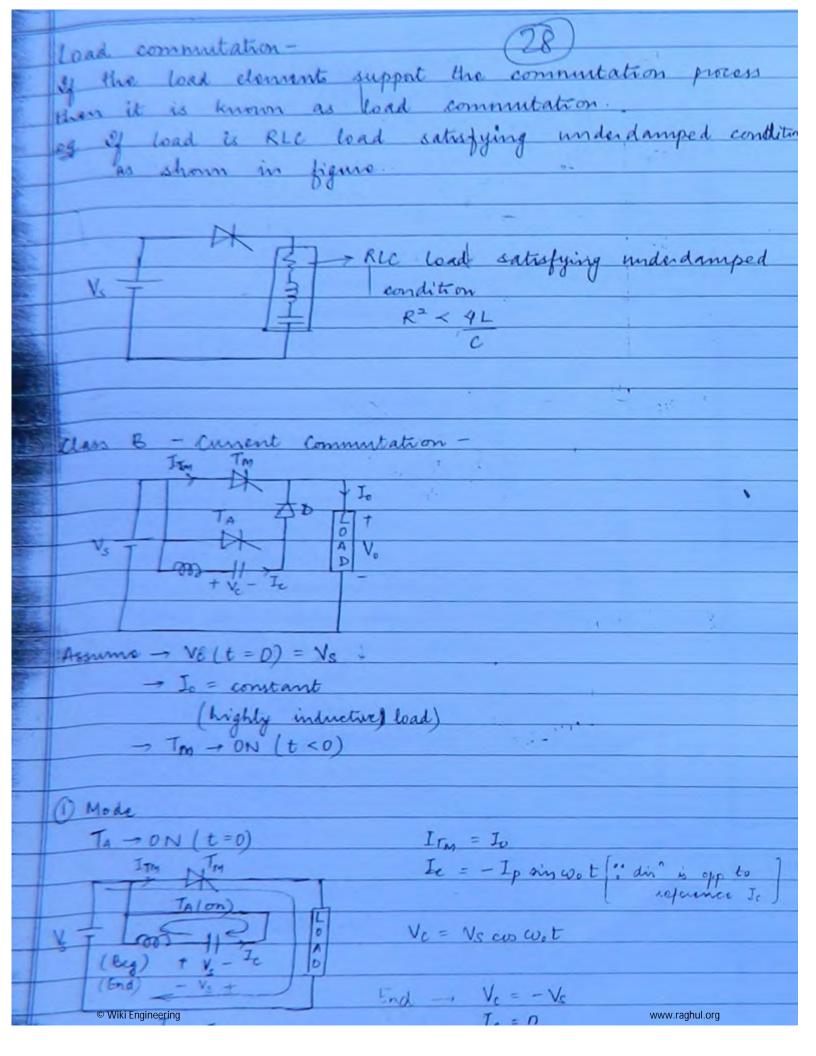


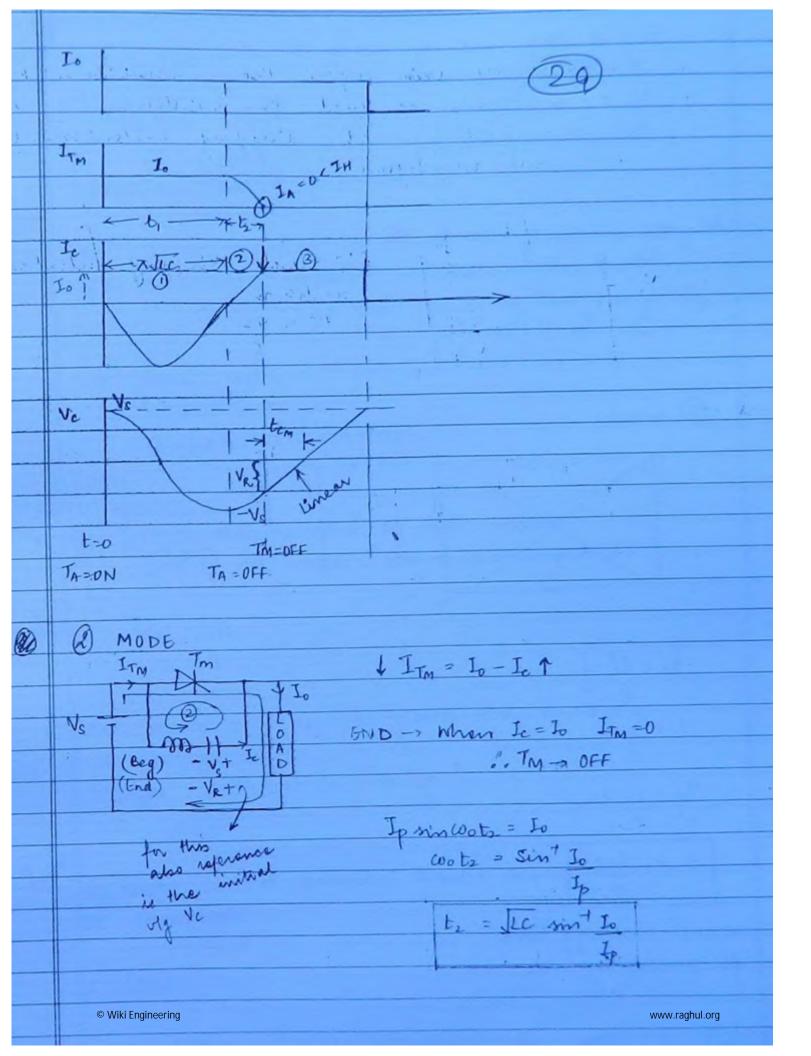


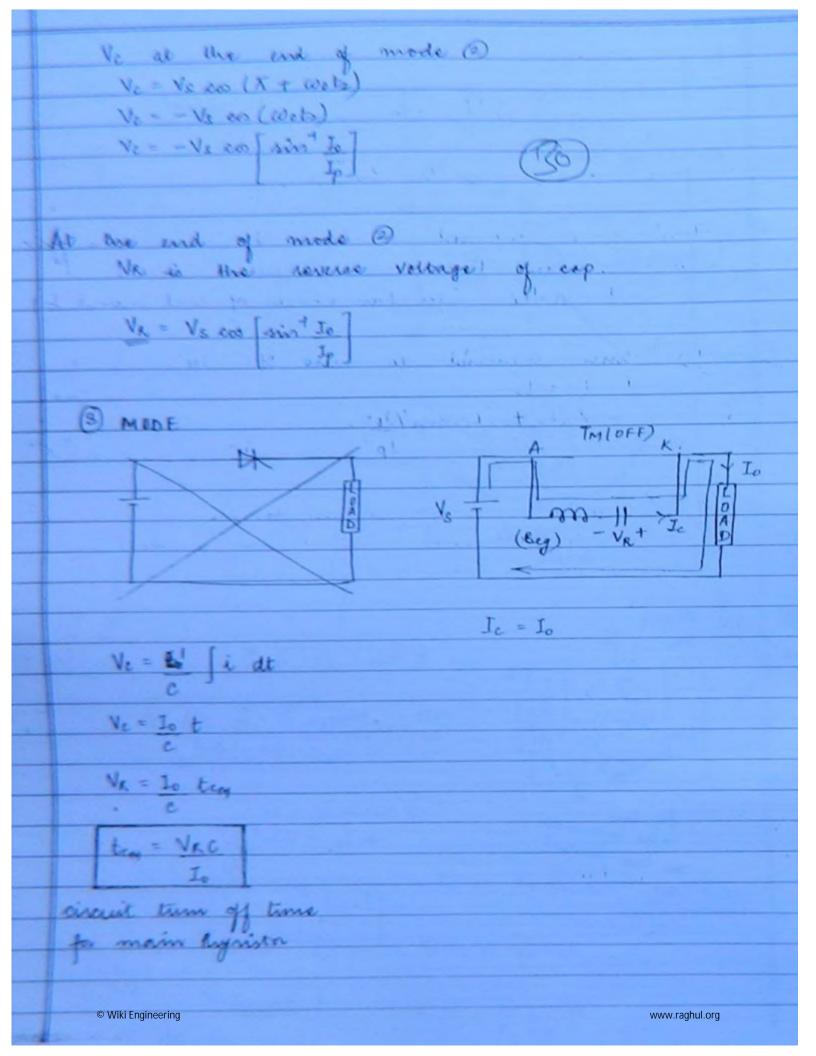


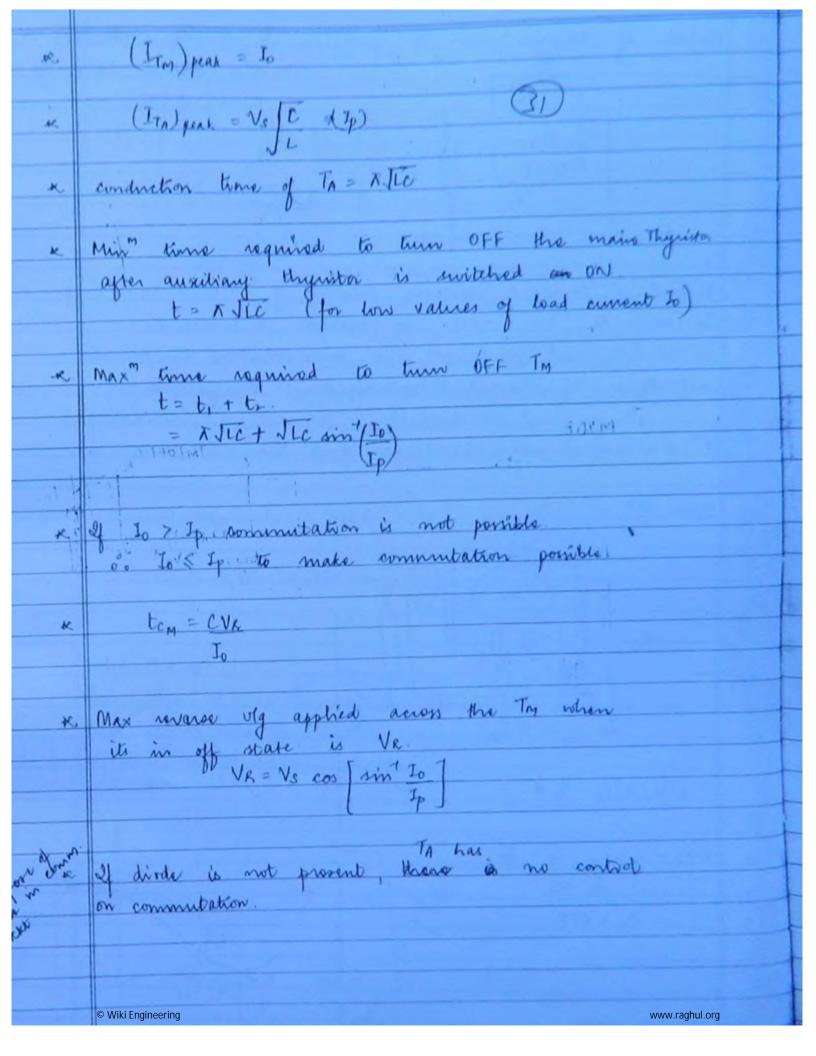


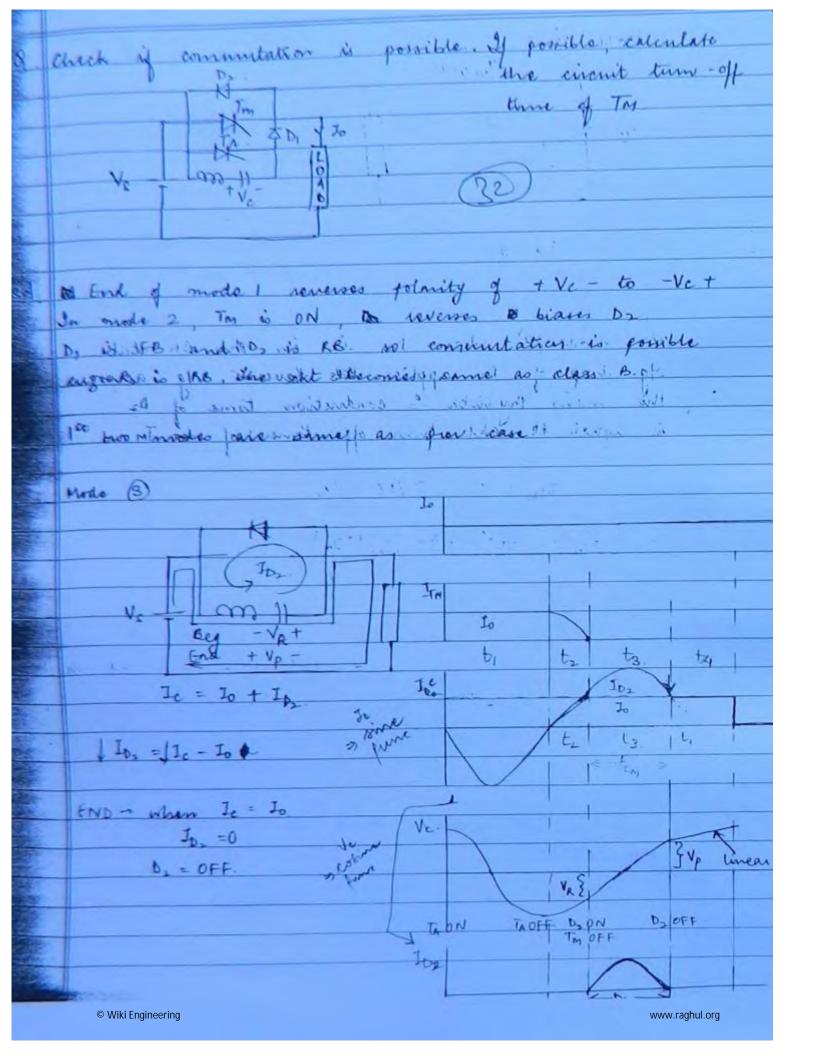


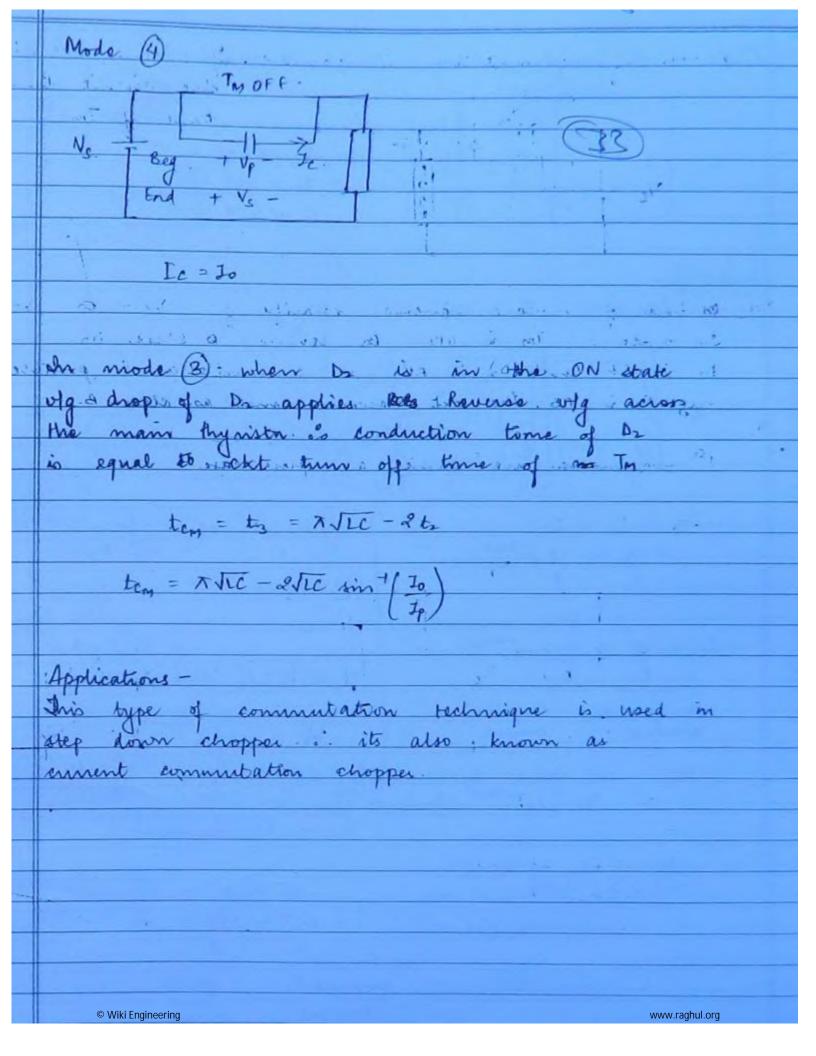


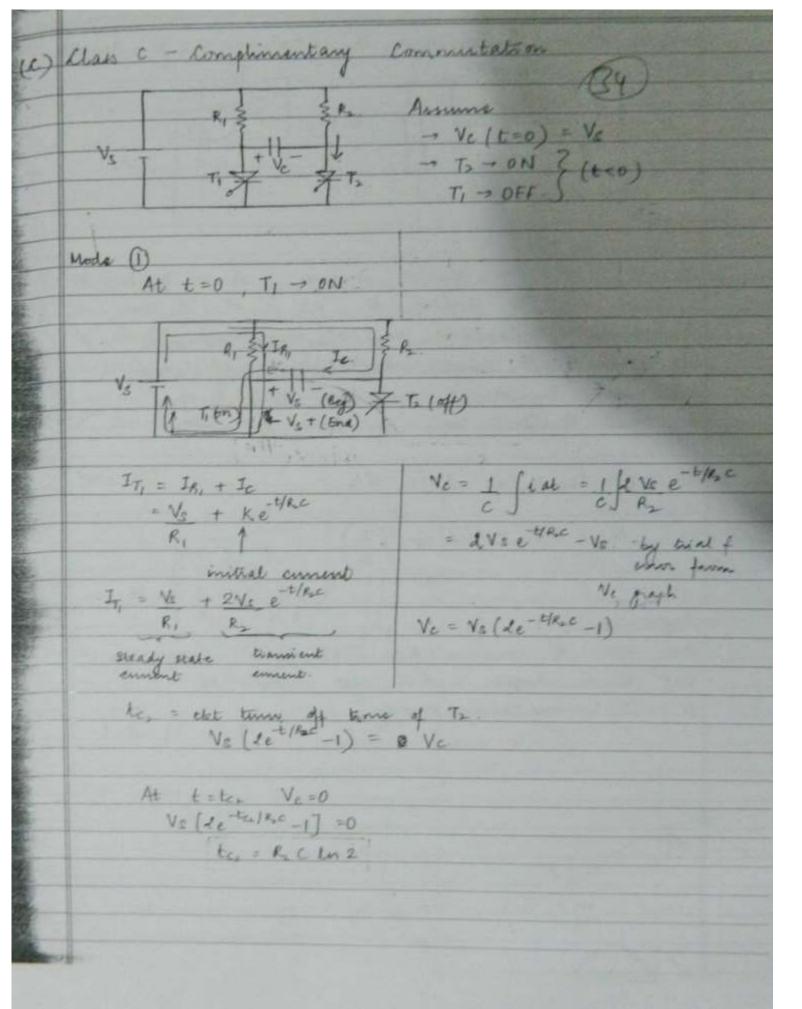


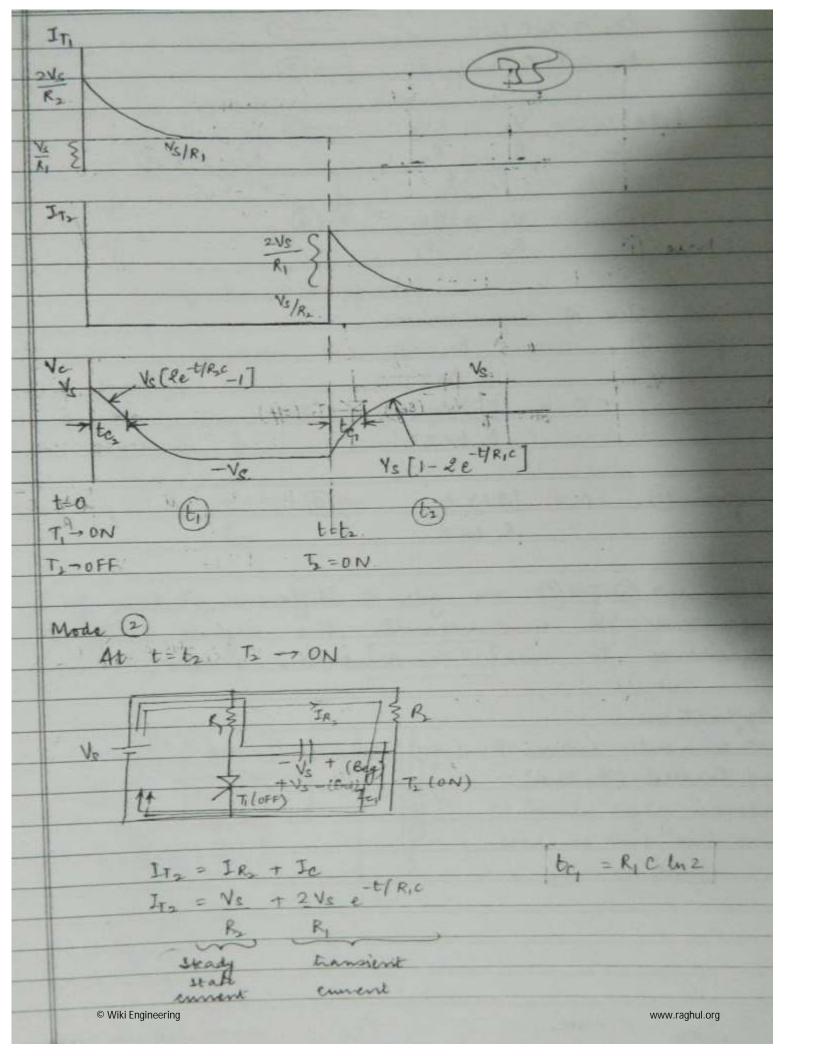


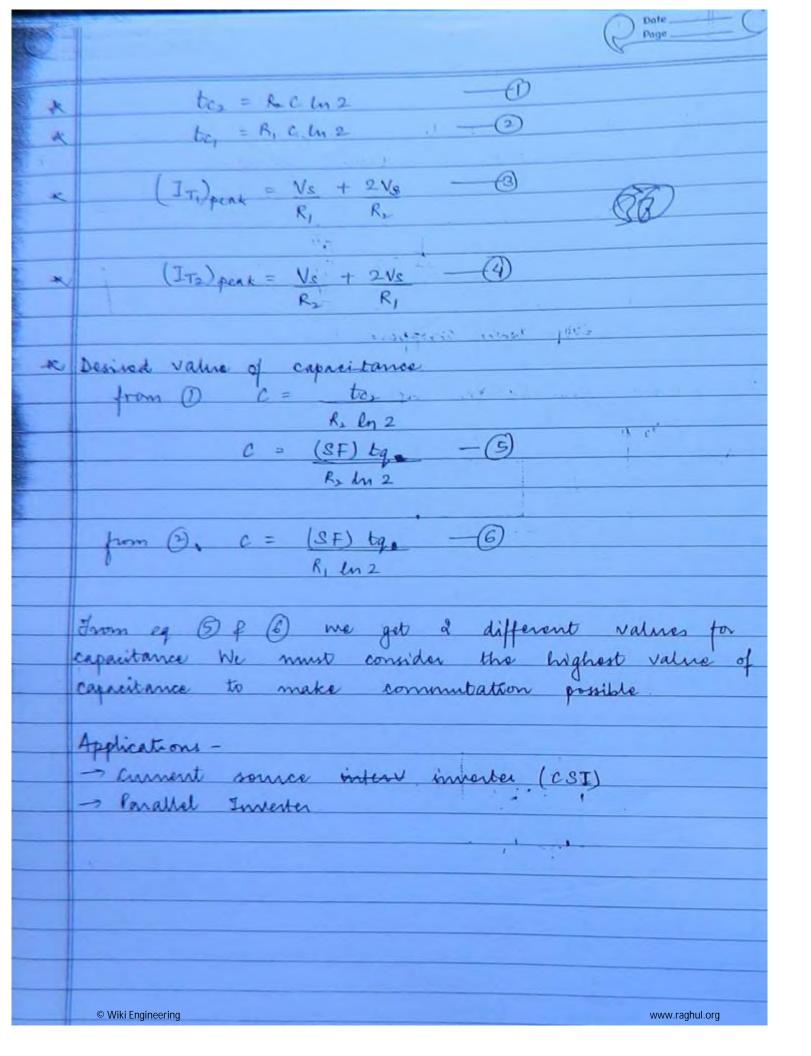


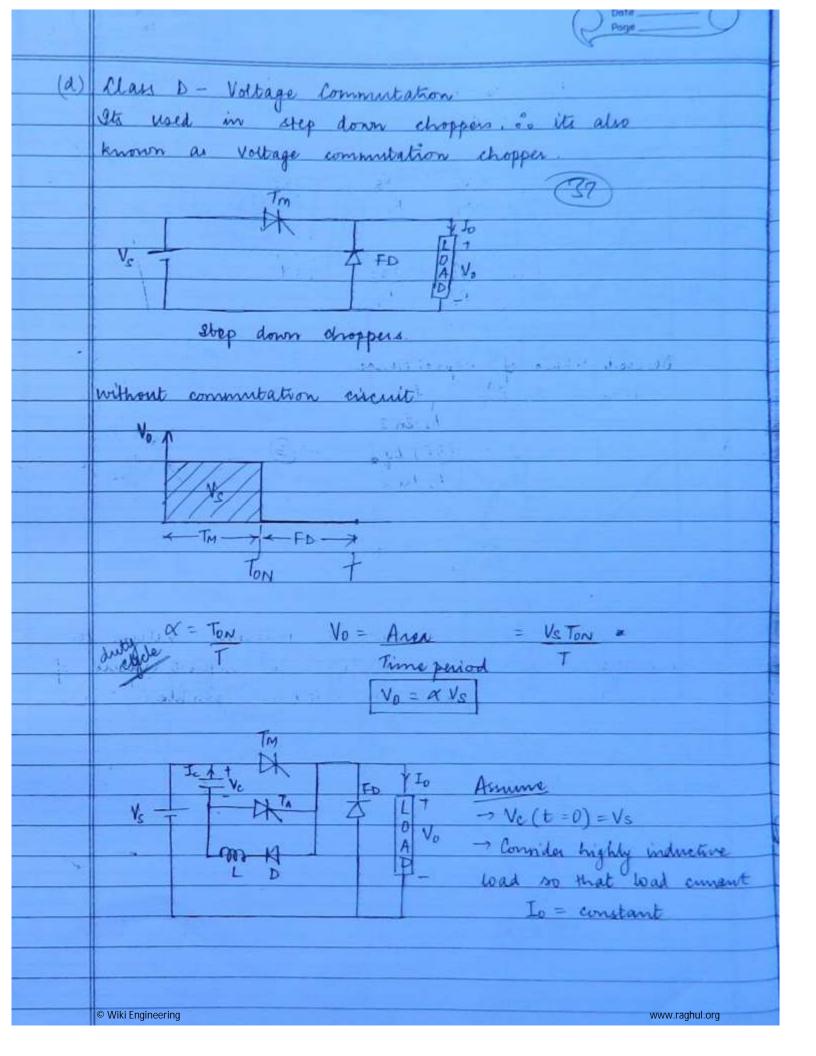


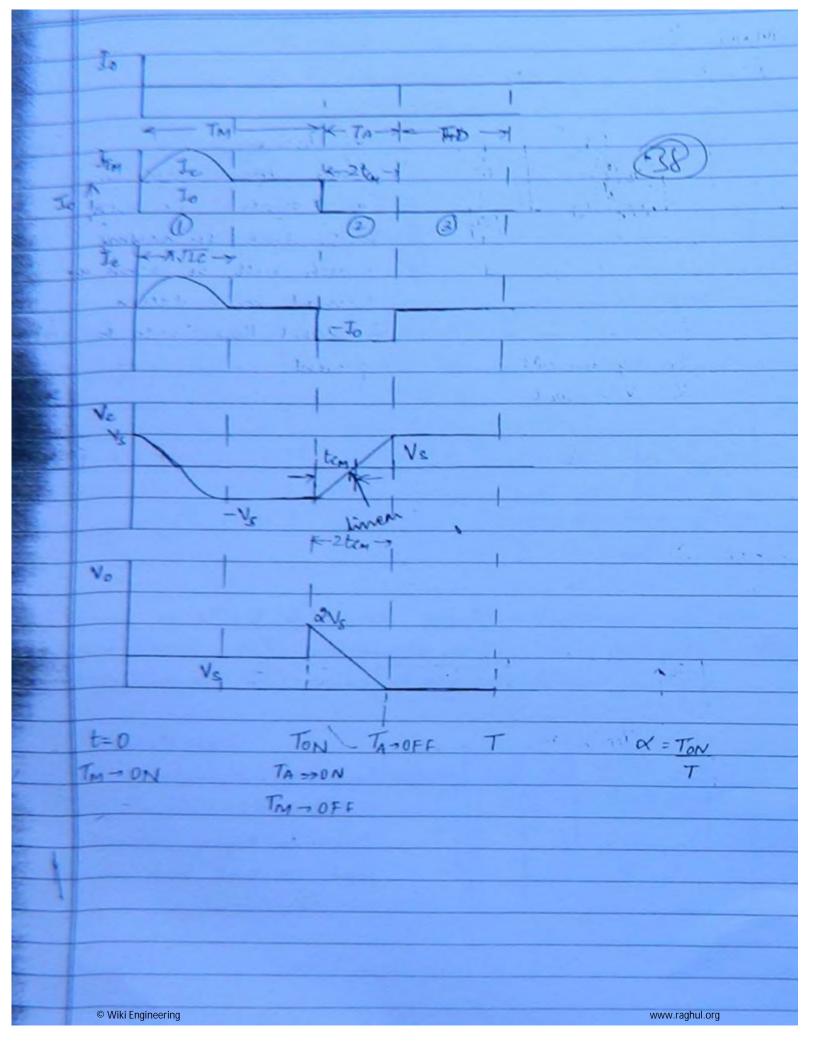


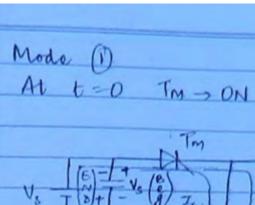




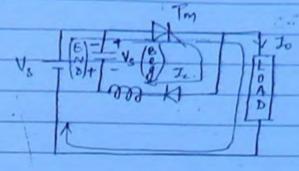








39



Alf diode is not,

there, after completion

of mode I capacita

will start discharging

which will be some as

ITM = Io + Ic

Ic = Ip sin wot

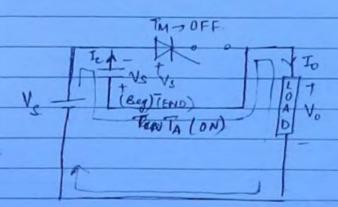
Vc = Vs coswot.

To avoid this biode is present.

 $5nd \rightarrow Vc = -Vc$ Ic = 0

Mode 2

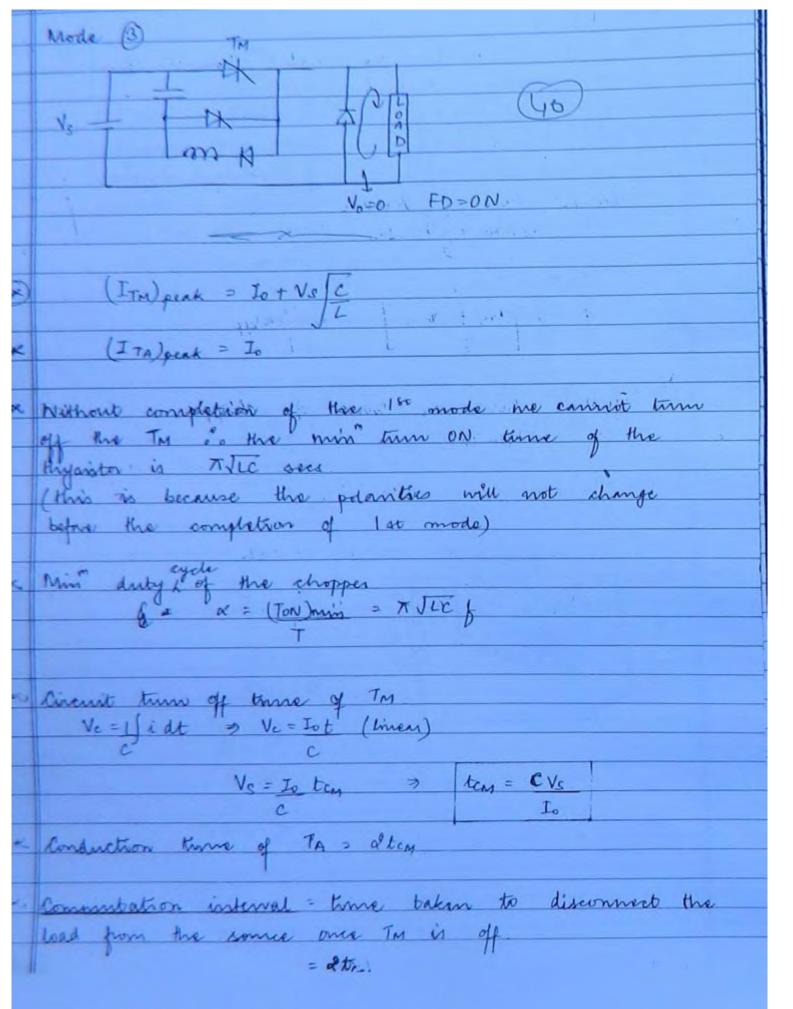
At t=TON TADON

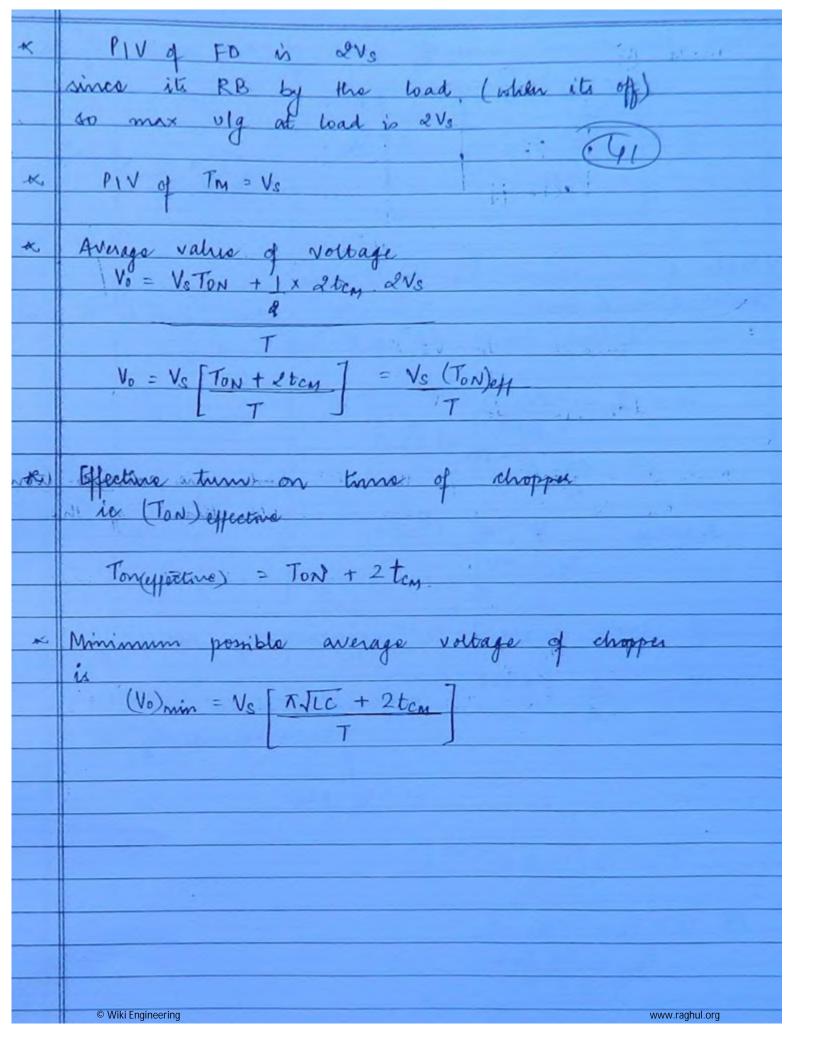


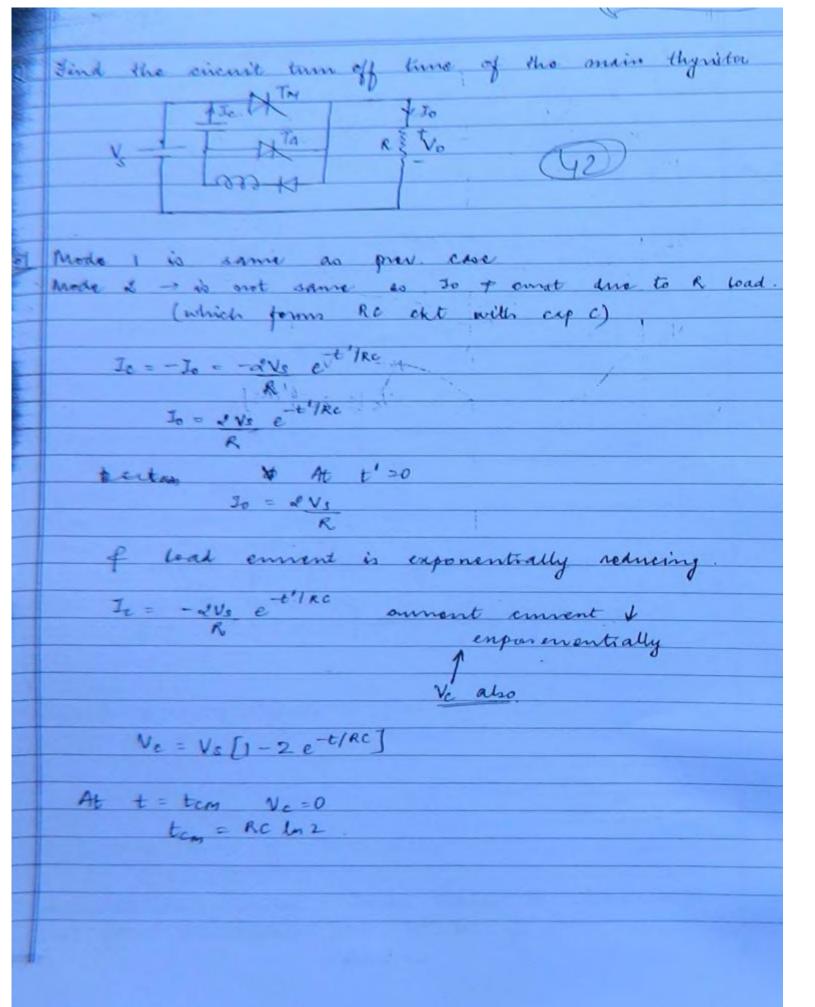
Je = - Jo

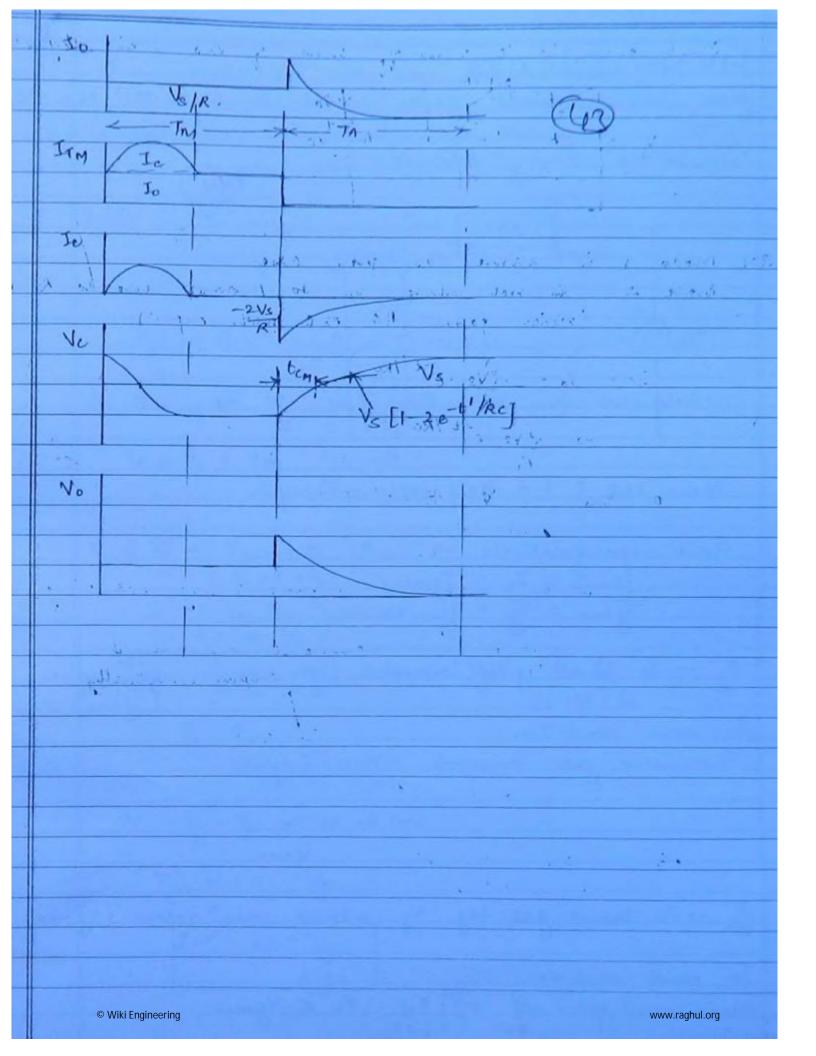
 $\frac{V_{\ell} = -V_{S}}{V_{0} = -2V_{S}}$

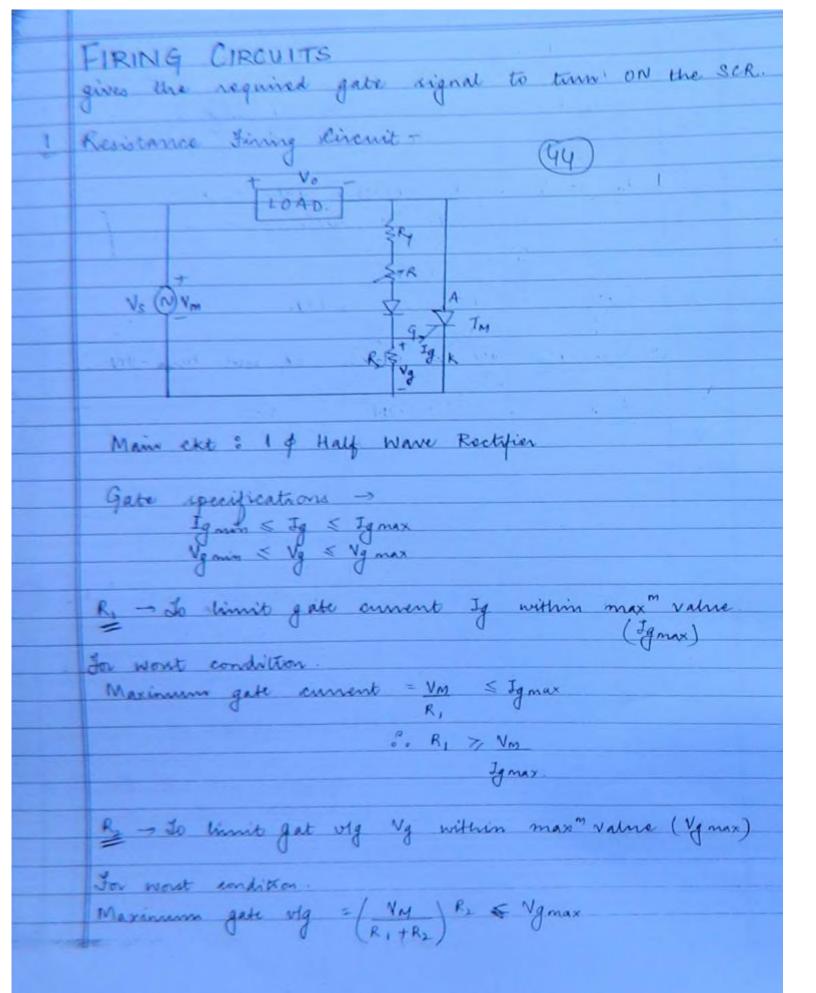
 $V_{c} = V_{s}$ $V_{o} = 0$ $I_{c} = 0$ $T_{A} \rightarrow 0 FF$



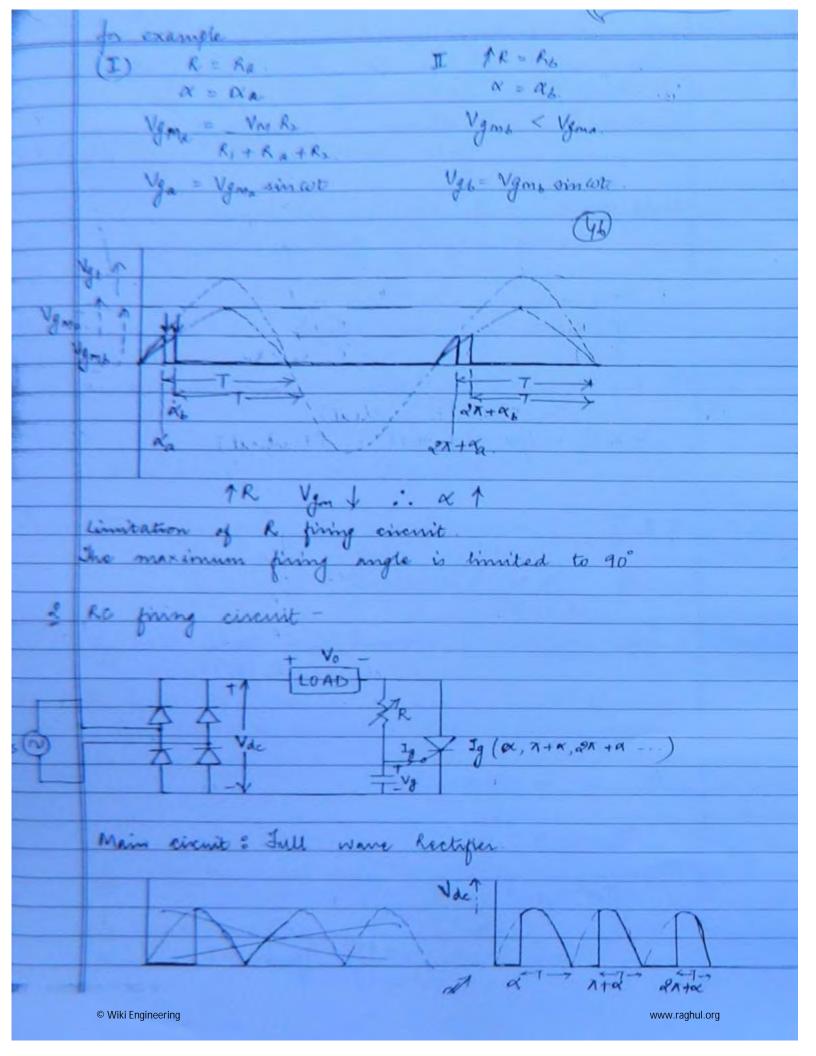


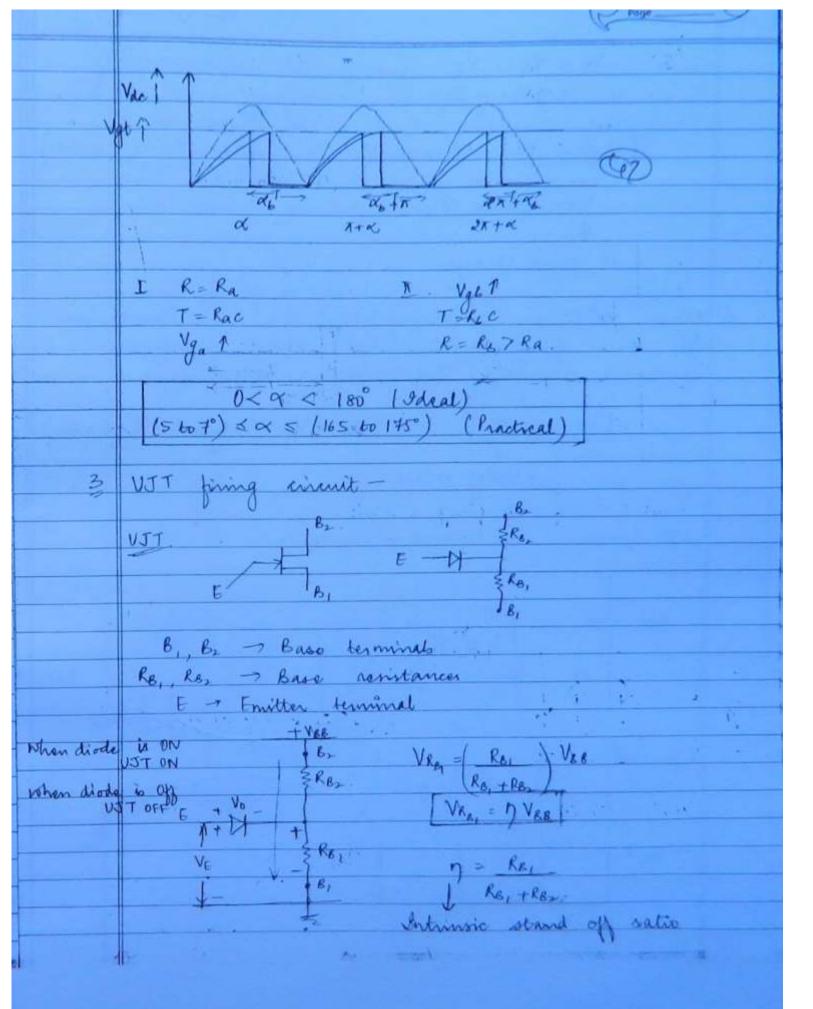


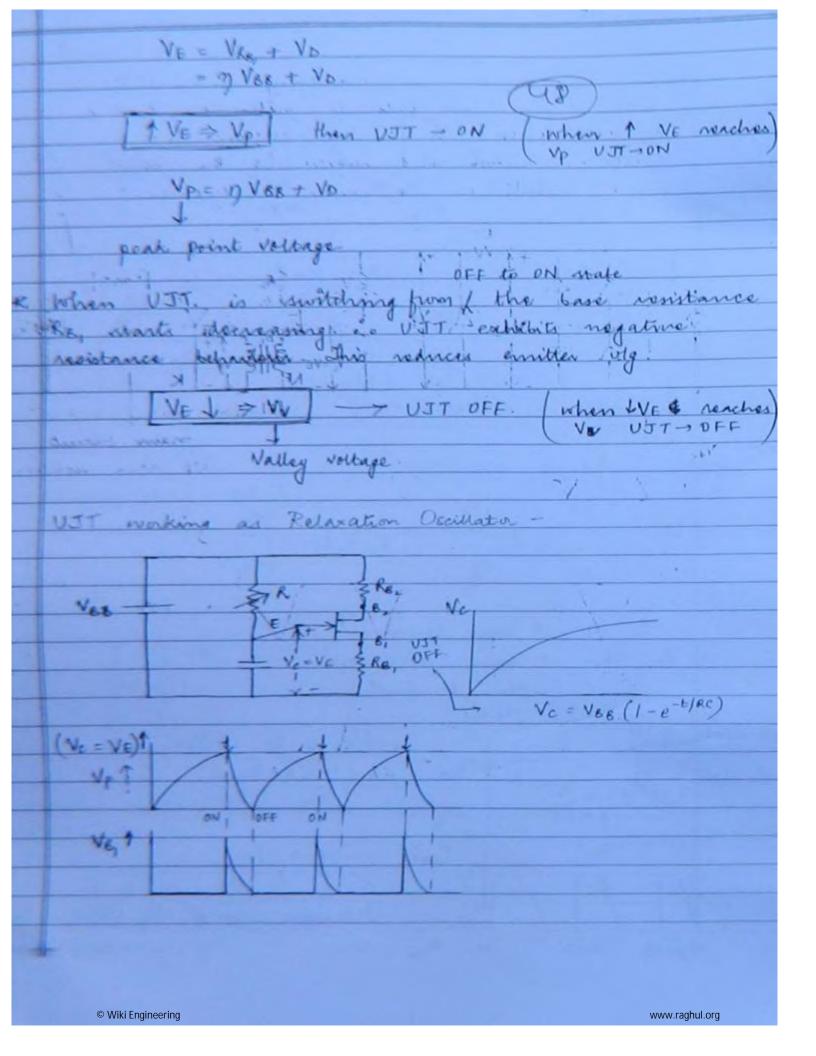


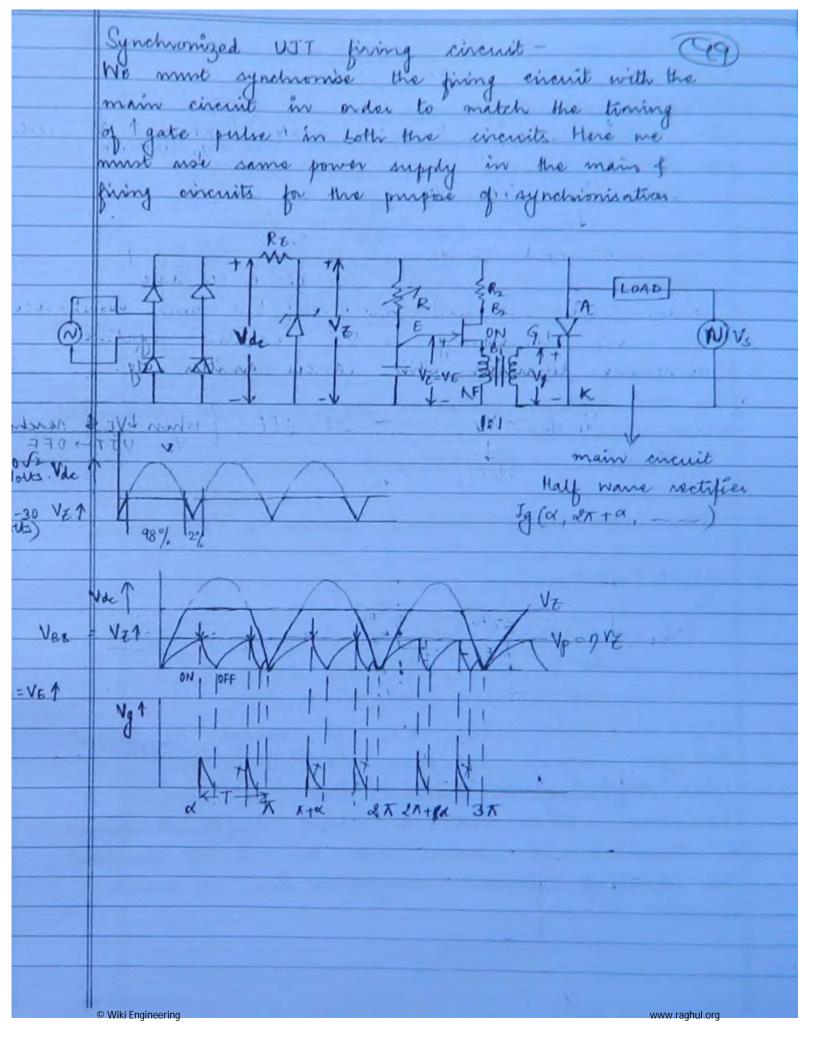


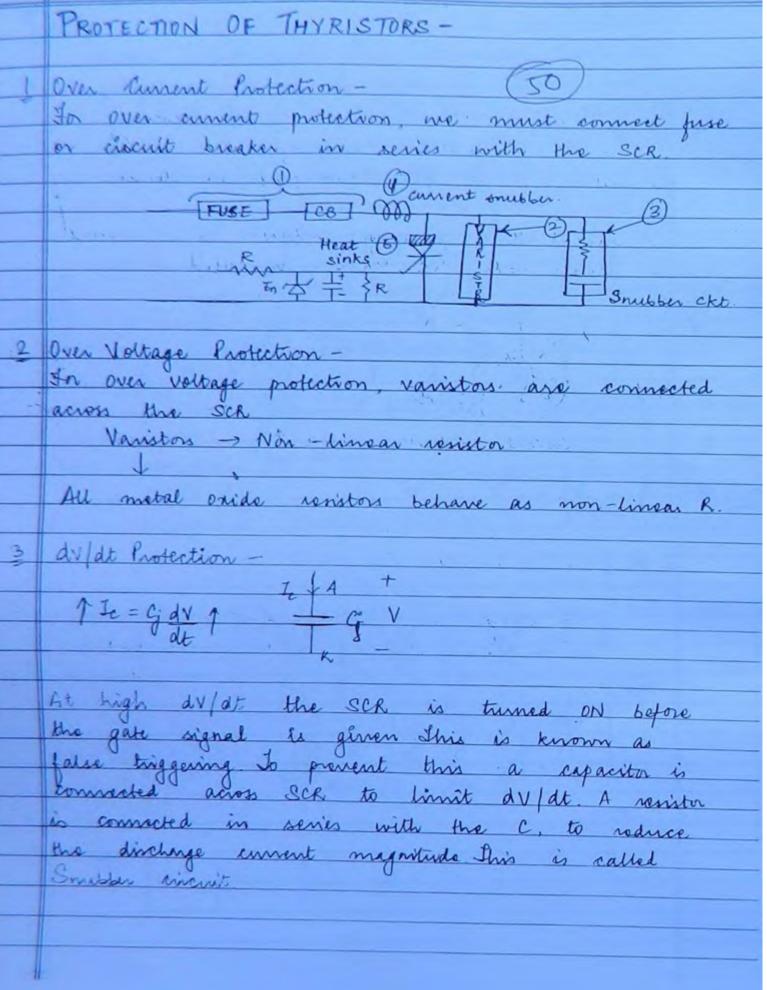
From above eg? ne can design value of Rs.
Variable R To change the turning of gate signal ie &
biode - to avoid negative gate signal during negative eyels of source
[Vgt] > Gate tring on voltage.
Its the gate Mg at which SCR will turn - DN
$ie \text{ at } V_g = V_{gt} SCR \rightarrow 0N$ $(\omega t = \alpha)$
$V_{0} = V_{0} = V_{0$
$V_g = \left(\frac{V_m R_2}{R_1 + 1R + R_2}\right) \sin \omega t$
Vg = Vgm svn wt where & Ygm = Vm Rz R, +187 Rz
Vg = 0
At Vg = Ngt SCR -> ON
Vgm sin & = Vgb
1x = sin / Vgt
TR Vgm L & T







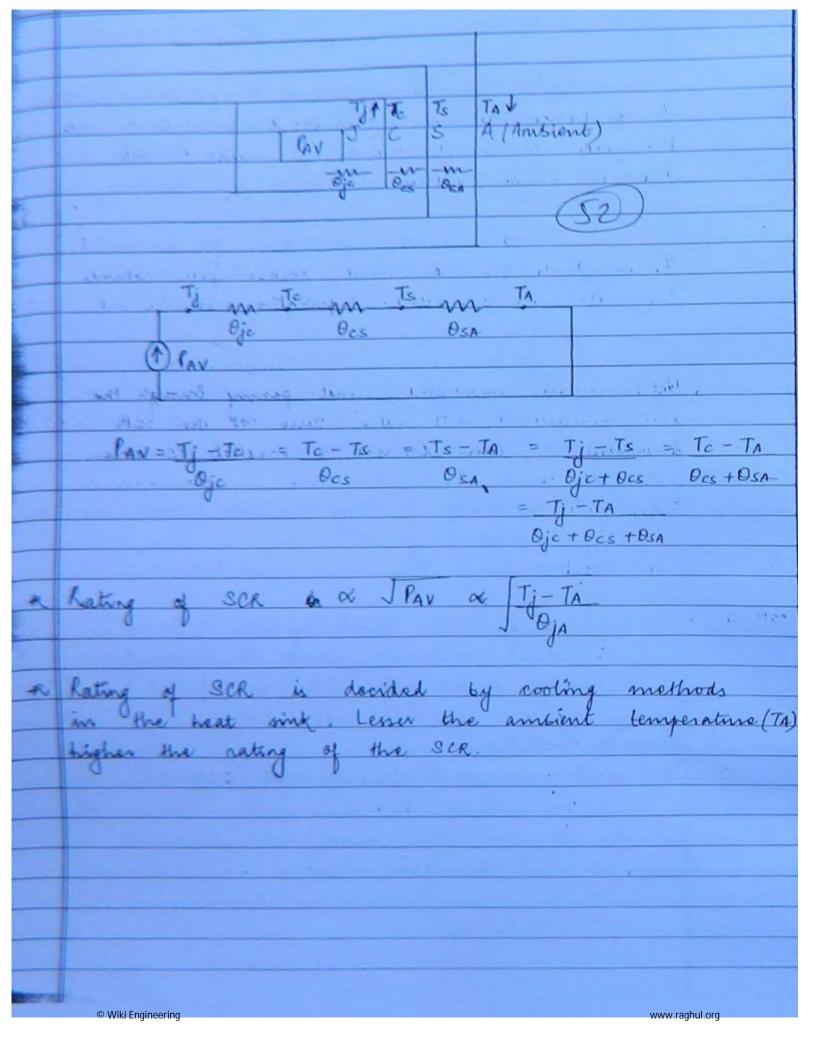




1.	
4	diff at Protection (7)
	Whom didt > (sound whether it stores somissed) the
	when di/dt > (spread velocity of charge carriers) the charge accumulation increases cumulatively in
1.1.3	charge accumulation increases cumulatively in
	a small conduction area of leads to the
	formation of hot spots. damaging the device
	You have a second of the secon
	To prevent this, a large inductor is connected in series with the SCR This is called current
	in series with the SCR. This is called current
	snubber
10 stal	to the state of th
	Jan Hotopole Suital sonduction area 1
	Initial conduction area 1
	A:/11
, A	i) -> by increasing Ig or
	i) -> by increasing Ig or
	→ by Encreasing dig
	de
	sil a la contra for it
	in sy using centre guild shipristor
	(initial conduction area is increased
	ii) → by using Centre Gated Thyristor (initial conduction area is increased when centre gated SCR is preferred)
1 -	
5	Thornal Profection -
	Heat while a second of the second
	Thermal Protection - Heat sinks are used for thermal protection
147	
- 3	6.2

www.raghul.org

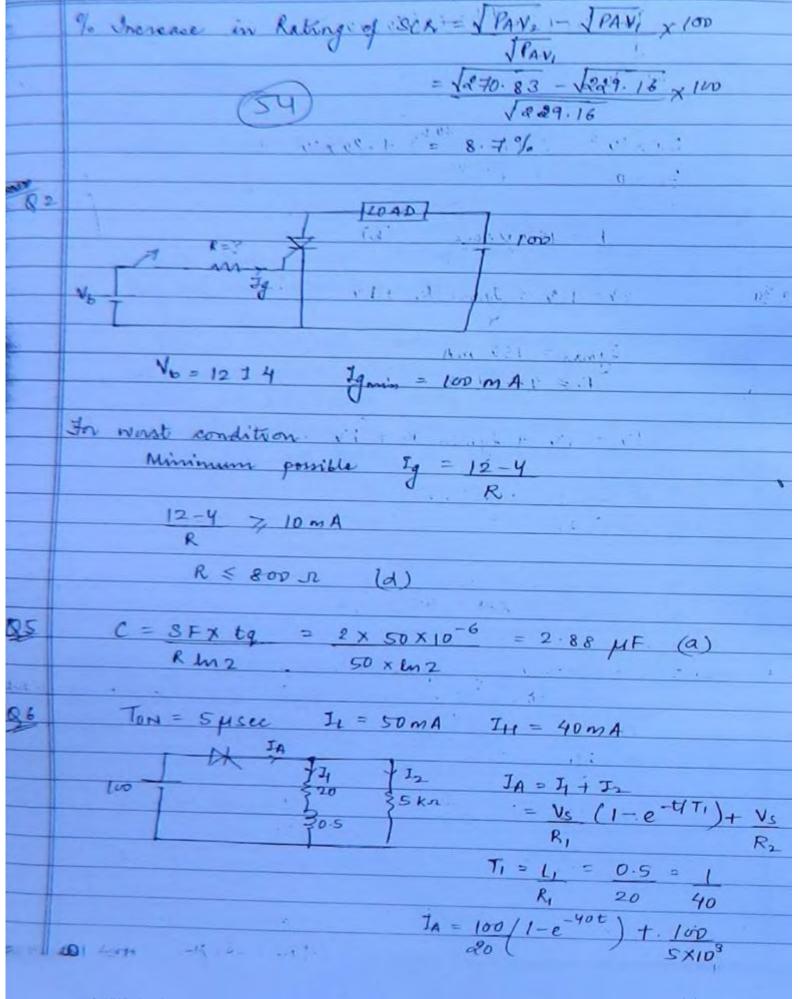
© Wiki Engineering



6	6 Gate Protection				
	(52)				
	a) Over Runent Protection				
`	A resistance is ex connected in sories with				
	the gate to limit the gate coment within				
	the permissible value.				
	5) Over Voltage Rolection				
	tener diode is connected across gate cathode				
	terminals for everyottage protection in the gate.				
	C) notection against noise signals-				
	is an inwanted signed passing through the				
	fact terminal It will false turn on the SCR				
919	Corpresent it, com Connect a parallel RC acion				
	gate cathode terminals, to project the SCR against				
	noue signals				
	CNE chapter 1				
- 81	b) T ₁ = 125°C				
	b) $T_j = 125^{\circ} c$ $T_s = 70^{\circ}$				
- 1	Ojc = 0.16				
	Ocs = 0.08				
	PAV, = Tj-Ts = 125-T0 = 229.167 W				
	Oje + Ocs 0.16+0.08				
	P = 10= 10				
	PAV, = 125-60 = 270.83 W				
	0.16+0.08				

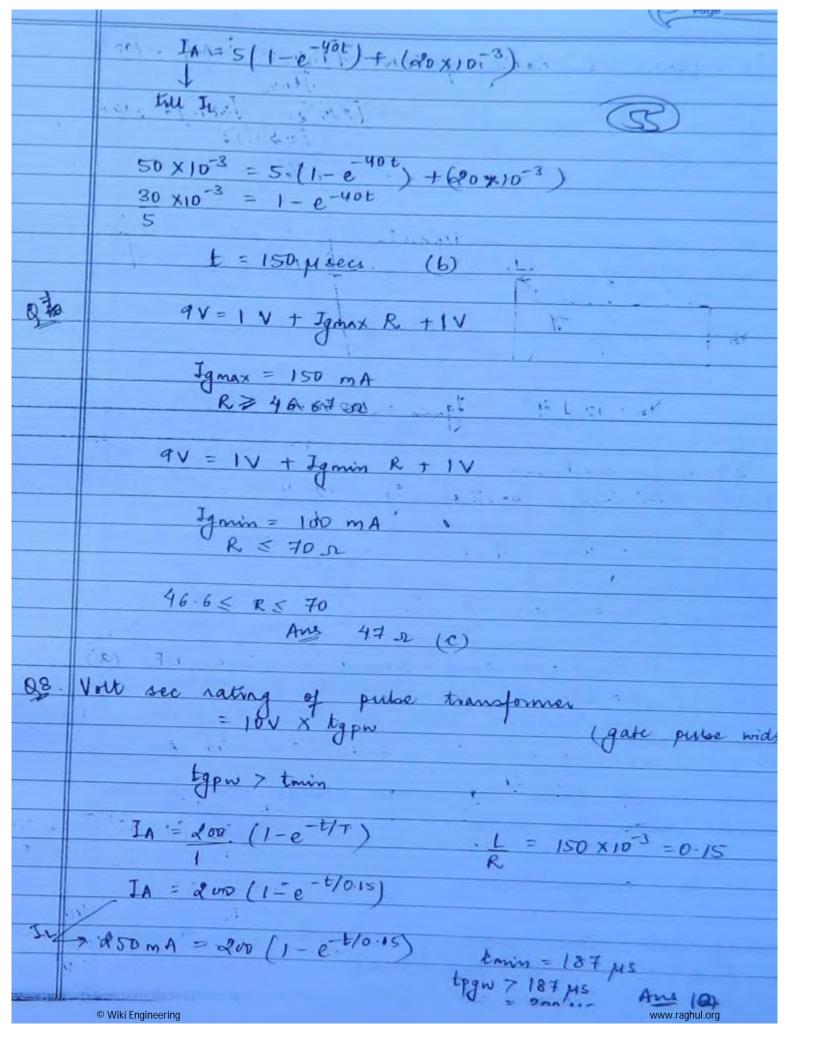
www.raghul.org

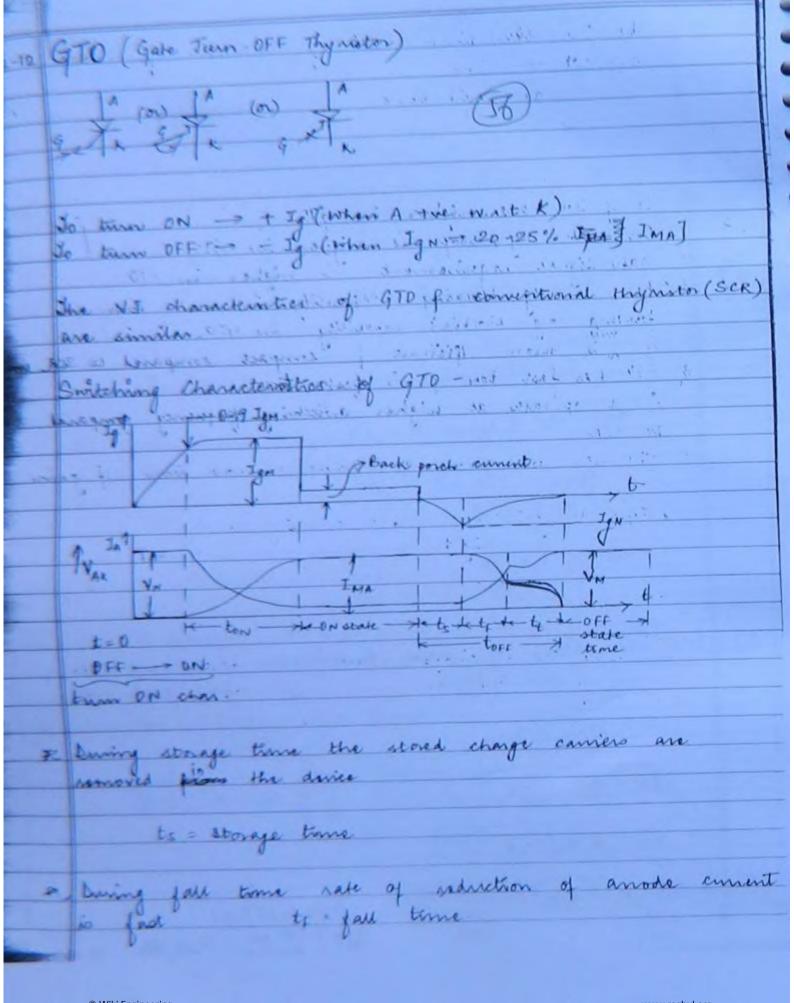
© Wiki Engineering



© Wiki Engineering

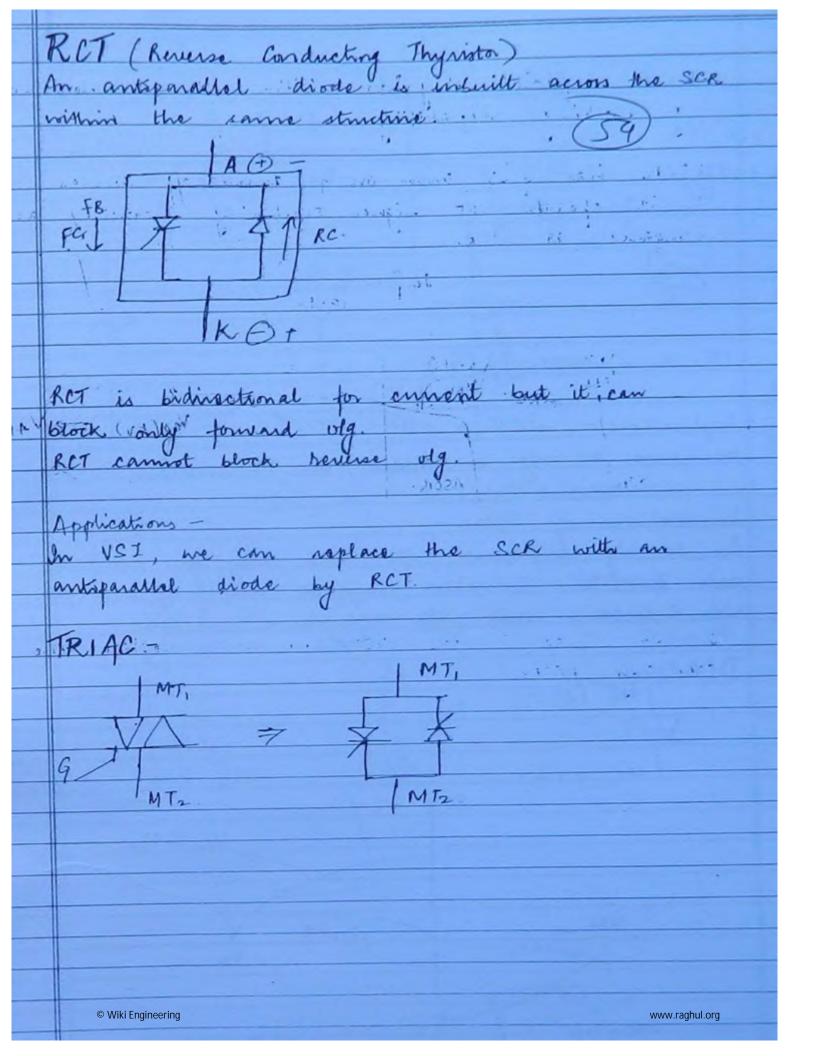
www.raghul.org

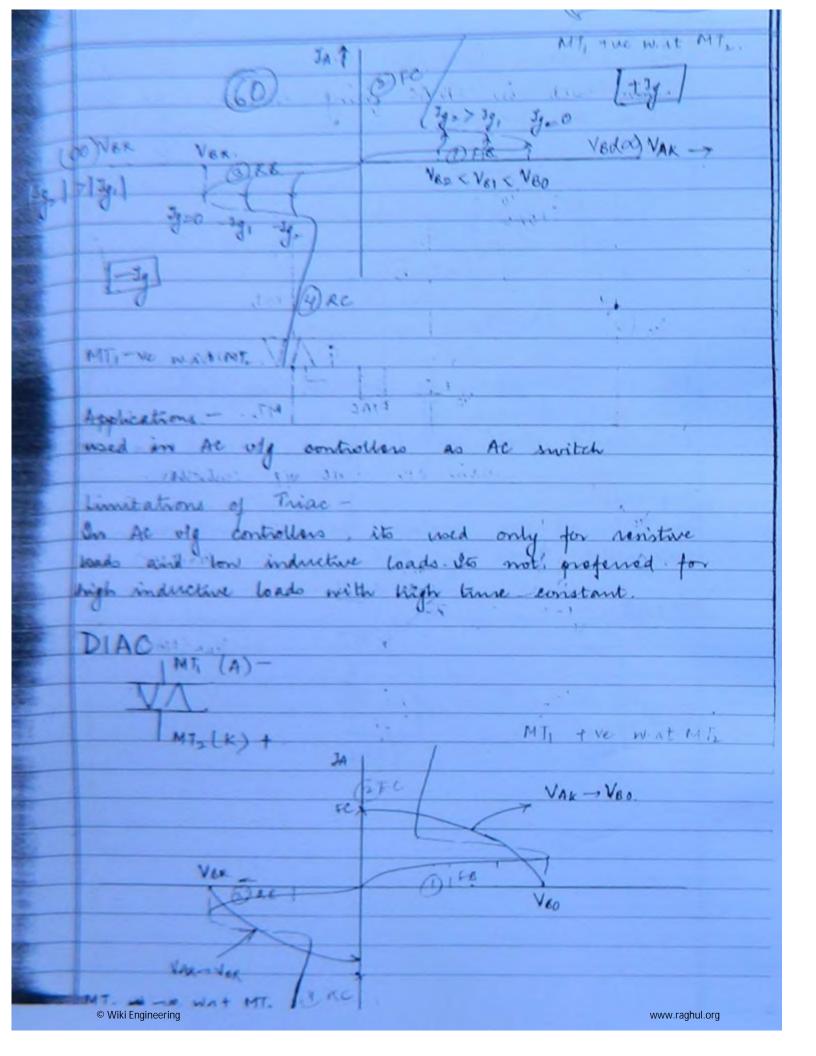


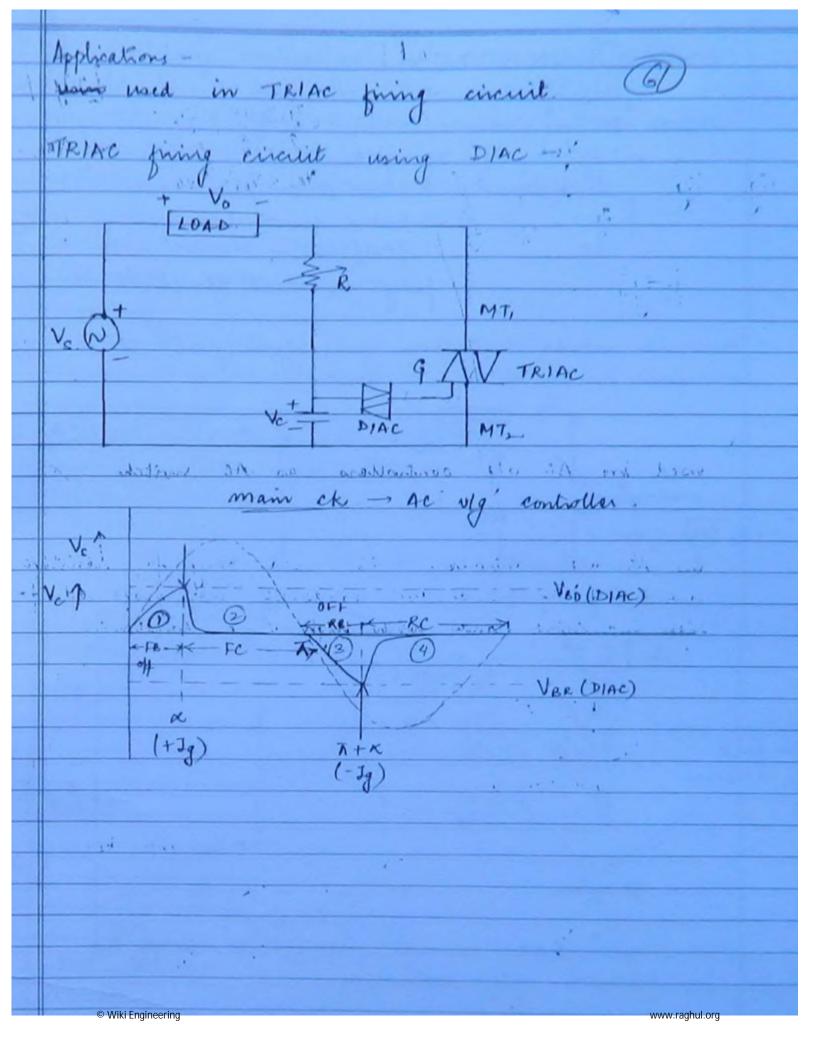


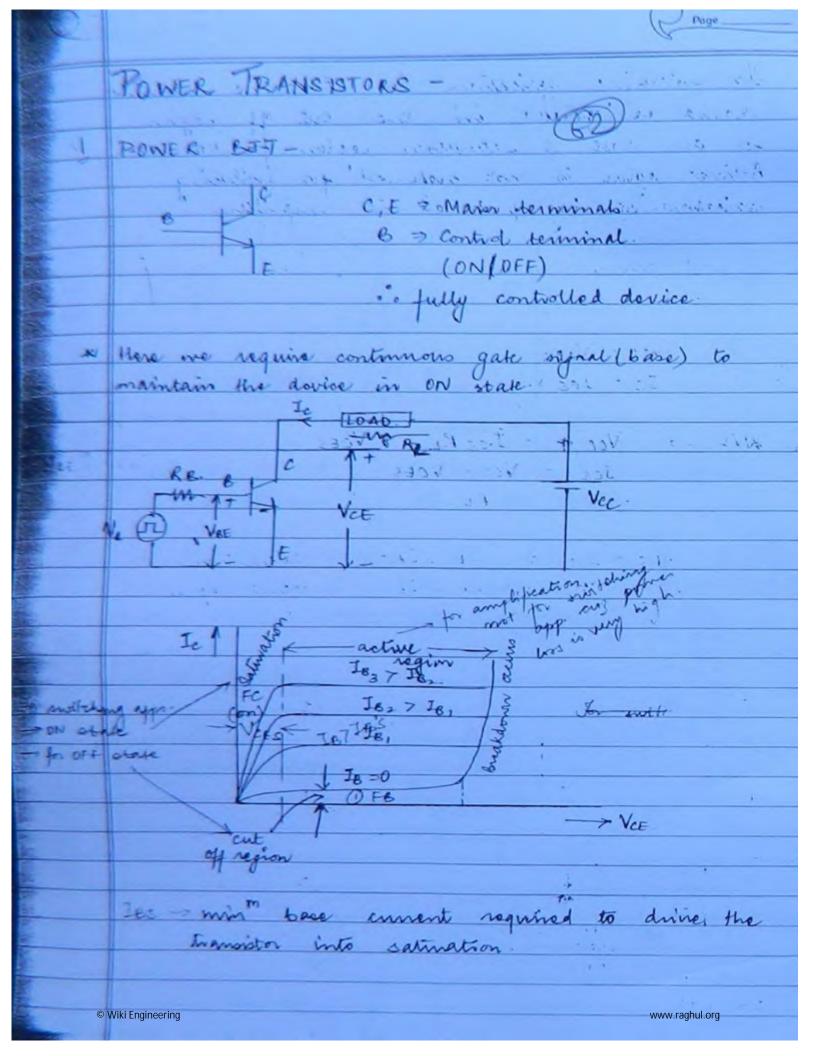
the tail time rate of roduction of anode the tail time Compare GTO with conventional thyristor (SCR) I I of In are higher invigate 3. Gate eignet requirement is higher in GTO A Reverse vig blocking capability is lasser than 5. GTO is more efficient of compact compared to SCR unit 6. GTO has fast ton of ... Gaster GOFF it operates at higher switching frequency compared 7. GTO has low turn on gain of low turn off gain tum on gain = Ina tum off gain = Ina - Ignit Applications by using a 970 to avoid commutation circuit.

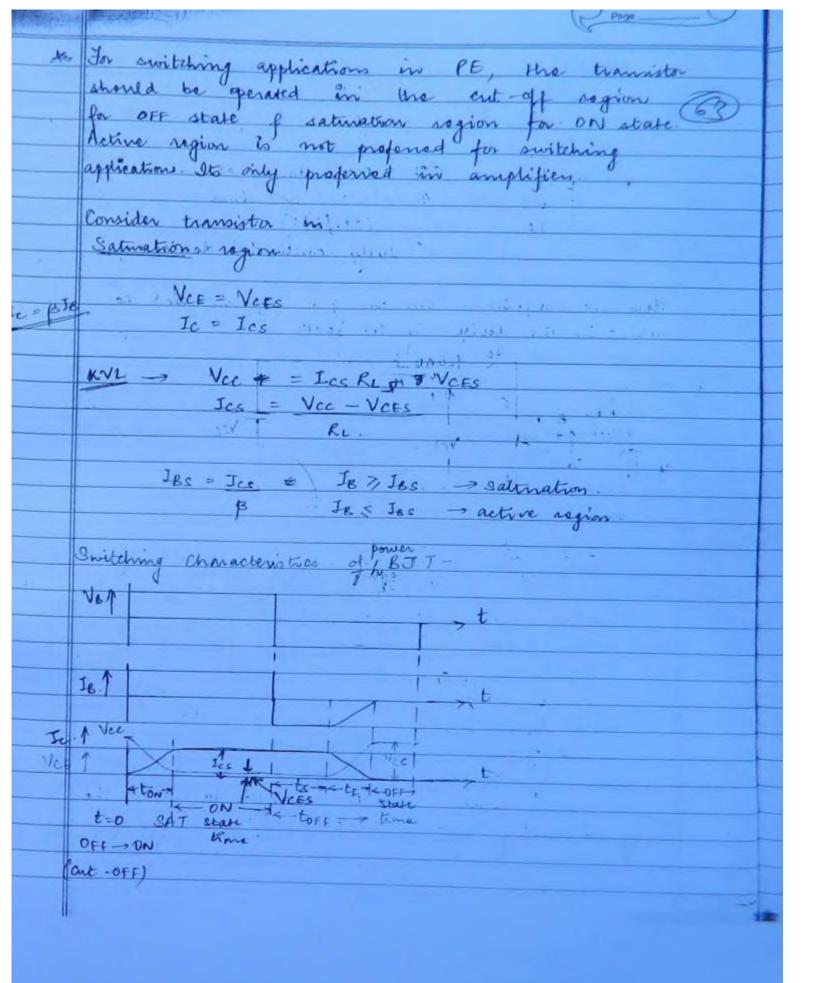
(Asymetrical SCR) thy vistor with reduced ASCR has fast turn on of turn of operates at higher switching @fc SCA © Wiki Engineering www.raghul.org

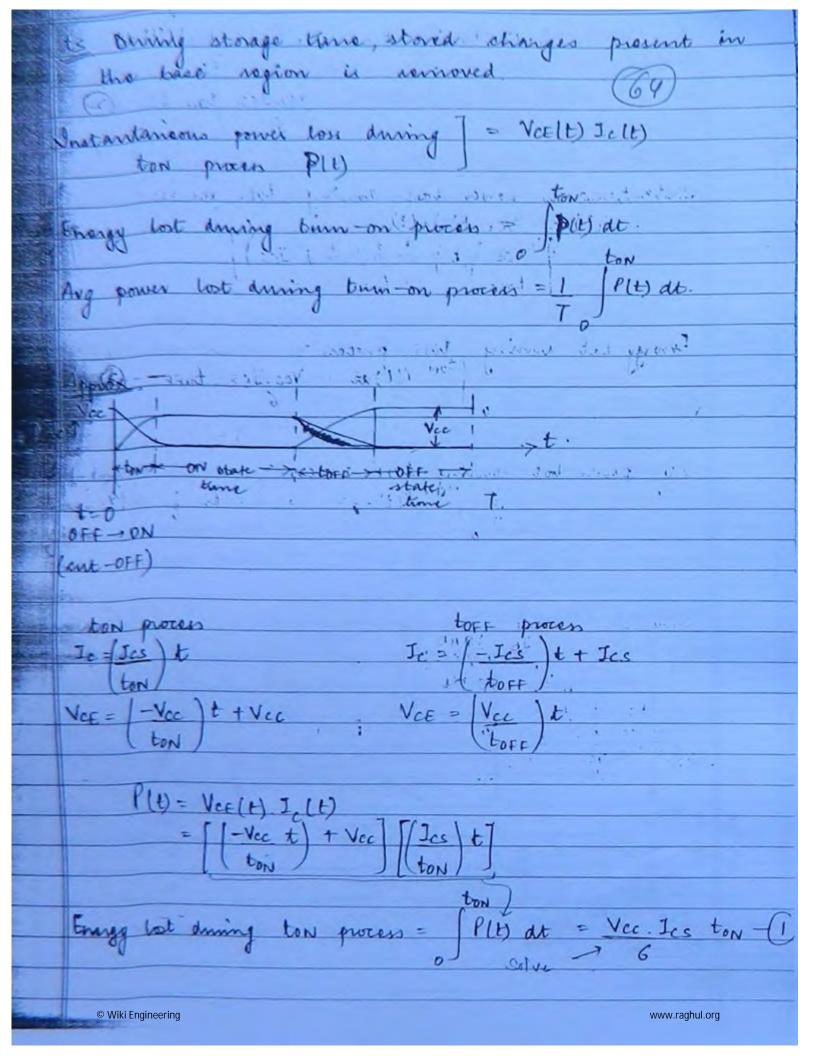


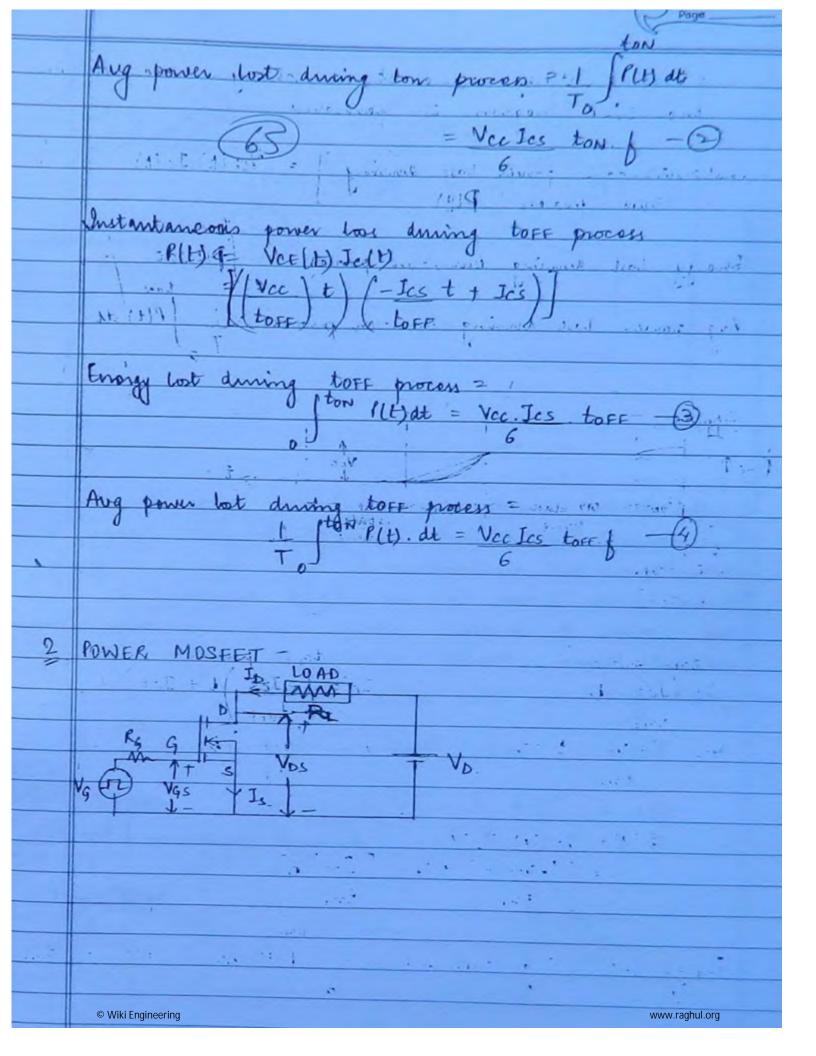


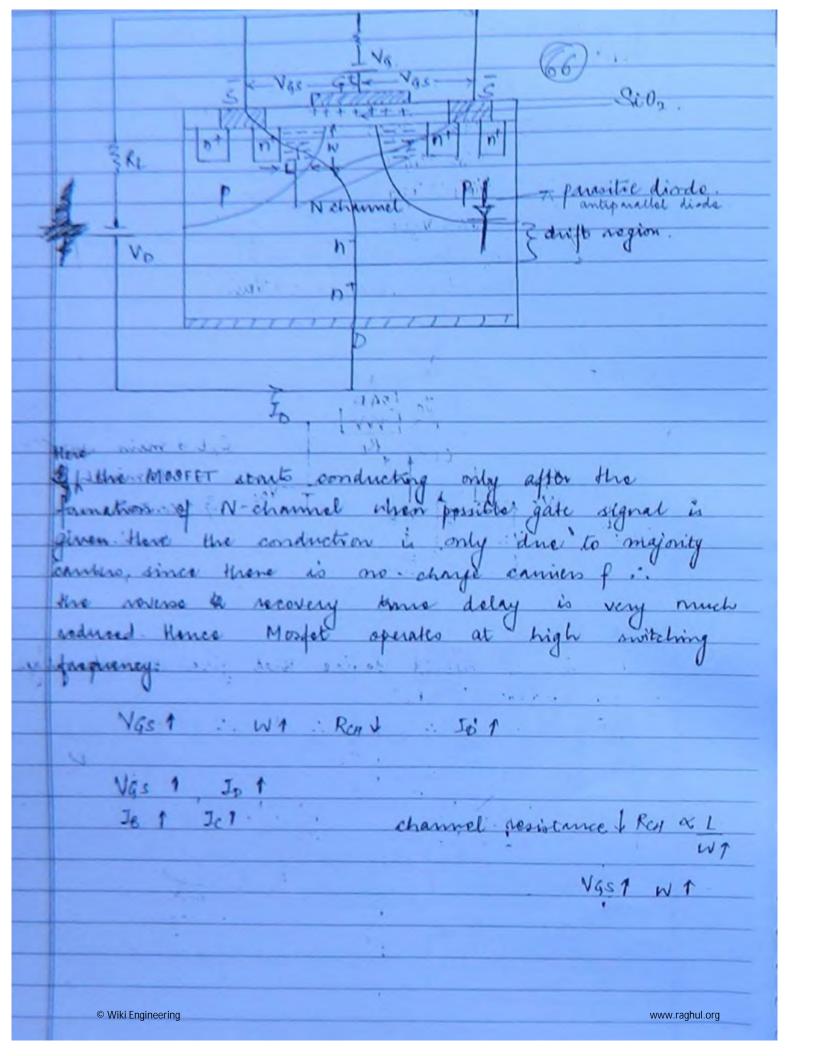


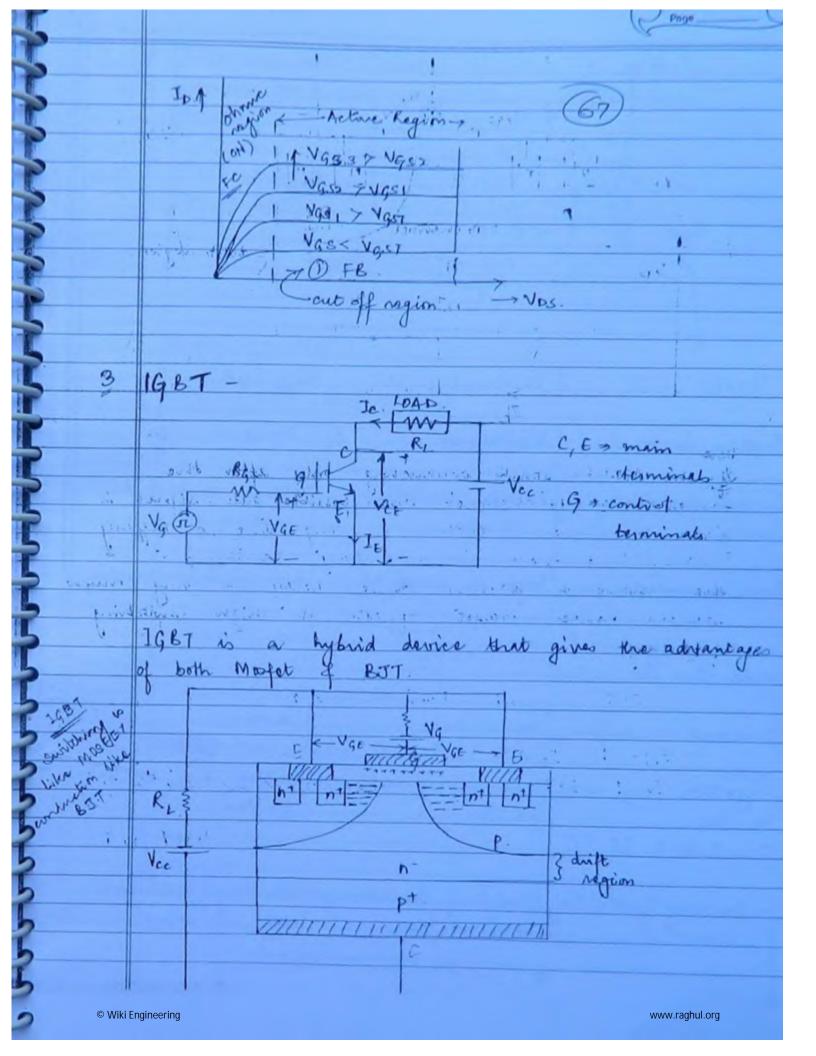






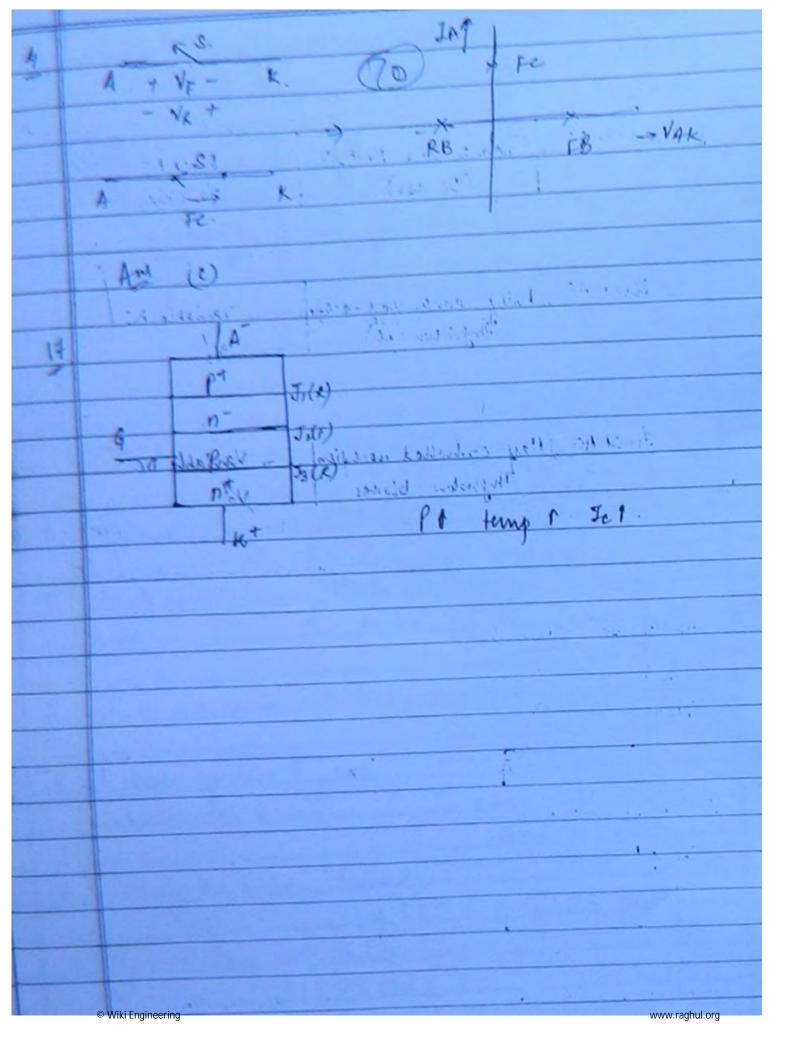


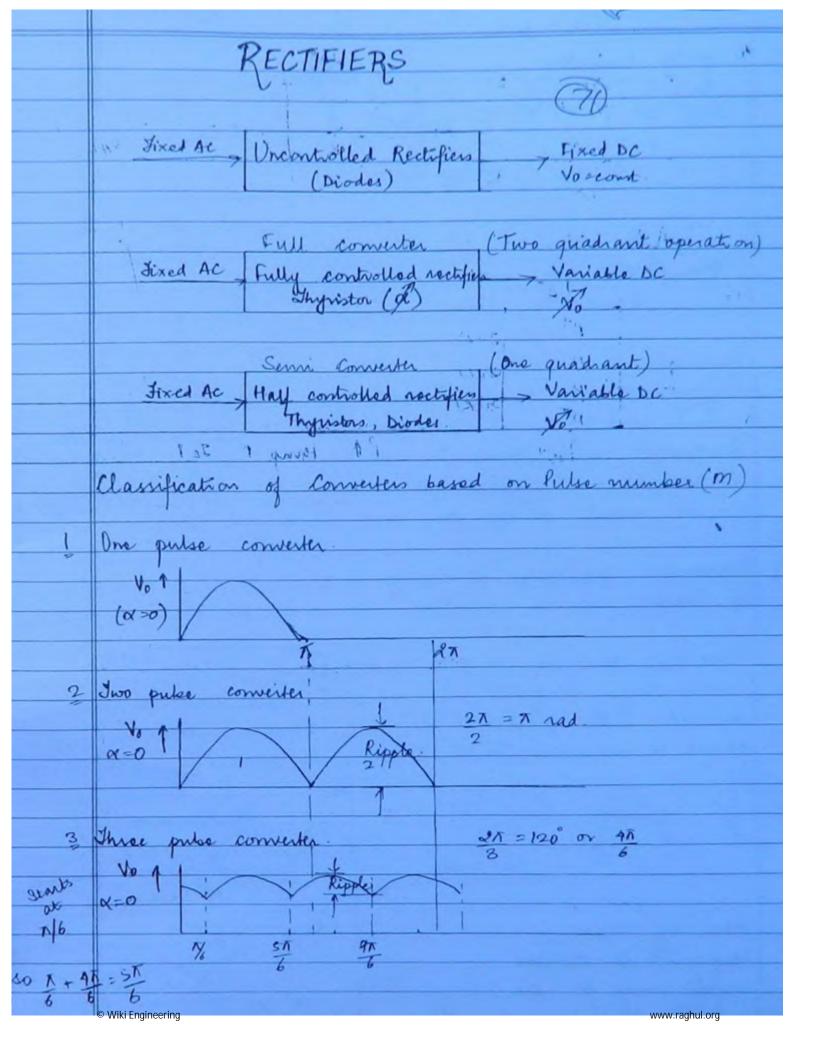


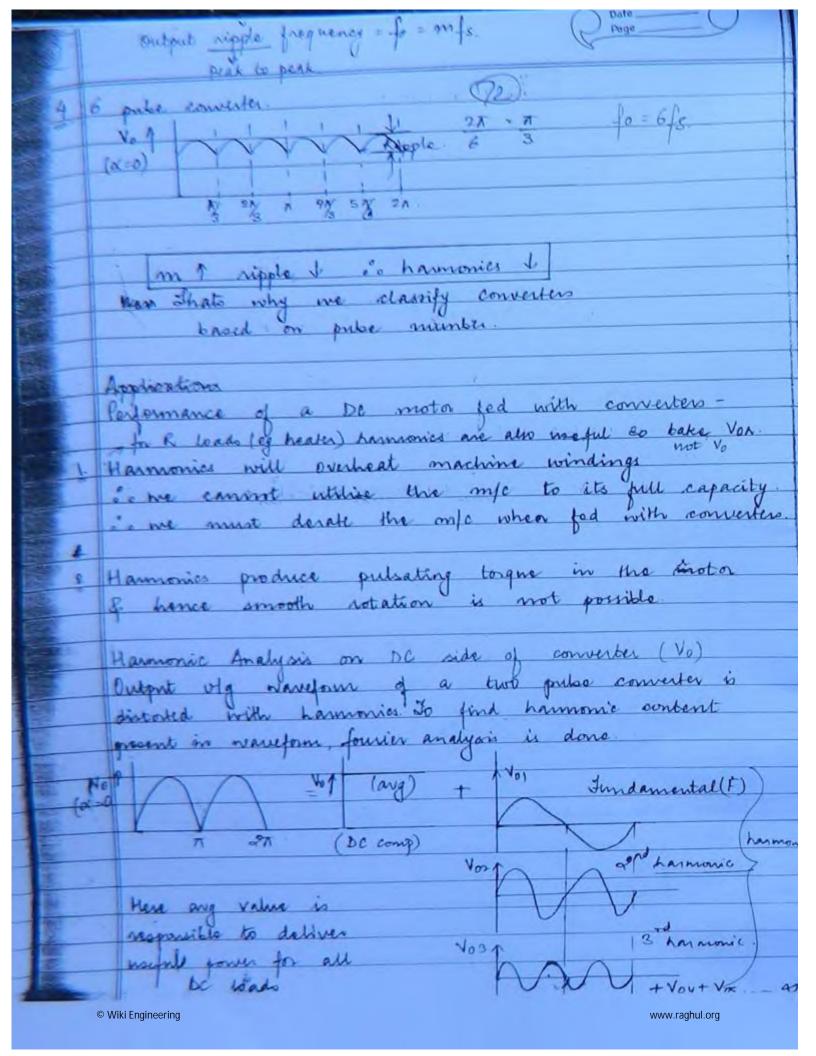


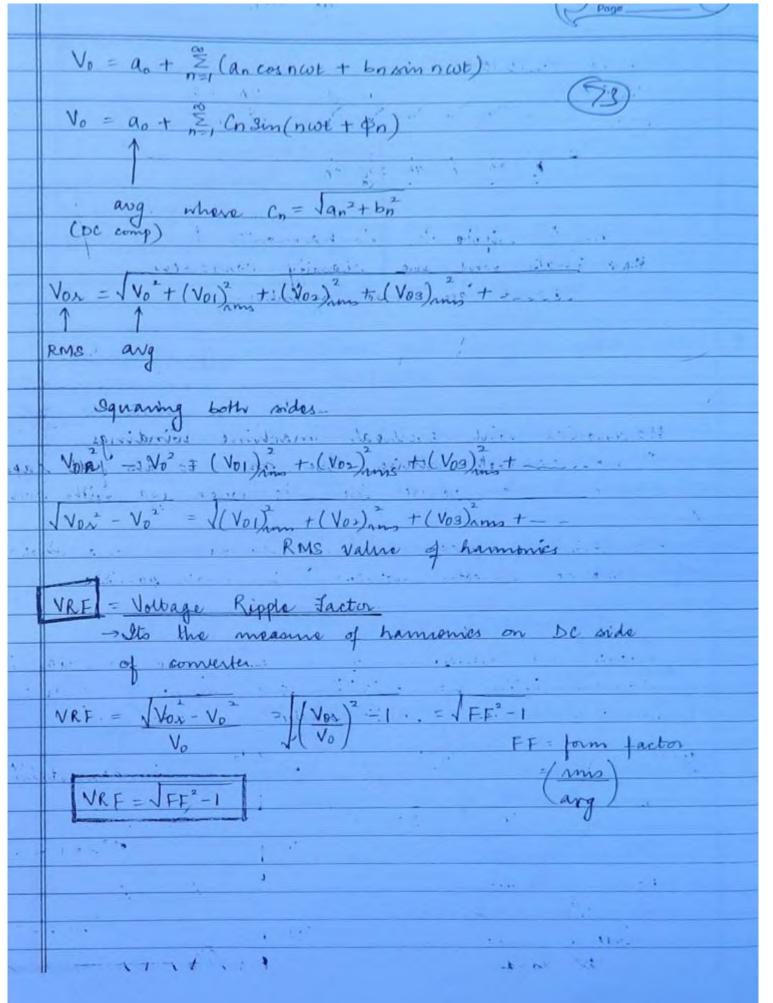
	Set .	the same of the same	300		
	Javie -	VG87Vg2	The state of the s		
	T Charles	Man - Mai			
	150/1	VG2 7 VG1			
		8			
	Yer.	VG FO. M. Yes.	1,-		
negion!					
	191000	POWER MOSFET	12 (
1-	Bipelar device	Impelar " -	Bipolan.		
2.	Harris and the second s	oltage controlled	Voltage controlled		
	device	dovice	device		
3	Low if impedance h	righ if impedance	high i/p impedance.		
	11.		-		
9.	on state up drop f	more	dess		
	on state up drop f	Ч.	i.		
			tossector.		
	Switching loss higher	tesses low			
6	Negative Temp co-41	Positive Temp co-Eff	Positive Temp co-eff		
	to how	too Row.	for Kon		
	to how IT PT.				
		Secondard Breakdown	Secondary Breakdown		
	vecno	will not occur	will not ocens.		
	+	4	1 .		

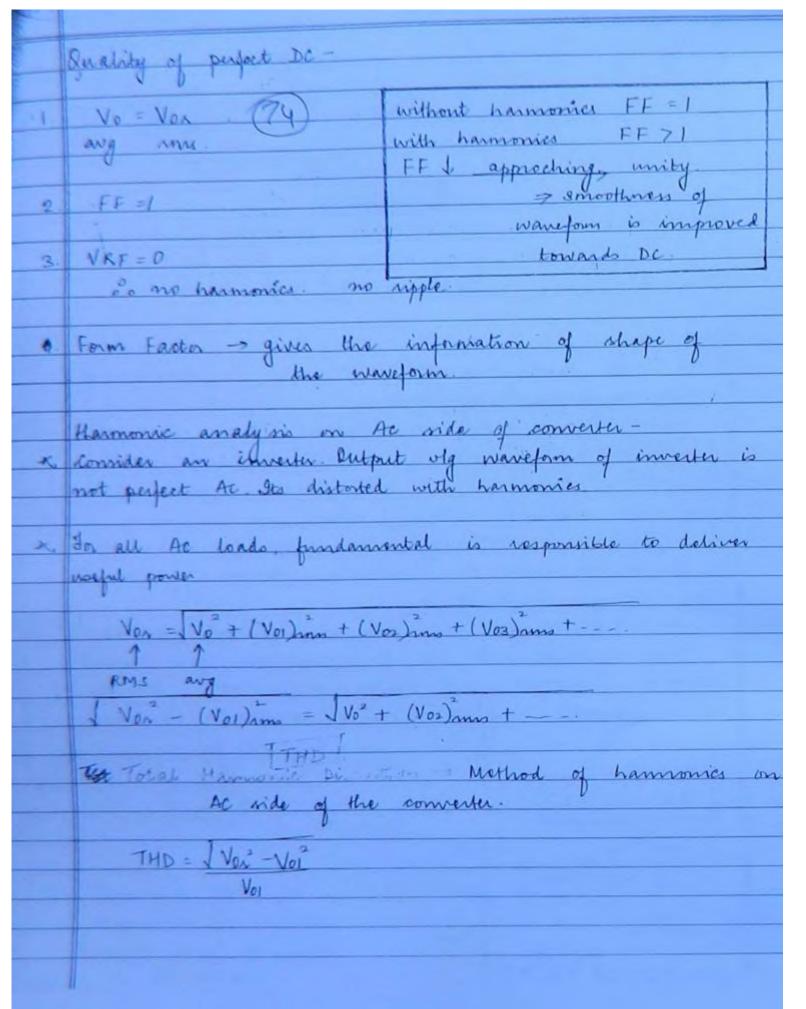
			Page		
4.	BJEs are not advisable for paralle operation.	Parallel operation	Paraeliel operation is possible.		
catings 8.	1200V, 800 A 10-20 KHZ	500 V , 40.4	1200 V 500 A 50 KHZ		
App	257	SMPS.			
	chapter 1 CNB.	gate signal.			
1.11.	s one material !				
3 V1					
	turn on p	The state of the s			
100	Energy bost during				
	= V. + J b, = 1 V J b, 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2				
+ 5	Bonergy bot during	1 V6 - 1 VSt.			
Total = IVII (1+t2) (a)					

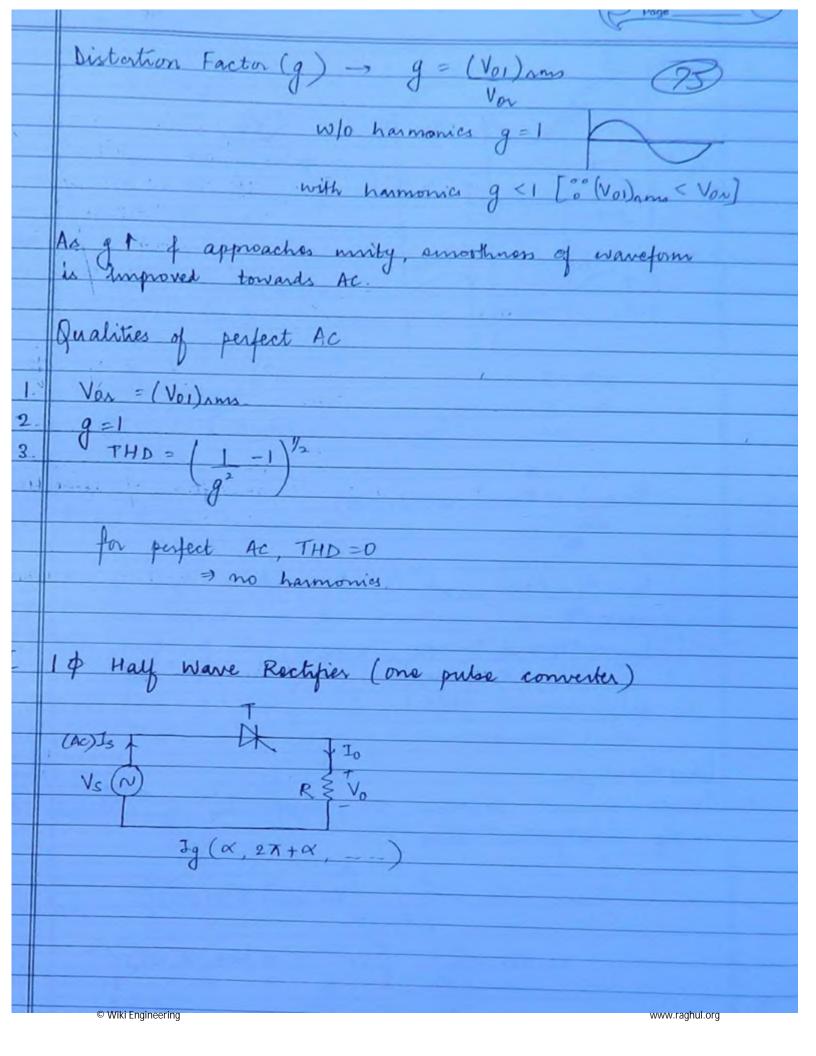


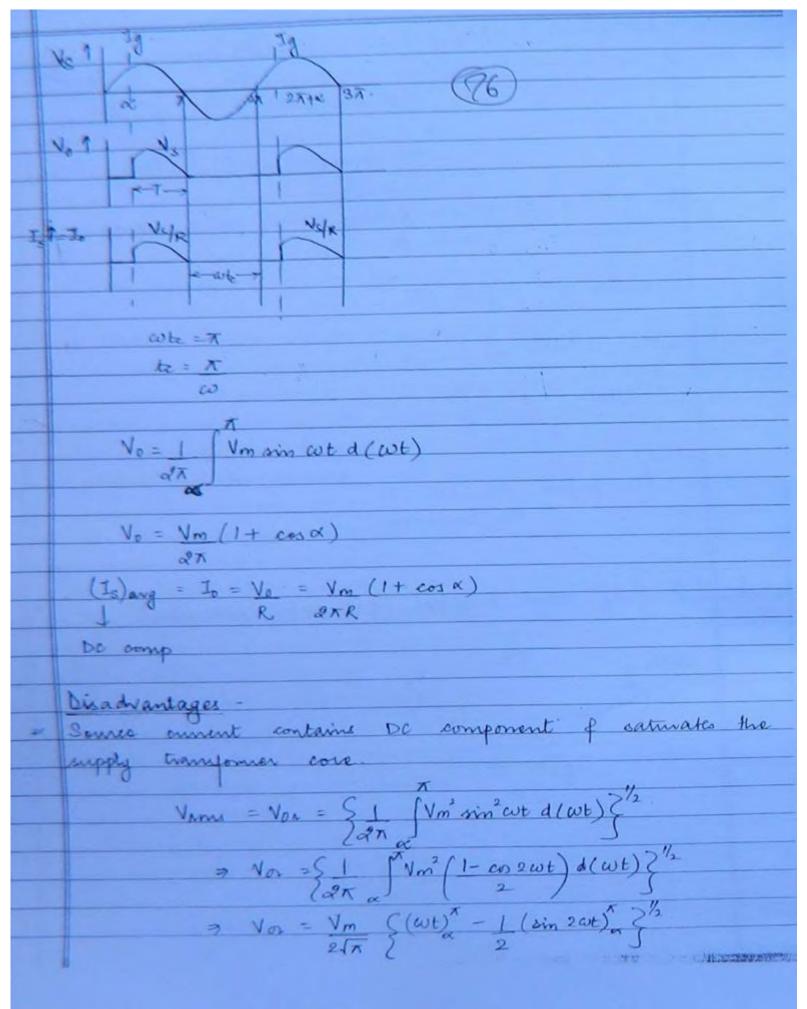






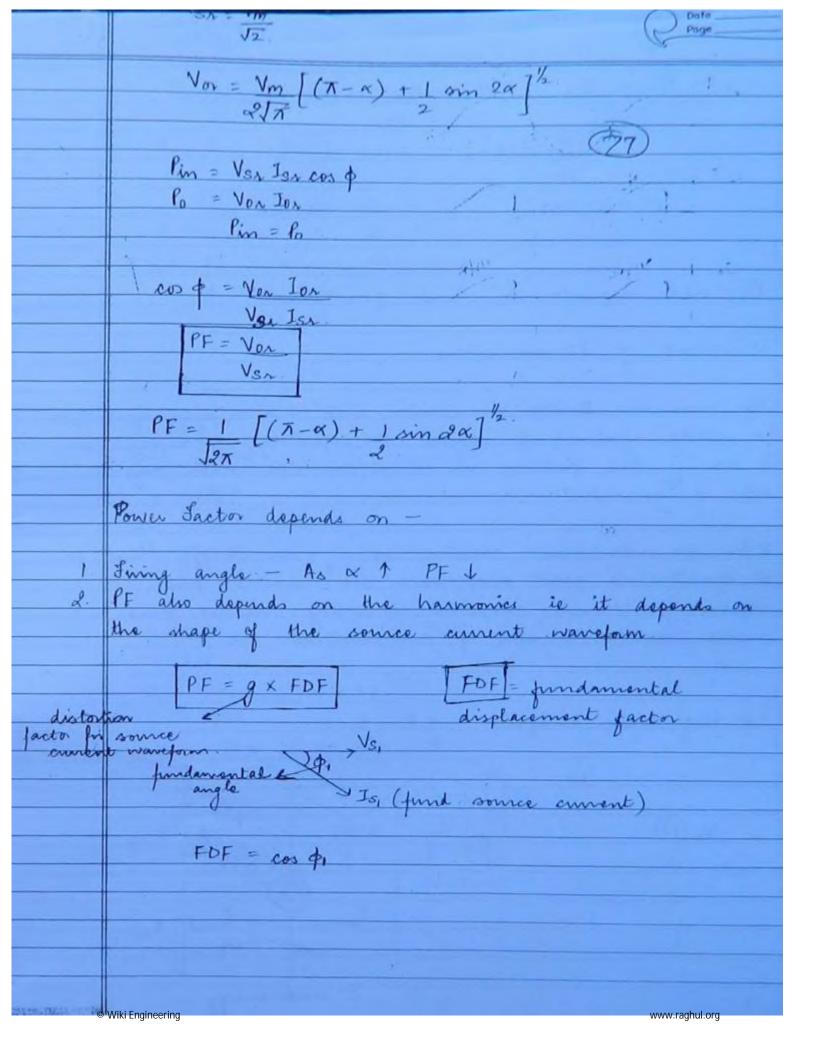


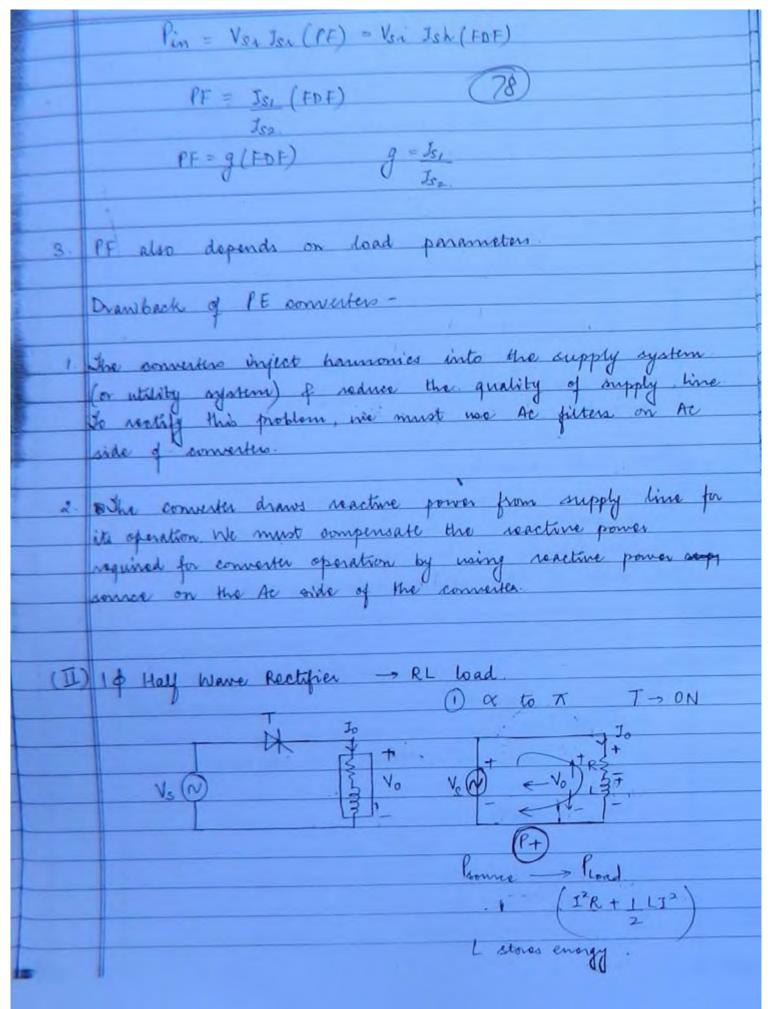




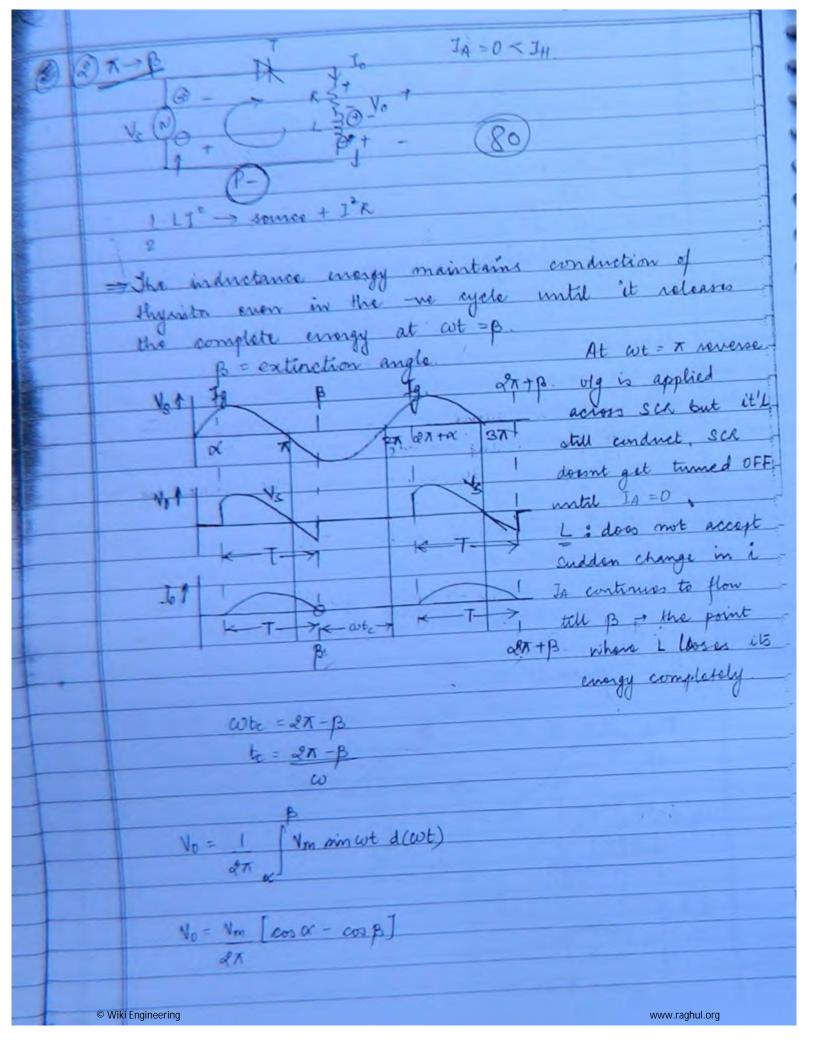
© Wiki Engineering

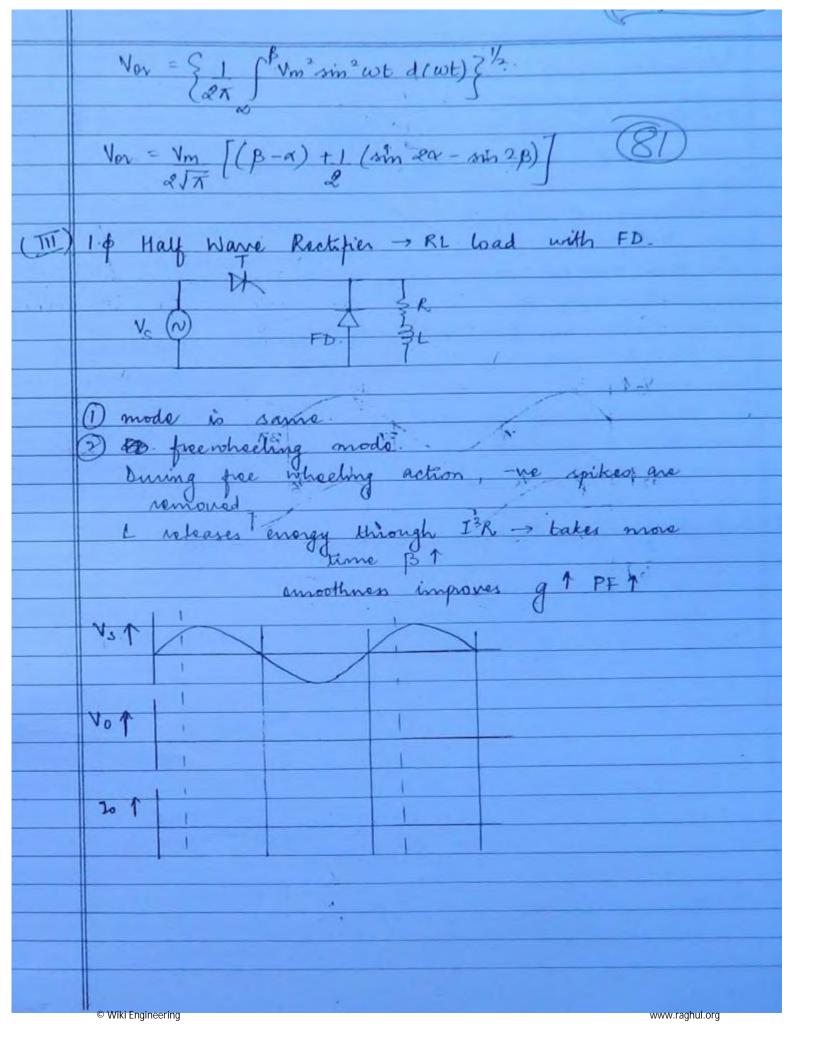
www.raghul.org

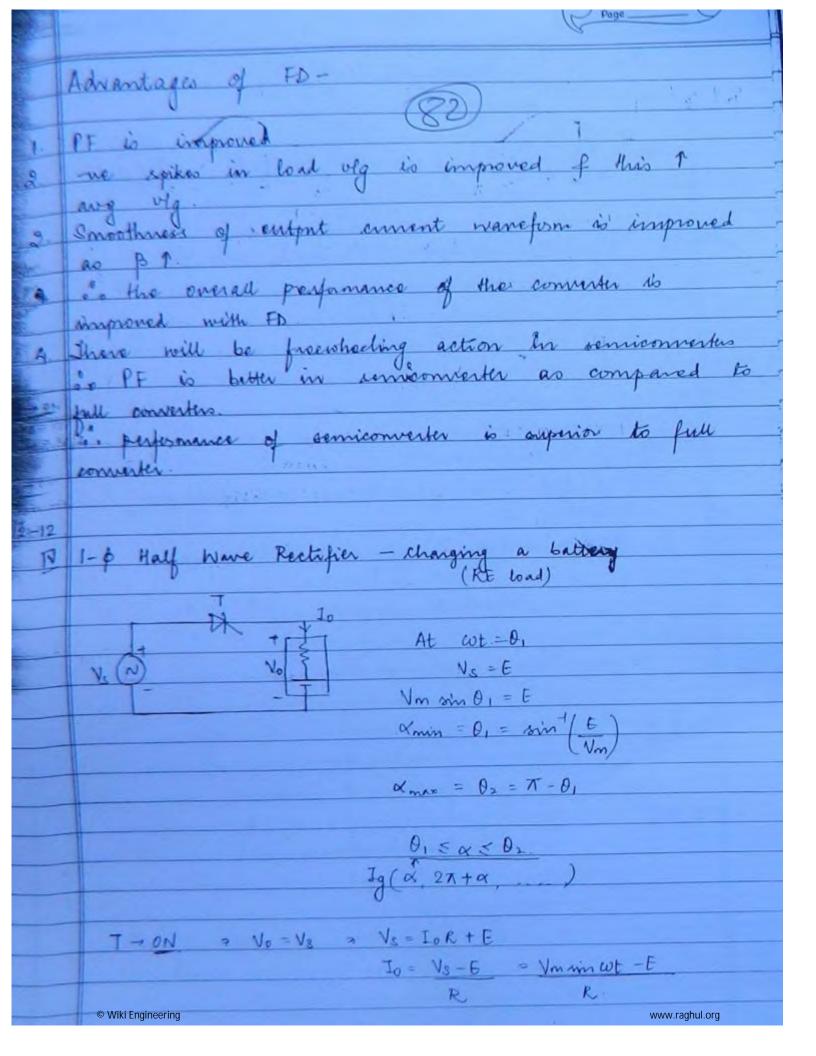


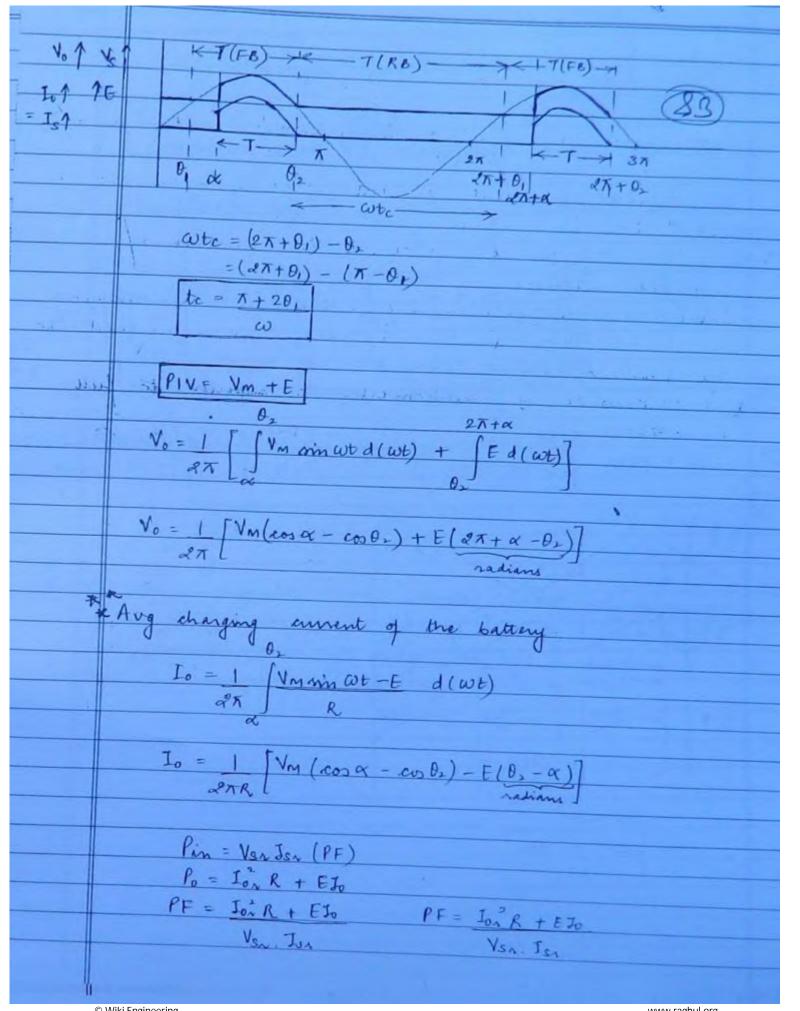


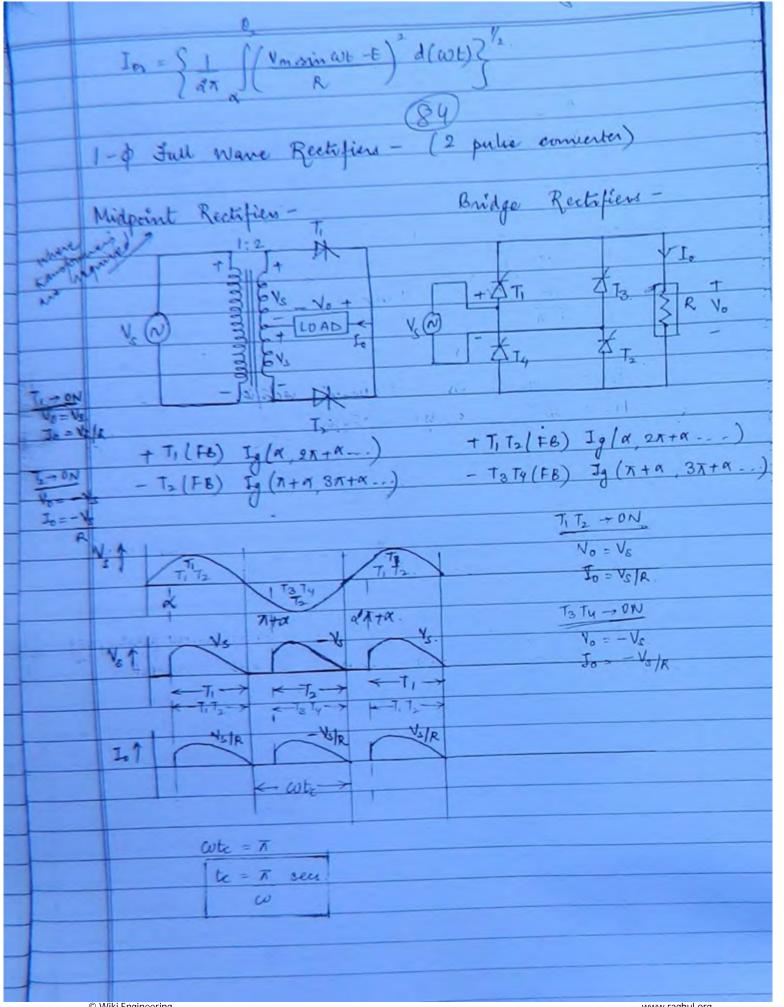
	$V_{m sin \omega t} = R \hat{\mathbf{t}} + L d\hat{\mathbf{u}}$ dt
	dt
× -	To = Ineary of Iterments 79
	Isteady = V_m $sin(\omega t - \phi)$ 171 $vihere$ $171 = JR^2 + (\omega t)^2$ $\phi = tans^{-1}\omega L$ R
	17/
	where 171 = JR2 + (w)2
	\$ = bas al
	K.
1	$\tau = t/r$
	Itamient = Ke ^{-t/r}
mote	
64.1	To Incary of Icrons
Lord	Io = Vm roin (wt - φ) + Ke-47
	At wt = K Io = 0
	$t = \alpha \gamma = L$
	$t = R$ $\gamma = L$. ω R .
74	
	0 = Vm sin(wt-\$) + Ke-Ra/col
	
	$K = -V_m \sin(\alpha - \phi) e^{R\alpha/\omega L}$
	VST TO
	a A AMA 3n.
	a Tan anta 3n.
	NOT VS
	←T→ ←T→
	Jo 1
	$\leftarrow \tau \rightarrow$
	N. Committee of the com
	© Wiki Engineering www.raghul.org

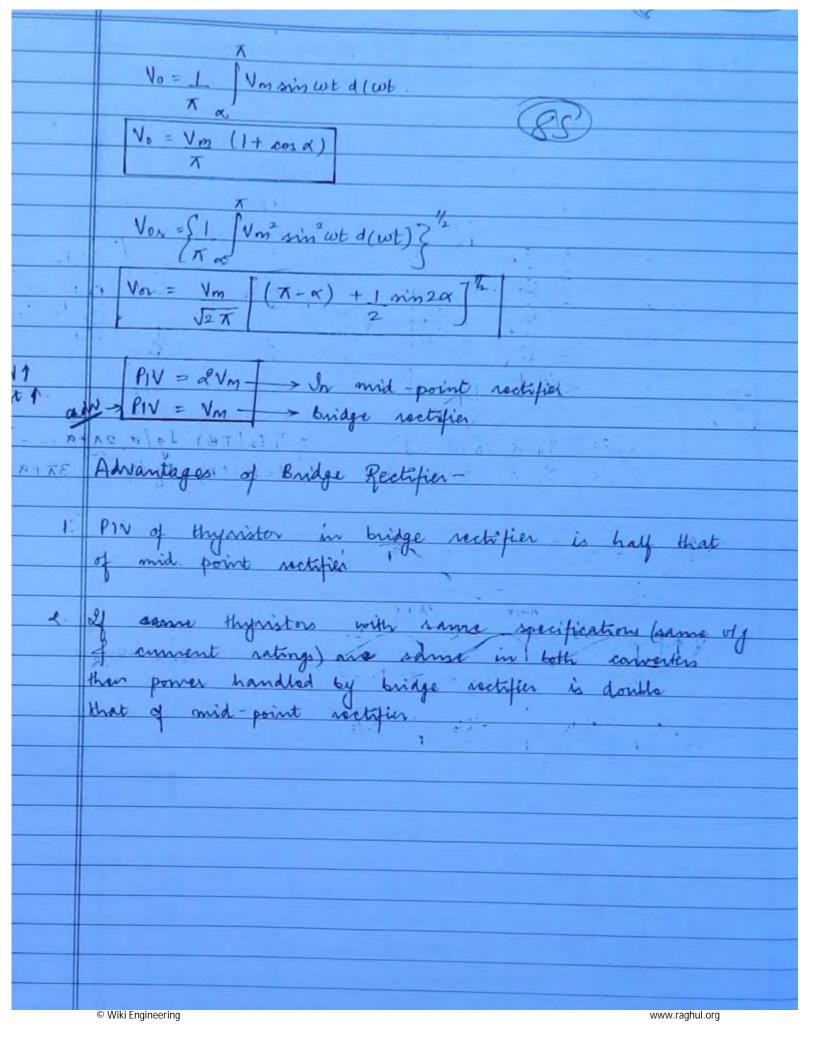


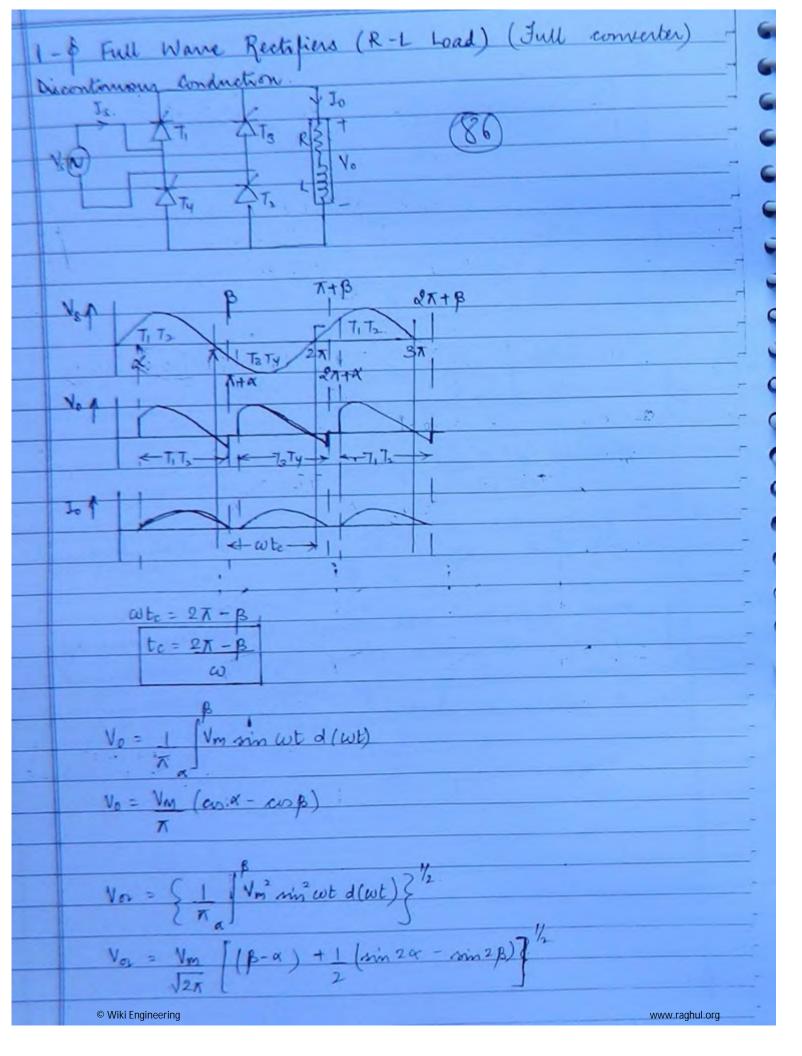


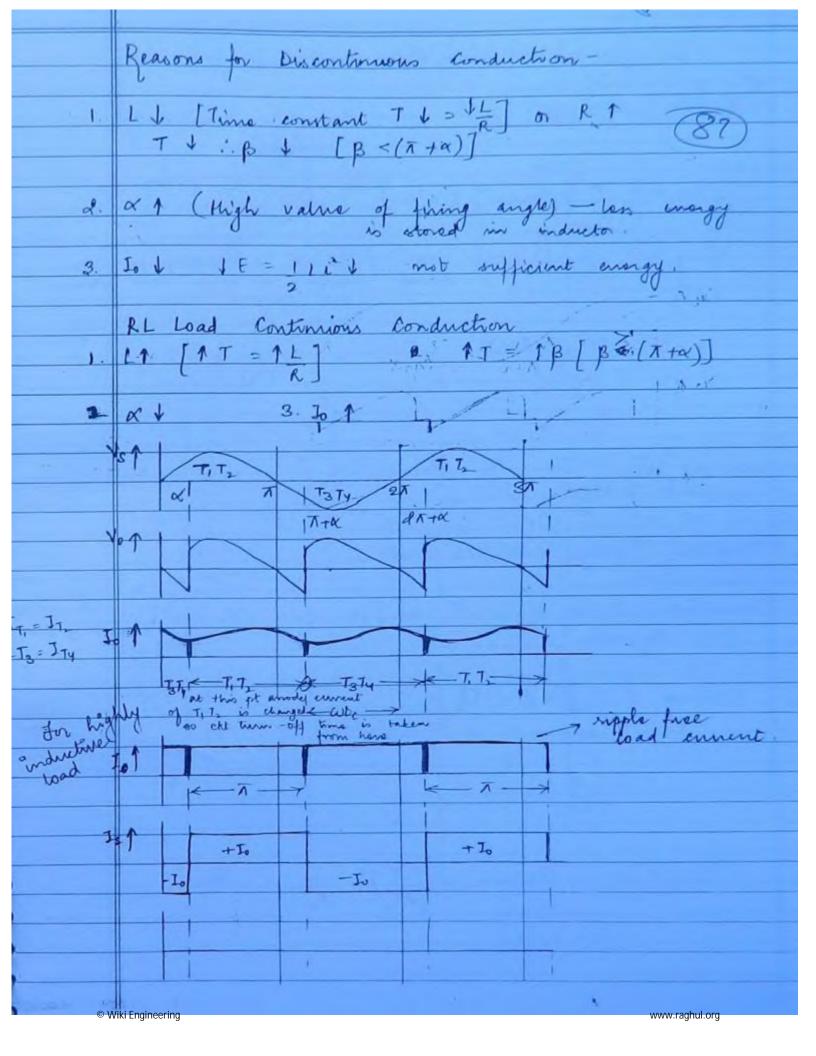


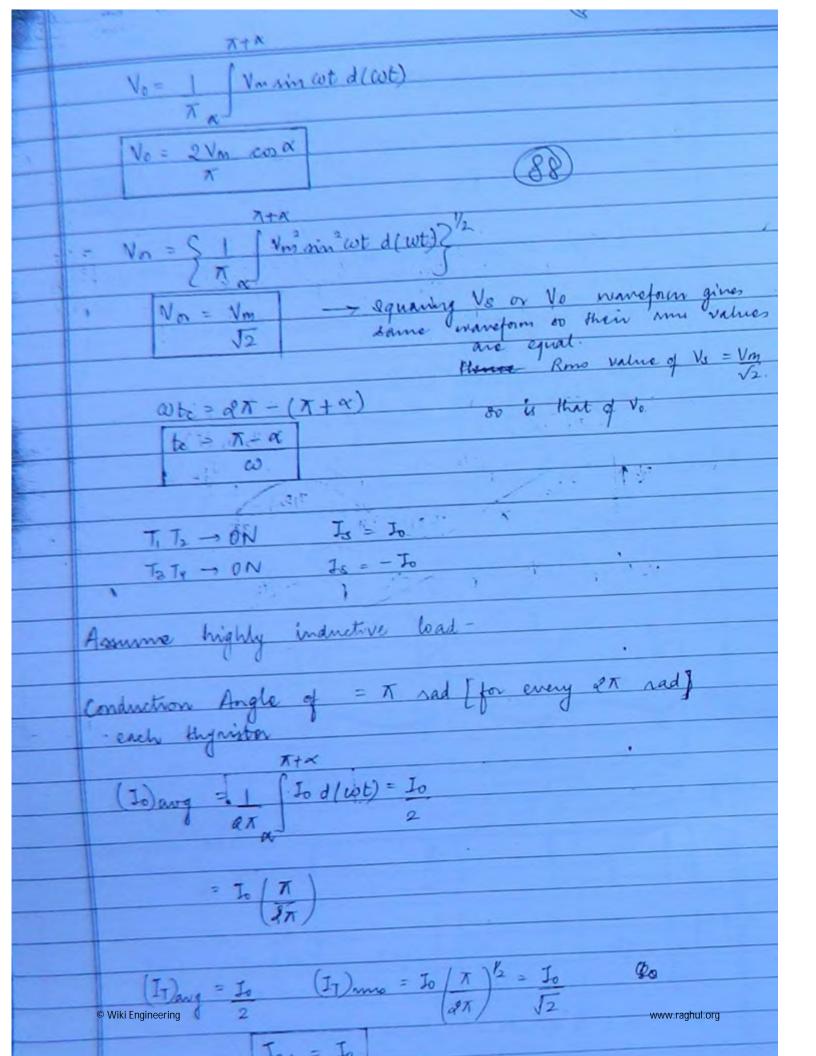


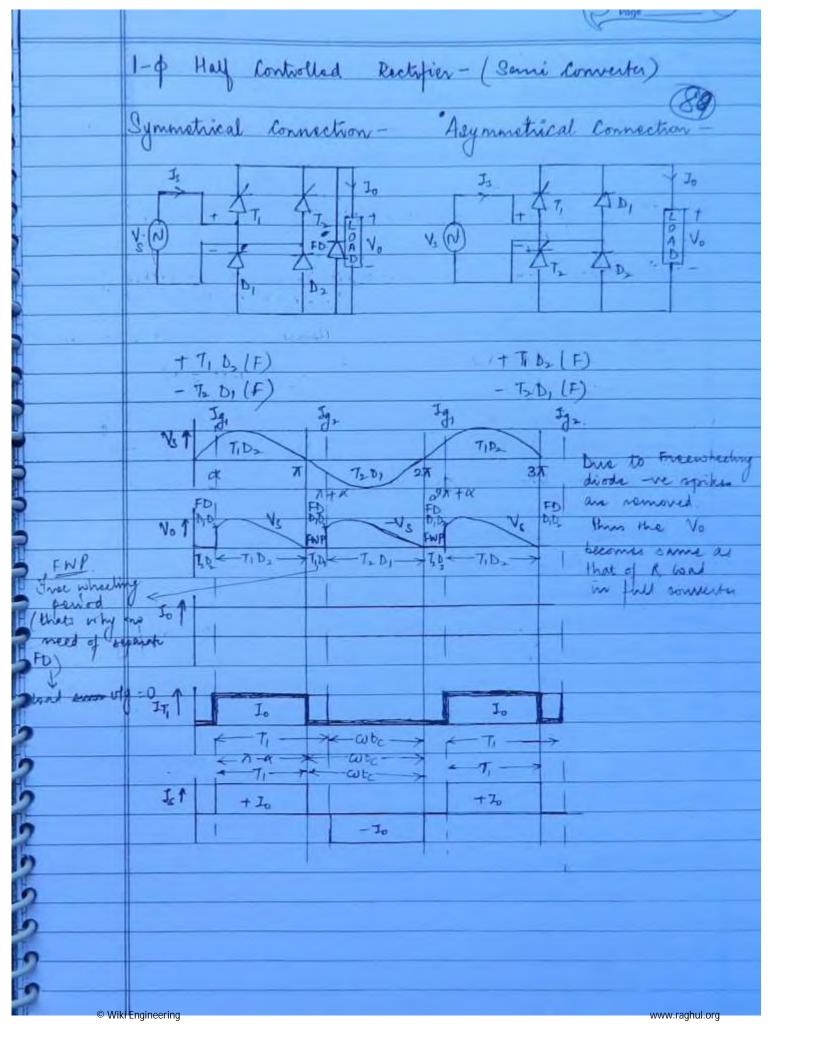




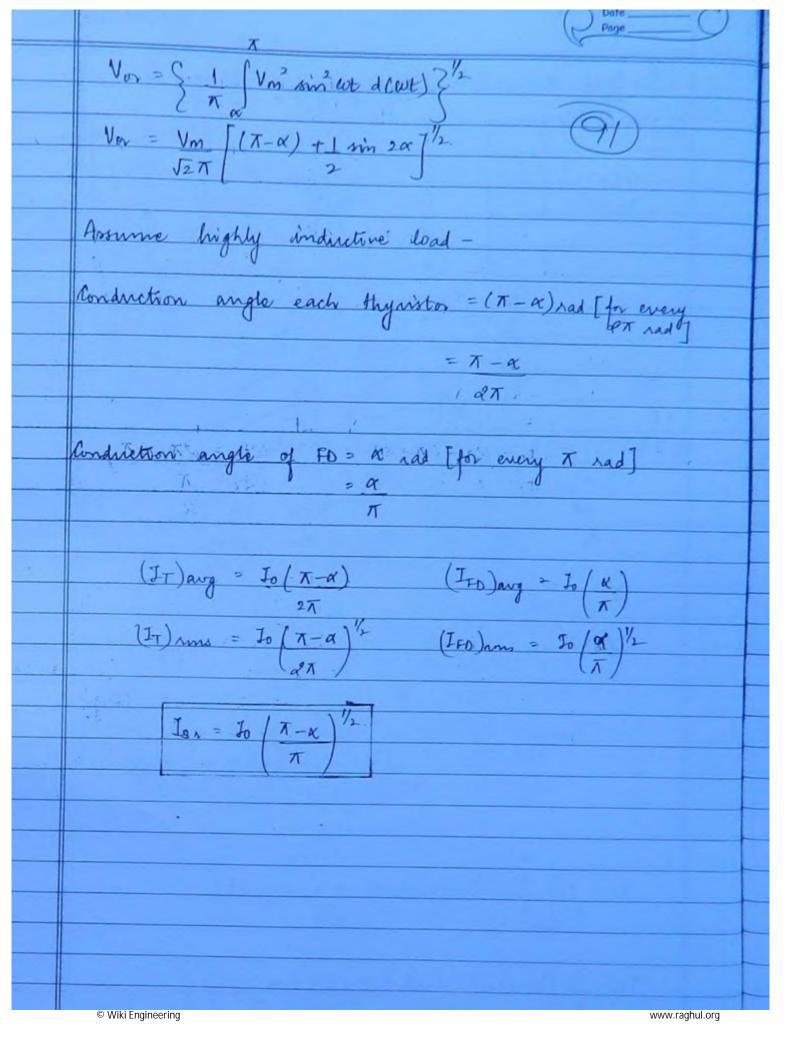


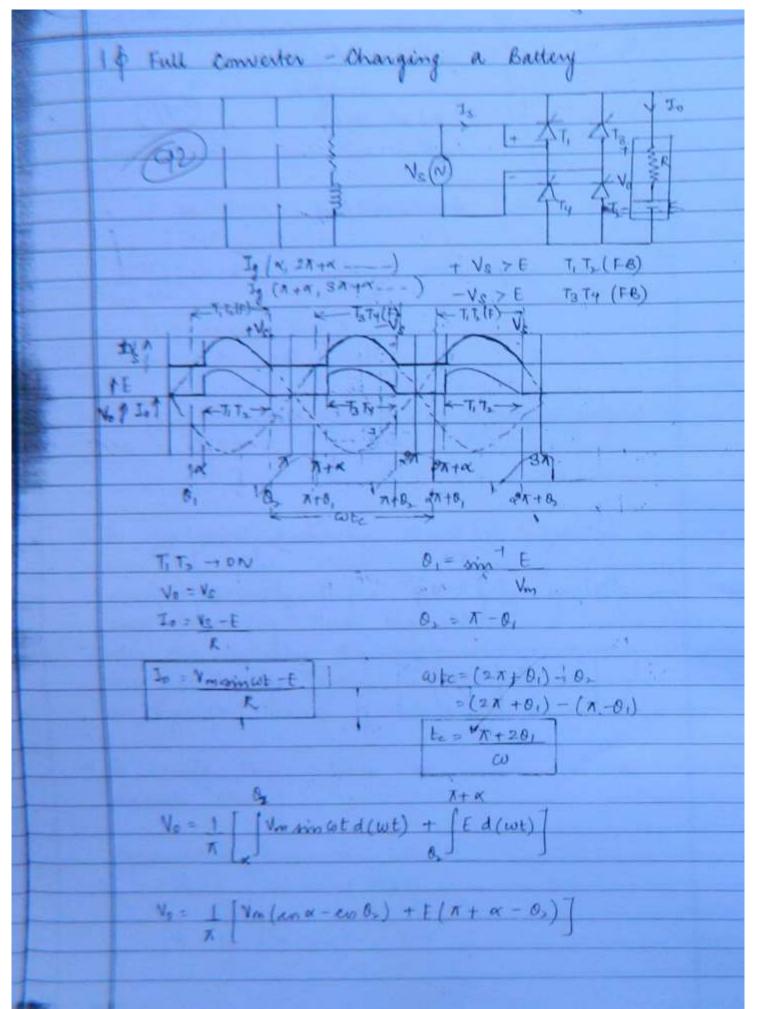


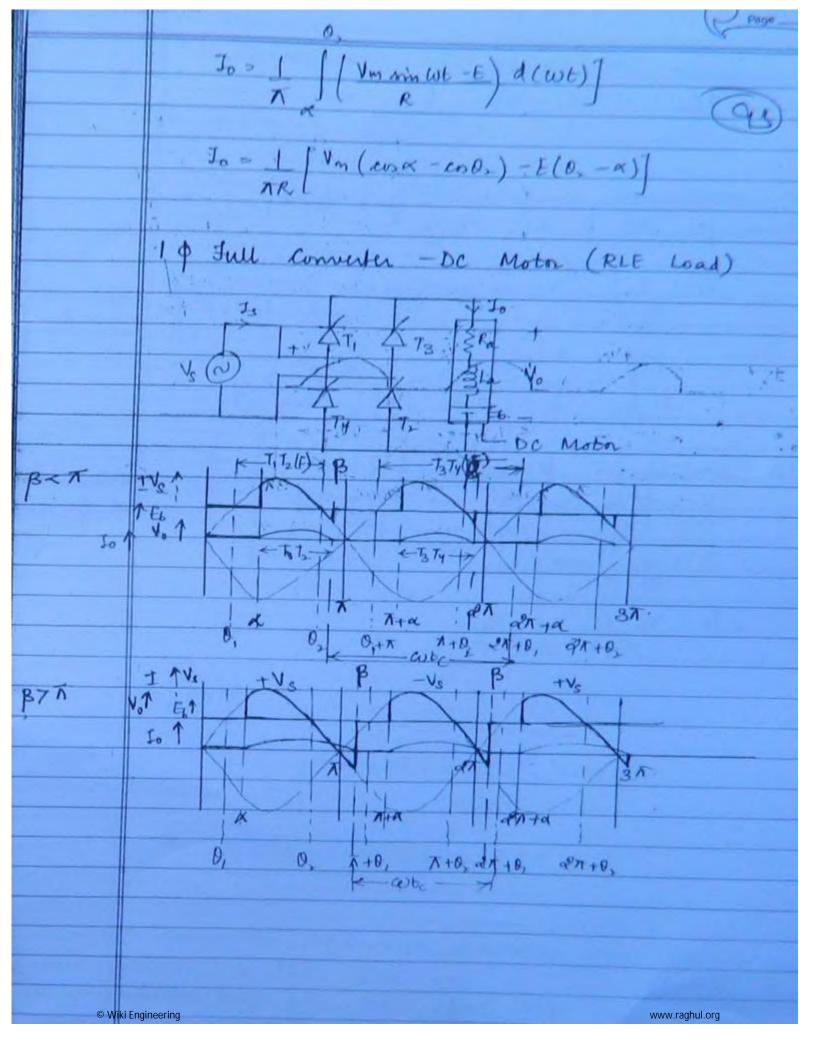


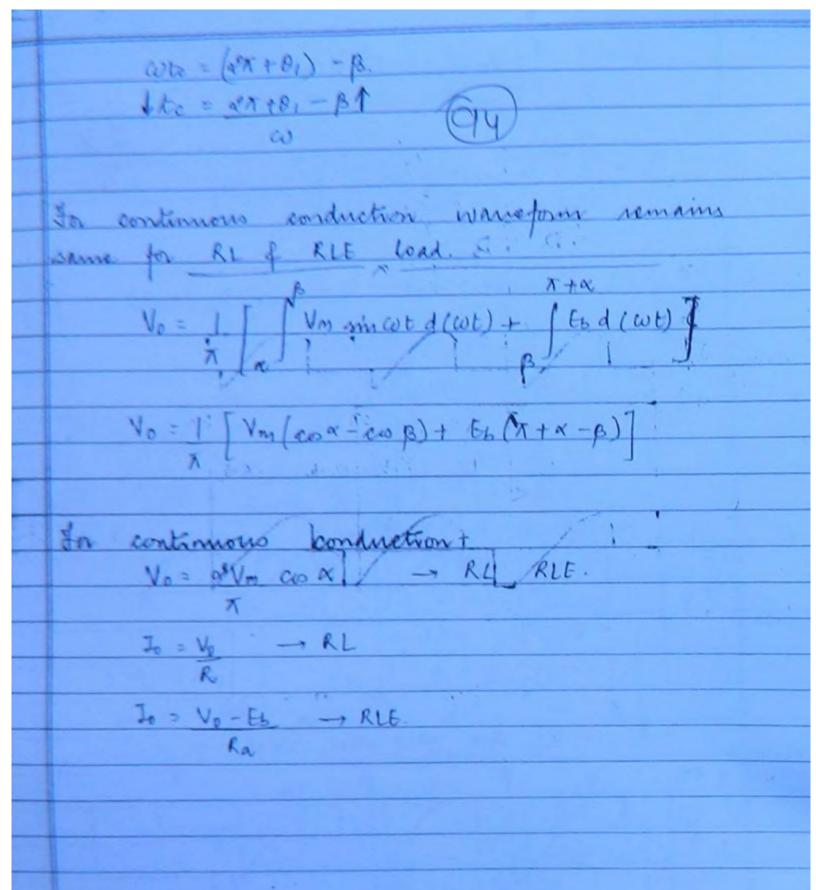


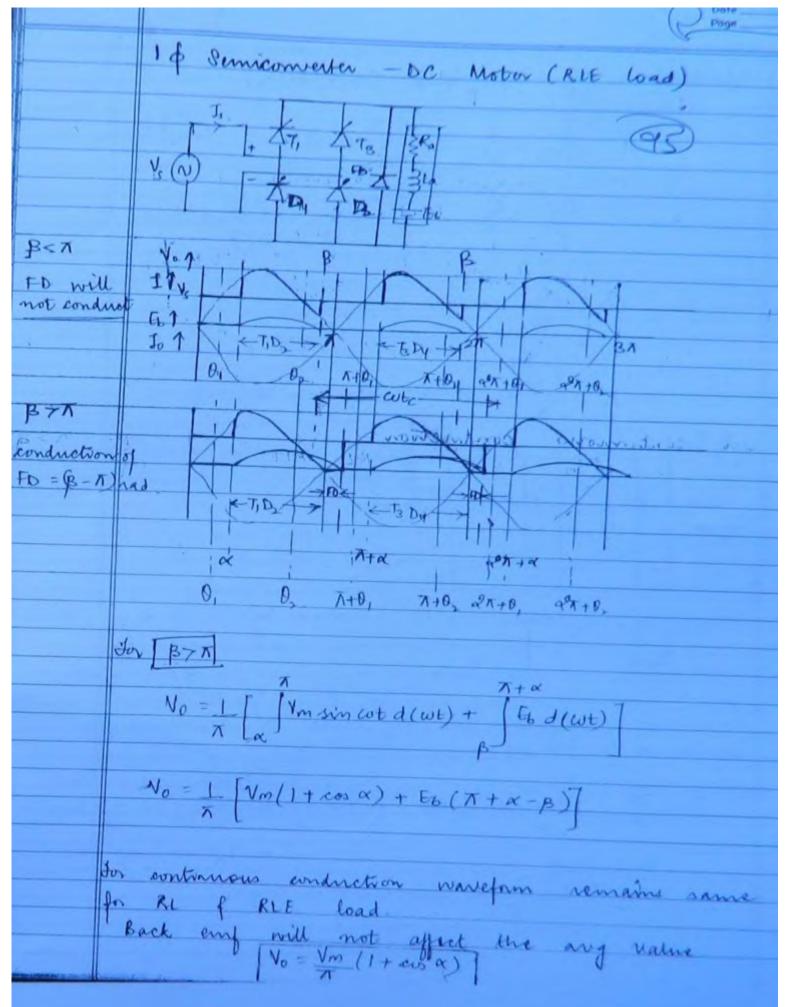
_	
	For resistive load wangorm remains same for full
	converter f semi converter
	Assume highly inductive load -
	(79)
	The THE TIDI -ON
	FNP $V_0 = 0$
	FWP Is=0
	$T_1 D_2 \rightarrow 0 N J_2 = J_0$
	To Do - ON N To - To
	$t_c = \pi - \alpha$ $t_c = \pi - \alpha$ $t_c = \pi$
	ω. ω.
*	In symmetrical connection theres a possibility of S.C. acron the supply when the incoming thyristor start conducting before the outgoing thyristor stops conducting. Here the problem is severe, because before the incoming thyristor starts conducting, the free wheeling action is through outgoing. The free wheeling action is through outgoing.
	acron the supply when the morning thyristor
	starts conducting before the outgoing try istor
	stops conducting. Here the problem is severe, because
	before the incoming hymster starts conducting,
	the free wheeling action is arrough outgoing
-	as tryingtor because of which is to period a more.
- 1	e To rectify this problem we must use a
	separate FD.
	An atreal connector with FD
	Symmetrical Connection with FD.
	Ve = 1 Vm sin (wt d(wt)
	Vo = Vm [It cox]
	© Wiki Engineering www.raghul.org

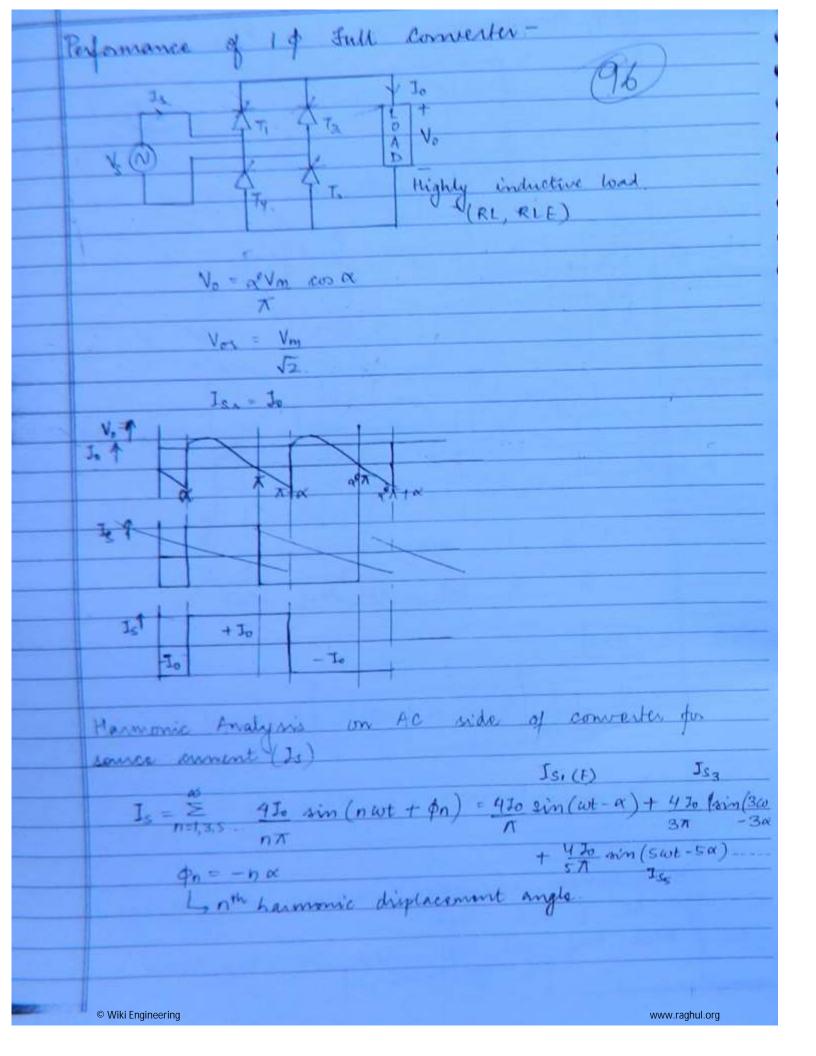


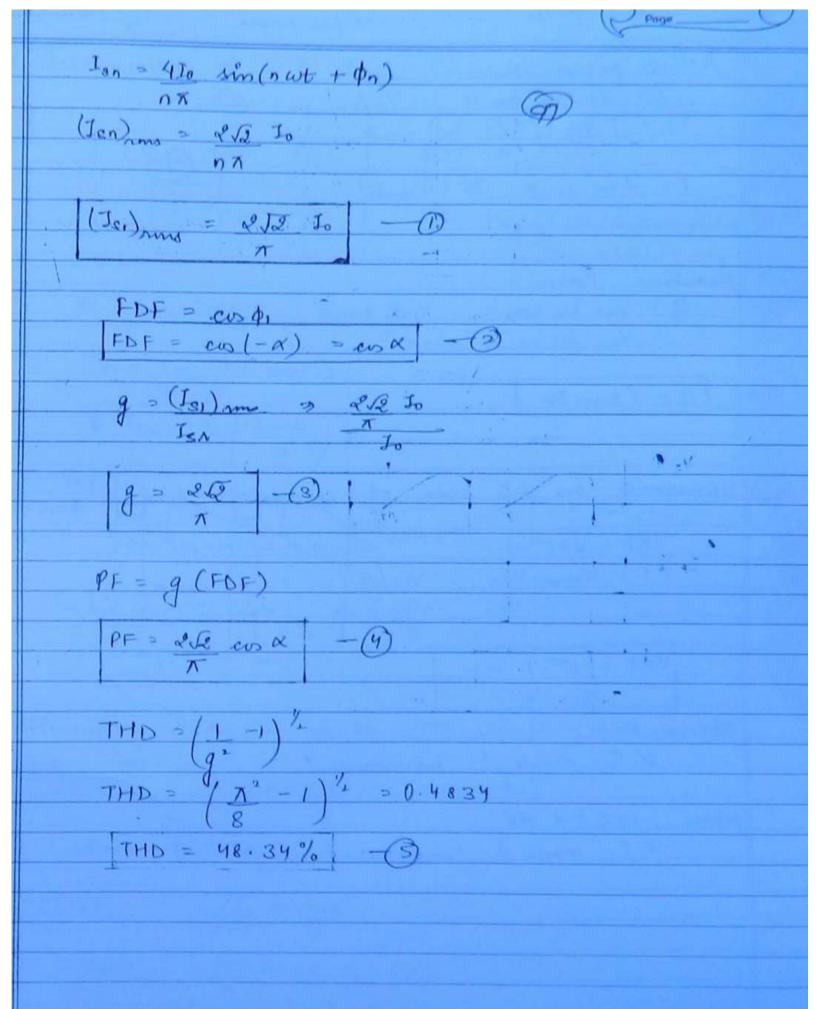


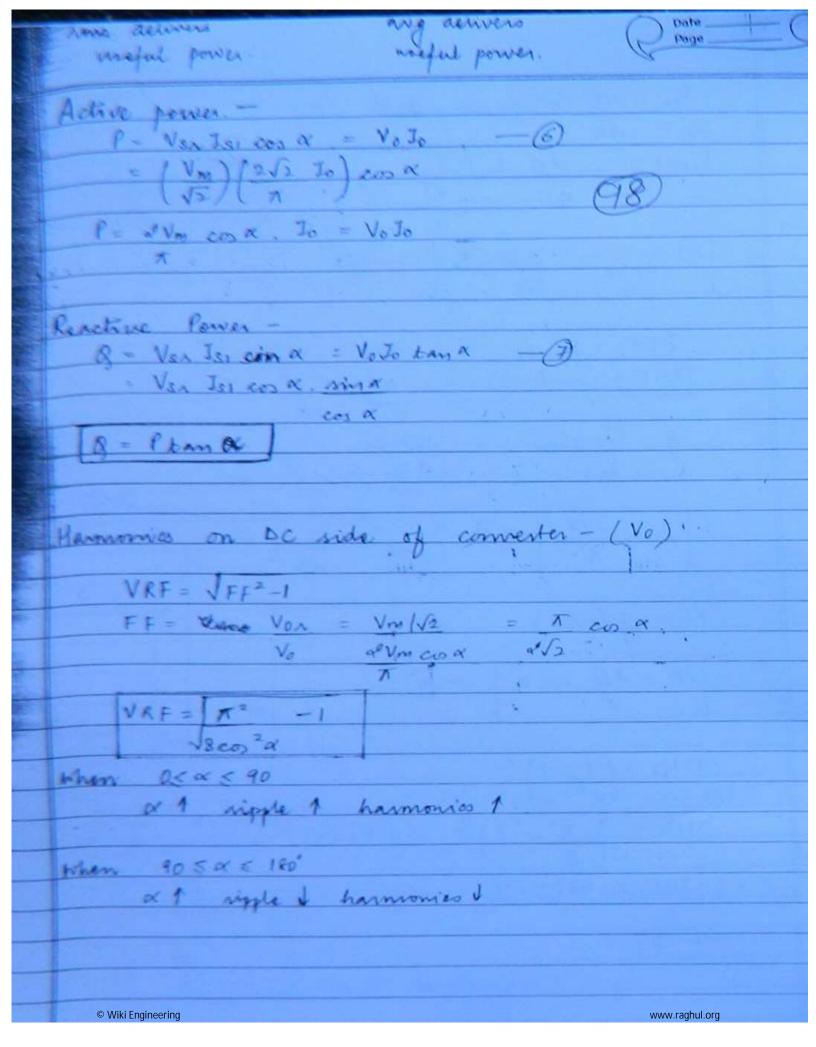


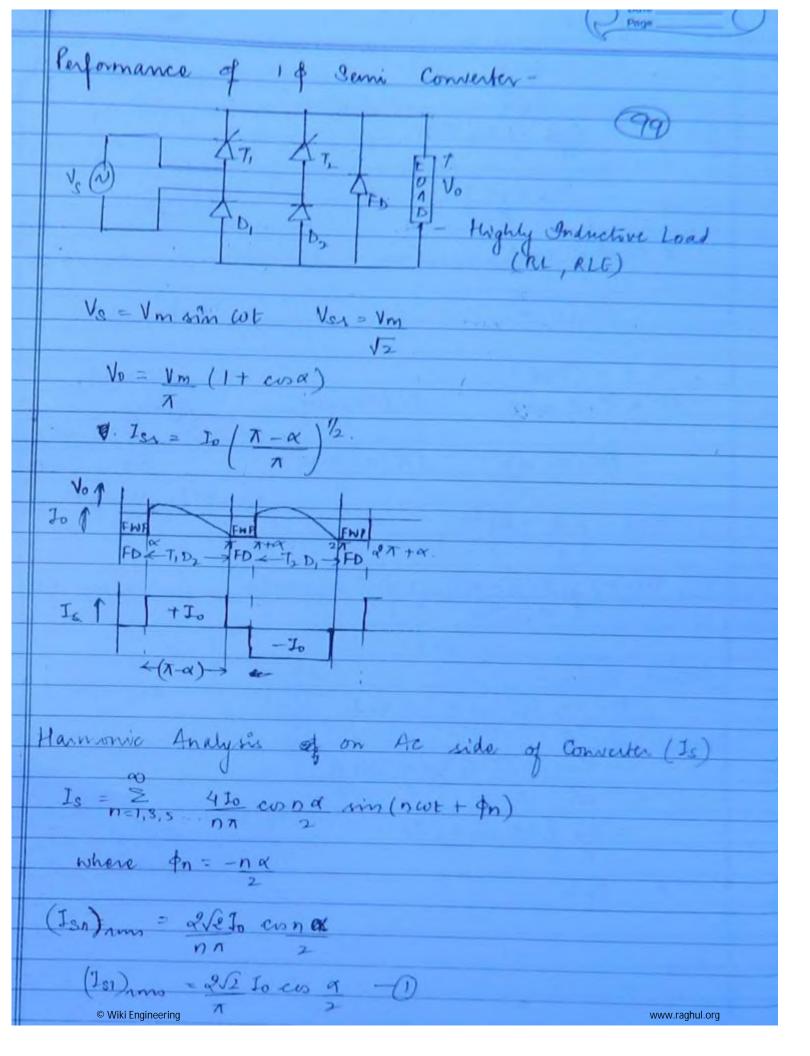


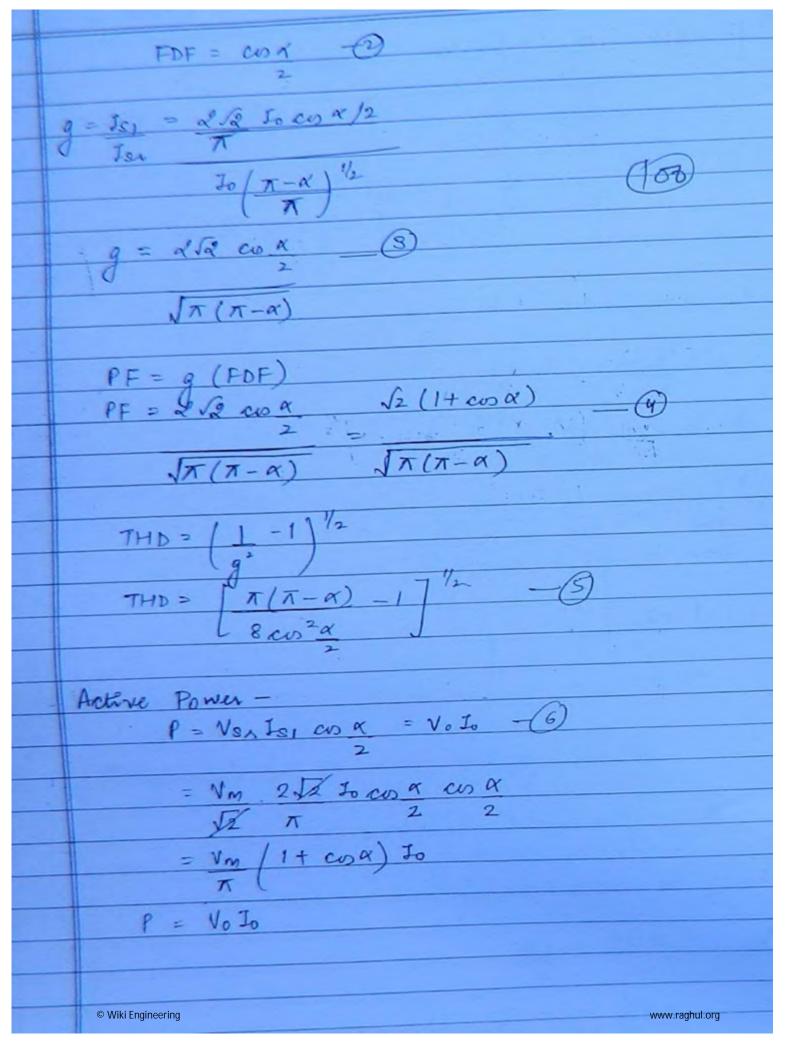


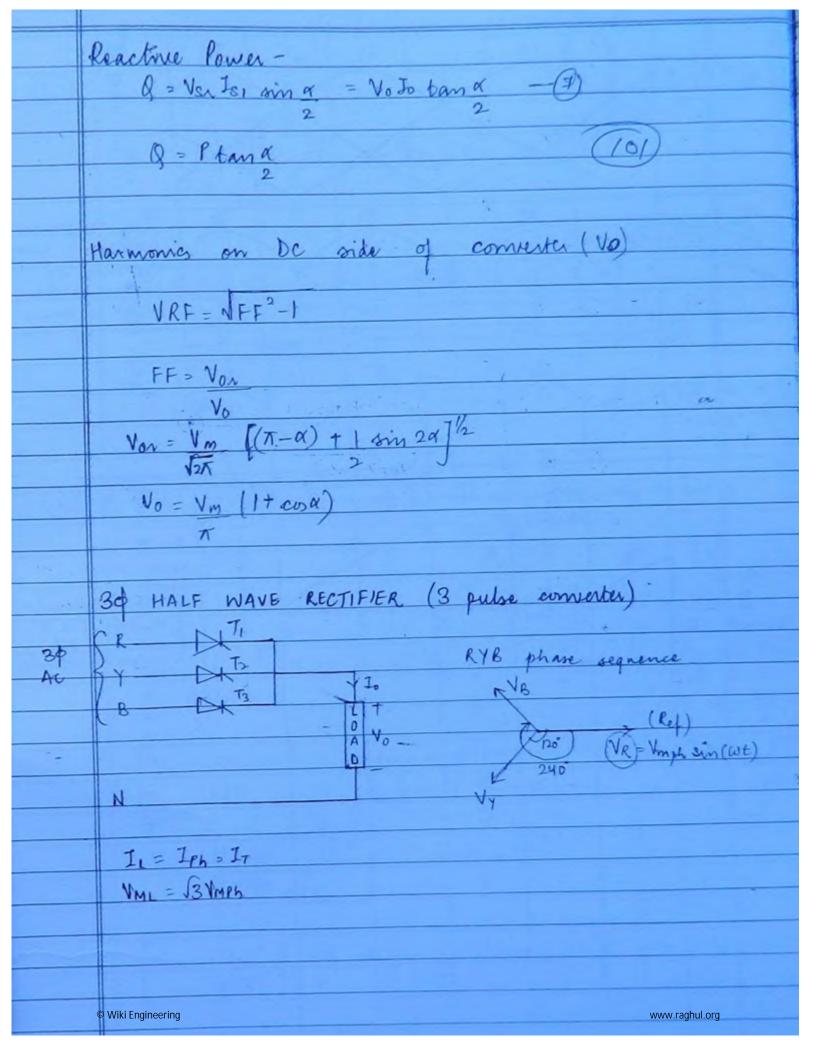


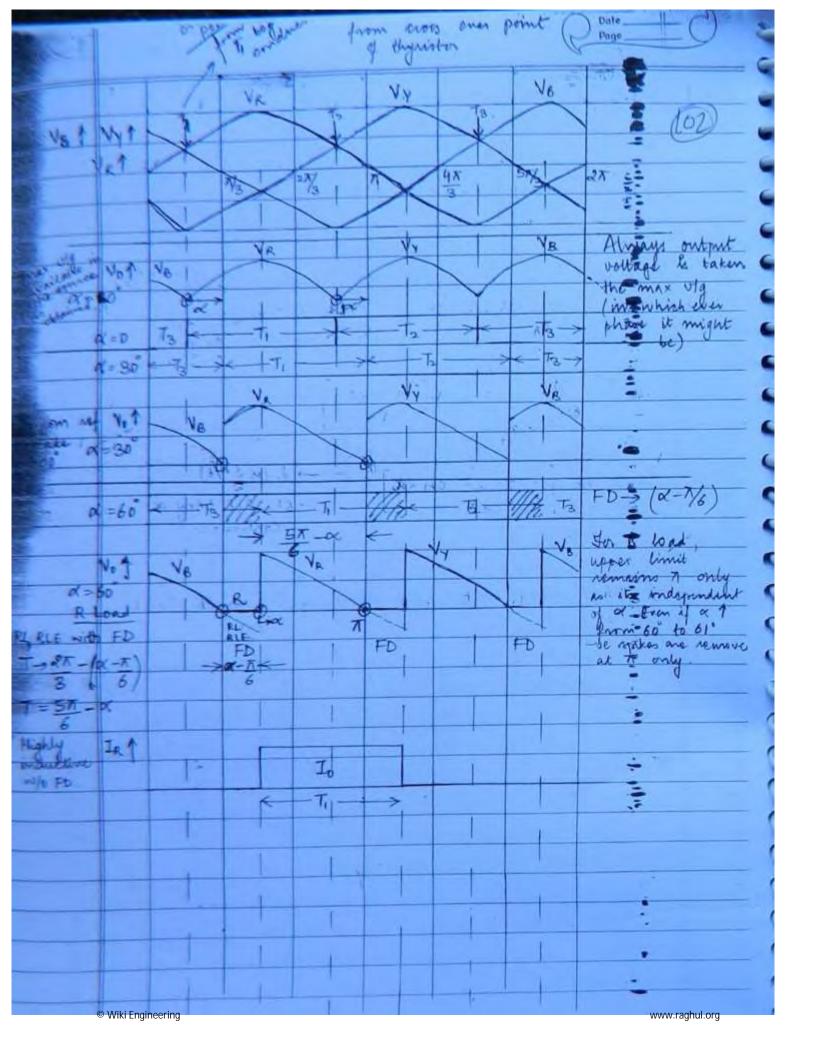


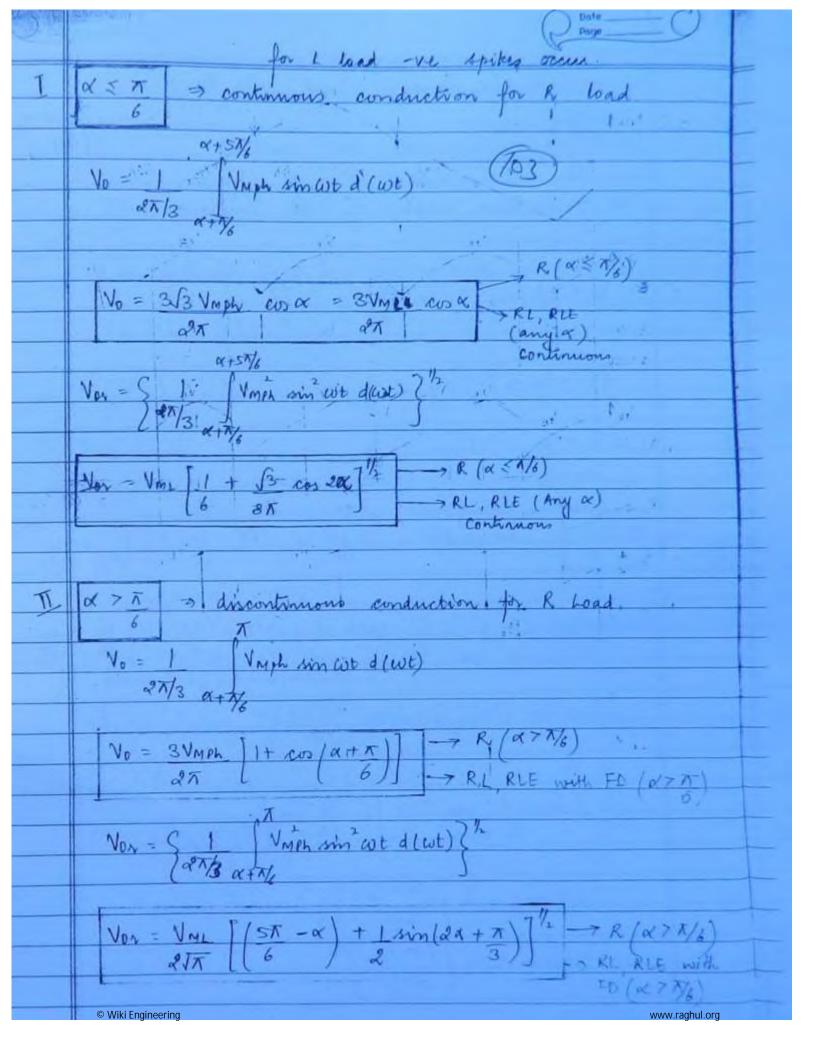


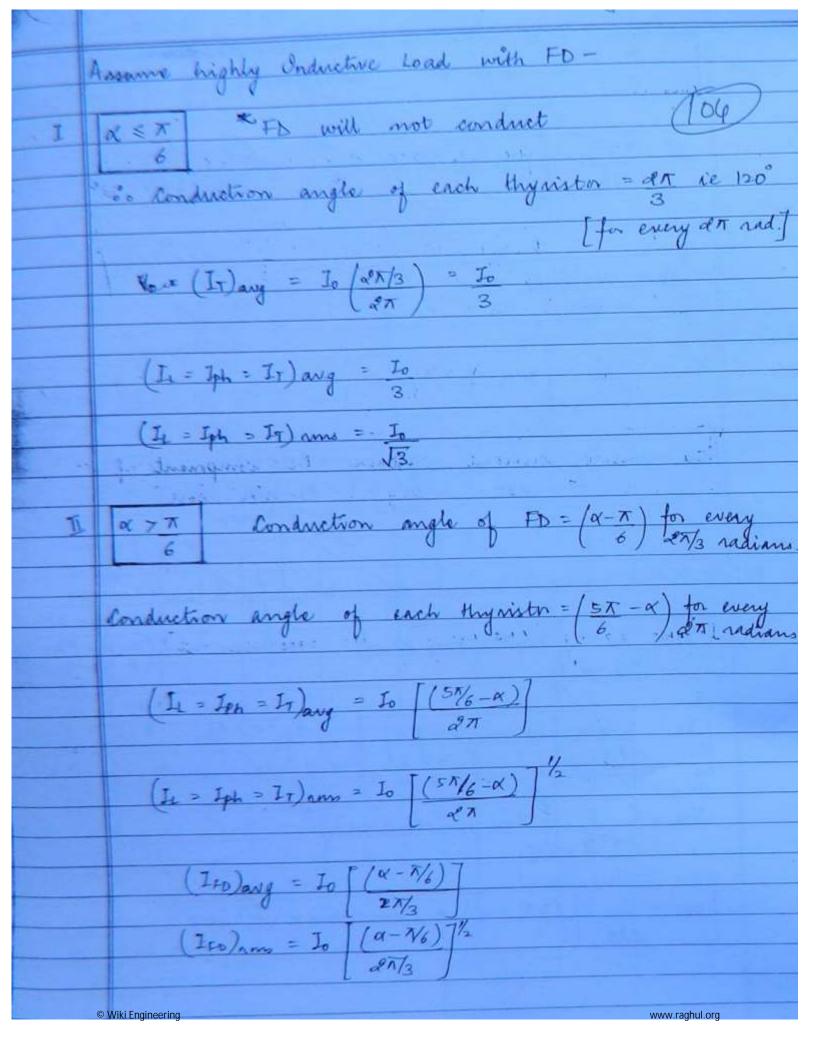


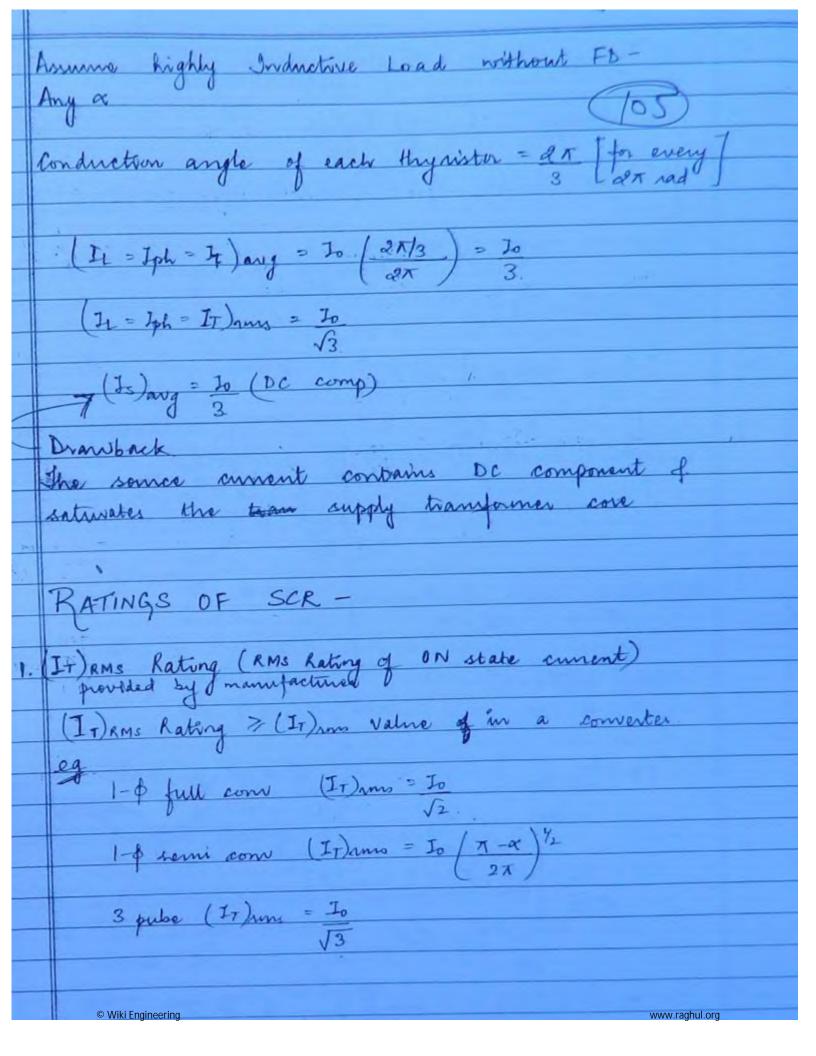


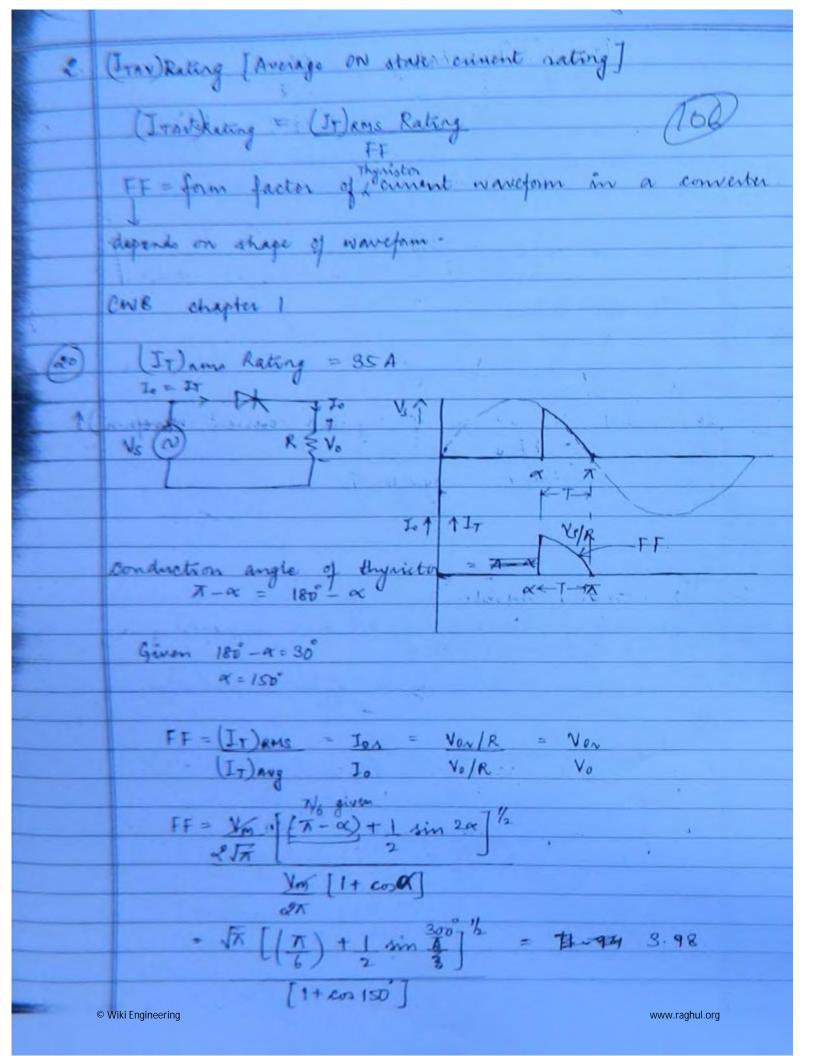


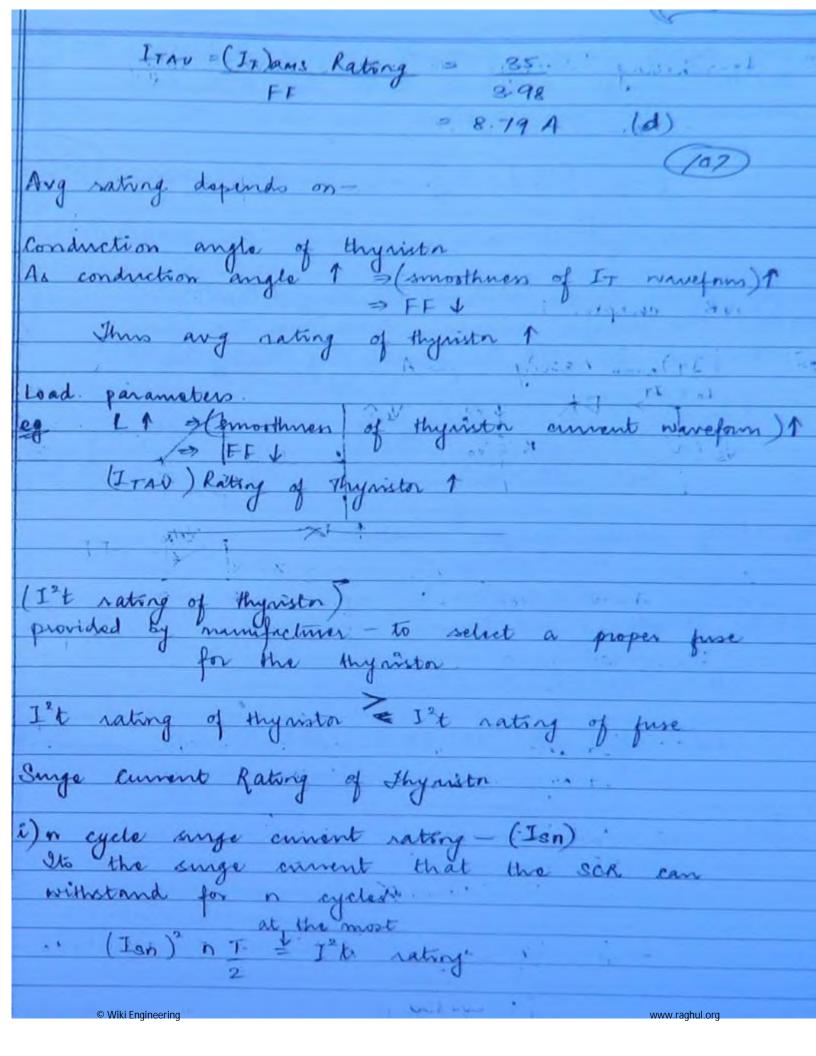


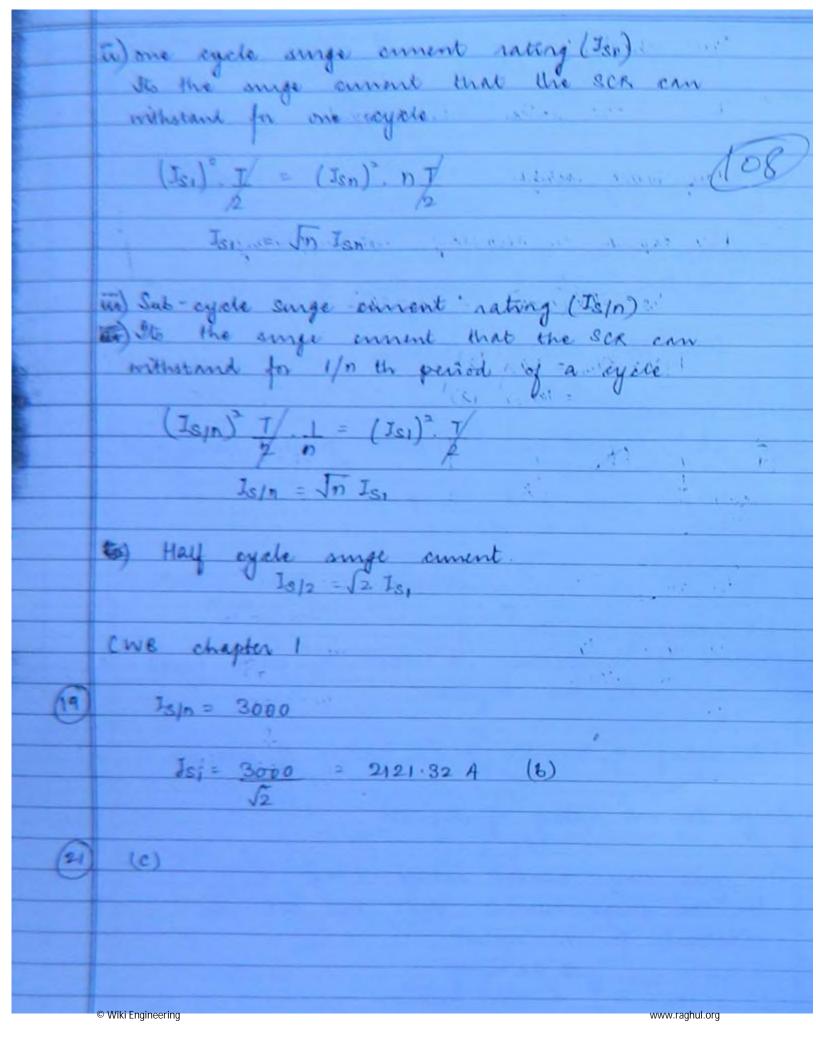




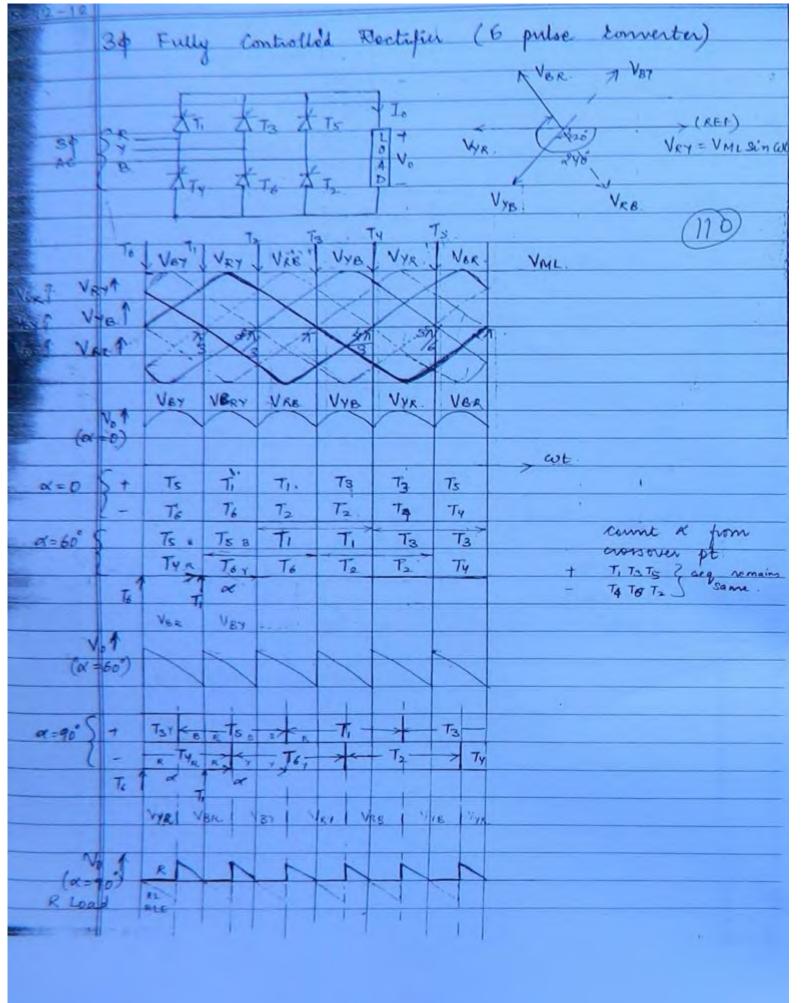


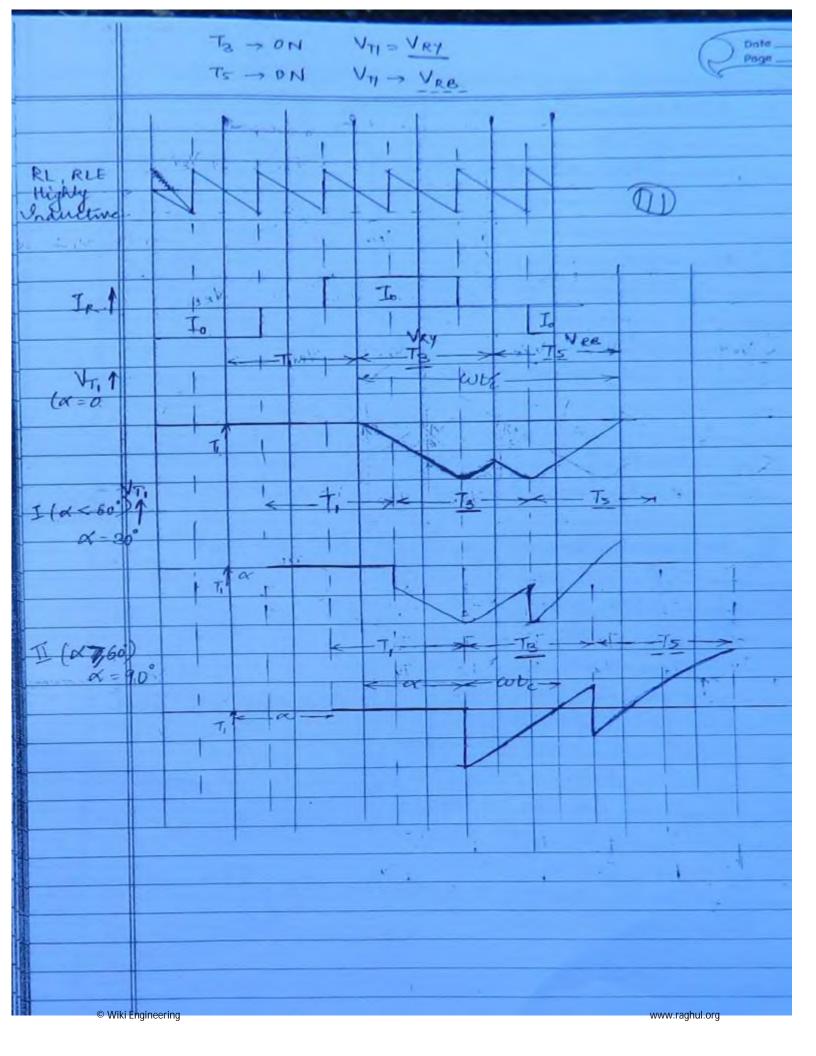


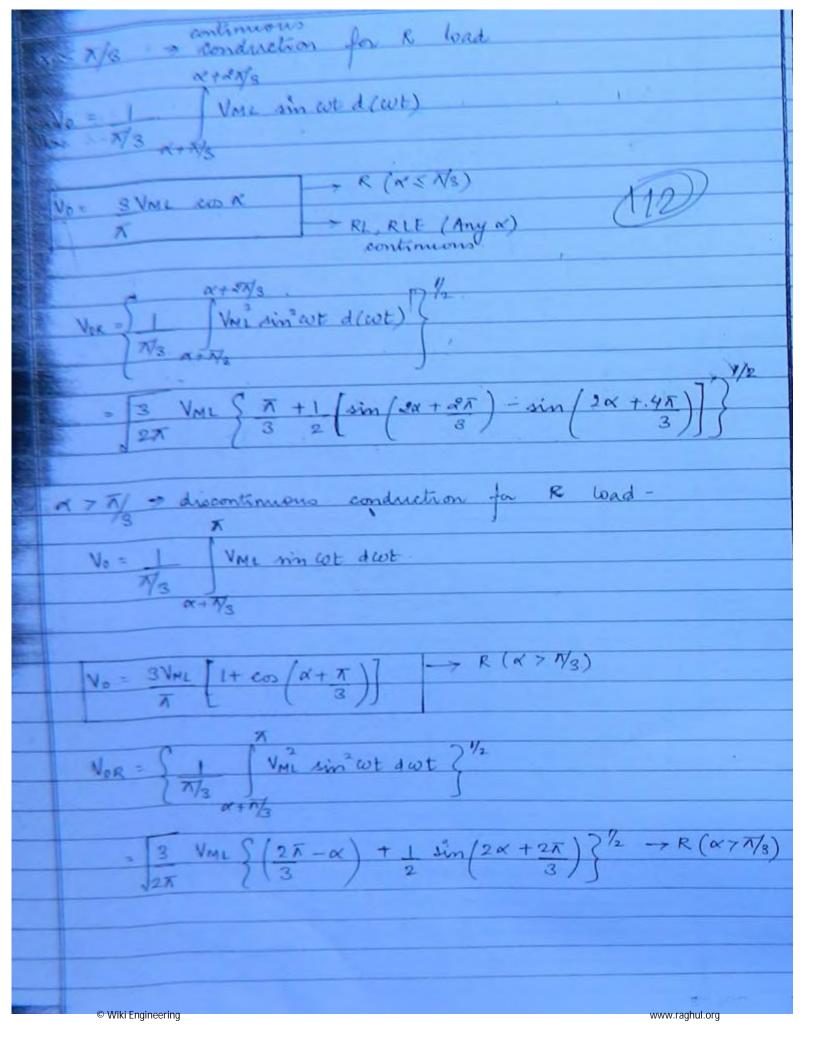




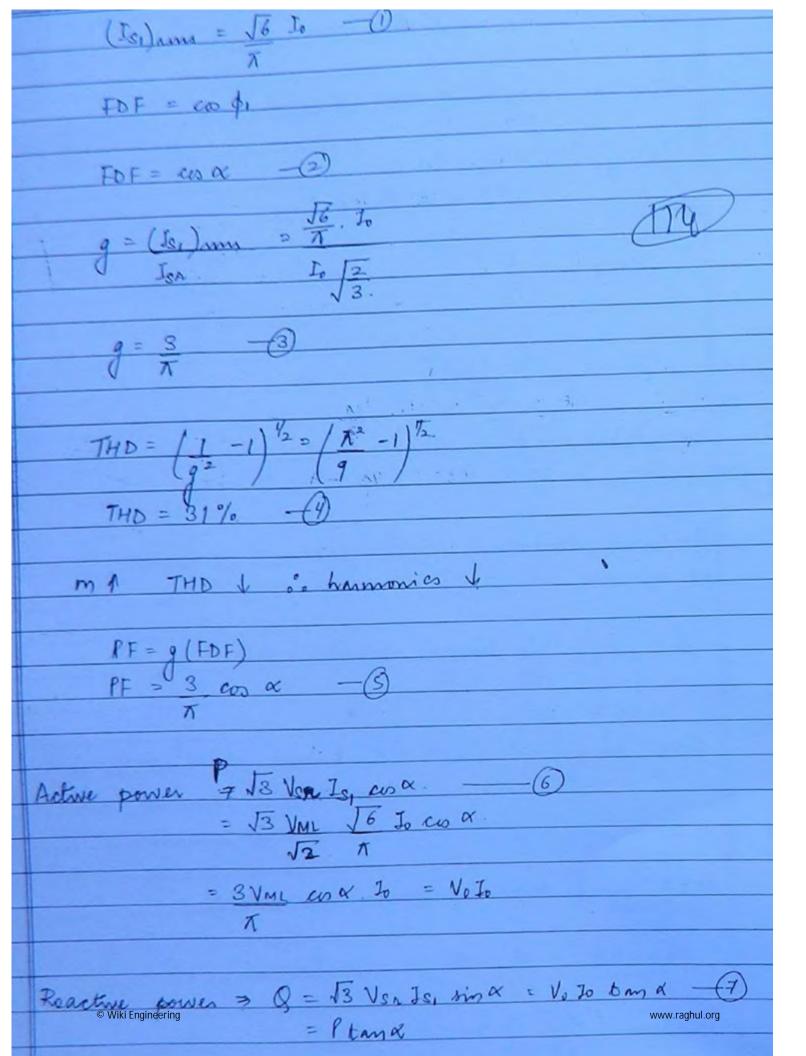
	Page
	CWB chapter 2
	The second secon
(2	(b) -ve spikes are removed.
-	ve spikes are removed.
(3	Hay wave rectifier
	Hay wave roctifier
	Pint de
	PIV depends on secondary mot on primary.
	Vs = .501V (ma) Vm = 50 /2
	PIV = 2VM = 50/2(2)
	= 100 Sz (a)
4	
331	230 V
(1	ns)
	No (wh) - seed w
	No (wt) Jeak = 230 V Vm sin x = 230"
	No ton a < 90°
	No for $\alpha \leq 90^{\circ}$ $N_{m} = 430 S_{2} \times S_{2}$ $S_{2} \times S_{3}$
	0
	So x 790 9 = 45, 135°
	Ans (b)
- 11	© Wiki Engineering www.raghul.org

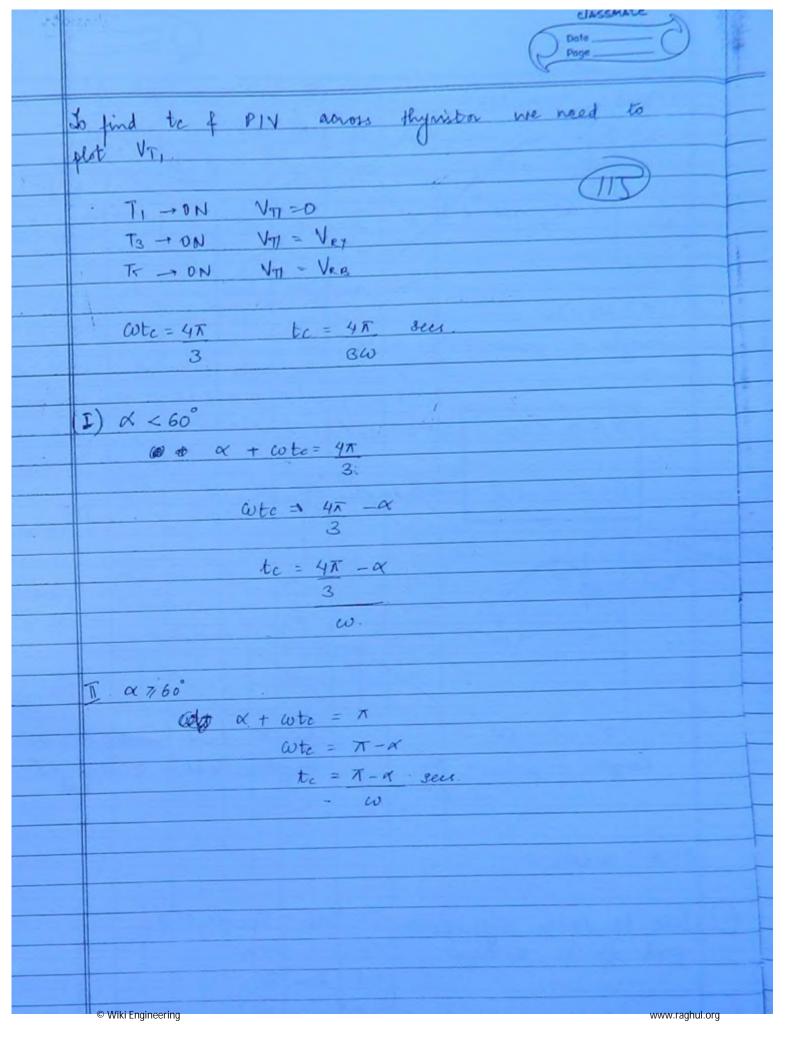


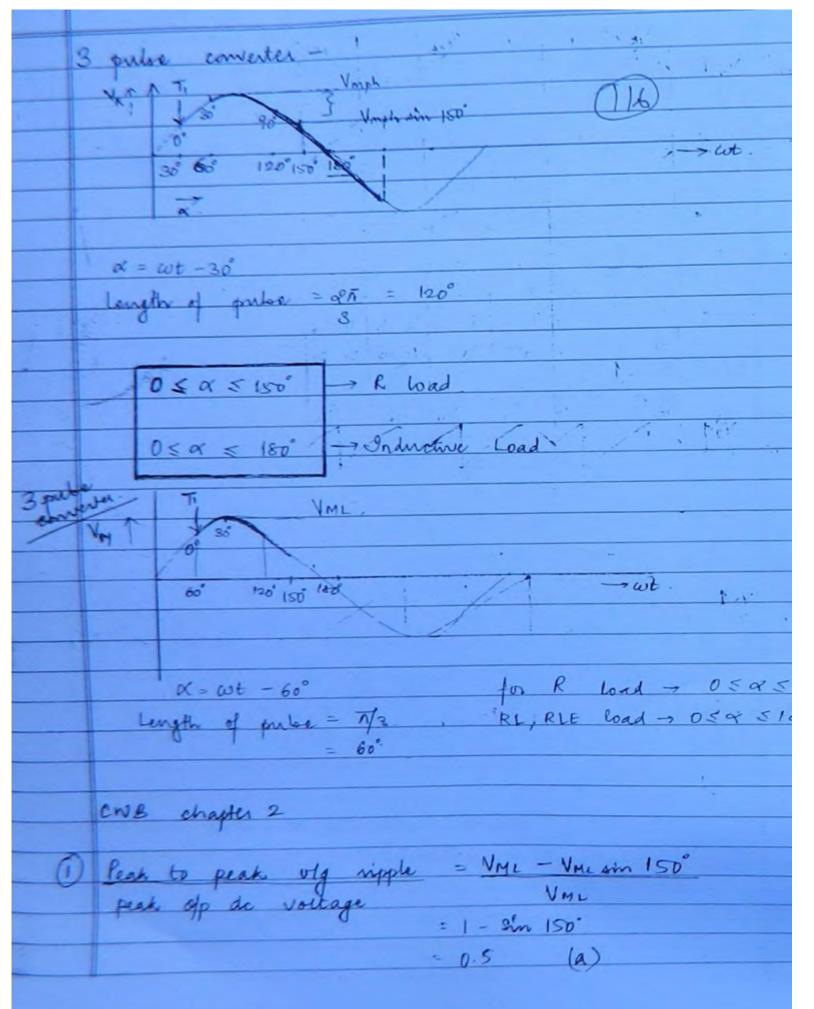


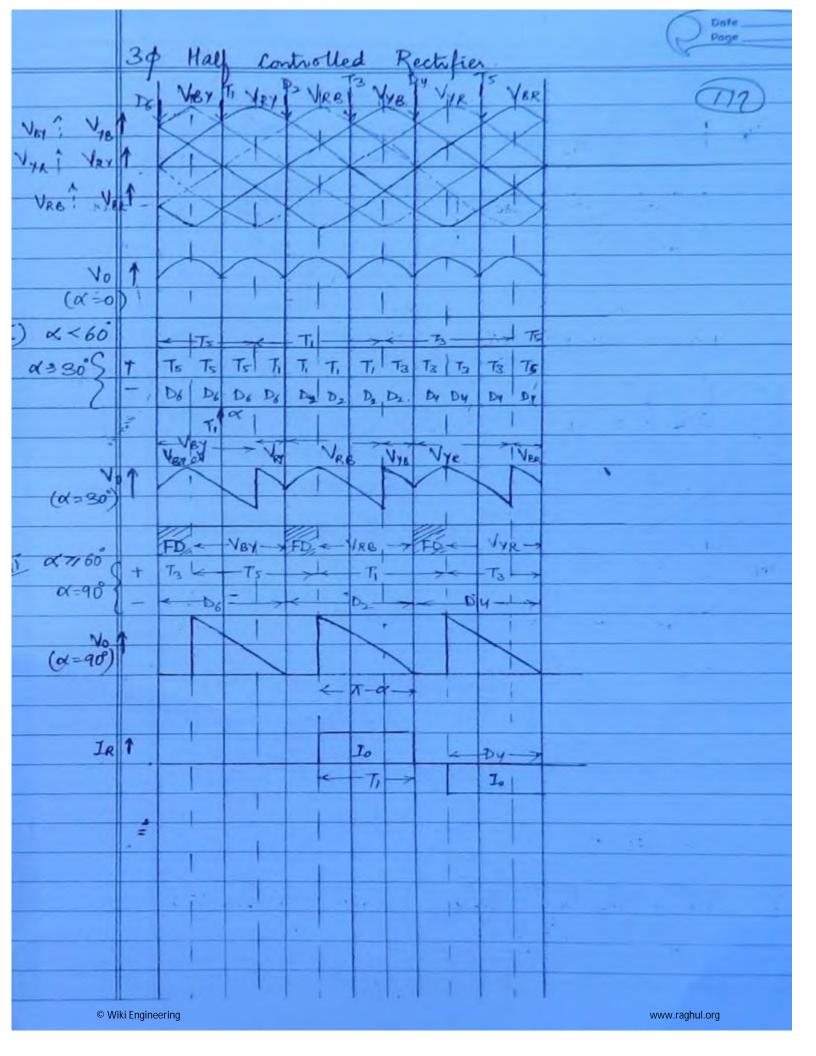


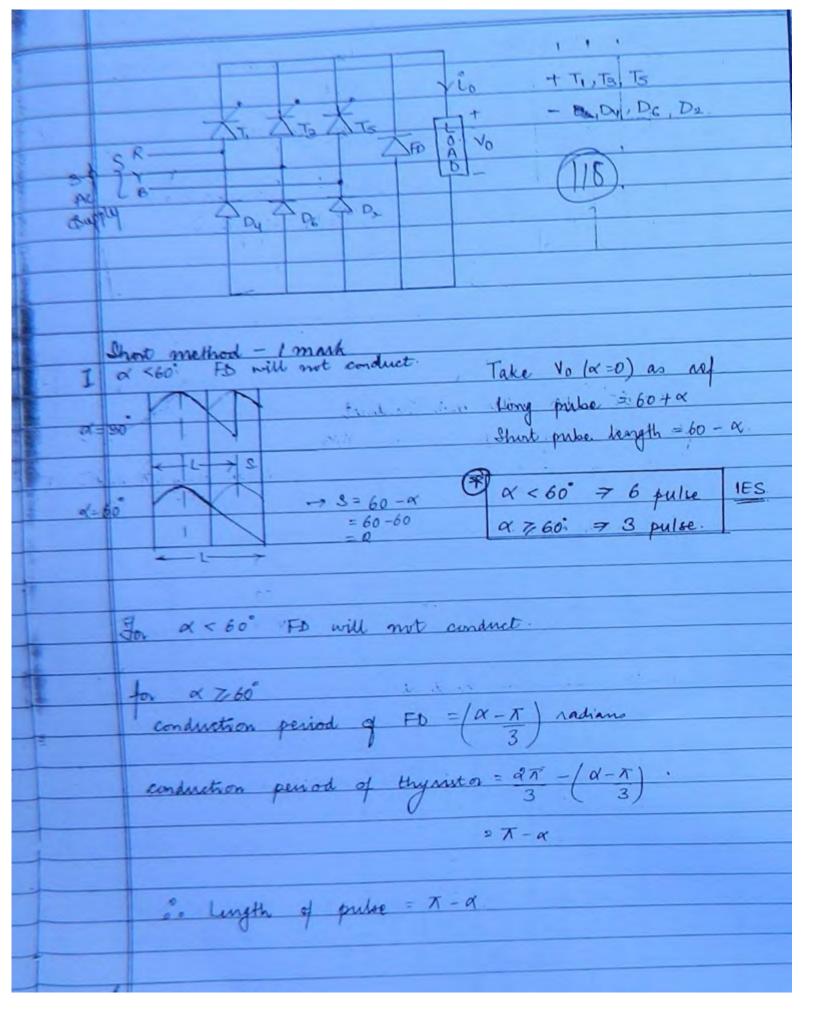
Assume highly inductive load - (RL, RLE) Conduction angle of each thyrister - 25 (for every (I) ang = Jo (2 x/3) - Jo (113) (II) mo = 10 (IR) my = Io (2/3) 1/2 IXR = (Ix) nm = 10 /2 Harmonic Analysis on AC side of converter for mource current (Is) naveform. $I_{e} = \sum_{n=1,0,5} \frac{4I_{e} \sin n\pi}{n\pi} \sin(n\omega t + 4n)$ n=6K 11 Since sin 31 : D so 3nd harmonic of multiples of 3 hamonics (triple harmonics) absent to are even harmonics NOTE: Even of triple harmonics are absent $\phi_{\eta} = -\eta \alpha \qquad \phi_{i} = -\alpha$ (Isn) ams = 2/2 To sin n T (Is) Am = 2 J2 Io. 8m 1 3 www.raghul.org

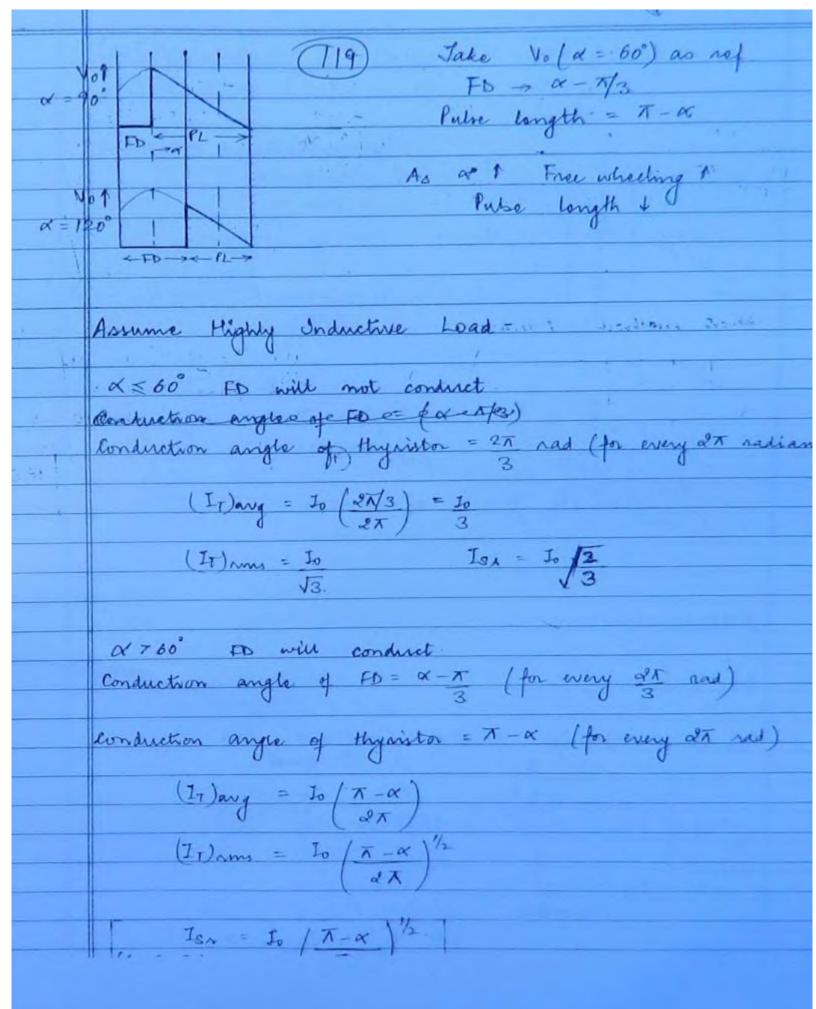


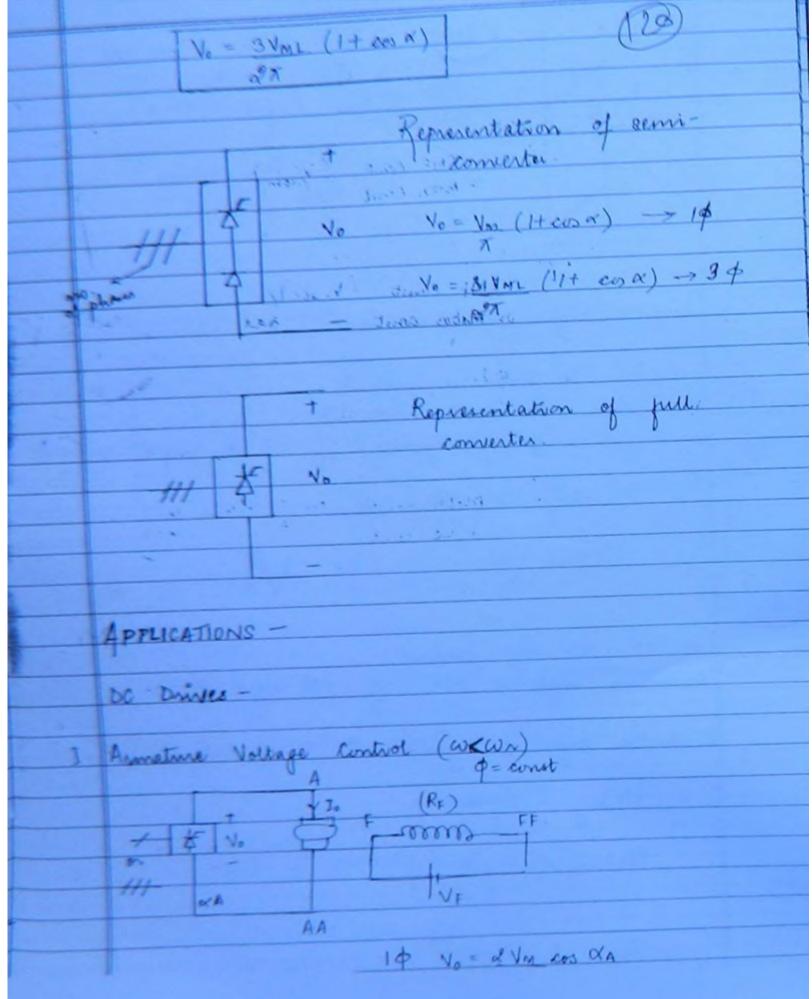


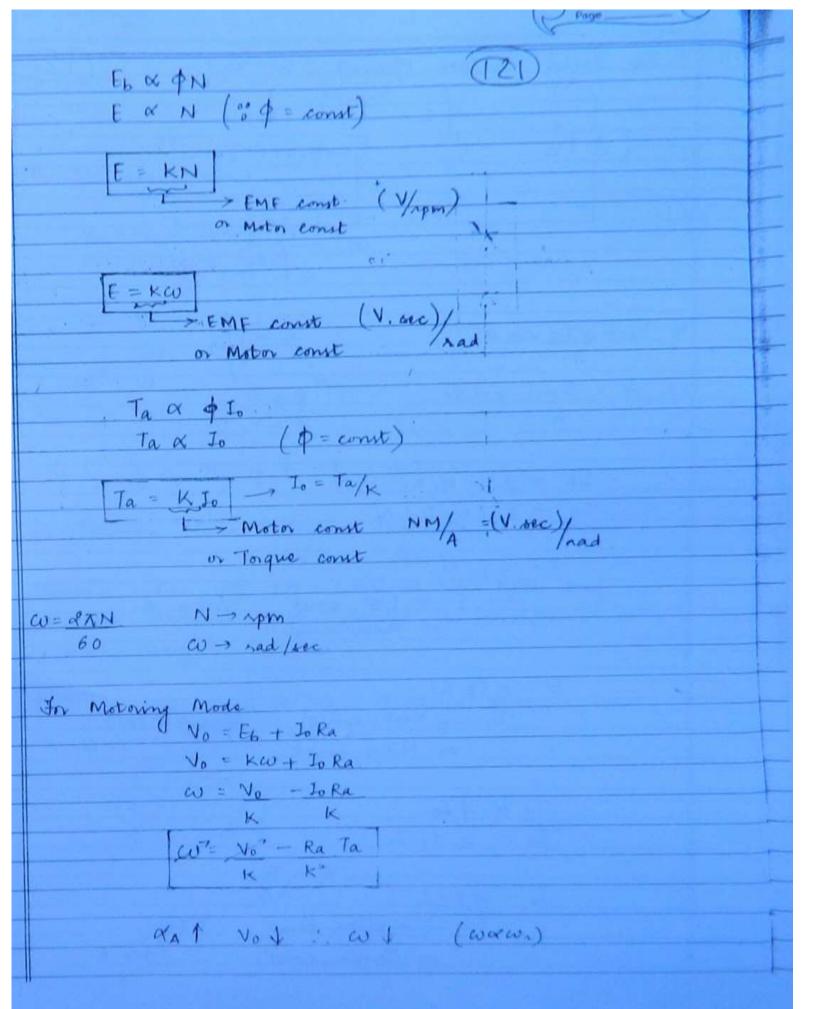


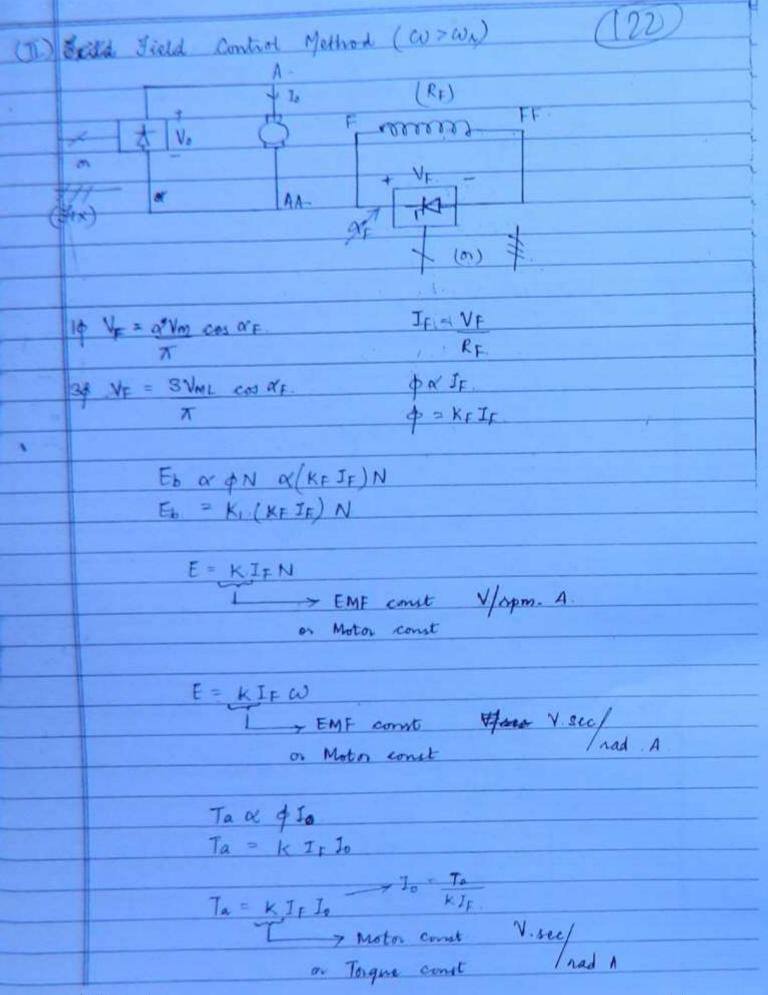


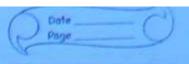












CU = STAN



for Motoring Mode

$$CV = V_0 - I_0 R_A$$

$$KI_F \cdot KI_F$$

$$CO' = V_0 - R_A \quad T_A$$

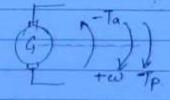
$$KI_F \cdot (KI_F)^2$$

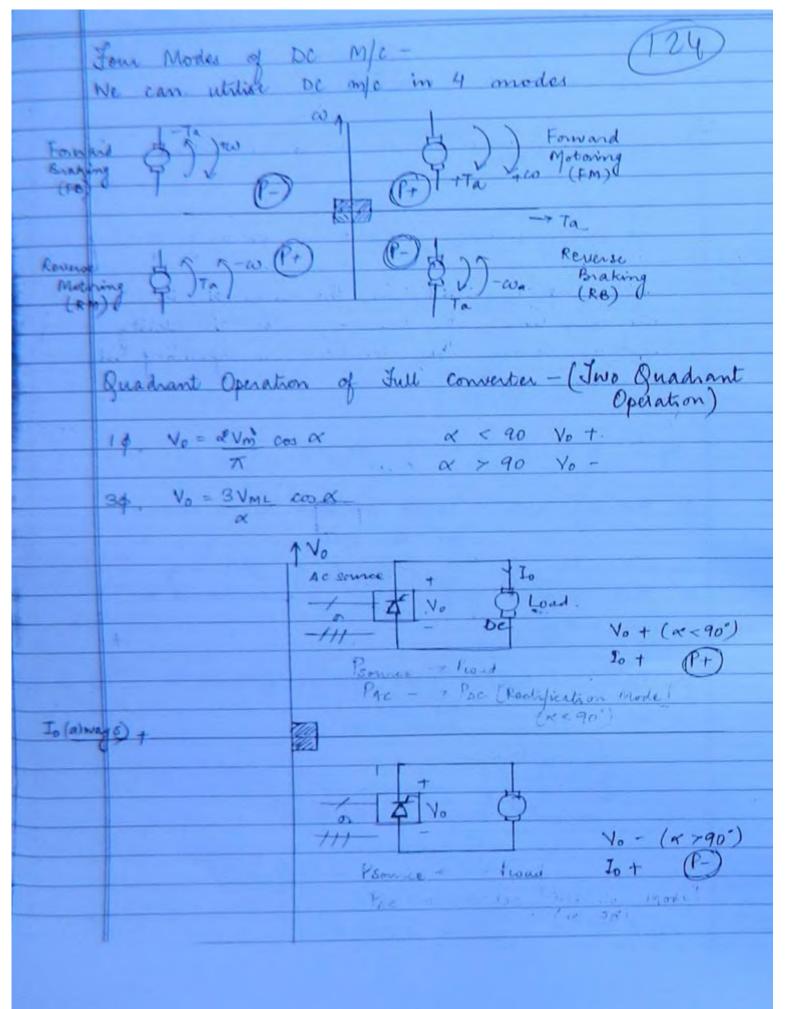
ay 1 Vy 1 = y 1 = wo > wn

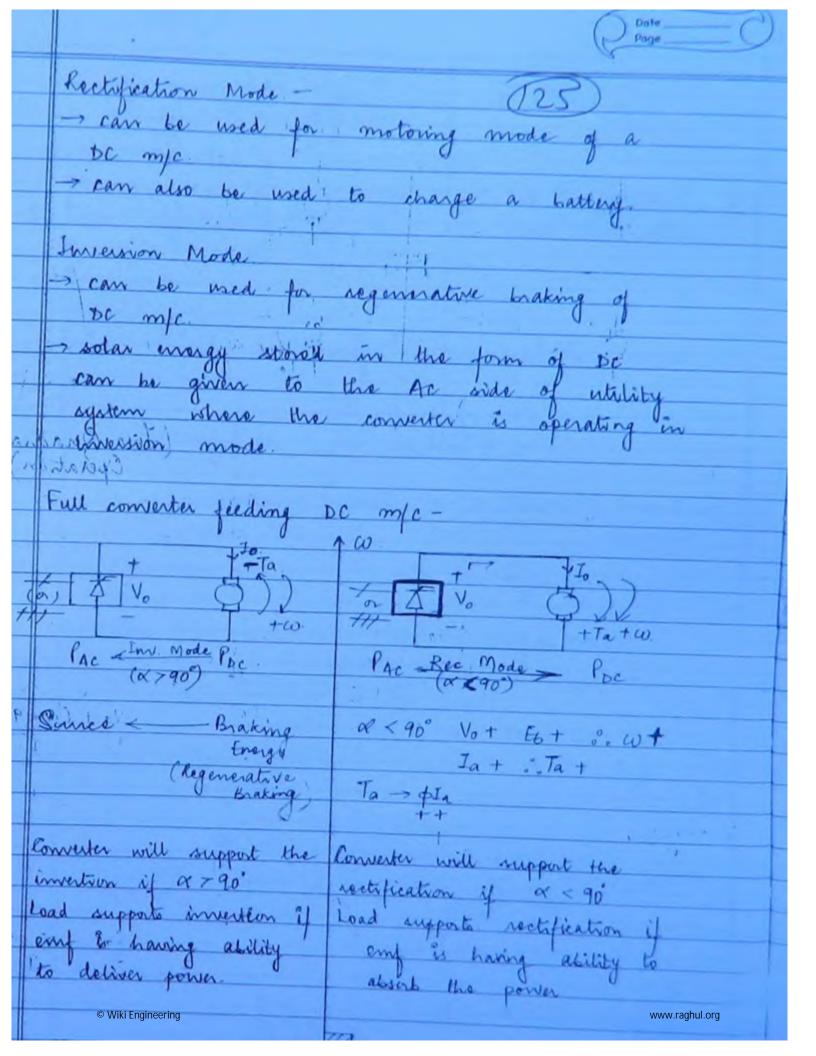
for Motring Mode & Torque developed is in same
dir as speed.

Coment enters at the terminal of back emp
Do that electrical effect absorbed is transformed in
much energy.

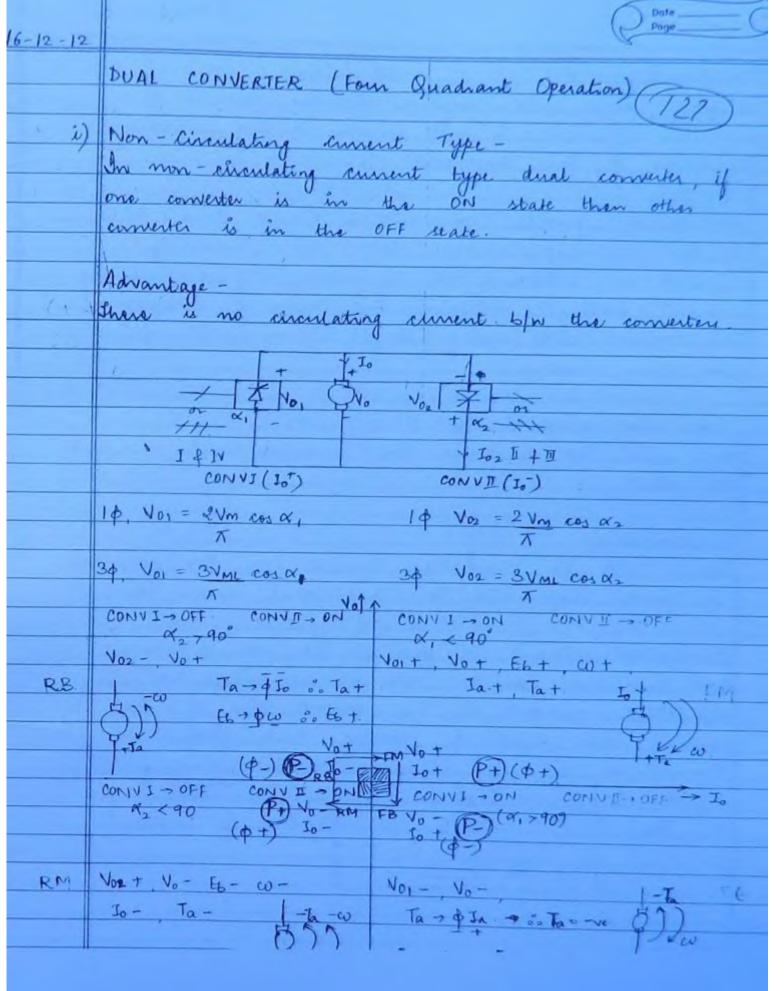
for Generating Mode = Torque developed of speed in



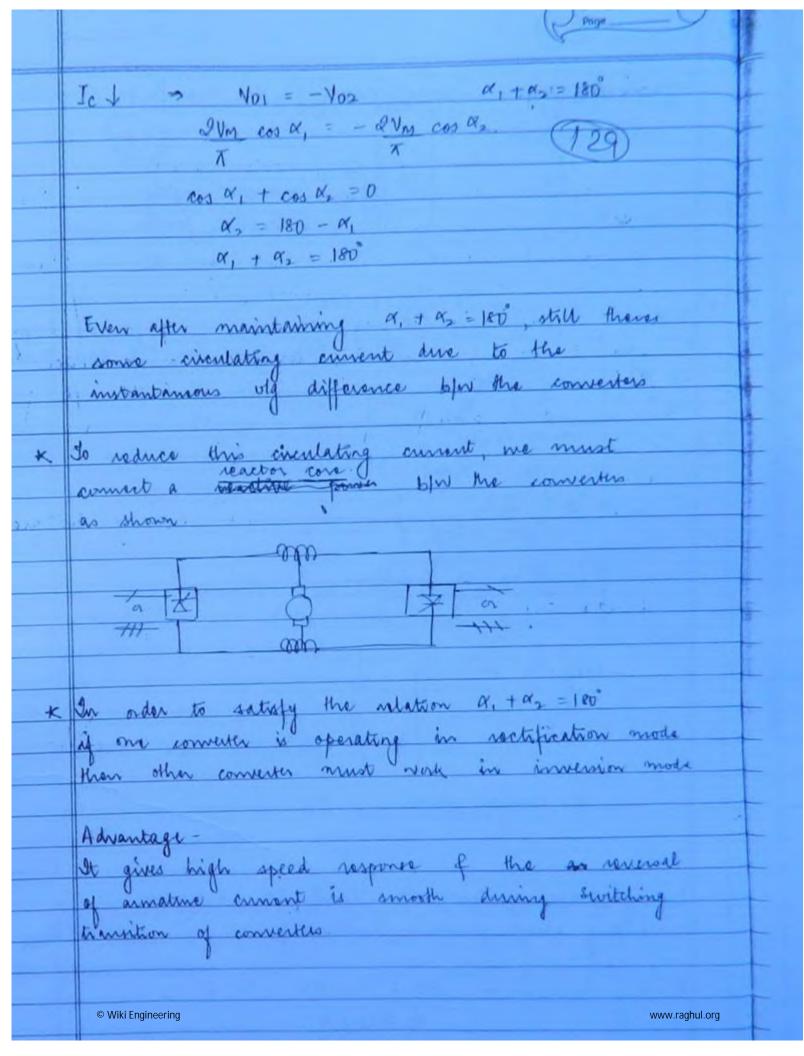


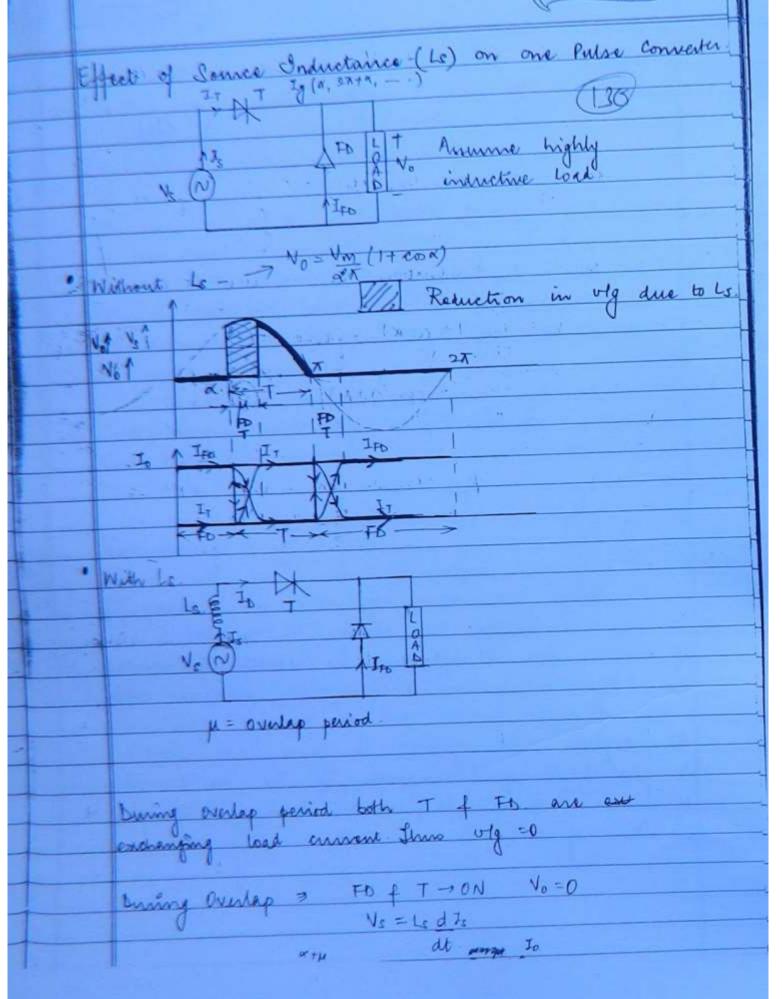


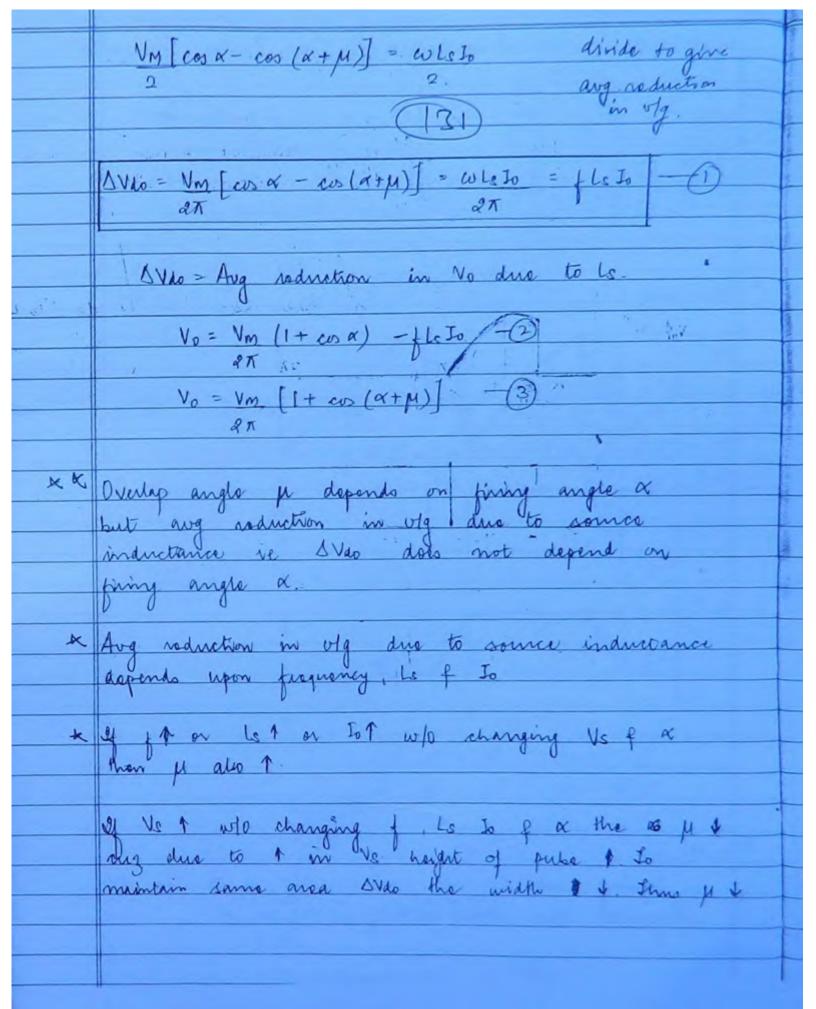
No = -6+ 10 Ra	No = Eb + Jo.Ra.
10 -0 1/4	w = 2 Vm cos x - Ra Ta -> 1\$.
	$\omega = 2 \text{ Vm } \cos \alpha - Ra \text{ Ta } \rightarrow 1 \phi$ $\pi \text{ K} \qquad \qquad \text{K}^2$
The state of the s	
(26)	w= 3 Vml cog - Ra Ta -> 3¢.
	TK K2
	the state of the s
States of the State of the Stat	Ta + cot . (P+) (+)
•	
	a di stano
Quadrant Operation Supports	of Semi lonverter.
Supports	
	in)'
© Wiki Engineering	www.raghul.org

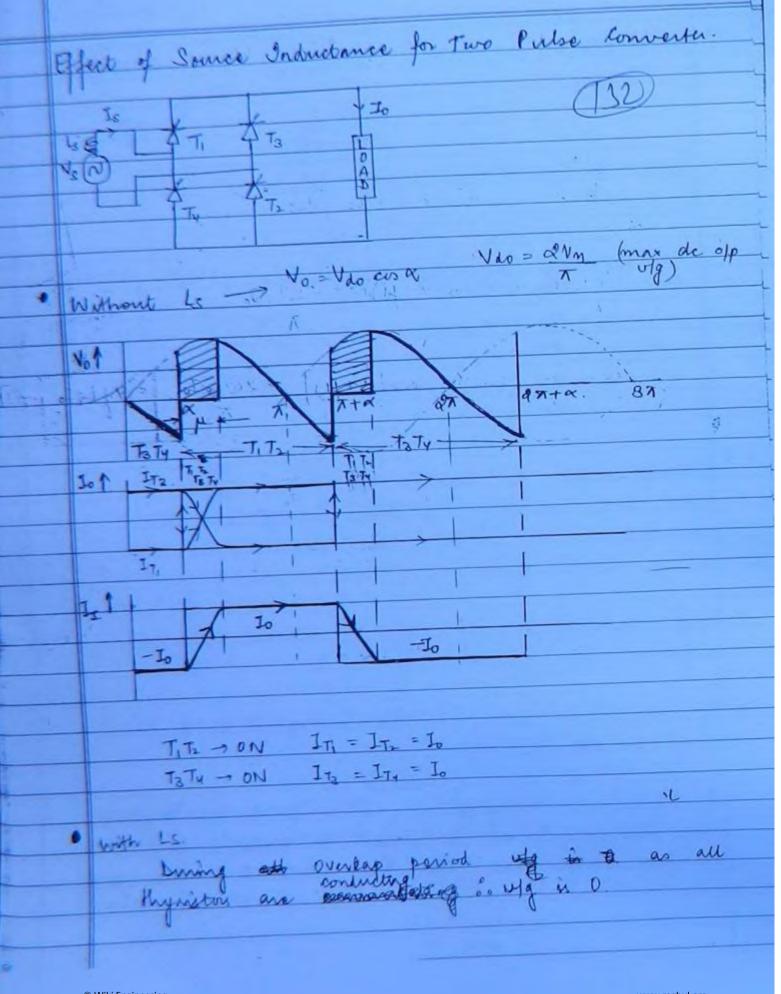


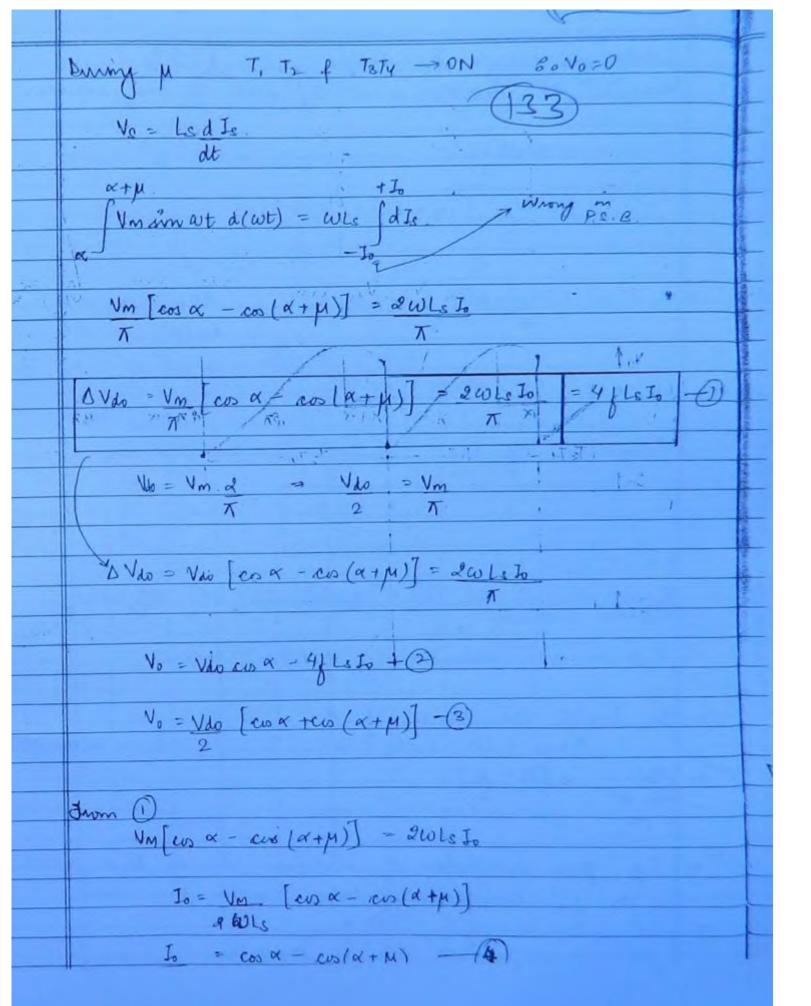
Disadvantage -It gives stow speed response of the reversal of armature current is not smooth during switching transition of the convertise. We must provide commutation delay time (sta) to the outgoing converter before the incoming converts is multihed on to avoid high circulating coment during witching transitions of converter The commutation delay time is responsible. alon speed response in Circulating ament Type -Here, both the converters are simultaneously in the DN state. Shadrentage -There will be circulating current byw the converters have responsible for additional Circulations enment is dure to the vig difference conserters. We can redrice the inculating current if the output ofgo of each other ... conserver are equal of opposing - actual polarity V02 © Wiki Engineering www.raghul.org



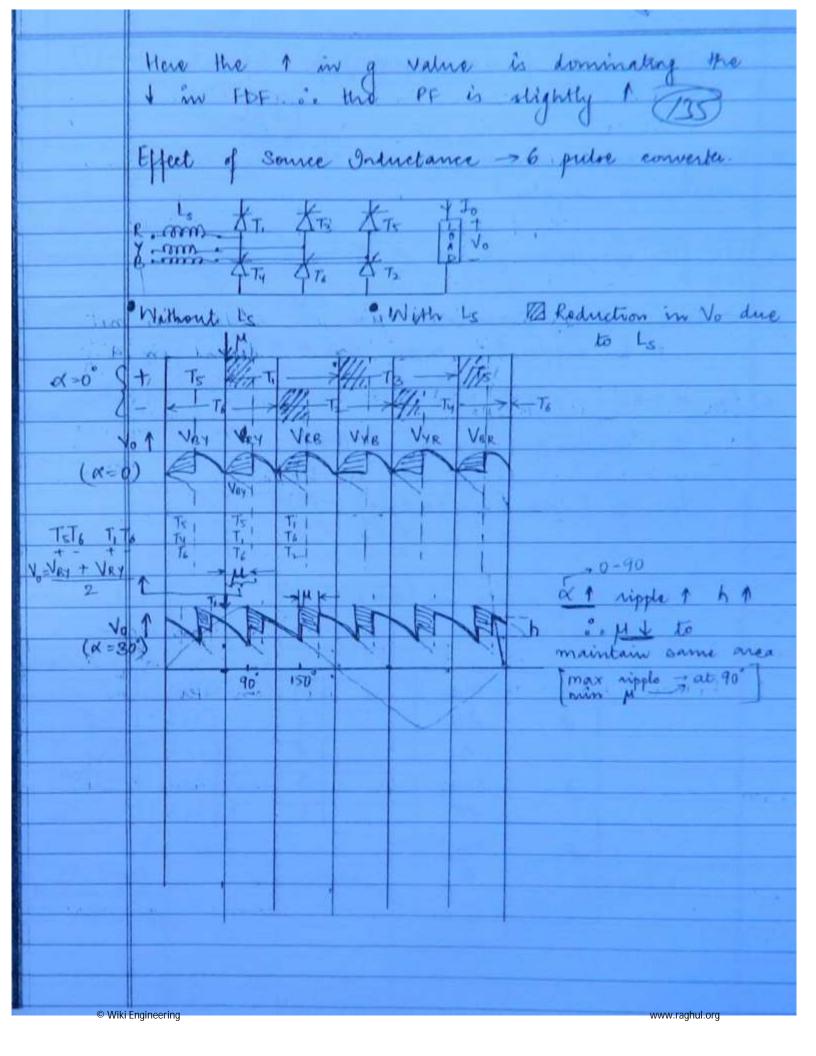




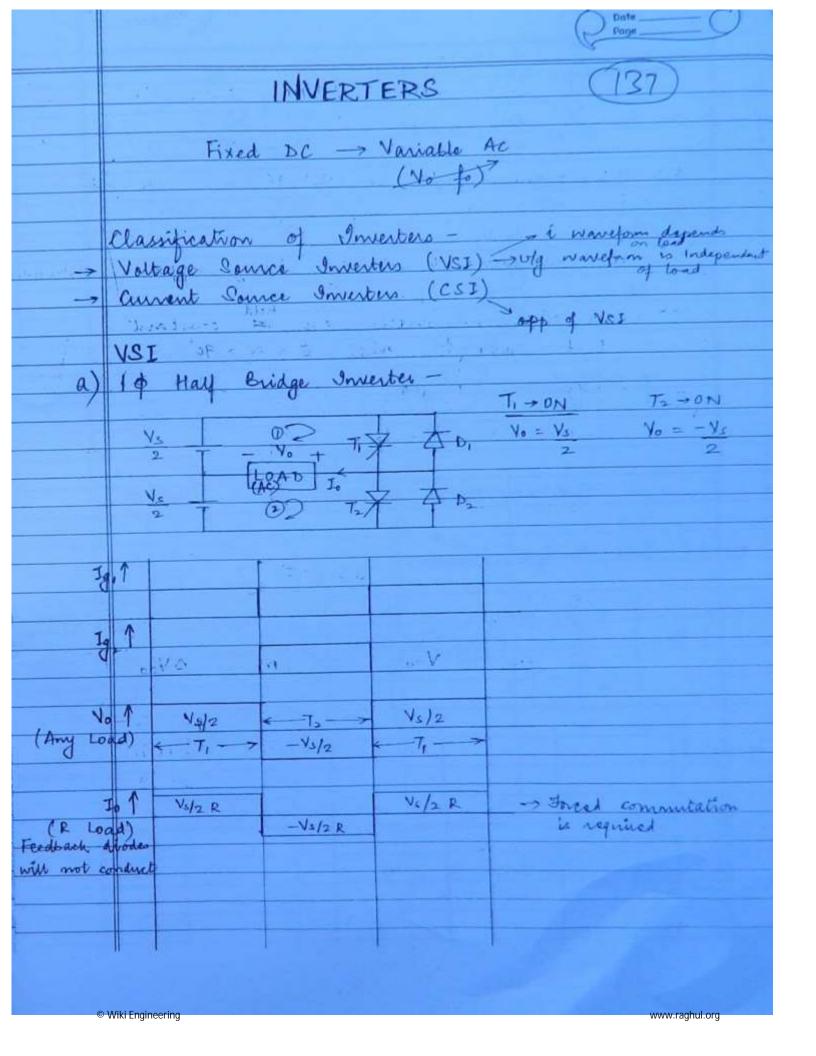


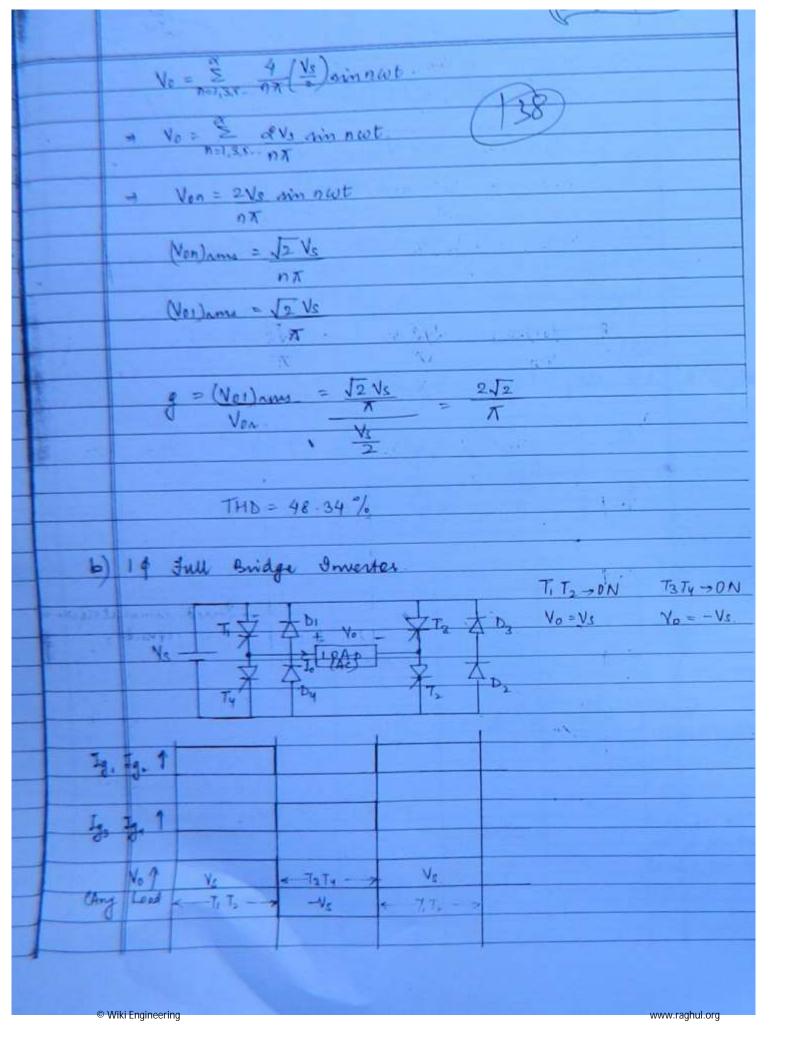


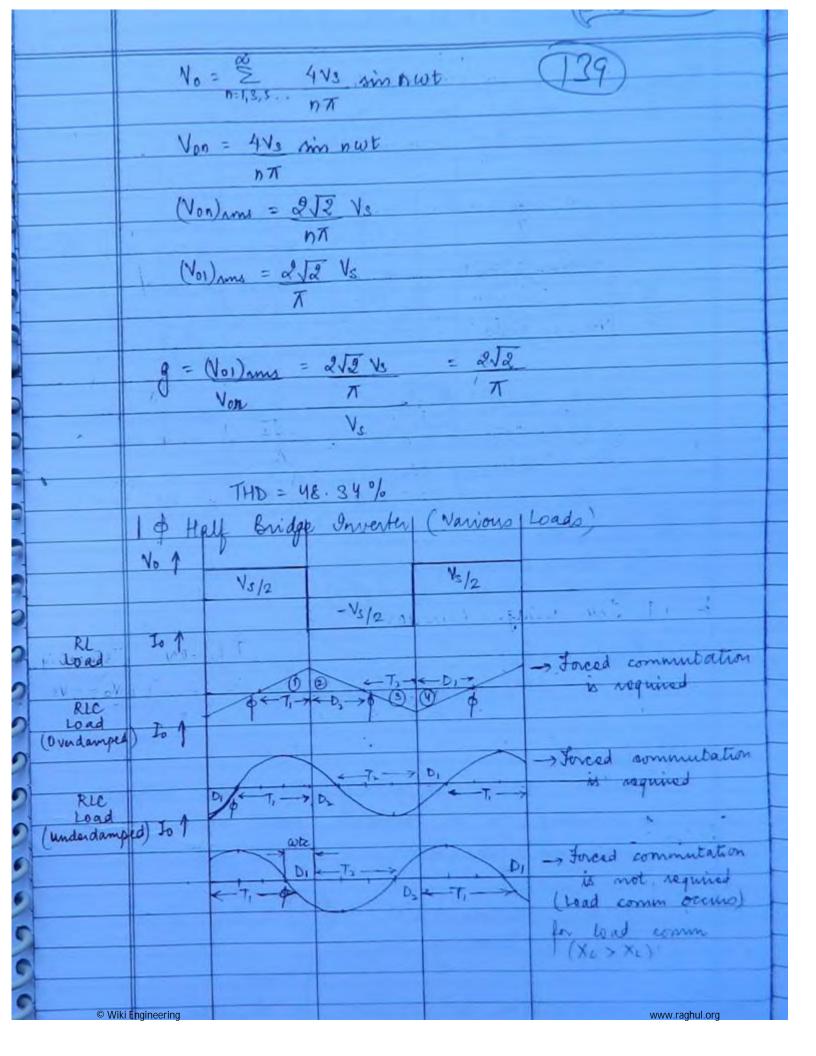
Inductive Voltage Regulation - (734) Messure of reduction in veg due to the source industrants = AVda = Nac [cox-co(a+M)] AVdo does not depend on a At x=0 lat M= A. Inductive V/g Reg = coo - co (0+ 100) = 1- cos 40 Effect of le on the performance of converter-Reduces any output of the converter the sange of a max = 180 - (wtg + 10) tg = device turn off time 1 = gives emostheress of waveform towards since wave, waveform egoroaches bowards since wave Harman & on Ac gile of converter

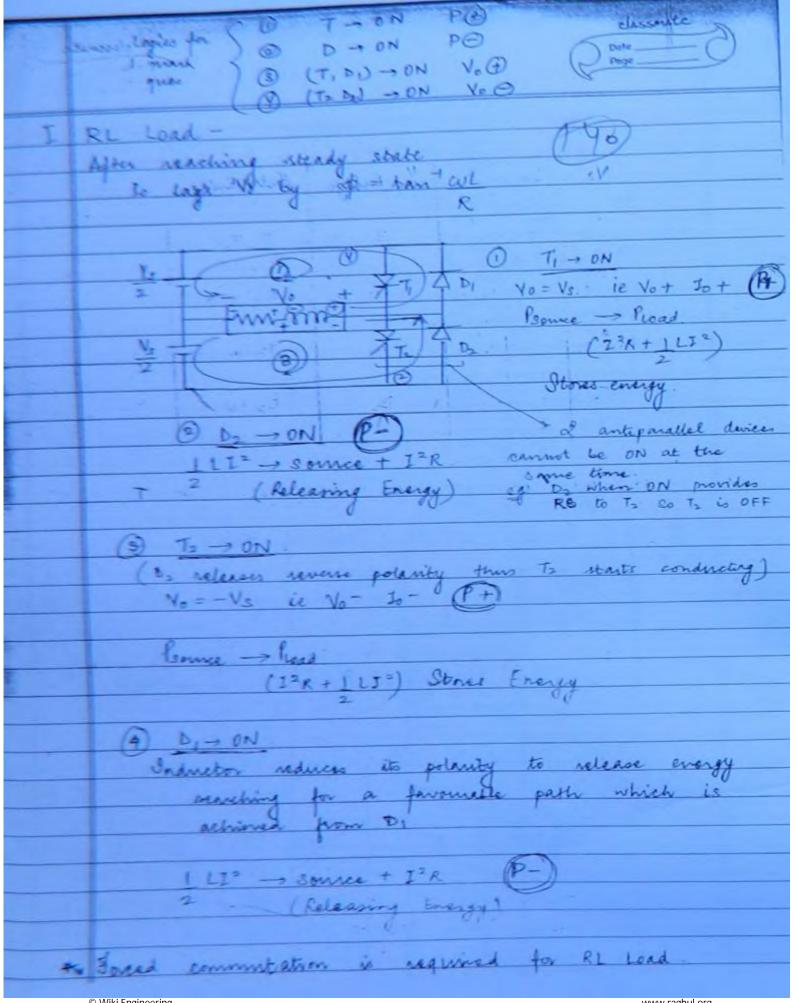


	DVdo = Vdo (cos x - cos (x + µ)) = 6 fels Io - 1									
=	2									
	2 (136)									
	i at &= 90° cuz ne get									
<u></u>	Ne get nummum									
	We get minimum pl'at $\alpha = 90^{\circ}$ ouz me get maximum ripple.									
	at $\alpha = 0^{\circ}$ cus ripplois is minimum									
-K	Ne get maximum μ at $\alpha = 0^{\circ}$ euz ripplois is minimum									
	held constant									
	> When other parameters are to 100									
	> When other parameters are at constant H tripple 1 when $0 \le \alpha \le 90$									
	The x 790 X 1 pt when 0 X X X Y 1014 \$1 (1)									
_ 3										
- 32	Vo = Vdo cos x - 6y LsIe - 2									
	Vo = Vdo [cosα + cos (α + μ)] -3									
	2									
	1~ 1~ 17 - 19									
	Io = Vm [coα - co (α+μ)] - (9)									
	2W Ls									
	M AVdo									
	m van 1 11 o T 7 o									
	2 2 Vm 1 1 LS 10 -10									
	2 21 1 5 7 10									
	3 3 VML 3 0 LE 10 0									
	6 3VML									
	T									

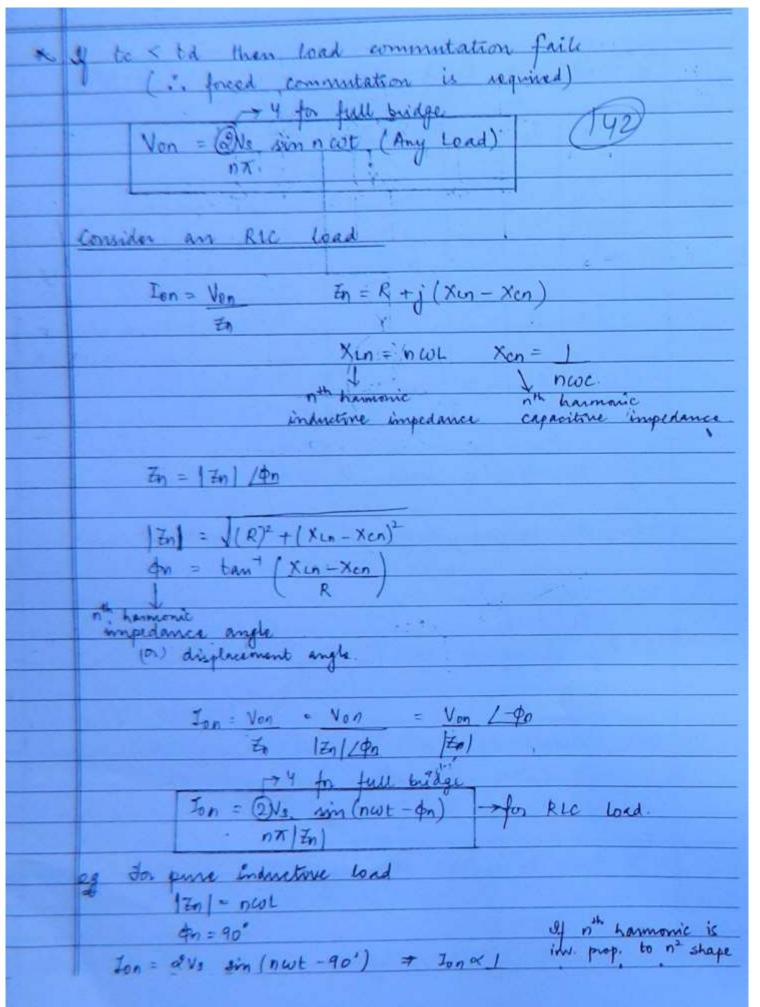


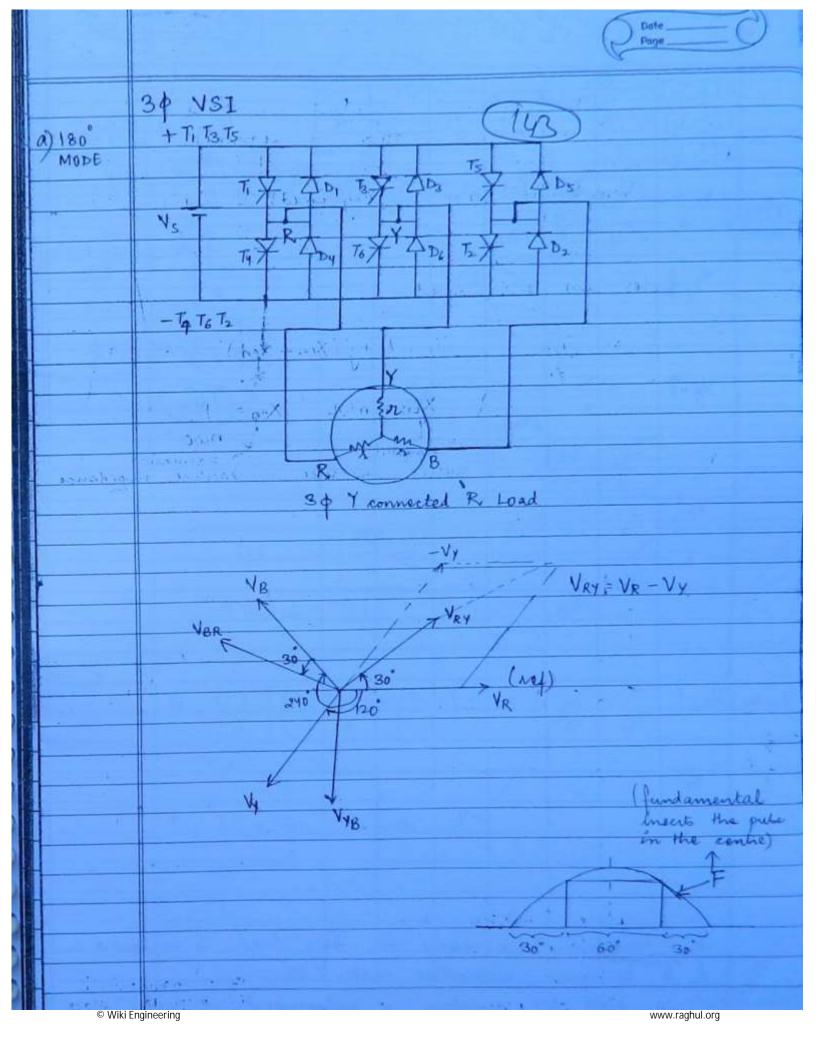


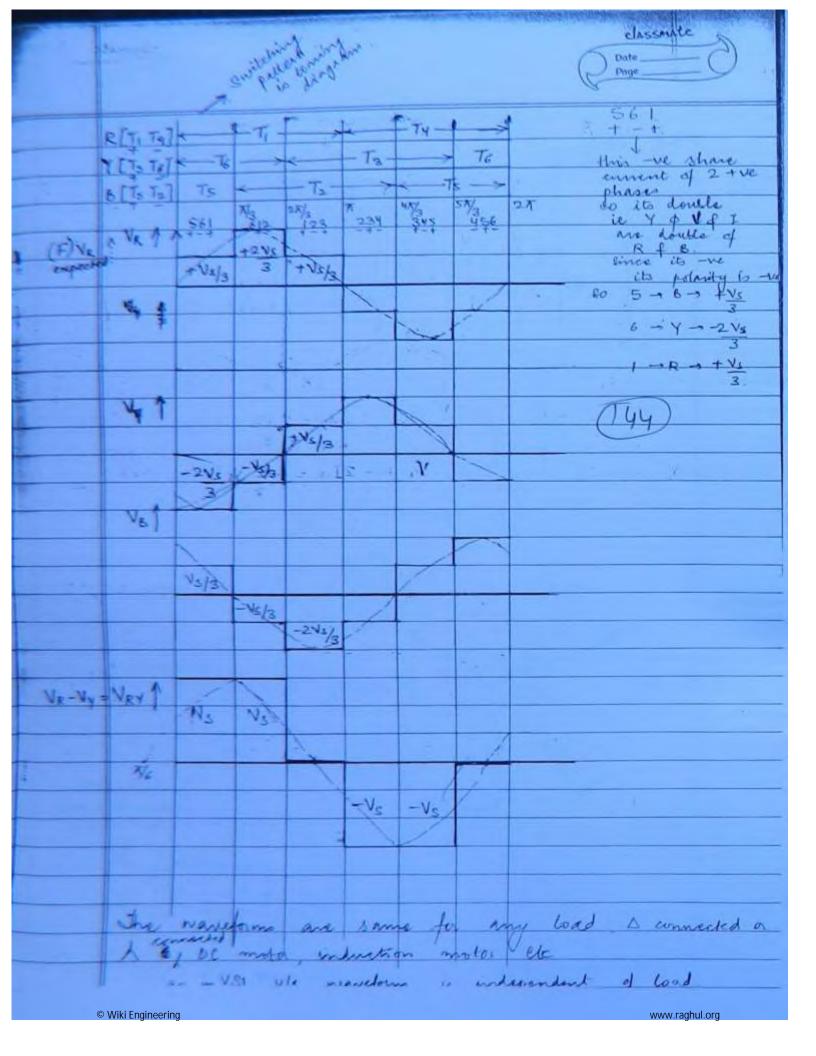


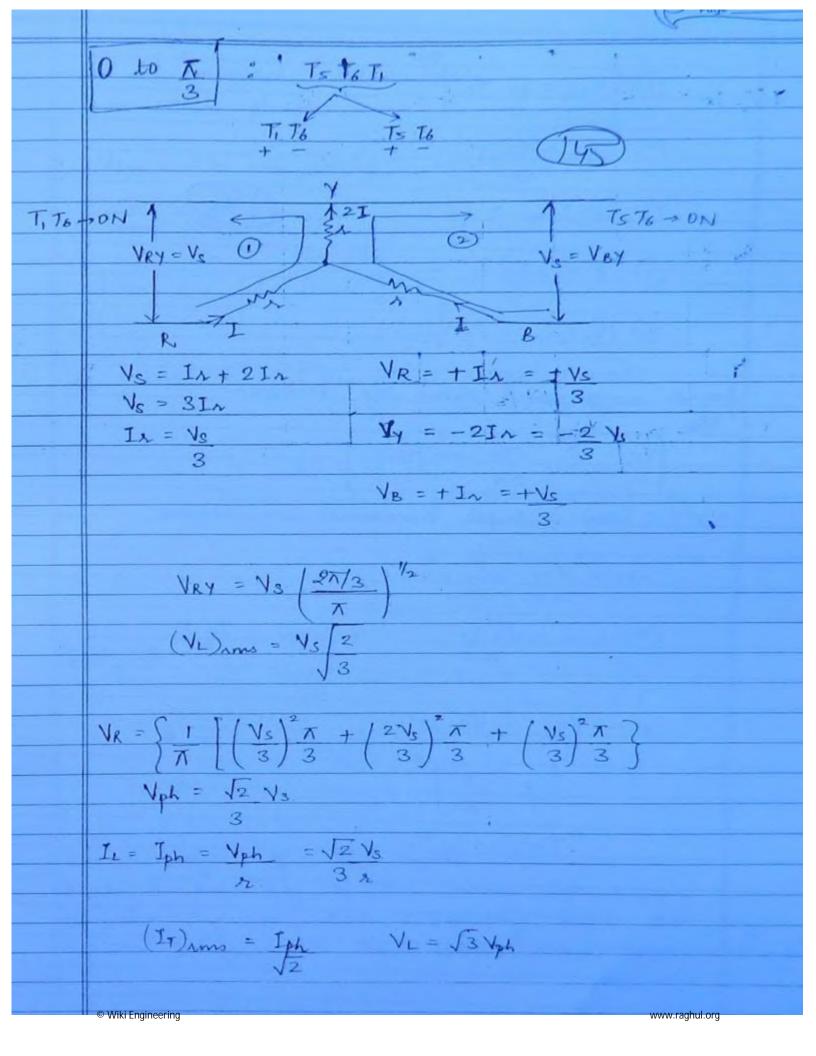


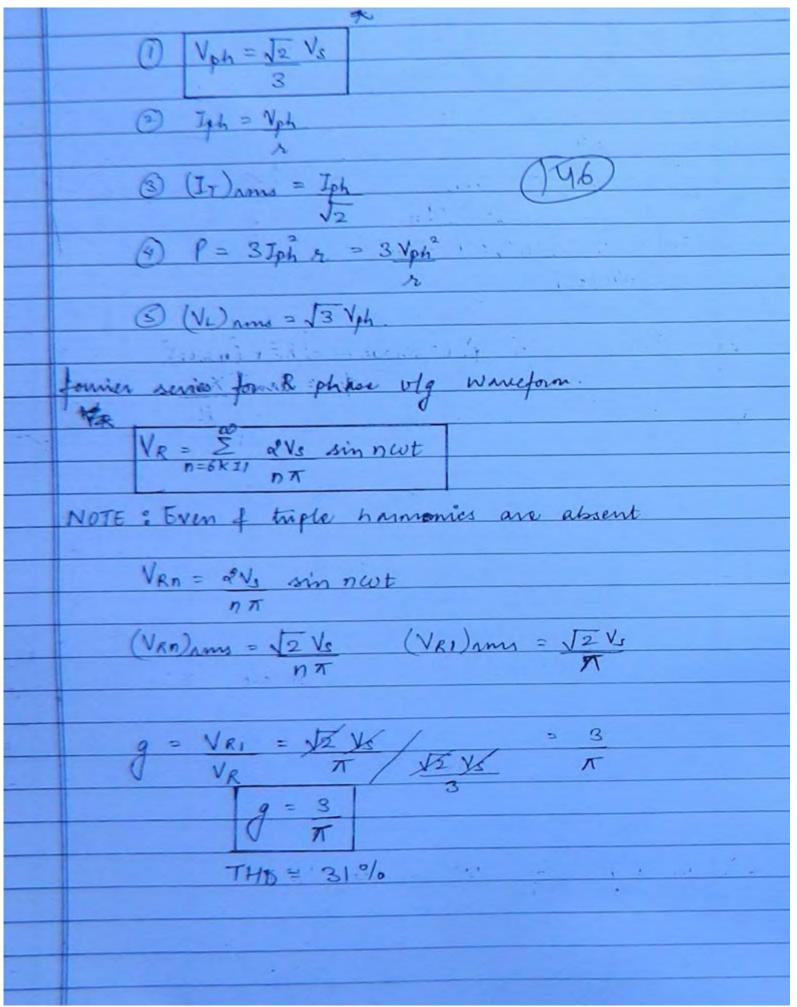
						6	Starys.				
	X, k	J. i.	Lina	100	in Table	(14)					
	R Switching Logic Table (141) Device (ON)										
	Vo Jo P 1/2 Bridge Full Bridge										
			50		0						
		T. D.	+	TI Ta	万	T, T2					
		1-	3	lv i							
F	1030	T) + b)	-44	Di Da	. b ₁	0,02					
-	Land.		.)			S. Art St.					
(5)	11.	173 Dz		Ti Th	T2.	TaTy -					
	1										
		T2 D2	+	Di Da	D2.	D ₈ Dy					
					-1-						
							_				
	for all leading loads it starts with T										
	for all lagging hoads it starts with D										
7 77	I RLC (Overdamped)										
	KI										
1	$X_L > X_C$										
18	To lags No by $\phi = \tan^{+}(x_{L} - x_{C})$										
	+				Link w						
Ti	1. R	ic (u	Inderd	amor	d)						
		X	. > 1	4							
	1	o lae	Vo	ьи	p = tant/X	- Xc)					
		-		0	,	R.					
	on To leads to by $\phi = tan^{-1} \left(\frac{X_C - X_L}{R} \right)$										
	Cotc = p										
	bc = 1 tant/xc-xc)										
	1.3 1 0 /										



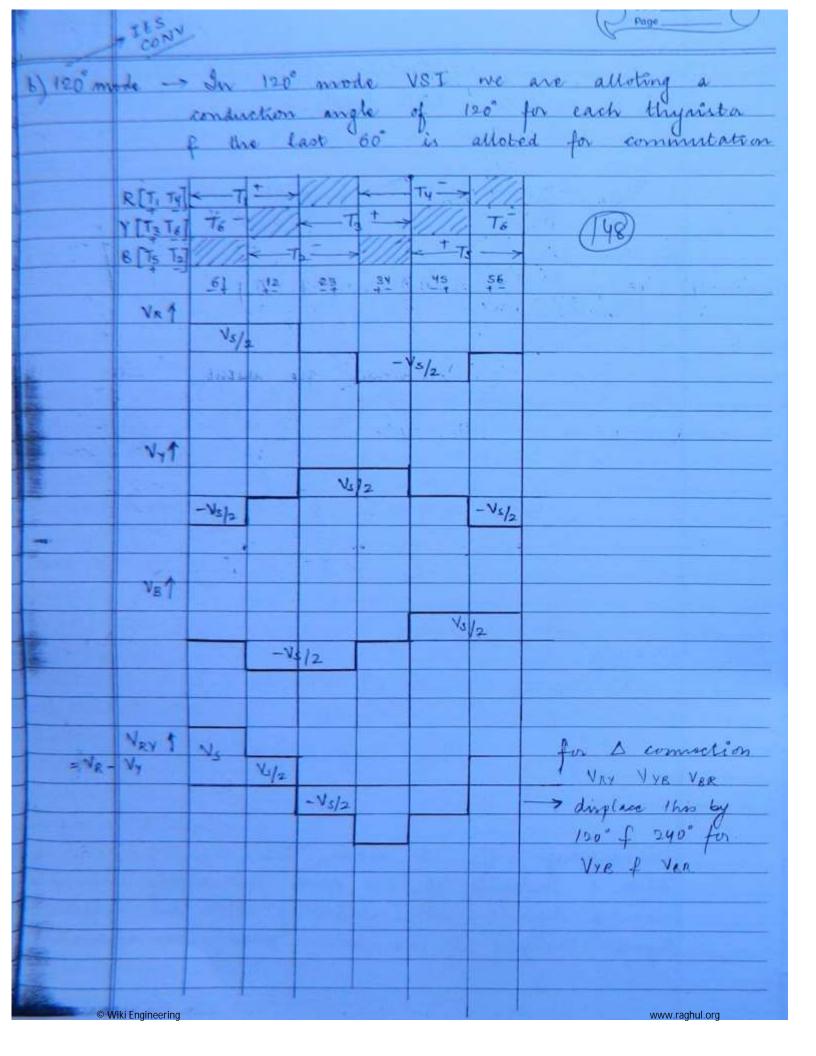


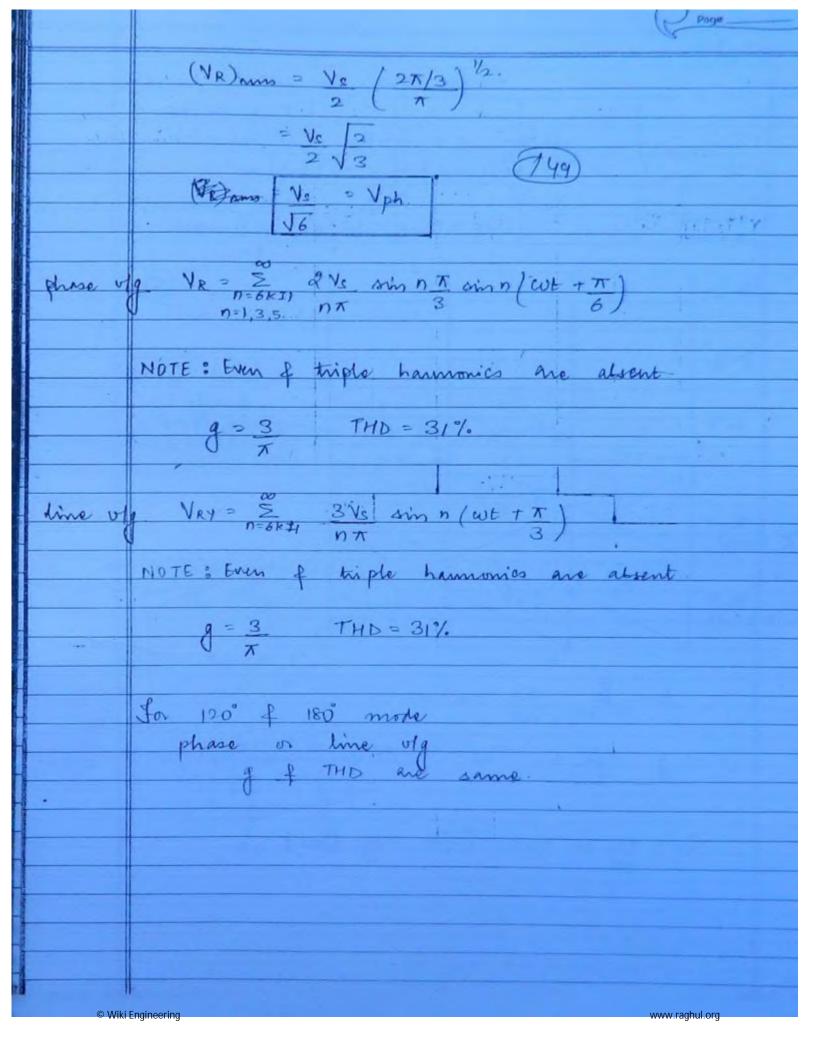


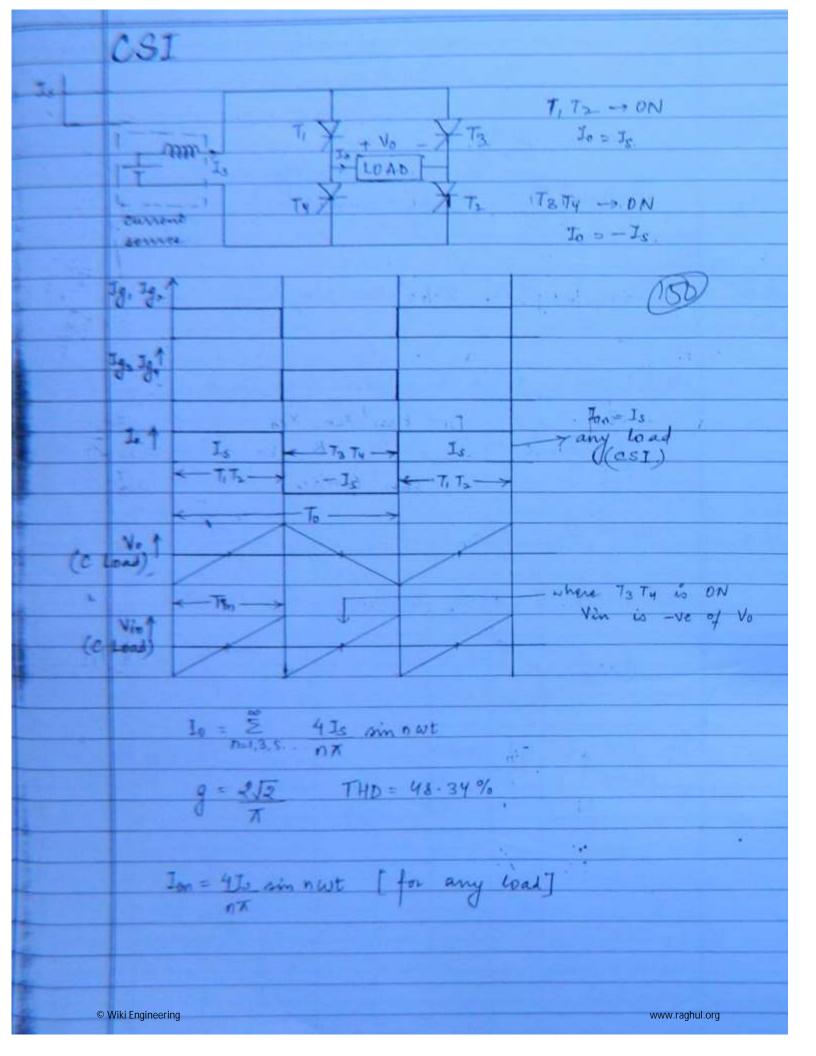


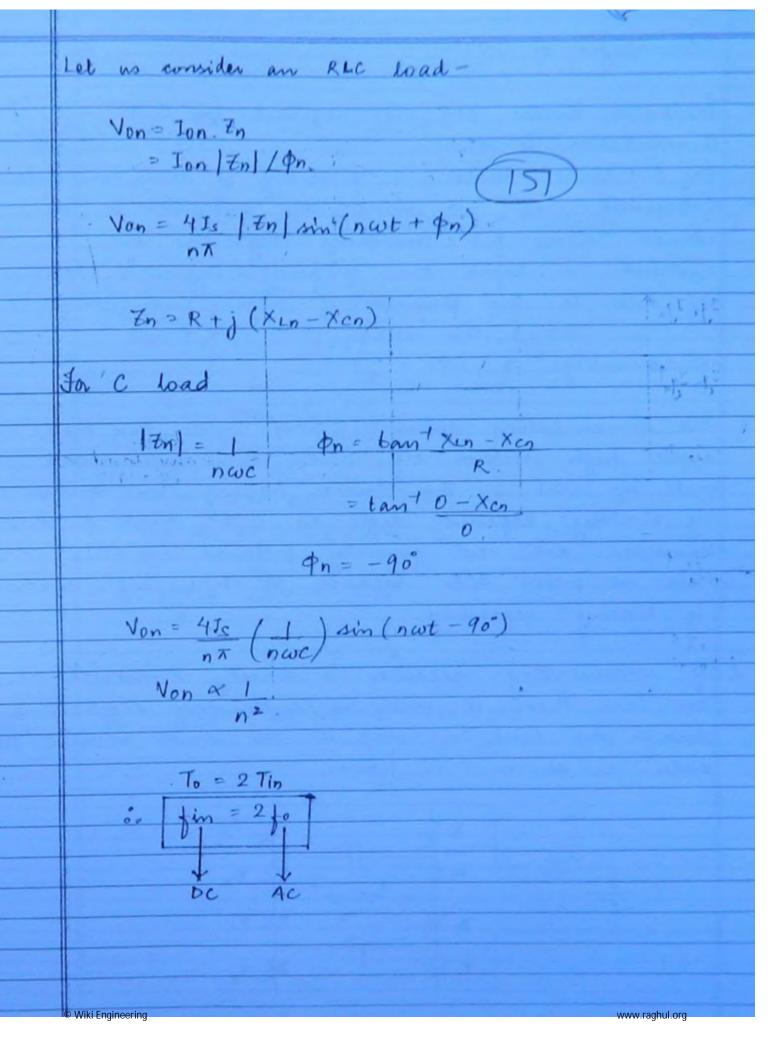


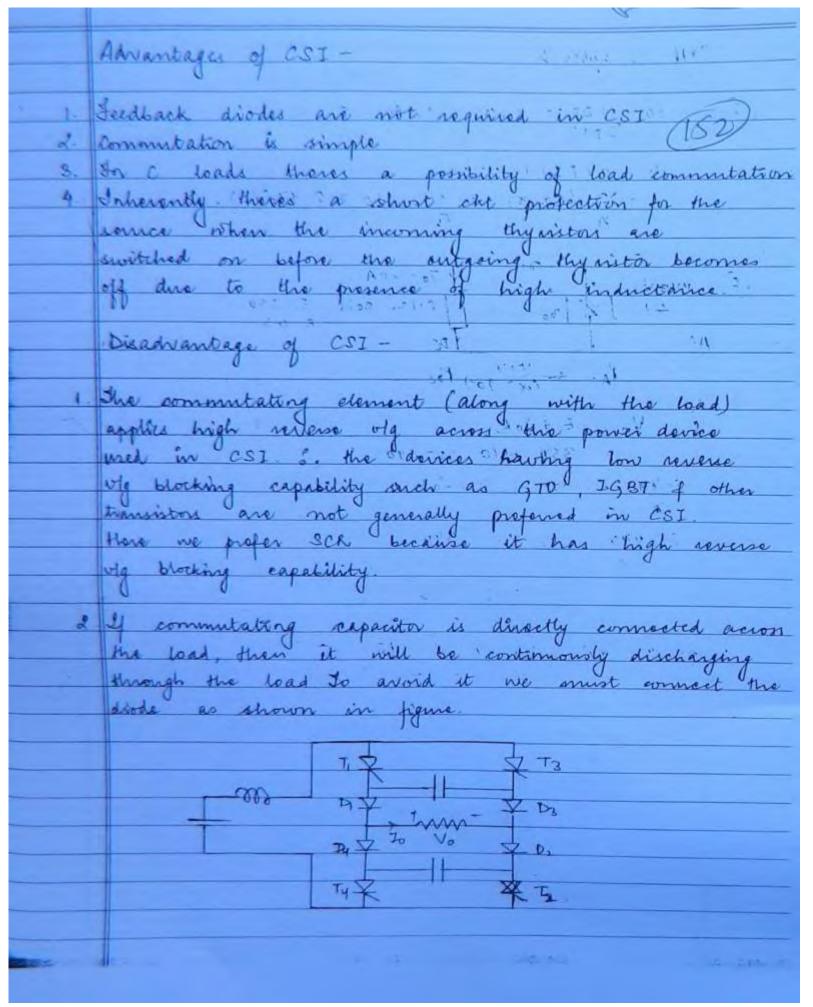
lot us as a DIA A I
Let us consider, RLC load
in each phase.
Va - By (Ti a)
VRn = 2 Ve sin nwt (47)
IRn = VRn - VRn
$\frac{Zn}{ Zn /4n}$
In = 2 ve sin (nwt - pn)
$n\pi z_n $
1 2 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
eg I.M Ti) per phase = VRi2+ (nWLI)2
on = tan Xin
<u> </u>
for n = 1 (E)
Diode conducts for \$ = tem XL for RL load
P b - 1 - 1 v v 1 pla 1 v
of \$= laint xc-x1 for Rlc load
x
VRY = $\sum_{n=1,3,5} \frac{4 \text{ Vs}}{n\pi} \frac{n\pi}{3} \frac{sin}{n} \frac{n}{n} \left(\text{wt} + \pi \right)$ $n=6k\pm 1$ $n\pi$ 3
NEV 1-1,3,5 NT 3 M (60)
0=6x11
g = 3 THD = 31%
Disadematores at 180° mande NCT
Disadvantage of 180 mode VSI
There a possibility of S.C across the supply when
thyrister belonging to the same phase stops conducting
thyrister belonging to the same phase stops conducting

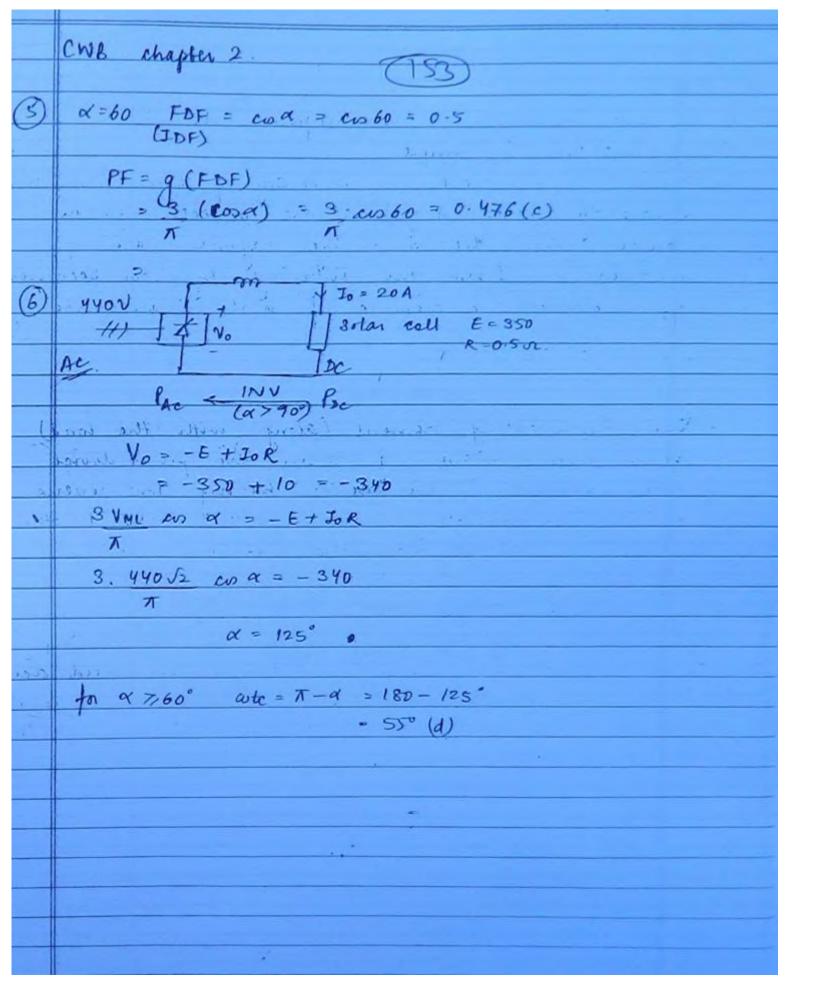


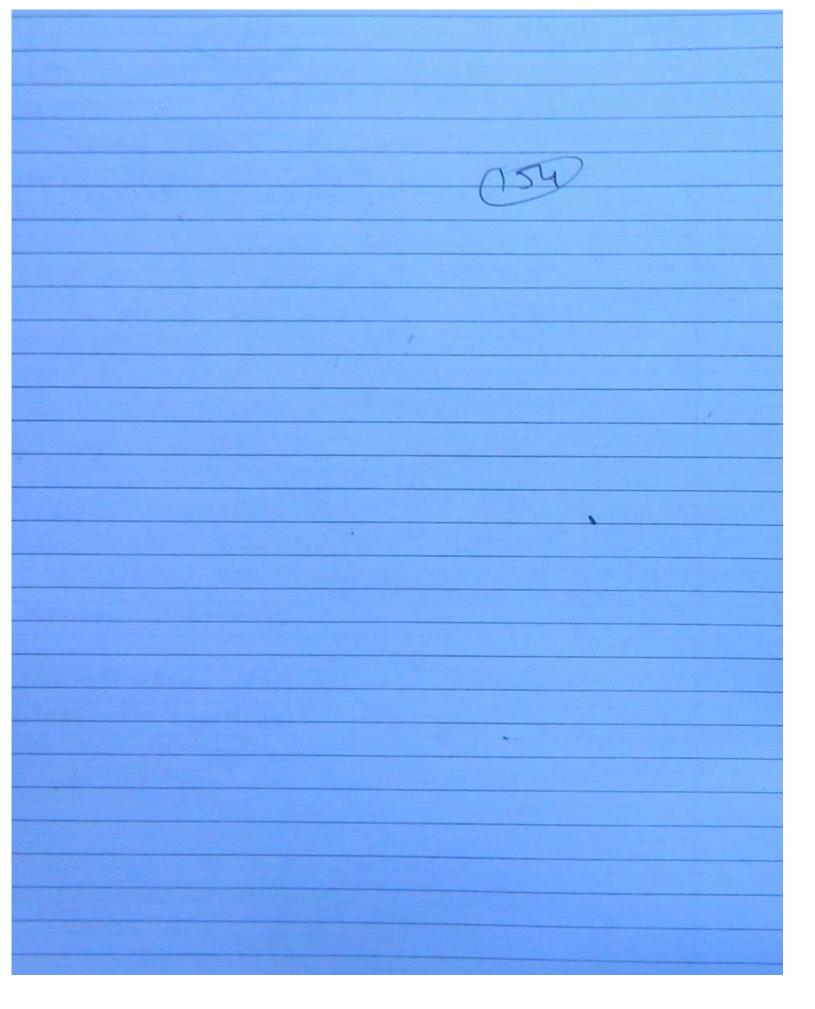




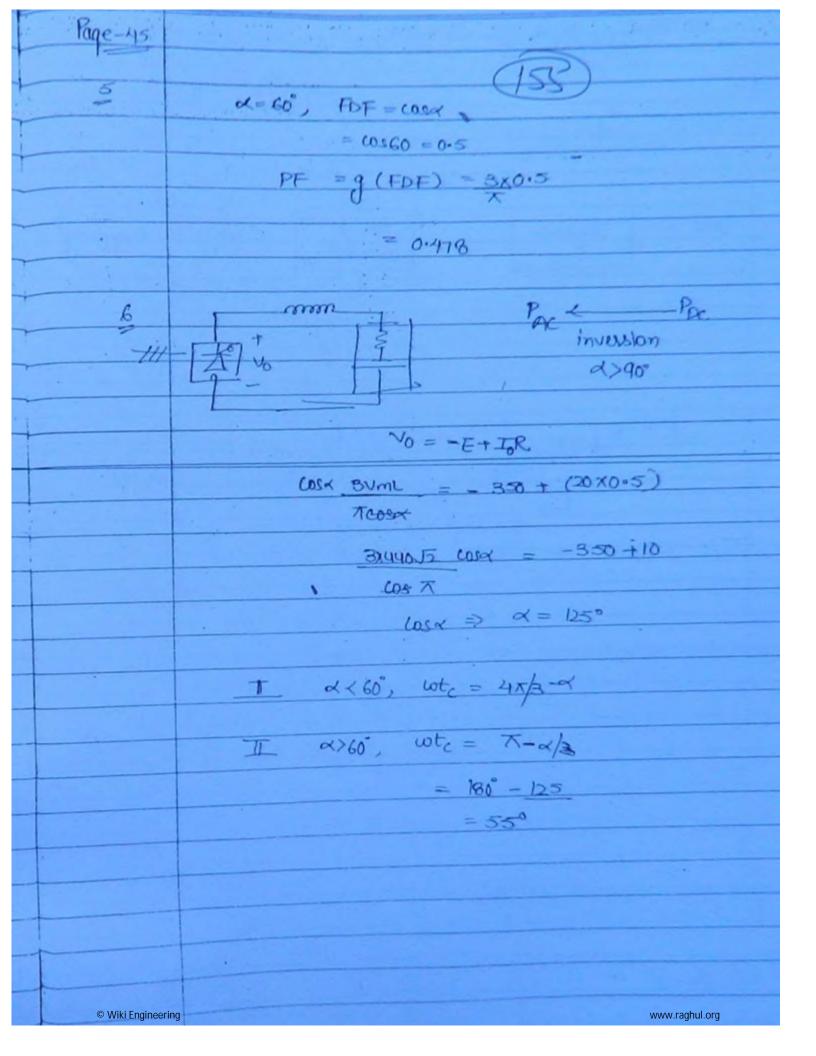




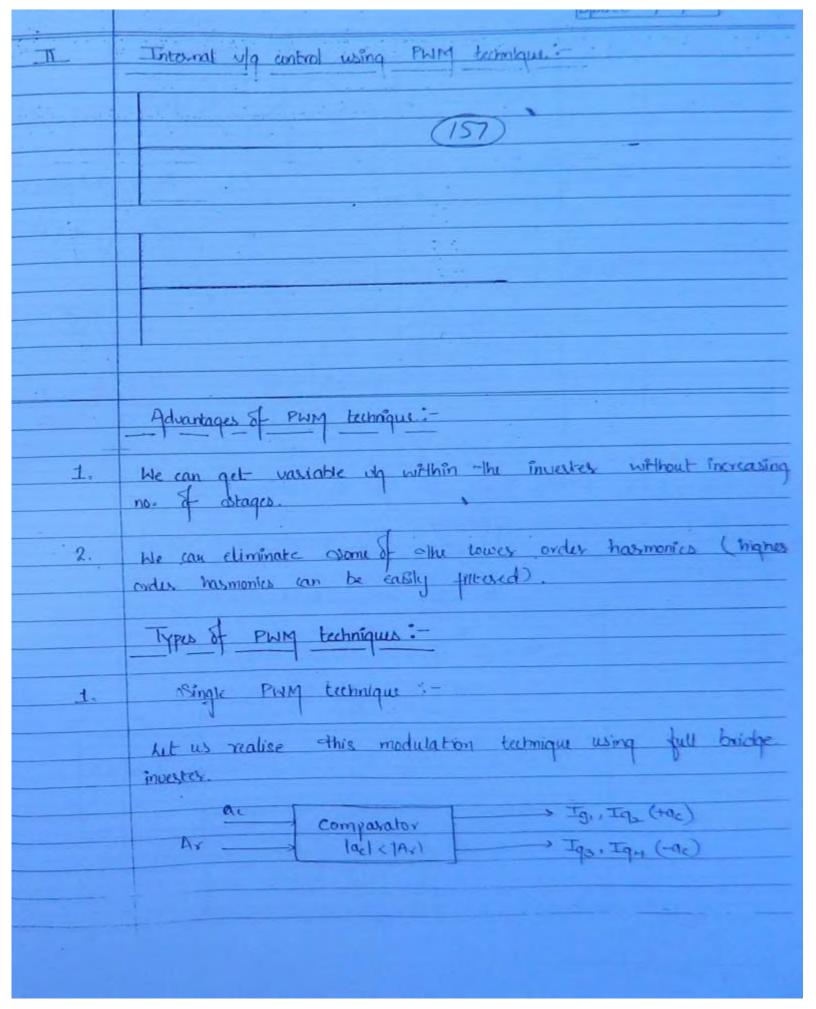


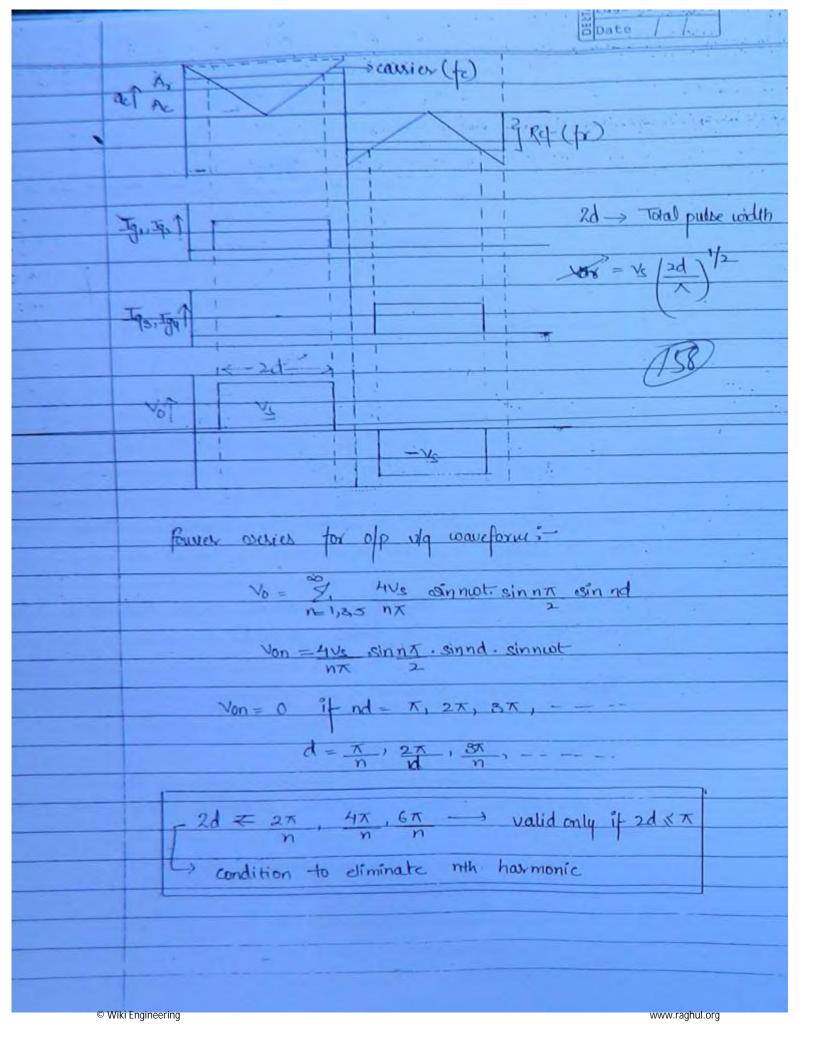


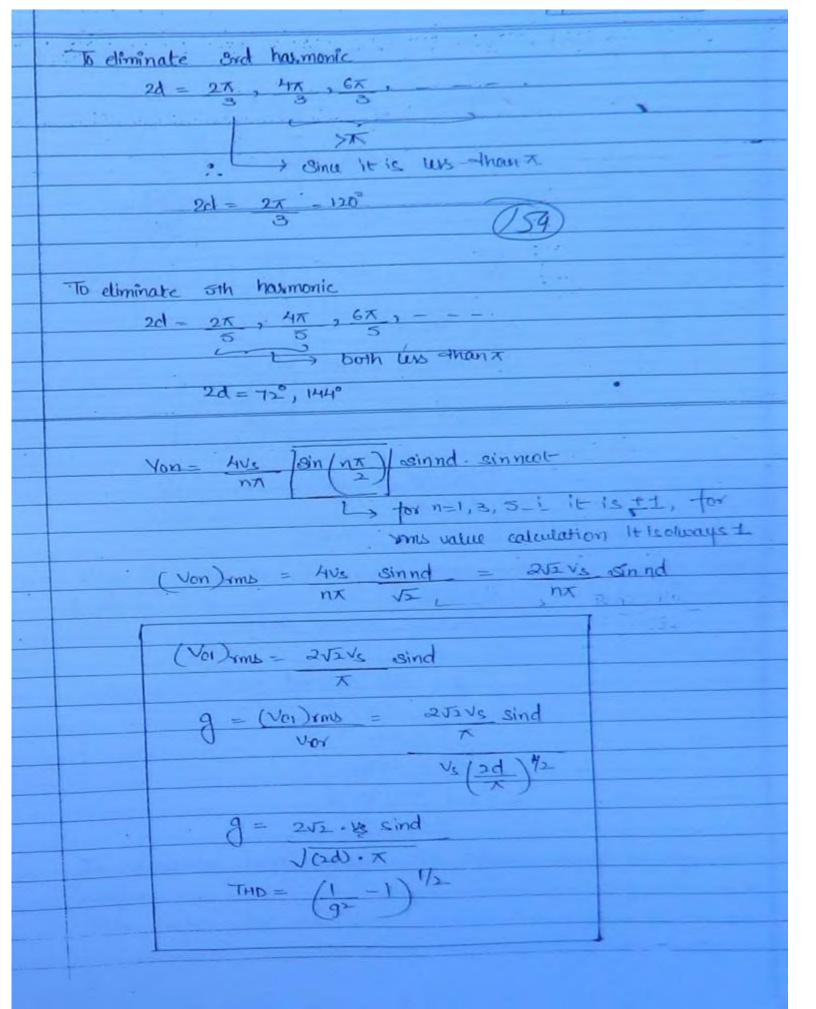
© Wiki Engineering www.raghul.org



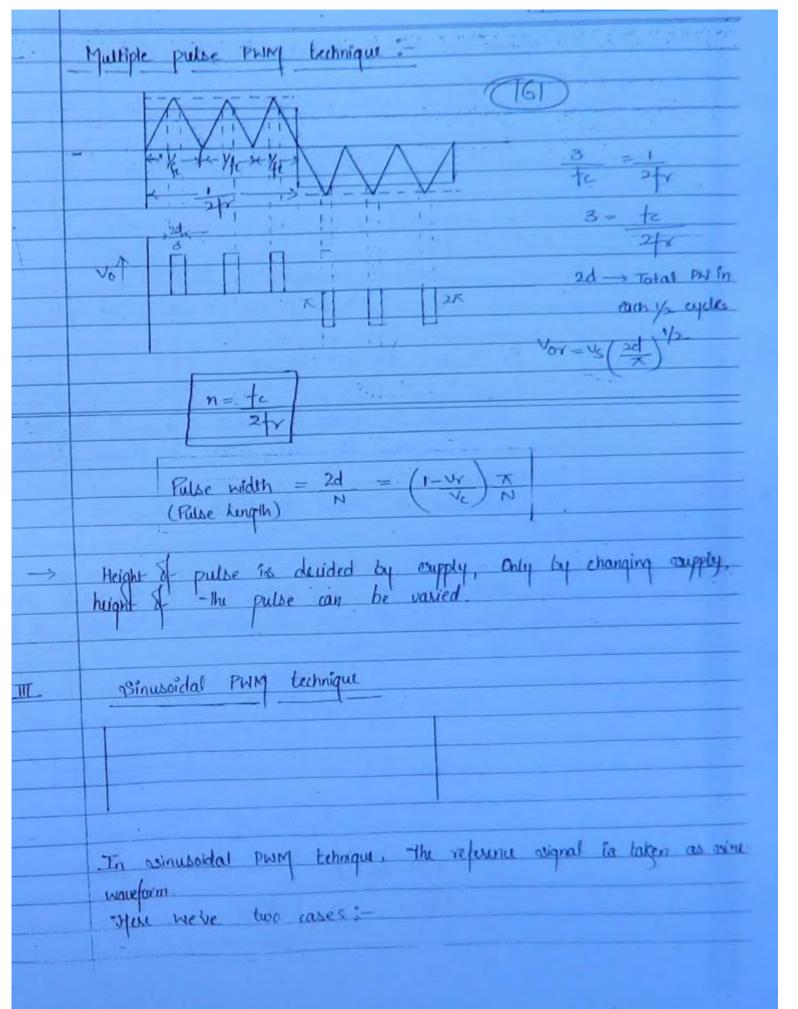
VOLTAGE Control of Invester Extranal control It is like a 1.e. charge who in v/g a) A/c 0/9 chang tixed DC Invester controller vac 6) Fixed DC Chopper Investor De level will change. © Wiki Engineering www.raghul.org

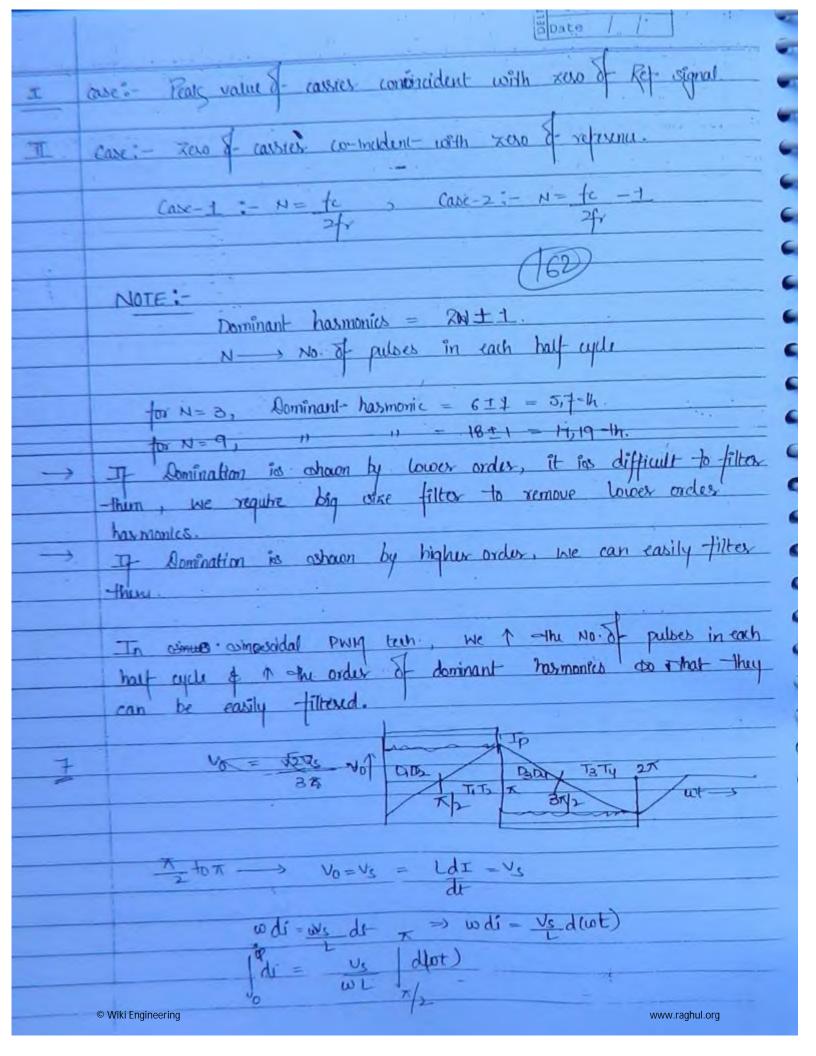


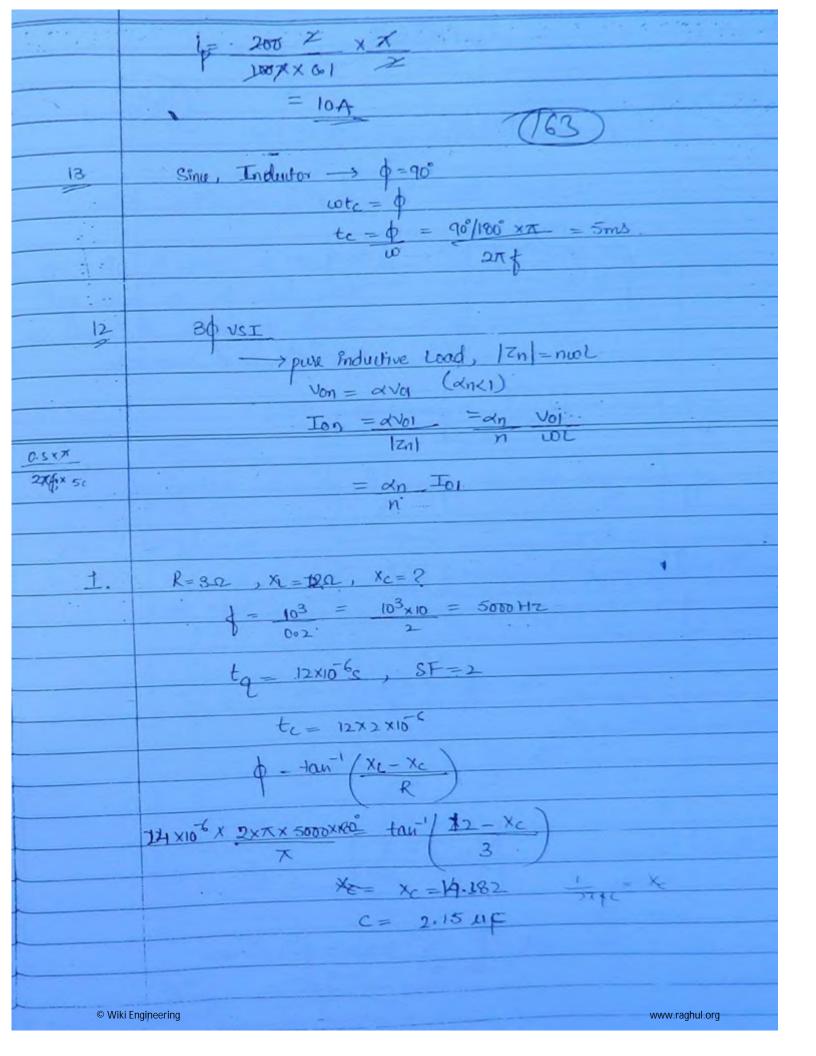


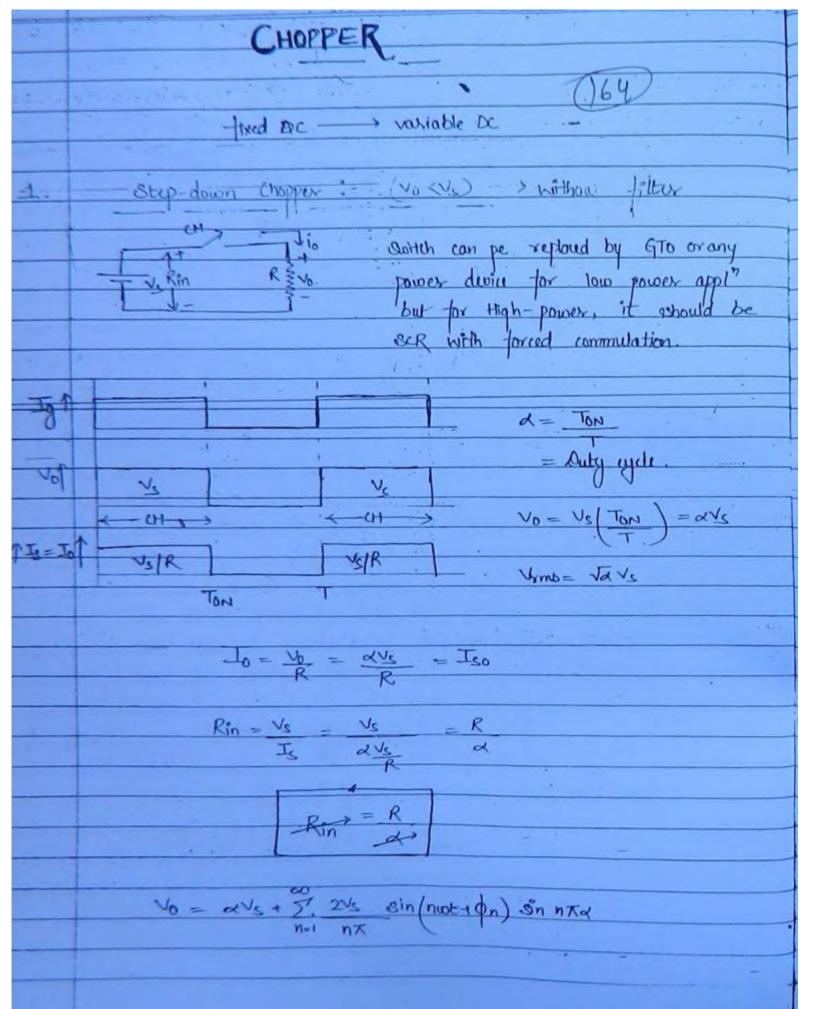


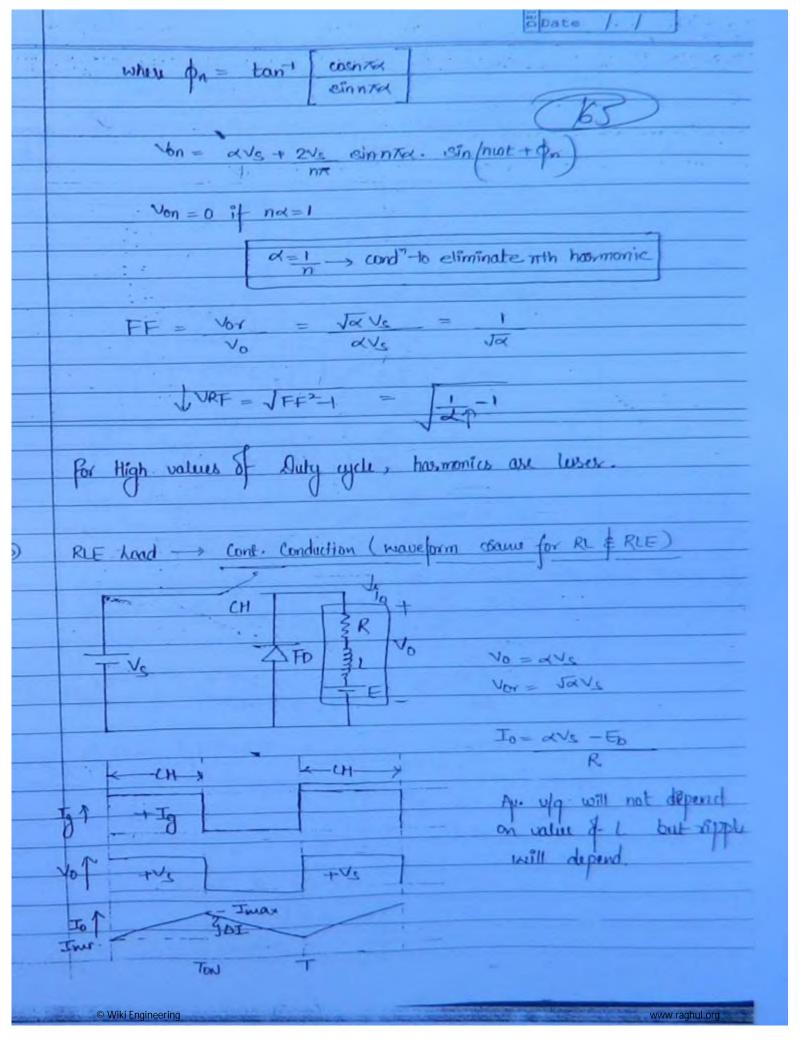
21 - 2 - 120 Vs = IV (Vor)mes - 2/2 ve sind = 25_ sin60° = 0.78 2d = 72° or 144° (V03) rms = 252 Vs sin 3d (.Voi wax) = 252Vs (Vos) - sinsd (VO) Max =19.6% 2d = 150° (VOL) = 252 Vs sind 9 = 252. 18 sind J(2d). T THD = 0.82 =3183%

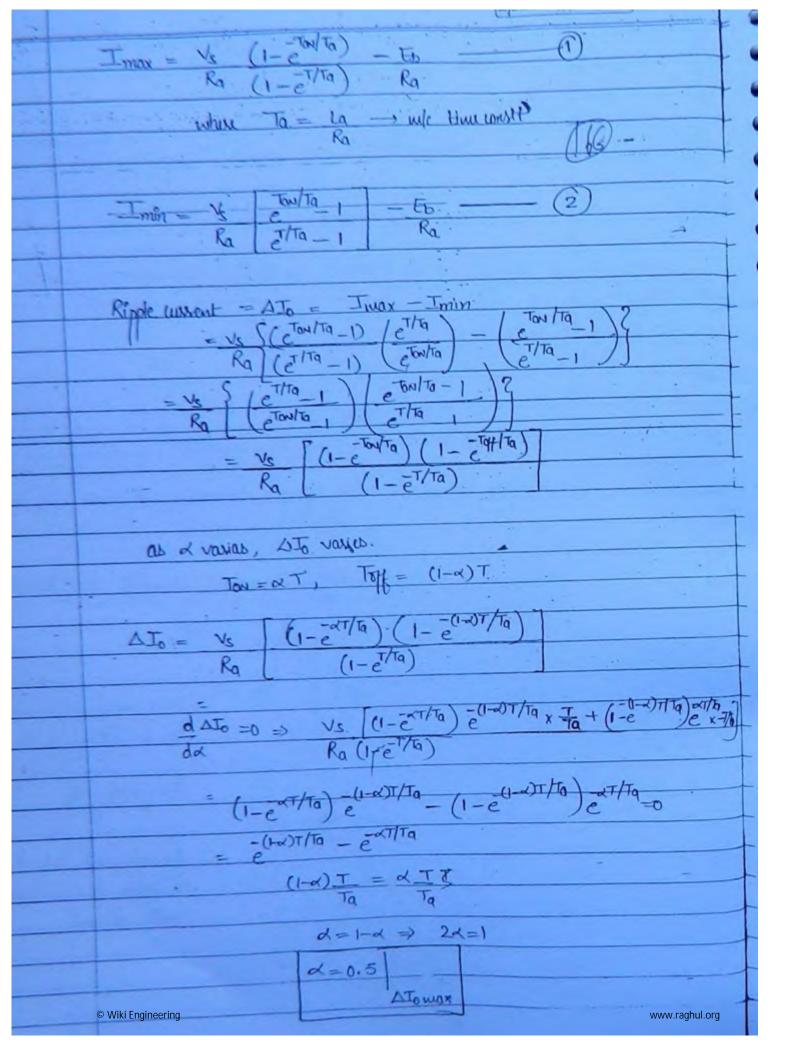


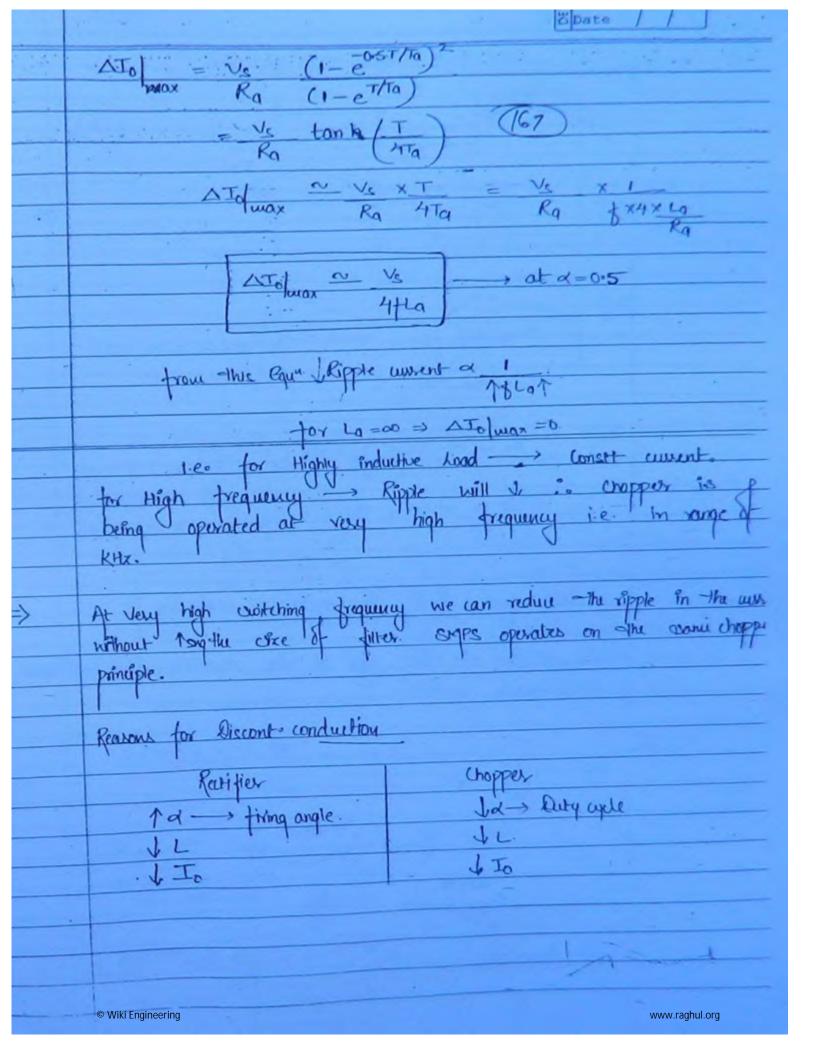


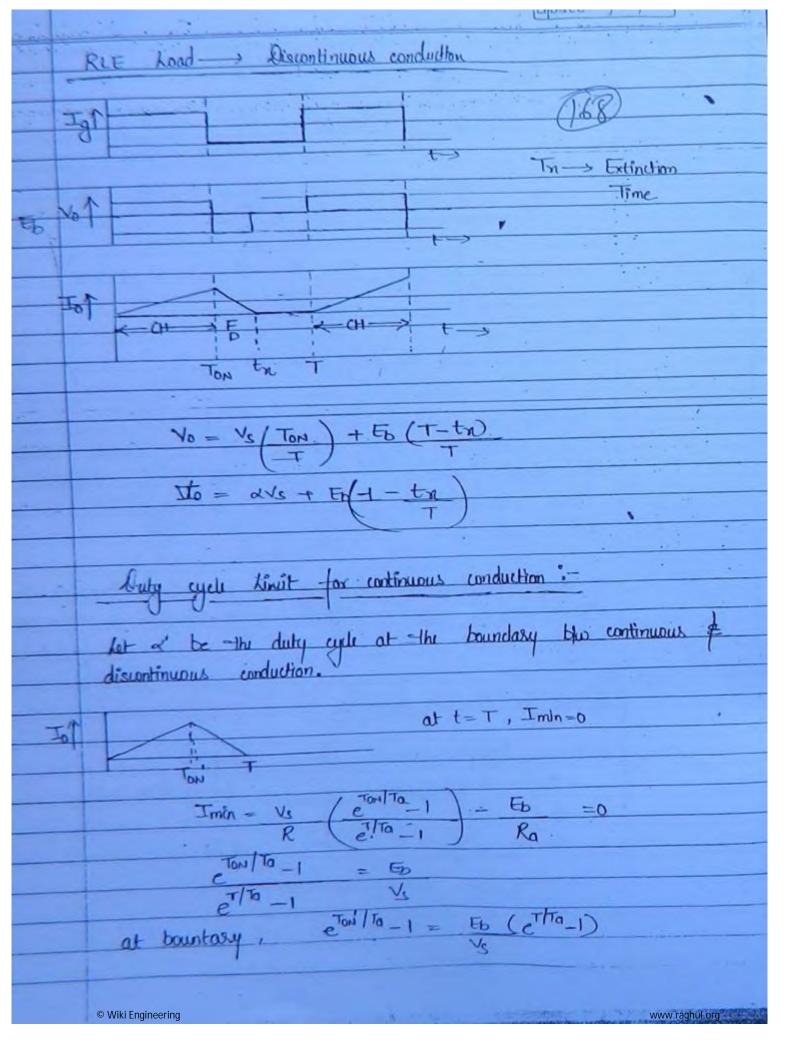


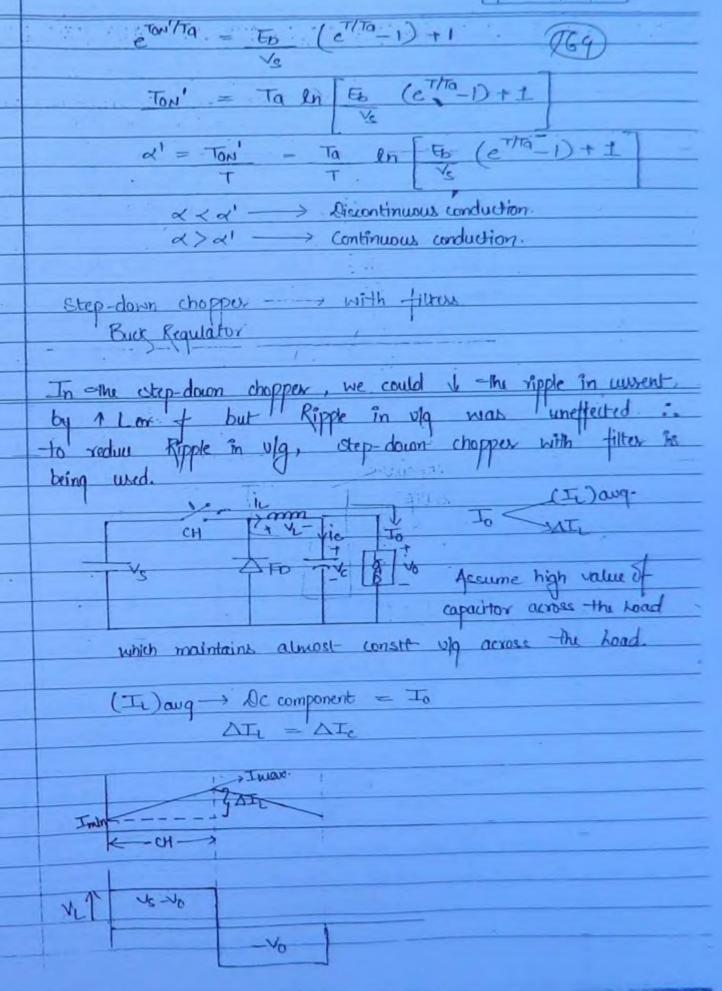


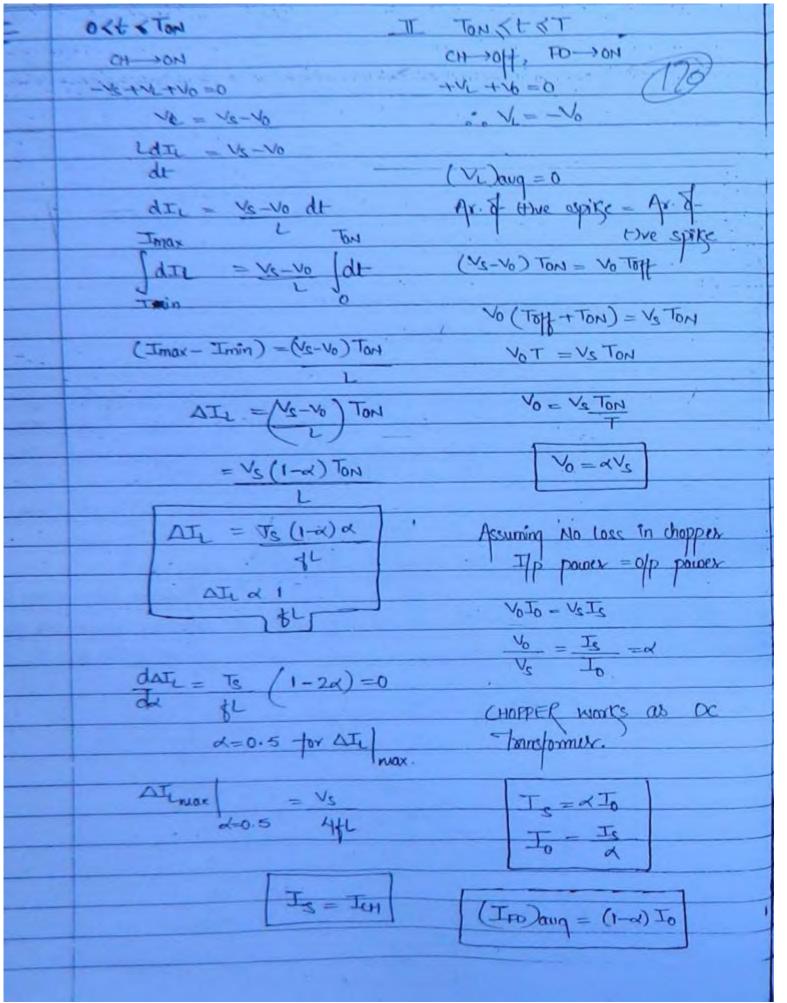


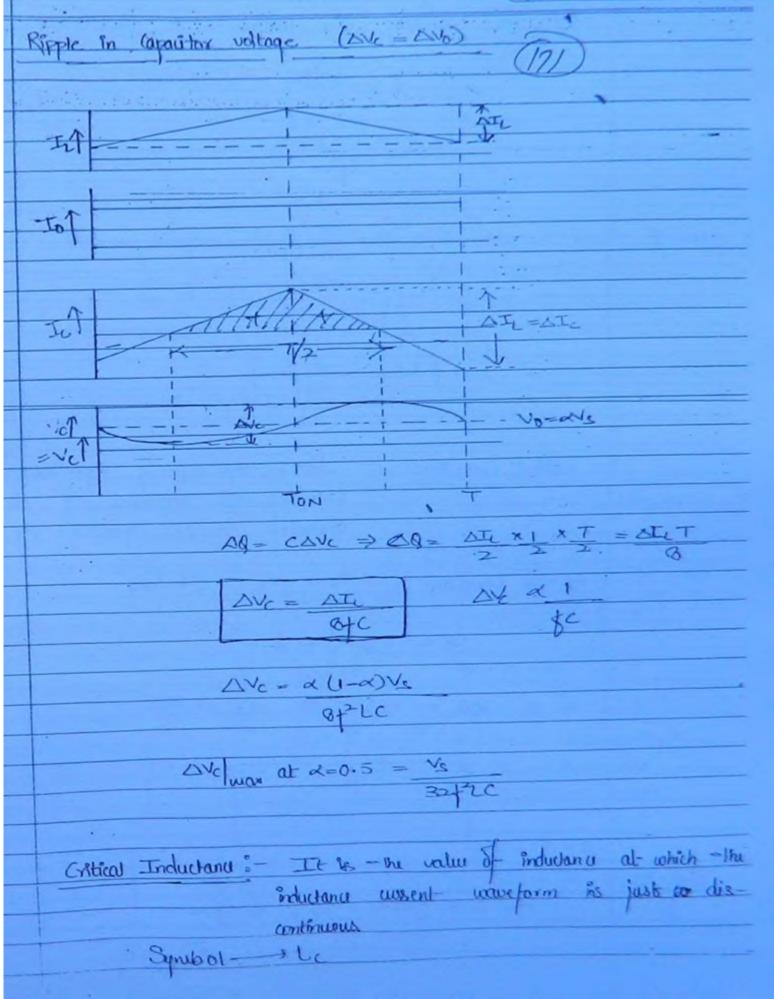




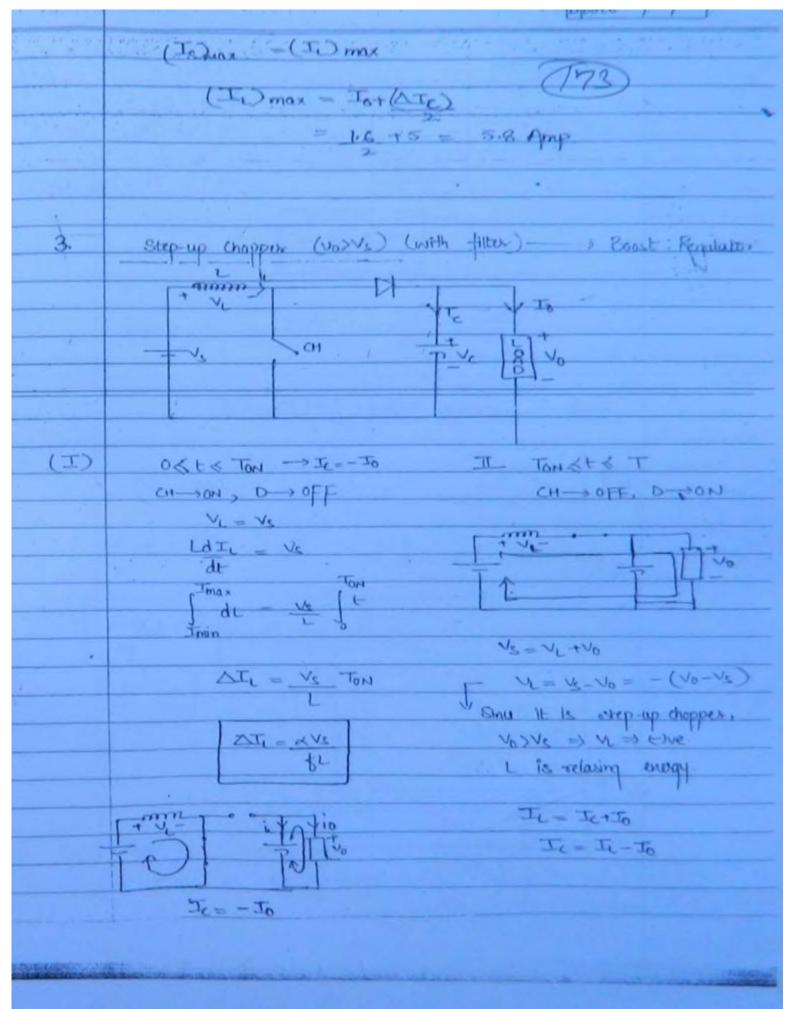


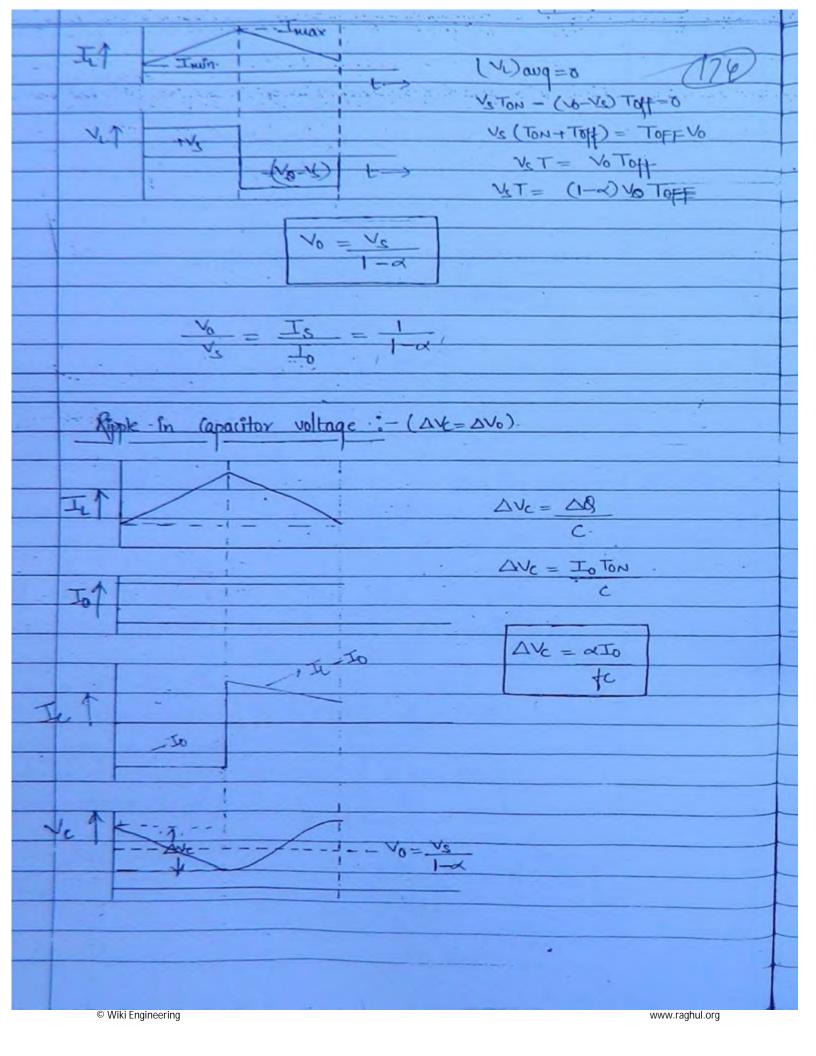


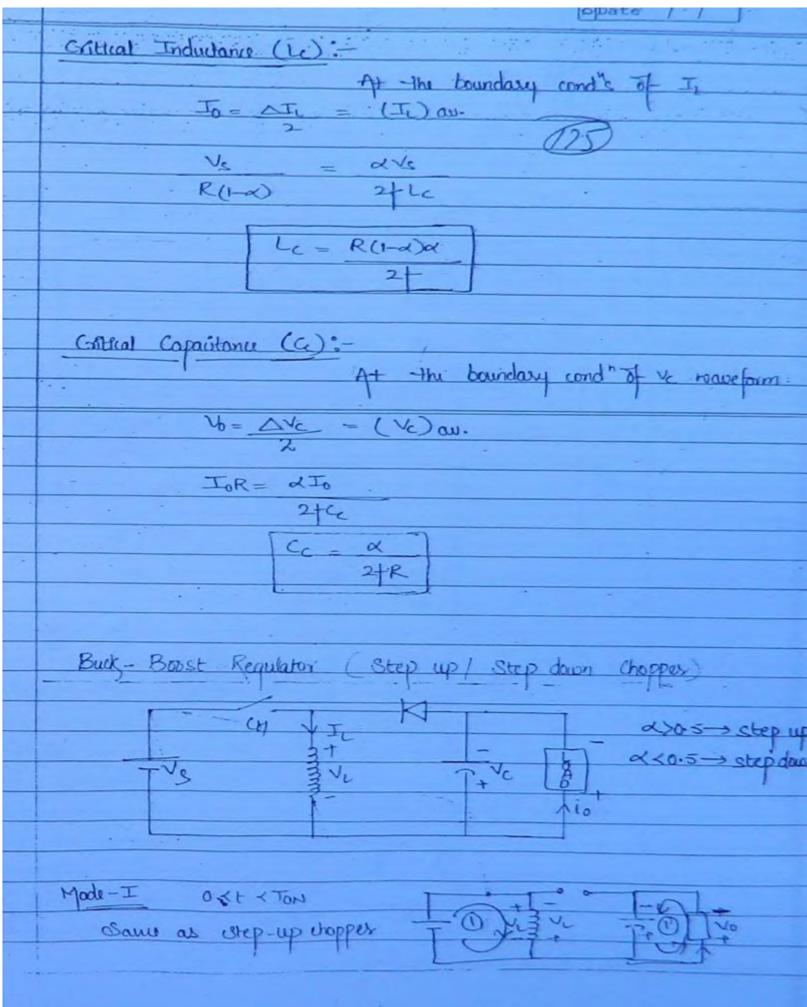


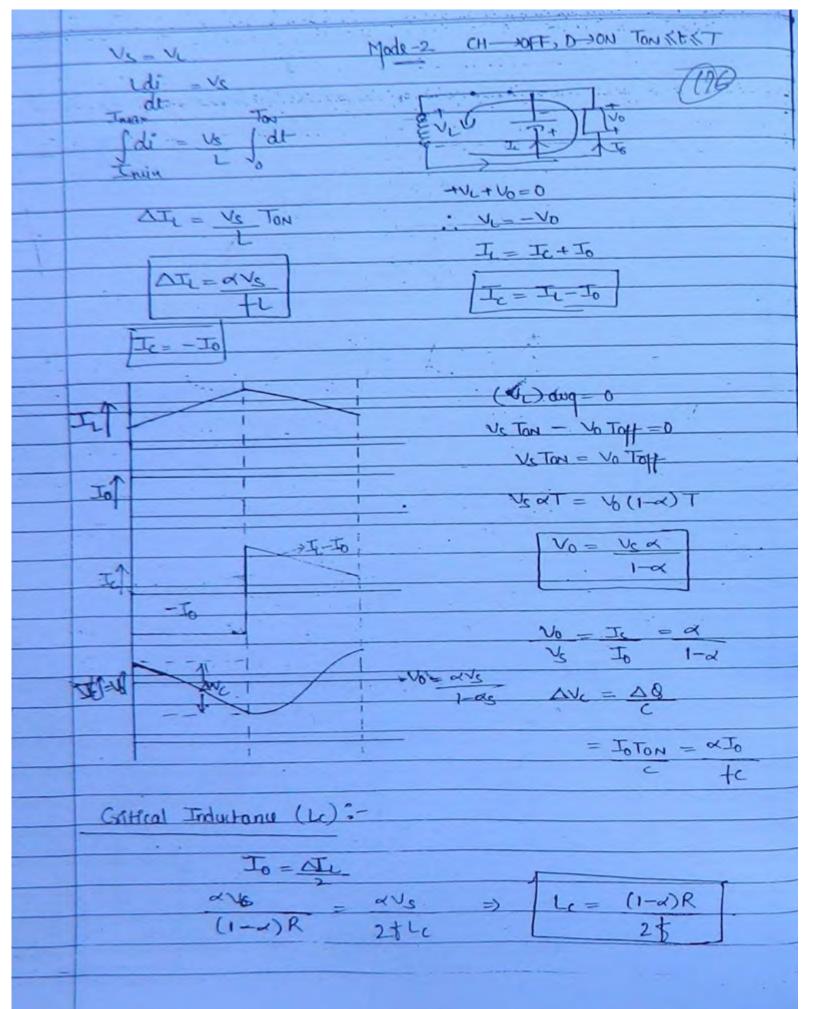


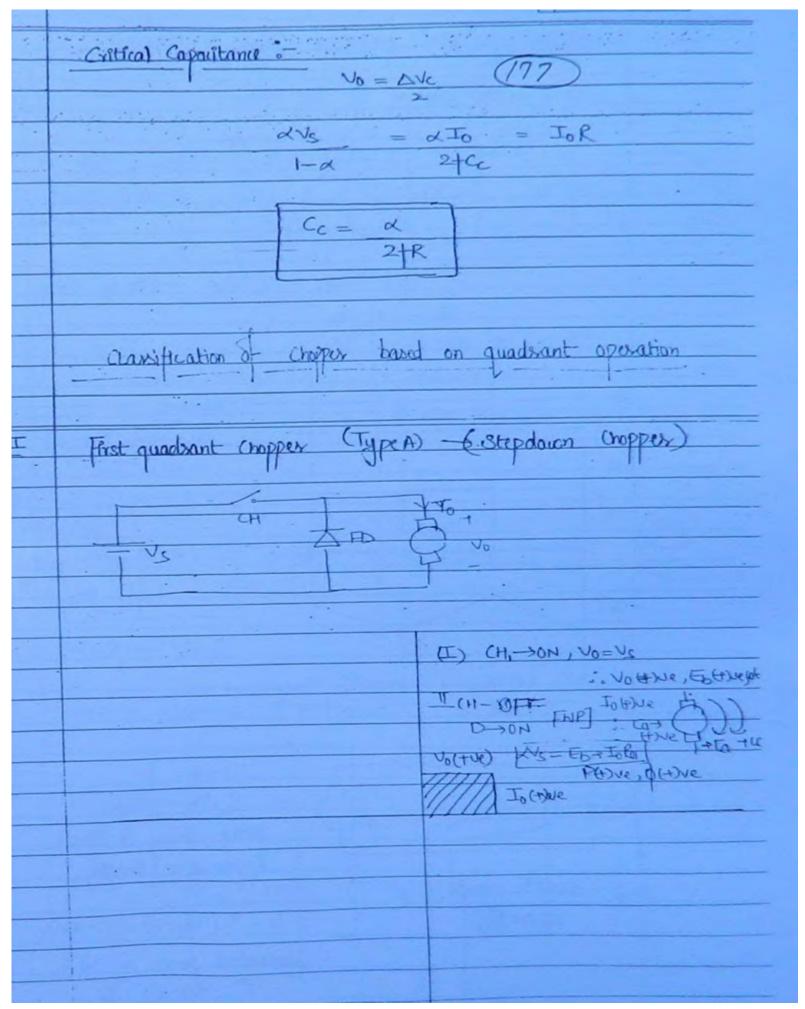
At the boundary you continuous of discontinuous continuous - - - - - - - - (I) ang. Jo - 26-2/4 L-UNR Gotten Capacitance: - It has the value of Capacitance at the boundary b/w continuous & discontinuous conduction for the capacitance up waveform. At -the boundary :- Vo = OVc = (Vc) and Cc = (1-2) d= 0.5, DIc=1.6, To=5A © Wiki Engineering www.raghul.org

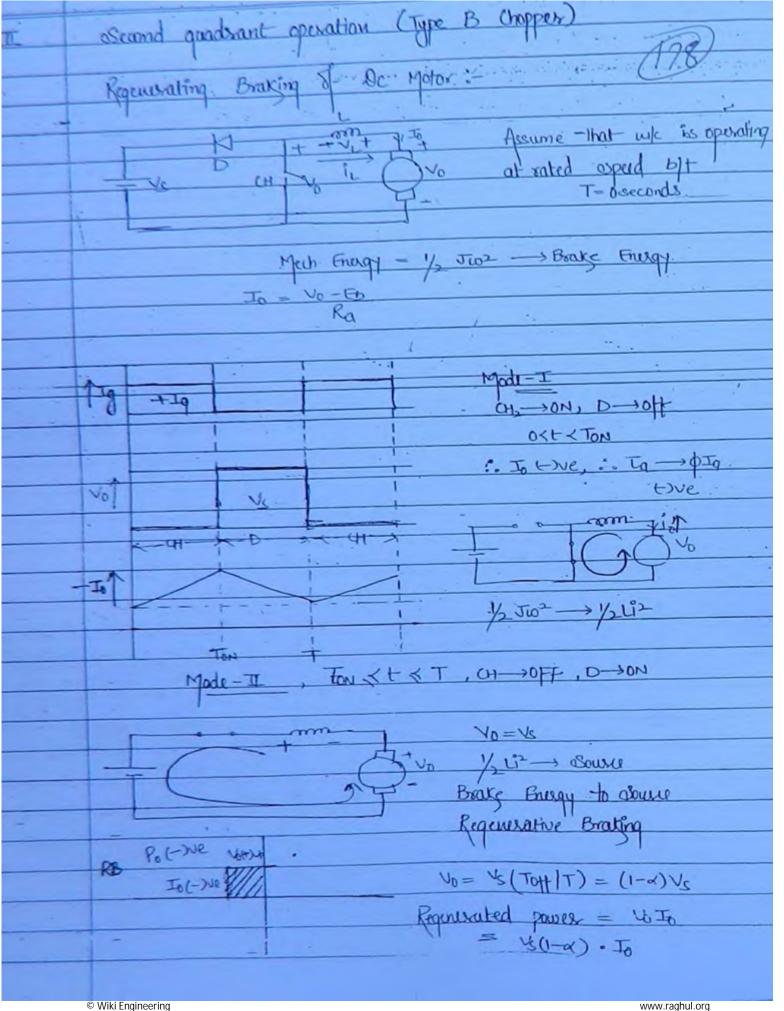


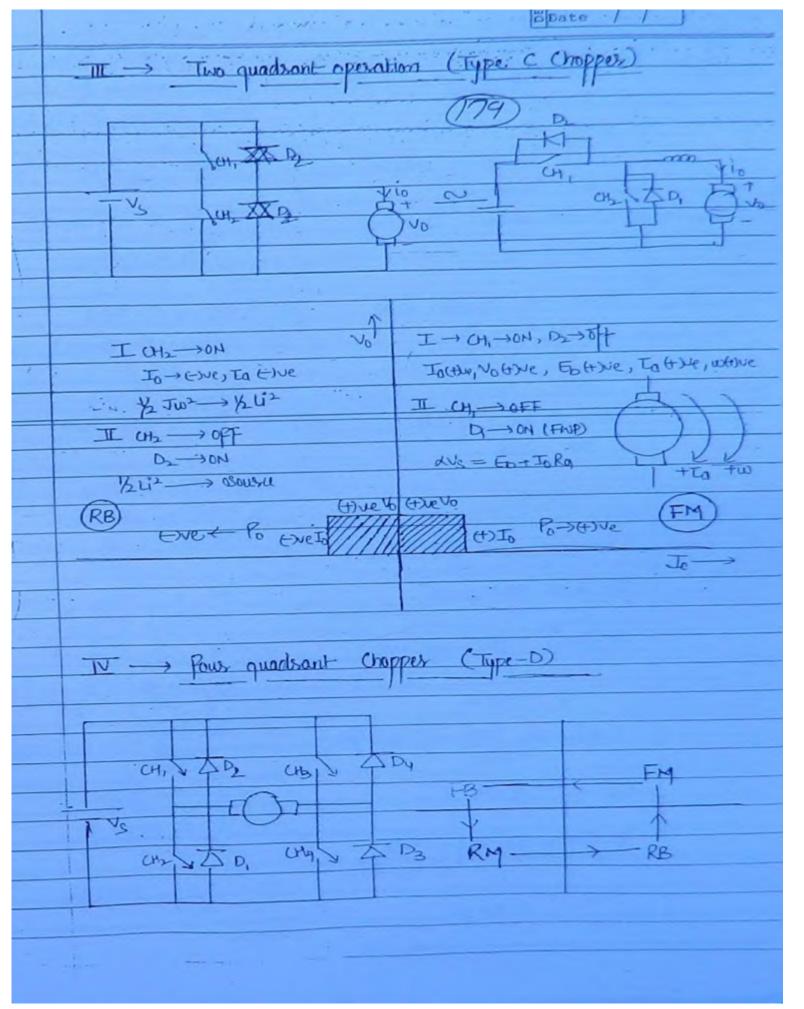


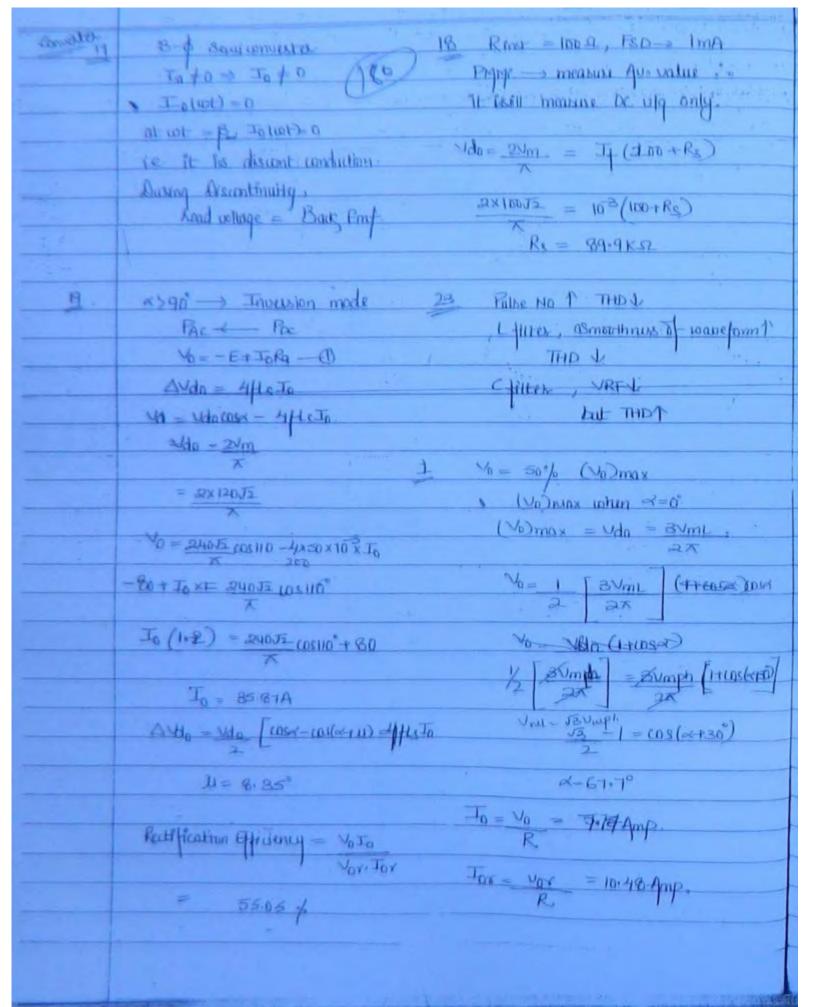


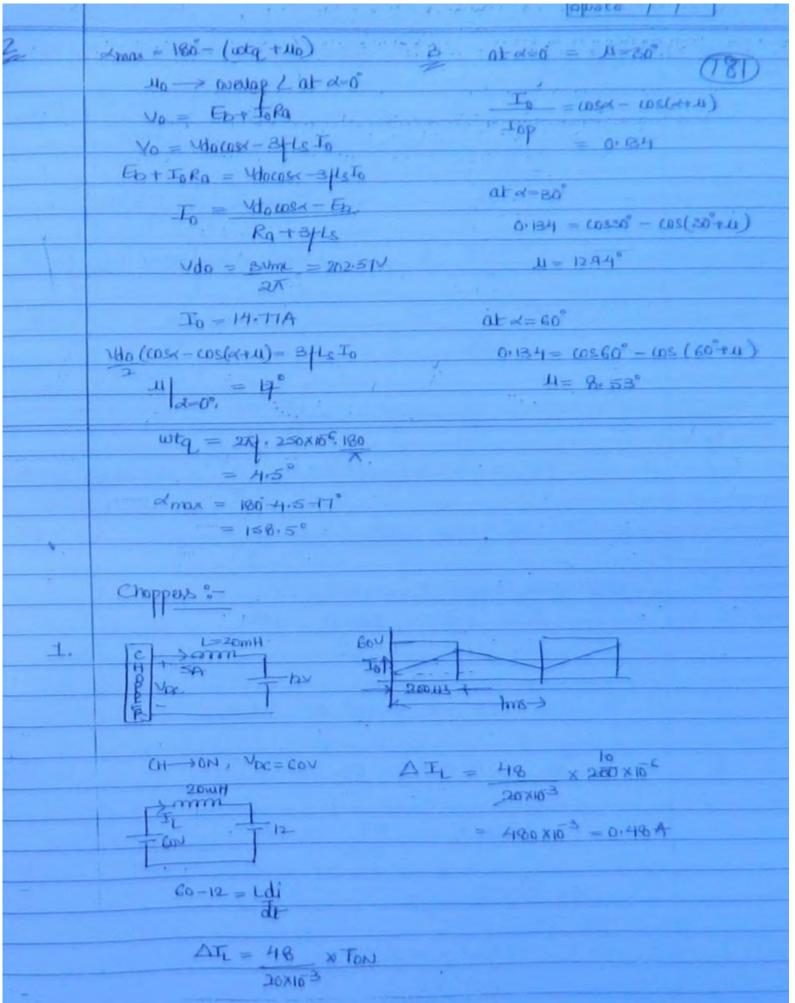


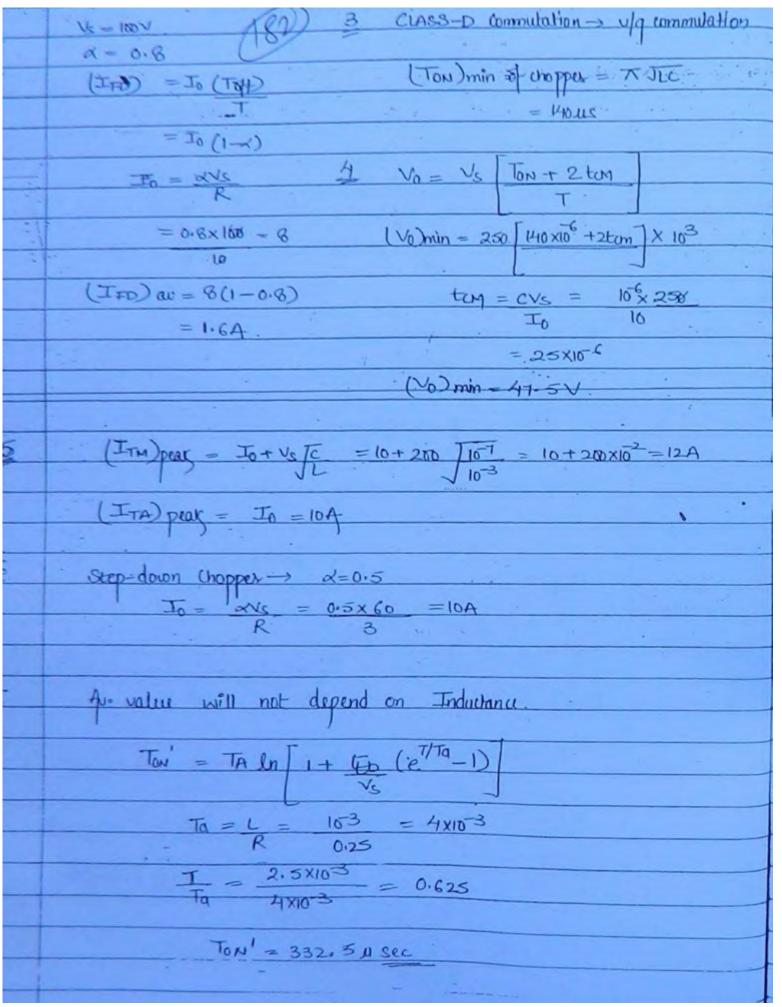


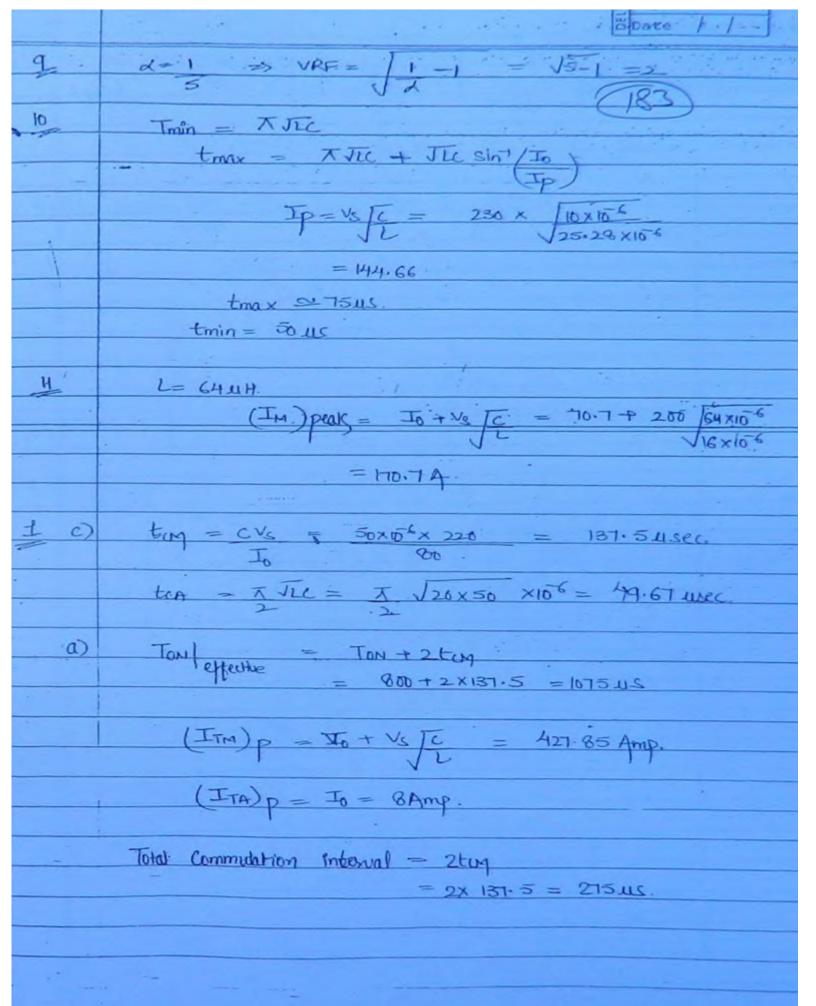


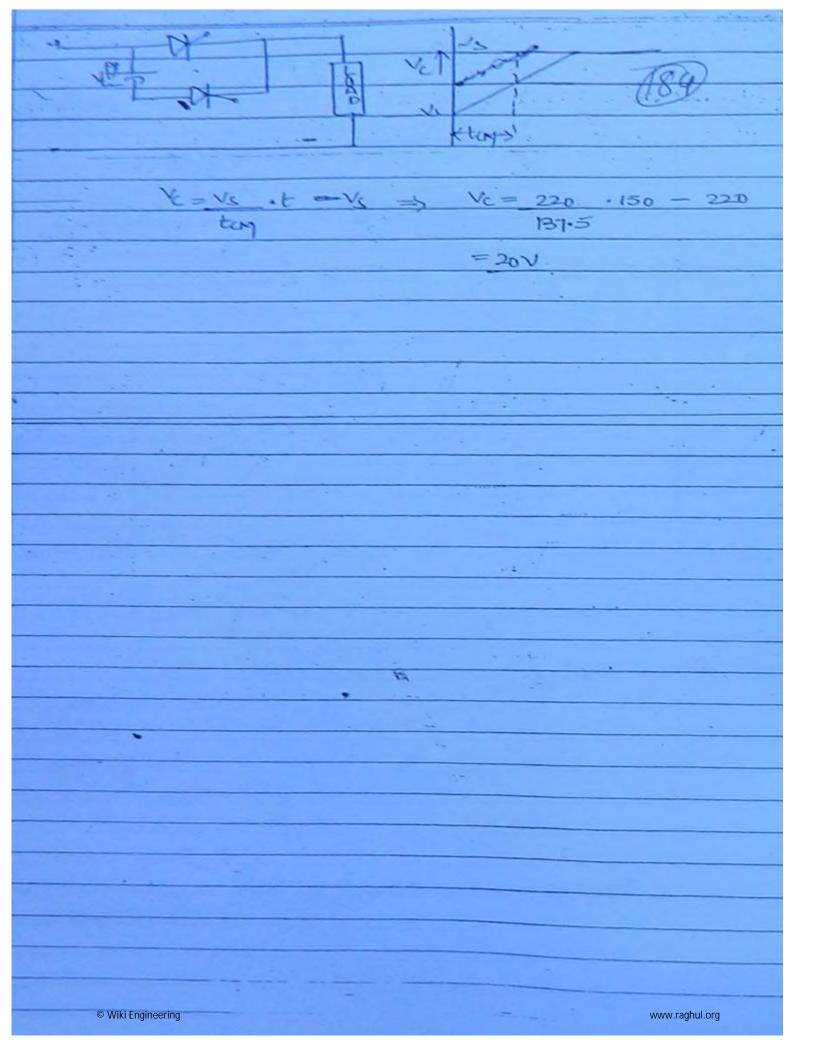


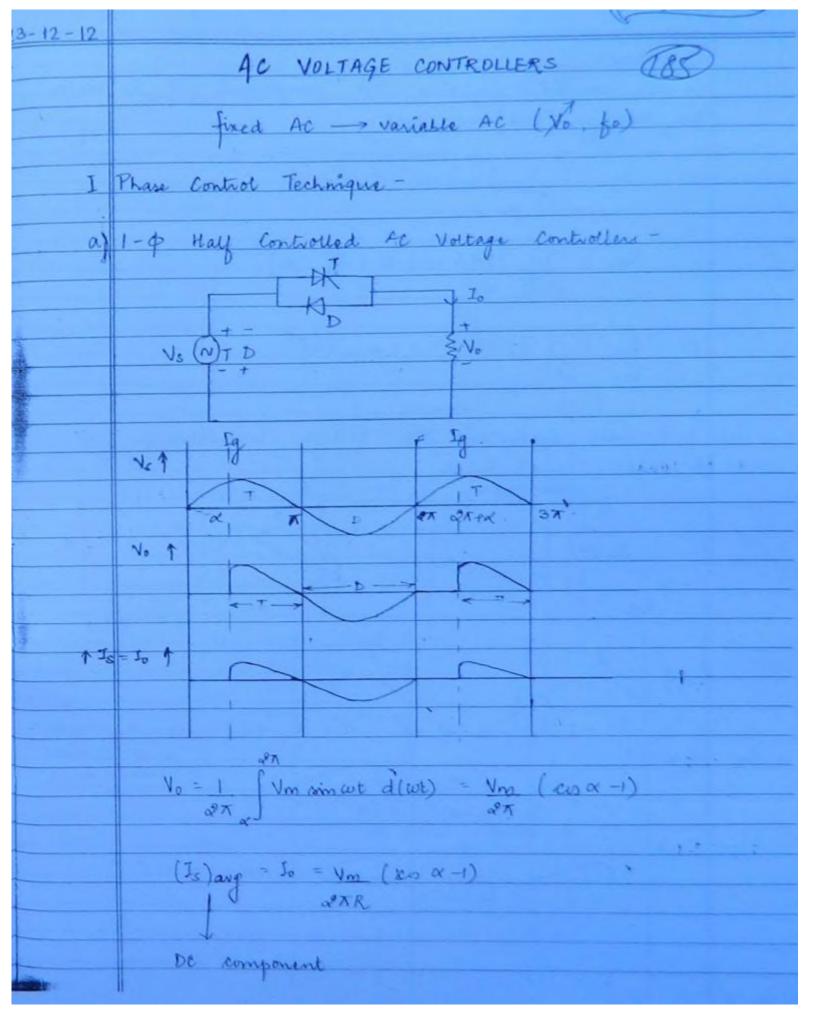


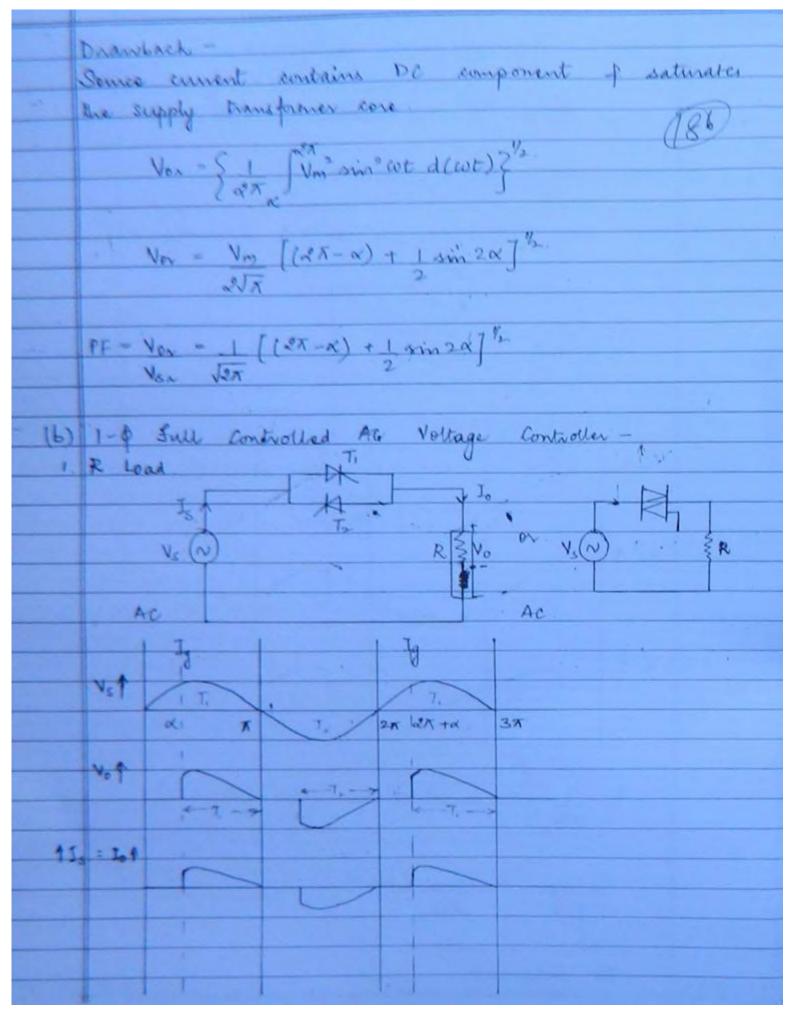


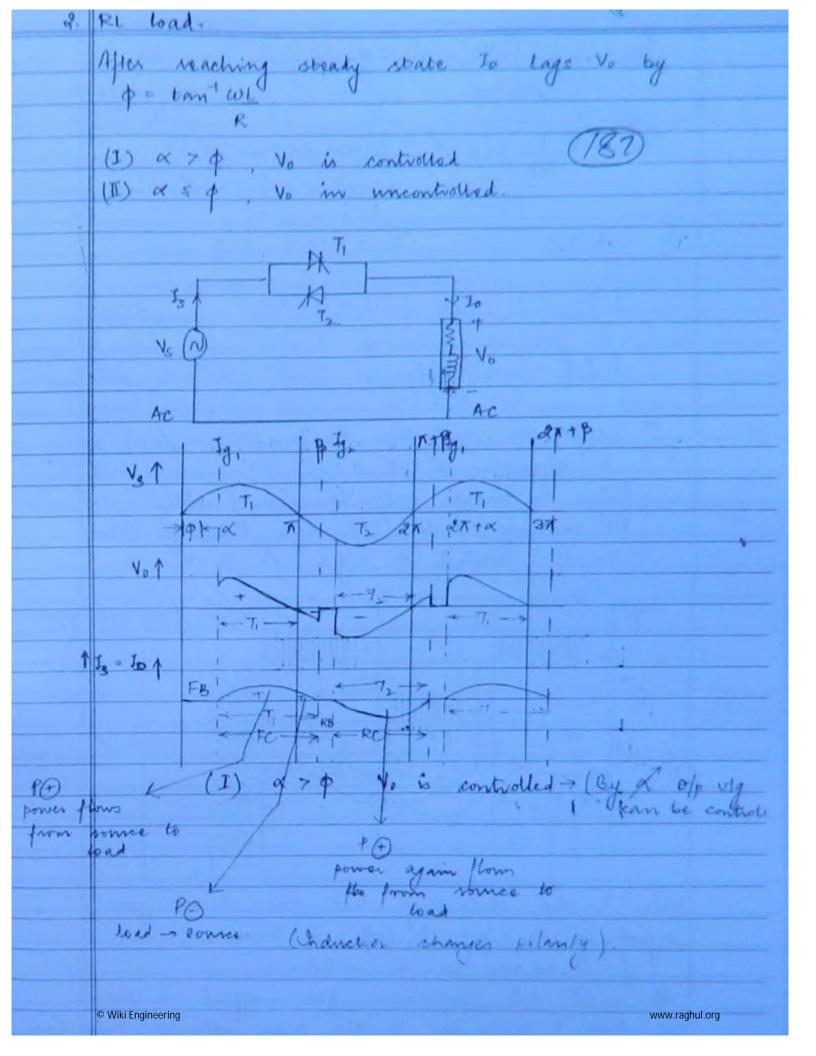


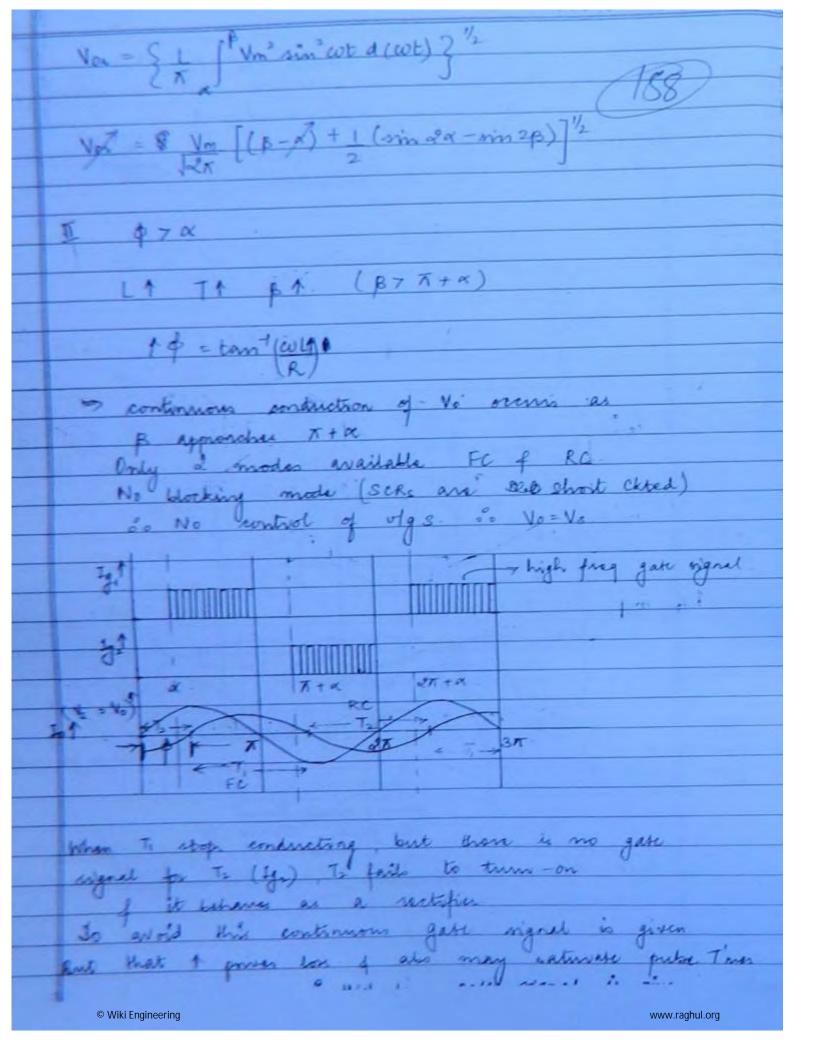


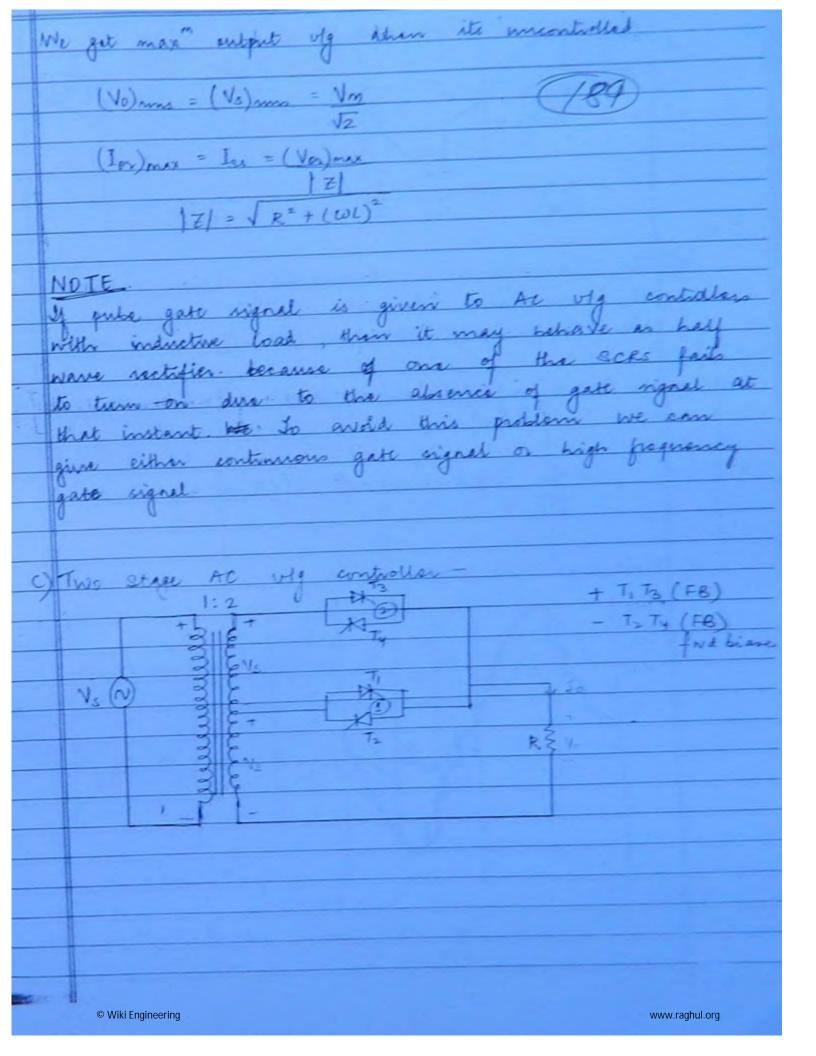


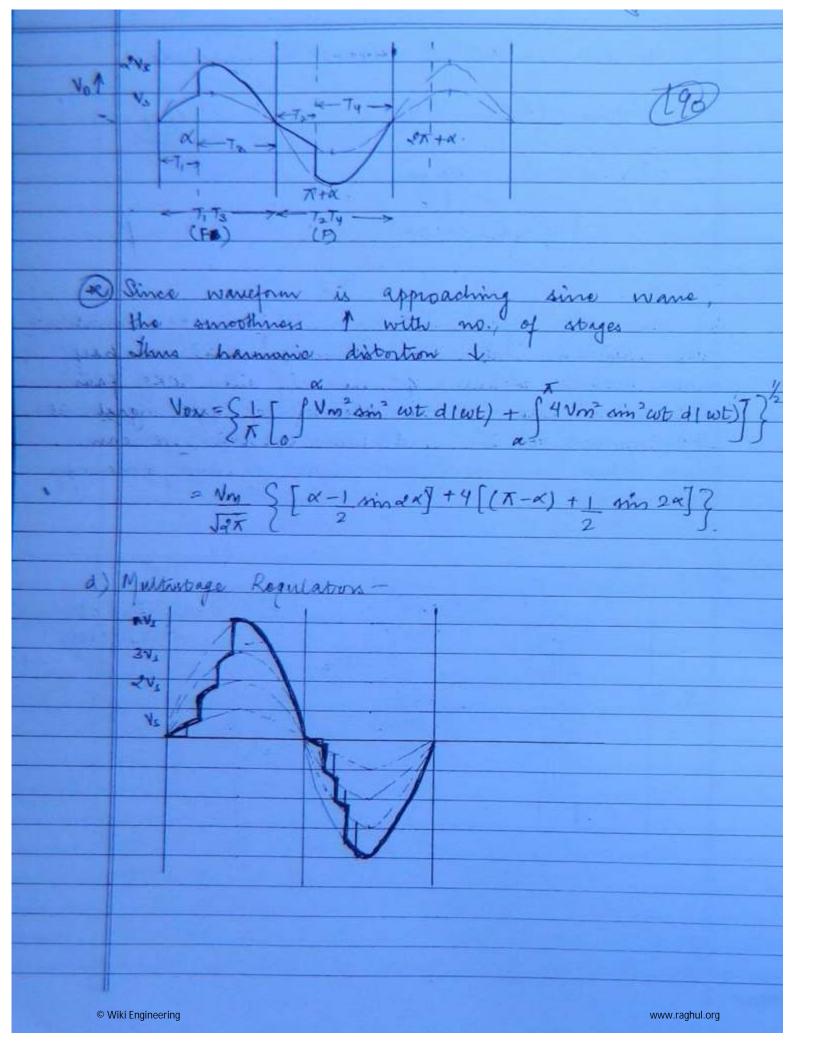


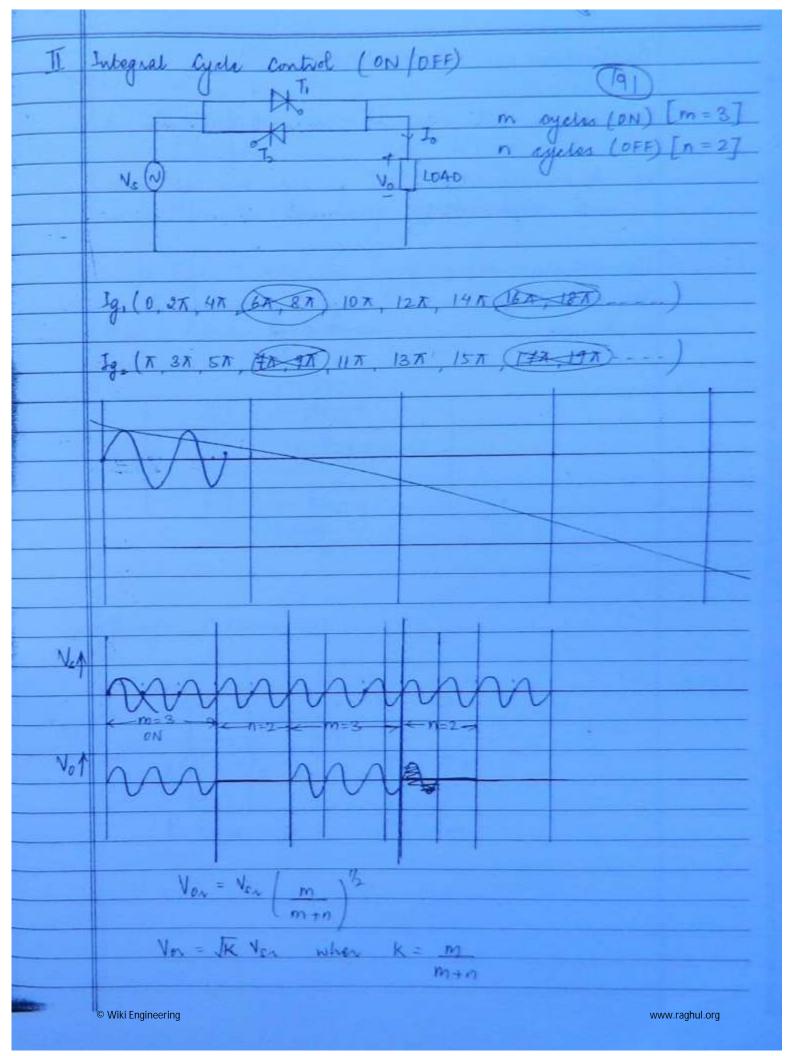


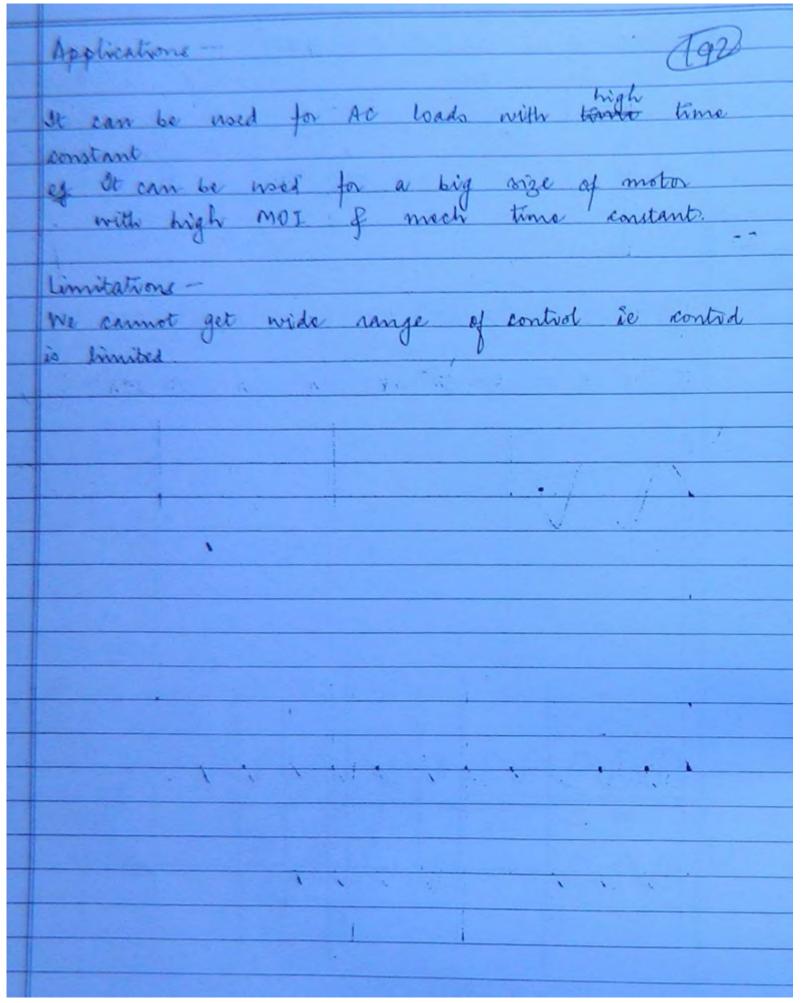


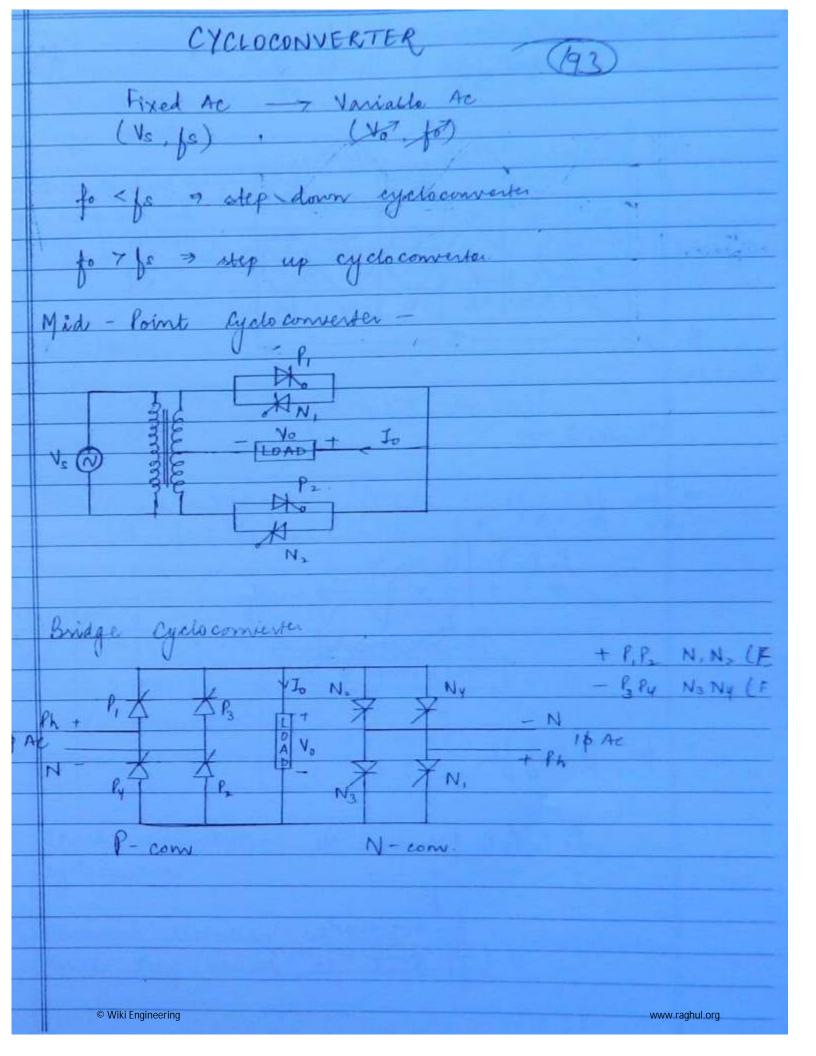


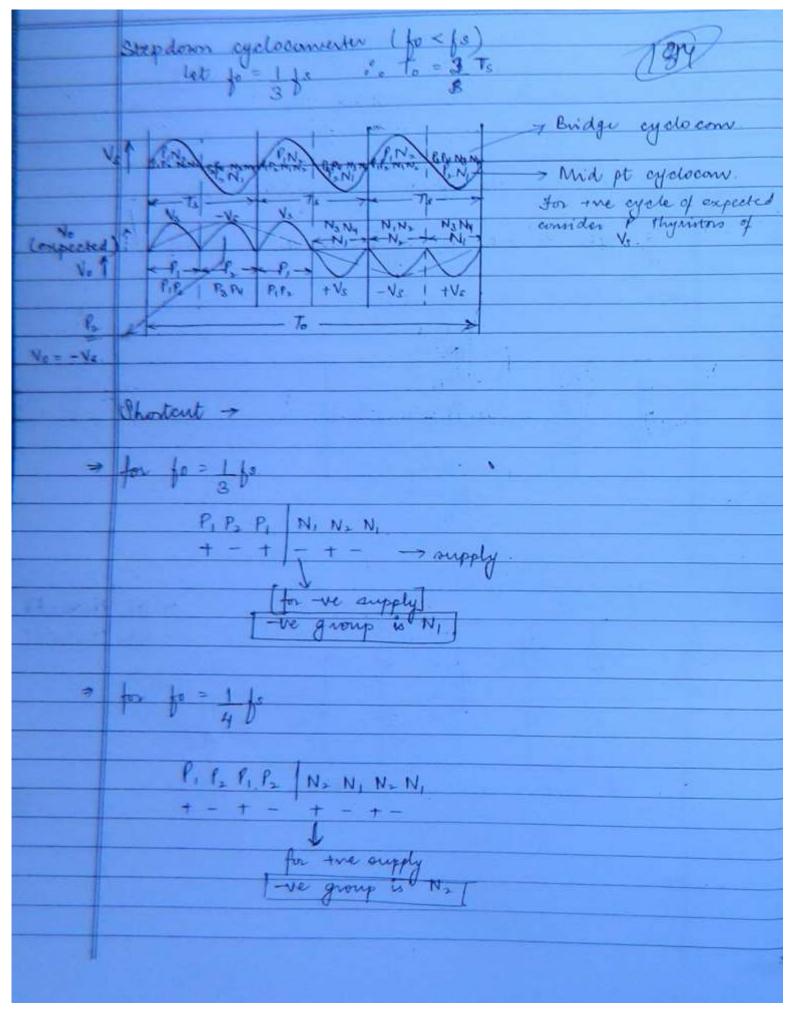






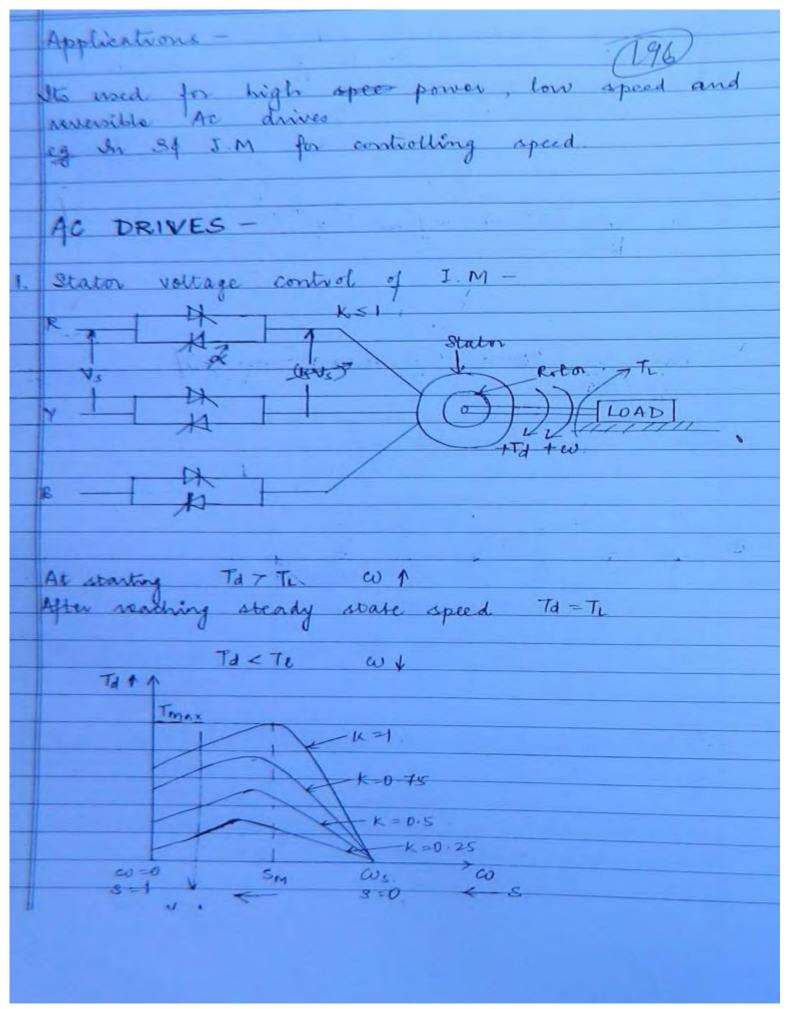


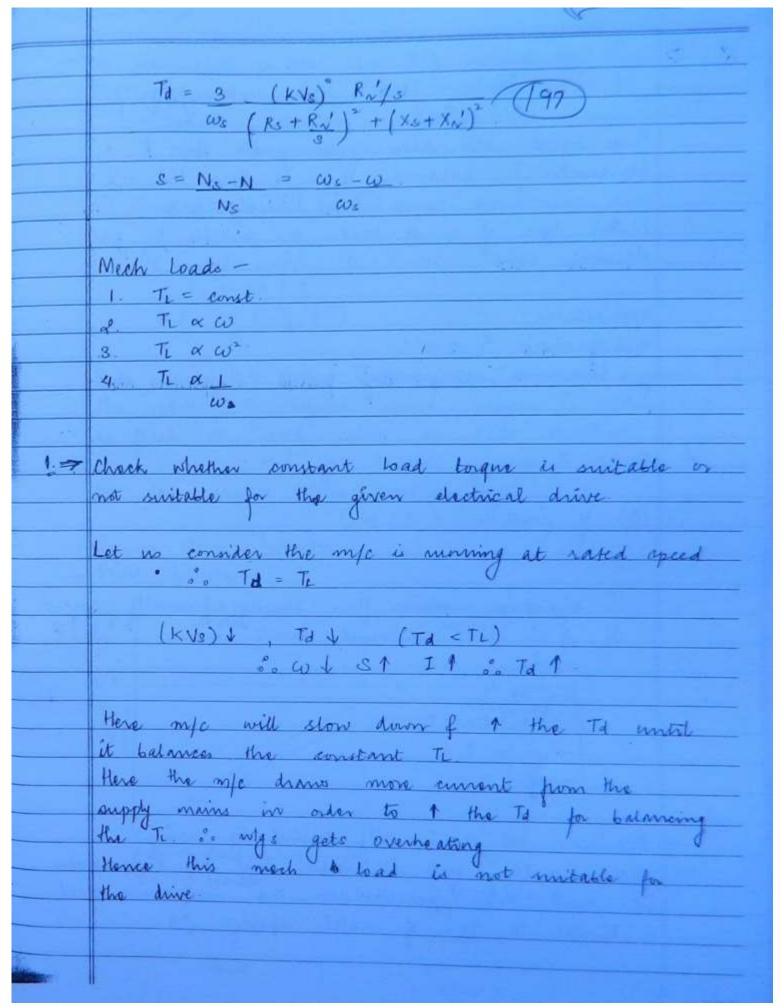




© Wiki Engineering www.raghul.org

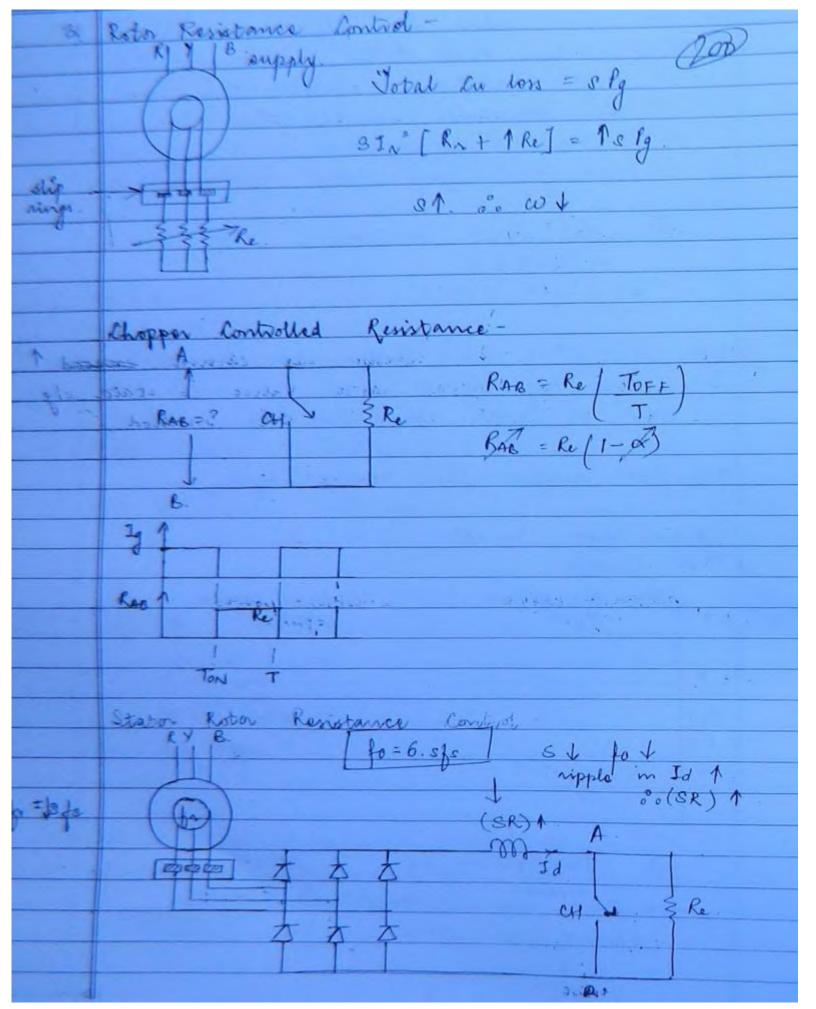
received any of is kept of but Here only frequency Vo of to is required with this estreme very or R-load -[(X-x)+1 sin 2x] 3 RL-Lord -+ 1 (minder - min 2 p)] Step Up anchesomerter -Greek commodation is required exclusions also Hamonic distrition is more Penns have appeals at low of a © Wiki Engineering www.raghul.org



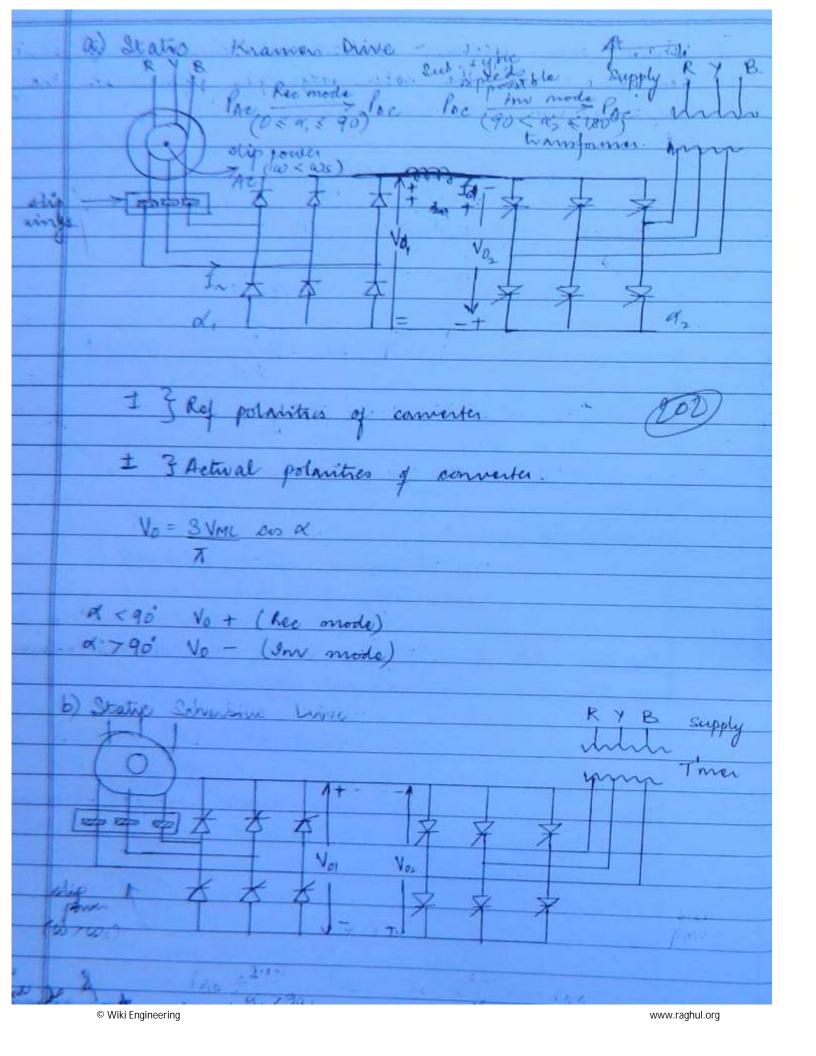


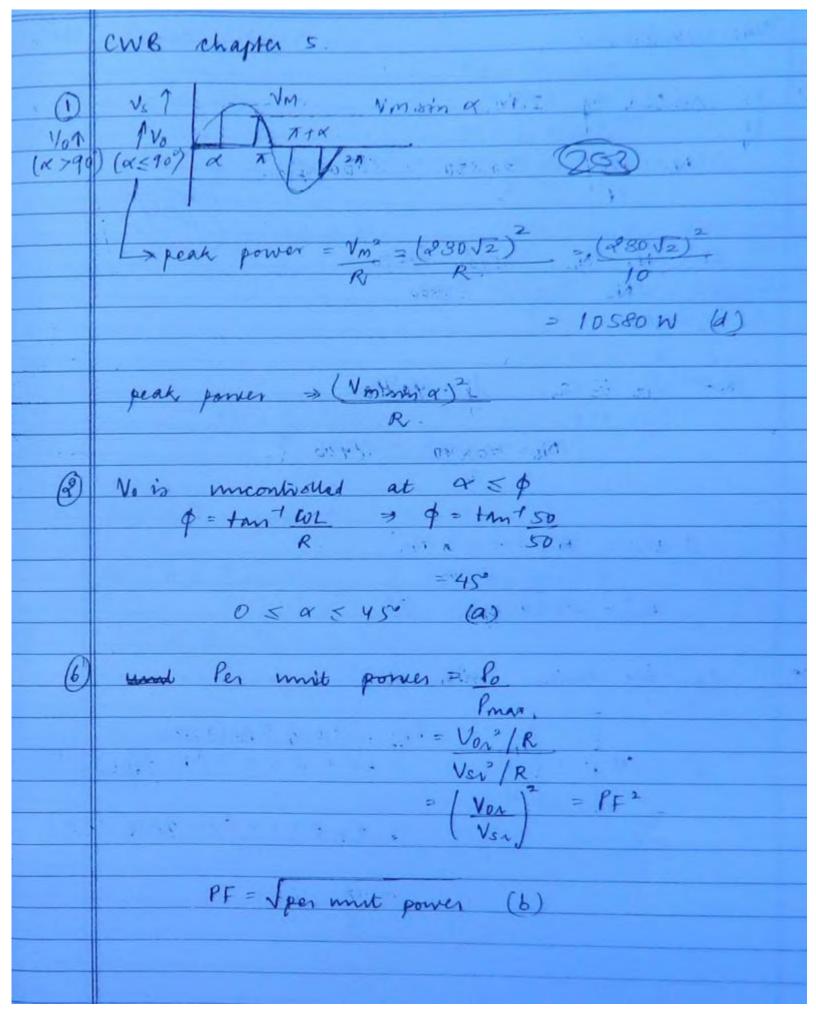
> TINW (kv) 1 Td 1 (Td 4 < TL) (98) cos Tis Here speed will slow down until the + + will not draw more than Joupply while. in this type of much load is mitable for given electrical drive. Applications -Used of where Ti K as2. for loads, reciprocating pumps, compressors etc. 2 Stator Inequency Control of I.M -(a) y control (co < was) I maintain const flux me go for V/ control overthing occurs hamanic 1 - losses 1 We can set realise V/J control by using special but its used only for high power low speed with cycloconverter the maximum speed © Wiki Engineering

We can also realise the V/f control by using PWM inverters. With PWM inverters -> smooth votation is possible any some lones order harmenice can be eliminated b) Constant V (for w > way) At rated speed Vs = Vrated NA STORY a constituted to the contract of the contract Hore as \$1 > \$ \$ because we cannot exceed 1
the stator vig beyond rated value so stator vig
is fixed at rated value in their mathod we can realise this method by: Square Warre Inventer PWM Inverter constant power To 1 p. 1 1 megion IT No = Varted Ns 1 14 (w< wn) wywn tontral. Pd = 4 Tdw 1 wa cont dirist. © Wiki Engineering www.raghul.org



I whato the effective resistance connected in some par phase for the other phase per phase for the above system? Total Cu loss = s lg 31, Ra + Id2 Re(1-0x) = 3Pg. Jen = Jo 12 = In = Id 2 Jd = In 3 3 JAR + 3 In Rel 1-0) = s. Pg. ⇒ 8IN [R1+10.5 Re(1-α)] = 8 kg eff renistance in series with notor wdy per phase This is not an efficient control ong the slip power is dissipated in external resistance This is an efficient speed control method because the slip power can be utilised or given back to supply line. 4. Stip Power Recurs

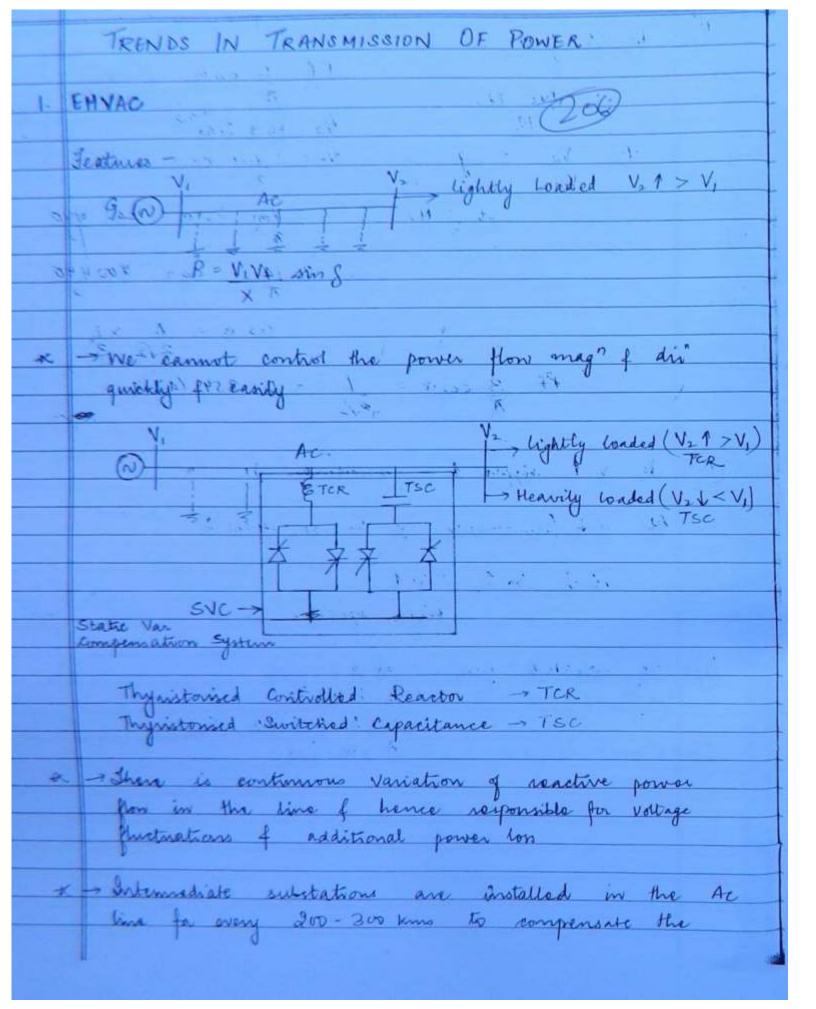




www.raghul.org

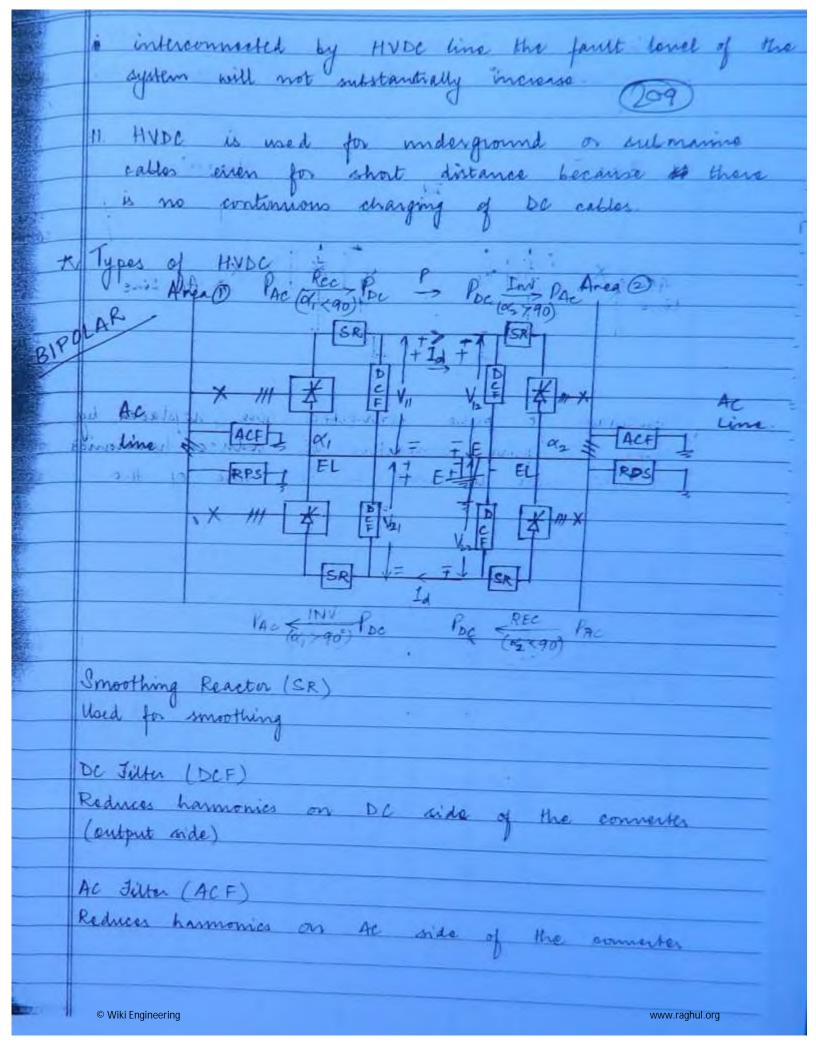
ONA chapter 6 V control of I.M -No - 100 = NO X50 = 3000 ym. 8 - Nx - Nx = 3000 - 2450 Sura 4 - 0-05 N= 9 at 1/2 Sa 1 - 90 He No : 10 x 40 - 4400 0.025 = M4400 - # No 2400 Na' = 2840 spm (C) da- in series with notes Reff : 2+ 0.5 Roll-W) tur · # + 0.5 x 4 [1- 4x10 x200) = 18 (45 © Wiki Engineering www.raghul.org

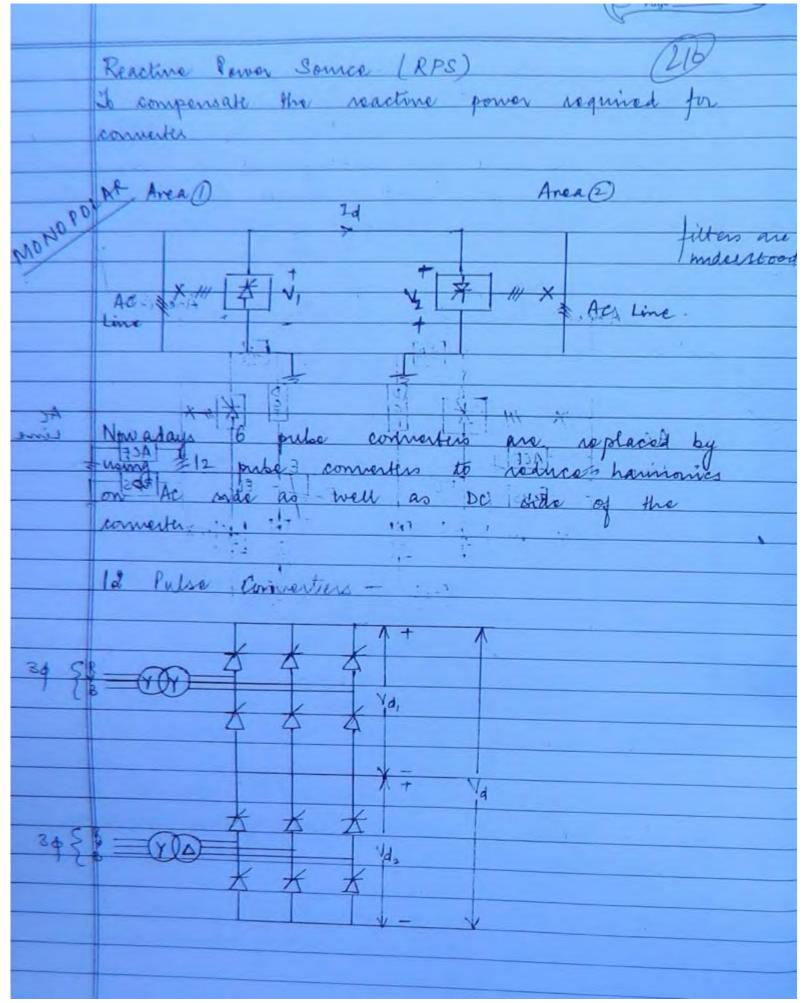
PF at I Na ? PF = B + 10 9 (205) S-NS-NX No = he + John Vo = 8 Yms con a = 66 3 VML CD Q = 400 440 AL J. Na 3,440 Sz co 4 - 200 440 1 nes N = K ×1 2/2 3 PF - 3 co W = 1 - 0.354 (A) (B) As at ripple t morthness & of & (smoothness of Vo svarafara) 7 d J Vot : wt high speed (6) Regenerated power = Vo 20 = Va (1-4) Io = 600(1-0.7)100 18 KW (05 © Wiki Engineering www.raghul.org

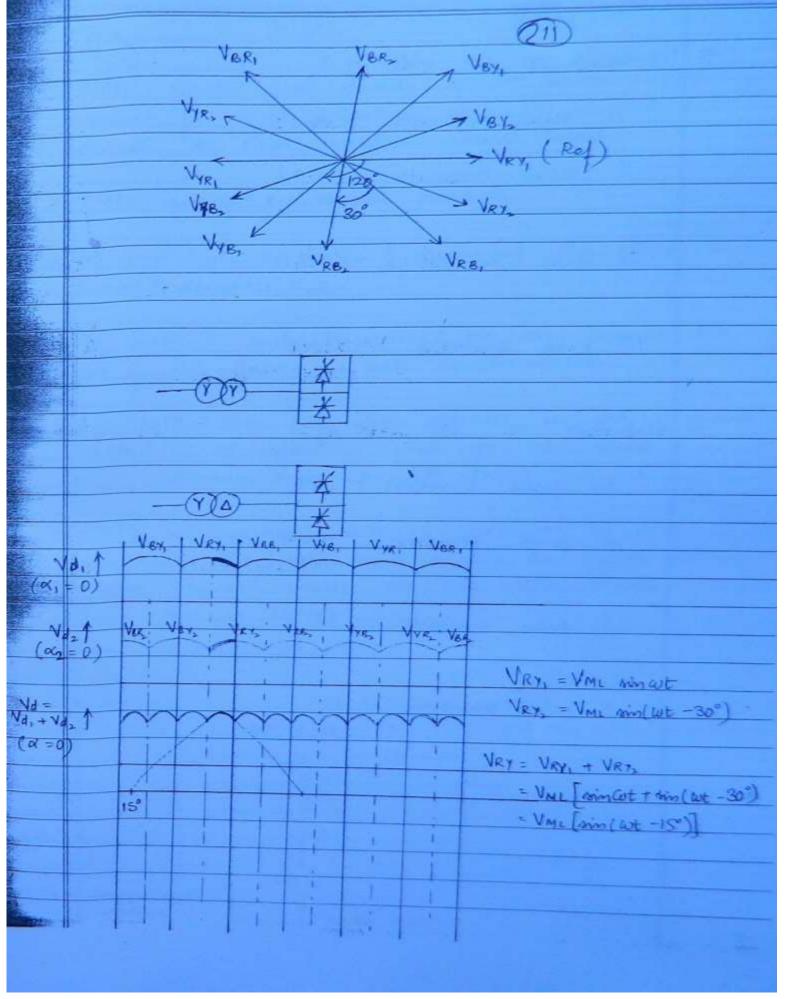


reactive power as per the requirement of reactive power in the time. x -> Other problems in the At line -> Skin Effect -> Corona loss. Asynchronous The ox - System disturbance in one of the area leads to that may lead to carcaded tripping of alternature (if protection system fails) * -> With Ac interconnection frequency distribunce is carried forward to other areas. interconnected by Ac lines then the facult level of the system increases © Wiki Engineering www.raghul.org

2 HVDC * HVDC is economical to transmit large amount of power over long distance. Advantages
1 The power flow magnitude of direction can be quickly and easily controlled I the transient stability limit is improved. Is we can just clear the fault in HVDC line 4 There is no Skin Effect problem of Corona loss 5. HVDC can utilize Earth for its no setum path. clearance of toner height requirement is losser F Power handling capacity of a Bipolan HVDC line is almost twice that of 3 p oringle circuit AC lin 8 We can interconnect independent areas at different prequencies because it is an asynchronous the. a frequency distribunce is not transferred to other independent areas, with HVDC interconnection 10 y andtiple no of independent area is

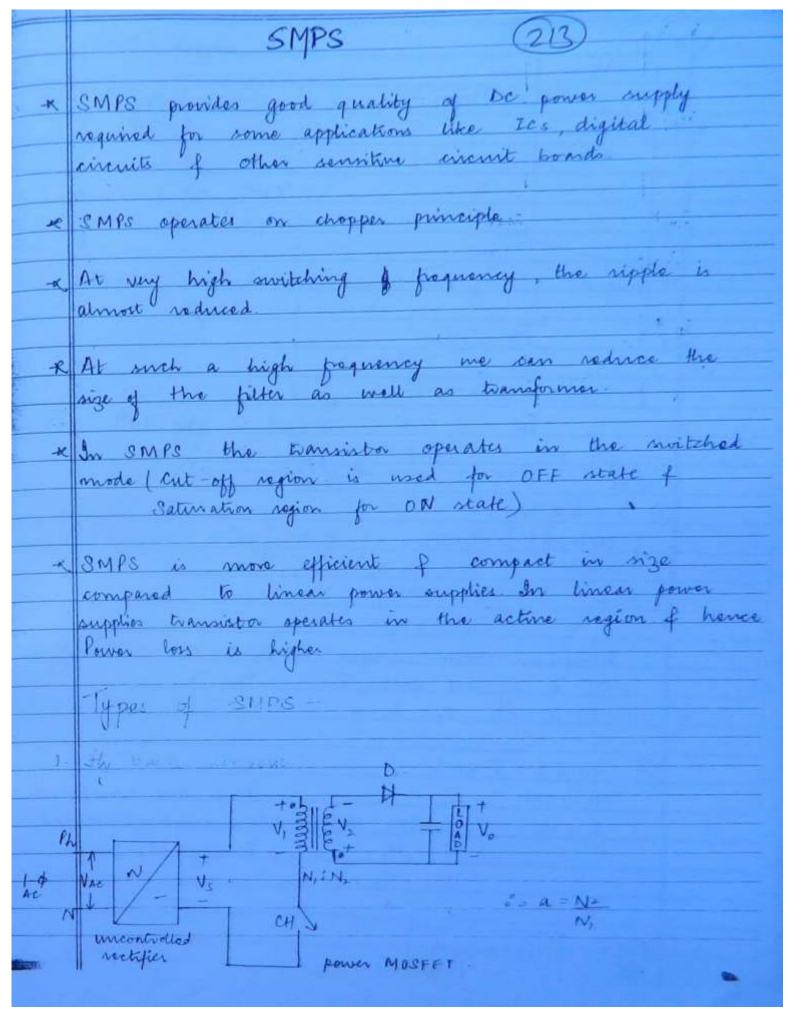


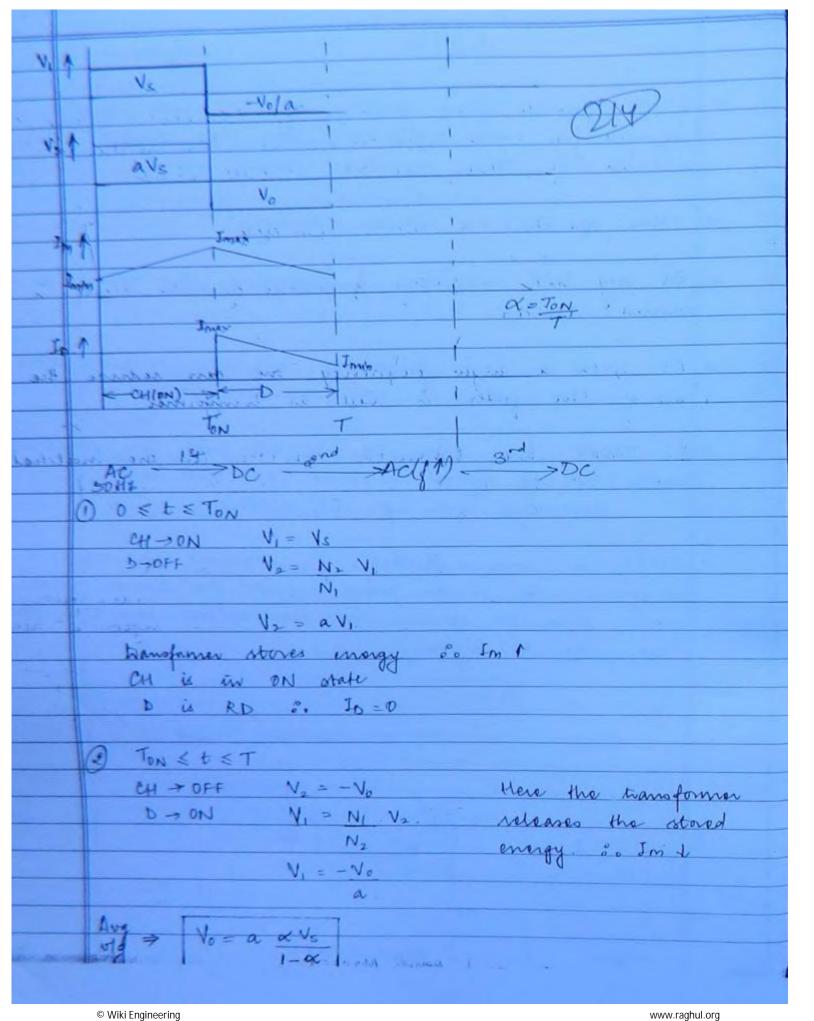


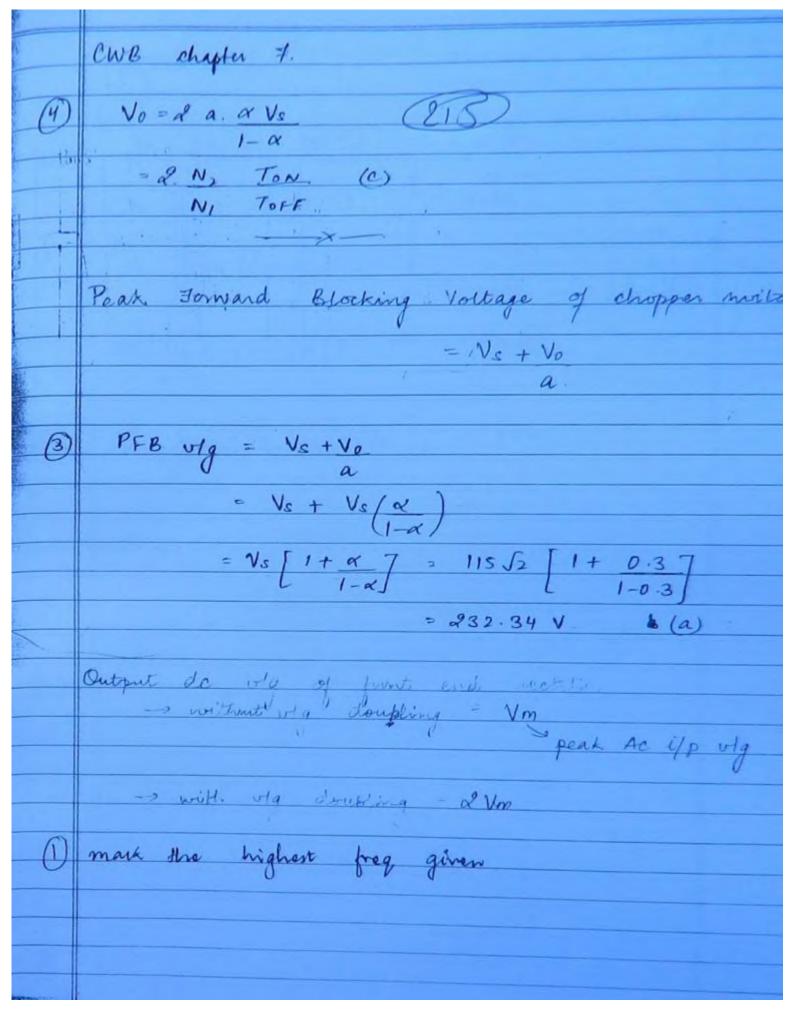


© Wiki Engineering www.raghul.org

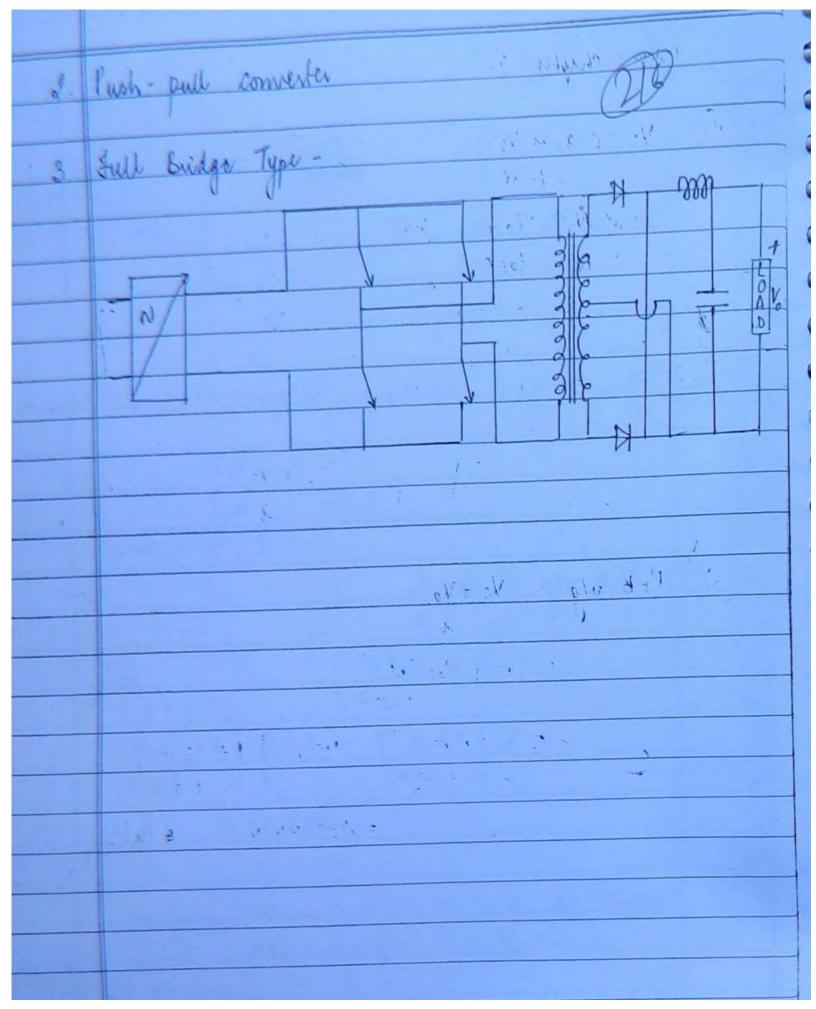
	19
收	Harmonics on Ac side of 8
3	
	m pube commenter - mk II
	& pulse connecter -> 2k ±1
	= 8,5,7,9,11
	6 pulse connecter → 6k II
	=5,7,11,13,17,19
	12 pube converter - 12k II
	= 11, 13, 28, 25,
×	Harmonics on DC side of :
	m pube connectes -> mk
	l pulse connecter → 2k to
	= 2,4,6,8,10,12.
	6 pulse connecter → 6 k
	=6, 12, 18
	12 pube converter -> 12k
	= 12,24,36,
© V	Wiki Engineering www.raghul.org







www.raghul.org



	Re	membering Formulas -	017)	
		g		
	R	-Load -	cent. You can K.	-
		Vo = Vm (1+ cox x) -> 1 pulse	discont vocal 1+ code	-
		AT .		
		Vo = Vm (1+ cos x) -> 2 pulse		
		T / / / / /	i) On 8 puba	
		Vo = Ymph [1 + cos (α+30)] → (α >30) ∂π/3 βρυβο) de 30 cont.	
		an/3 Brube	. > 0730 am	
			On himster.	
		to > Vmph [++ cos (x+60)] -> (x 76	de 60 cont	
	1	40 = Vmph [++ cos (x+60)] -> (x 76	Lia 760 liscont.	
		Vo = VML [1+ cos (x+60°)] -> (x	760)	
		7/6		
	1			
-	1			
	7			
9				_
Ž.				
100				
36				_
2007		© Wiki Engineering	www.raghul.org	